



ELSEVIER

Applied Surface Science MI 81-90 (1995) 1-32

applied
surface science

Author index to volumes 81-90

- Aarik, J. and H. Siimon, Characterization of adsorption in flow type atomic layer epitaxy reactor 81 (1994) 281
- Aarik, J. and H. Siimon, Erratum to "Characterization of adsorption in flow type atomic layer epitaxy reactor" [Appl. Surf. Sci. 81 (1994) 281] 90 (1995) 109
- Ababou, A., see Le Normand, F. 81 (1994) 309
- Abbas, N.M., see Mohamed, M.H. 90 (1995) 409
- Abdillahi, M.M., see Mohamed, M.H. 90 (1995) 409
- Abe, H., see Kanazawa, I. 85 (1995) 124
- Abon, M., see Debaugé, Y. 90 (1995) 15
- Abukawa, T., see Sasaki, M. 82/83 (1994) 387
- Adnot, A., see Lamontagne, B. 90 (1995) 447
- Adsool, A.D., R. Pande, R.B. Sharma, M.A. More and D.S. Joag, Adsorption studies of iron on tungsten by probe-hole field emission microscopy 87 (1995) 37
- Aers, G.C., P.A. Marshall, T.C. Leung and R.D. Goldberg, Defect profiling in multilayered systems using mean depth scaling 85 (1995) 196
- Afonso, C.N., see Gonzalo, J. 86 (1995) 40
- Aguiar, R., see Queral, X. 86 (1995) 95
- Aguiar Colom, R., see Reihls, K. 84 (1995) 107
- Ahlgren, T., K. Väkeväinen, J. Räisänen, E. Rauhala and J. Keinonen, Range profiles of 6-10 MeV ^{15}N ions implanted in silicon 90 (1995) 419
- Ahmed, M.F., see Ashour, A. 89 (1995) 159
- Aisaka, T., see Ishii, A. 85 (1995) 33
- Akamatsu, M., S. Narahara, T. Kobayashi and F. Hasegawa, Optical in-situ analysis of GaAs/AlAs/GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using GaCl_3 , AlCl_3 and AsH_3 82/83 (1994) 228
- Akazawa, H., Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane 82/83 (1994) 394
- Akinaga, H. and K. Tanaka, Atomic layer epitaxy of ZnSe using reflectance difference spectroscopy 82/83 (1994) 298
- Al-Kassab, T., M.-P. Macht and H. Wollenberger, FIM/AP analysis of Cu-Pd multilayers 87/88 (1995) 329
- Alavi, K., see Hozhabri, N. 85 (1995) 311
- Aleskovski, V.B., see Drozd, V.E. 82/83 (1994) 587
- Aleskovski, V.B., see Drozd, V.E. 82/83 (1994) 591
- Alexandrescu, R., see D'Anna, E. 86 (1995) 170
- Alexandrescu, R., see Peled, A. 86 (1995) 538
- Alexandrou, I., see Logothetidis, S. 86 (1995) 185
- Alford, T.L., see Russell, S.W. 90 (1995) 455
- Aliev, V.S., M.R. Baklanov and V.I. Bukhtiyarov, Silicon surface cleaning using XeF_2 gas treatment 90 (1995) 191
- Allan, G., see Lang, B. 81 (1994) 17
- Allegrini, M., see Amoruso, S. 86 (1995) 35
- Allinger, Th., see Engelhard, H. 90 (1995) 89
- Alnot, M., see Lobstein, N. 89 (1995) 307
- Amarendra, G., see Vasumathi, D. 85 (1995) 154
- Amarendra, G., see Canter, K.F. 85 (1995) 339
- Ambigapathy, R., see Manuel, A.A. 85 (1995) 301
- Amirhaghi, S., see Craciun, V. 86 (1995) 99
- Amoruso, S., V. Berardi, N. Spinelli, R. Velotta, M. Armenante, F. Fusco, M. Allegrini and E. Arimondo, Time of flight mass spectrometry and covariance mapping technique investigation of charged specie evolution in $\text{Pb}(\text{Ti}_{0.48}\text{Zr}_{0.52})\text{O}_3$ laser ablation 86 (1995) 35
- Anandan, C., X-ray photoelectron spectroscopic study of room-temperature evolution of oxide-covered hydrogenated amorphous silicon/aluminium interface 89 (1995) 57
- Andrei, A., see Peled, A. 86 (1995) 538
- Andrén, H.-O., G. Cai and L.-E. Svensson, Microstructure of heat resistant chromium steel weld metals 87/88 (1995) 200
- Andreu, J., see Puigdollers, J. 86 (1995) 600
- Antoni, F., E. Fogarassy, C. Fuchs, B. Prévot and J.P. Stoquert, $\text{Si}_{1-x}\text{Ge}_x$ thin films deposited by the pulsed excimer laser ablation technique 86 (1995) 175
- Aono, M., see Kawai, M. 82/83 (1994) 487
- Aoyagi, Y., see Isshiki, H. 82/83 (1994) 57
- Aoyagi, Y., see Meguro, T. 82/83 (1994) 193
- Aoyagi, Y., see Ishii, M. 86 (1995) 554
- Arai, M., Y. Nishiyama, T. Masuda and K. Hashimoto, The distribution of activation energy for hydrogen desorption over

- silica-supported nickel catalysts determined from temperature-programmed desorption spectra 89 (1995) 11
- Arenholz, E., see Heitz, J. 81 (1994) 103
- Arimondo, E., see Amoruso, S. 86 (1995) 35
- Armas, B., see Aspar, B. 81 (1994) 55
- Armenante, M., see Amoruso, S. 86 (1995) 35
- Armstrong, J.V., see Farrell, T. 86 (1995) 582
- Arnaud, Y.P. and H. Bertrais, Identification of active species and theoretical classification of simple catalyst oxides using surface redox couples 81 (1994) 69
- Arnold, J., U. Dasbach, W. Ehrfeld, K. Hesch and H. Löwe, Combination of excimer laser micromachining and replication processes suited for large scale production 86 (1995) 251
- Arnold, N., P.B. Kargl and D. Bäuerle, Laser direct writing and instabilities: a one-dimensional approach 86 (1995) 457
- Arpatzanis, N., see Thurzo, I. 90 (1995) 39
- Aruga, T., see Taguchi, Y. 82/83 (1994) 434
- Aruga, T., S. Takamura, K. Nakata and Y. Ito, Depth profiles of defects in Ar-ion-irradiated steels determined by a least-squares fit of S parameters from variable-energy positron annihilation 85 (1995) 229
- Arvia, A.J., see Hernández Creus, A. 81 (1994) 387
- Asahi, H., see Kim, J.H. 82/83 (1994) 76
- Asahi, H., S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda, Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy 82/83 (1994) 109
- Asami, K., see Kim, J.H. 82/83 (1994) 76
- Asami, K., see Asahi, H. 82/83 (1994) 109
- Asami, S., N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt, Adaptive temperature program ALE of $\text{Si}_{1-x}\text{Ge}_x/\text{Si}$ heterostructures from $\text{Si}_2\text{H}_6/\text{Ge}_2\text{H}_6$ 82/83 (1994) 359
- Ascherl, M., see Wang, P.W. 90 (1995) 413
- Asensi, J.M., see Puigdollers, J. 86 (1995) 600
- Ashino, M., M. Tomitori and O. Nishikawa, Atom probe and field emission electron spectroscopy studies of semiconductor films on metals 87/88 (1995) 12
- Ashour, A., M.R. Ebeid, N. El-Kadry, M.F. Ahmed and A.A. Ramadan, Thermal effects on structural characterization of evaporated CdTe films during and after deposition 89 (1995) 159
- Asikainen, T., M. Ritala and M. Leskelä, Growth of In_2S_3 thin films by atomic layer epitaxy 82/83 (1994) 122
- Asoka-Kumar, P., see Umlor, M.T. 85 (1995) 295
- Aspar, B., R. Berjoan, C. Labatut and B. Armas, Auger studies of chemical bonds and oxygen minimization in the interfaces between AlN and SiC thin films deposited by LPCVD 81 (1994) 55
- Asskali, A., see Reniers, F. 81 (1994) 151
- Atanassova, E., T. Dimitrova and J. Kopriarova, AES and XPS study of thin RF-sputtered Ta_2O_5 layers 84 (1995) 193
- Athenstaedt, W. and M. Leisch, A three-dimensional atom-probe study of preferential sputtering of a Ni91Pt9 alloy 87/88 (1995) 318
- Atkinson, A., see Leung, T.C. 85 (1995) 292
- Aubert, P., G. Garry, R. Bisaro and J. Garcia Lopez, Structural properties of LiNbO_3 thin films grown by the pulsed laser deposition technique 86 (1995) 144
- Auger, P., see Schmuck, C. 87/88 (1995) 228
- Augugliaro, V., see Navío, J.A. 81 (1994) 325
- Autric, M., see Grangeon, F. 86 (1995) 160
- Auvert, G., Laser chemical vapour deposition for microelectronics 86 (1995) 466
- Ayame, A., see Tomizuka, H. 89 (1995) 281
- Babu, S.S., S.A. David, J.M. Vitek and M.K. Miller, Atom probe field ion microscopy of type 308 CRE stainless steel welds 87/88 (1995) 207
- Babu, S.V., see Kononenko, T.V. 86 (1995) 234
- Bachmann, K.J., see Kelliher, J.T. 86 (1995) 453
- Backes, G., see Kreutz, E.W. 86 (1995) 310
- Badawi, K.F., see Durand, N. 81 (1994) 119
- Badaye, M., see Wang, F. 90 (1995) 123
- Baeri, P., R. Reitano and N. Marino, SiO_2 film deposition by XeCl laser ablation of fused silica 86 (1995) 128
- Baev, A.A., see Tutov, E.A. 90 (1995) 303
- Bai, C., see Fang, Y. 89 (1995) 331
- Bajikar, S.S., T.F. Kelly, C.-M. Teng and P.P. Camus, Microfabrication of extraction electrodes for local-electrode atom probes 87/88 (1995) 438
- Bakhtizin, R.Z., C. Park, T. Hashizume and T. Sakurai, Scanning tunneling microscopy study of the (3×1) reconstruction induced by Li adsorption on the Si(111) surface 87/88 (1995) 347
- Baklanov, M.R., see Aliev, V.S. 90 (1995) 191
- Balducci, L., see Garbassi, F. 84 (1995) 145
- Bali, K., see Geretovszky, Zs. 86 (1995) 494
- Bali, K., Zs. Geretovszky, A.L. Tóth and T. Szörényi, The effect of process parameters on the O/Mo ratio in laser deposition of molybdenum oxides from aqueous solutions 86 (1995) 500
- Ballutaud, D., C. Debiemme-Chouvy, A. Etcheberry, P. De Mierry and L. Svob,

- Reactivity of III-V and II-VI semiconductors toward hydrogen: surface modification and evolution in air 84 (1995) 187
- Bannerjee, S., see Asami, S. 82/83 (1994) 359
- Bao, X., see Deng, J. 81 (1994) 341
- Baraban, A.P., see Drozd, V.E. 82/83 (1994) 583
- Baranauskas, V., G.P. Thim and A. Peled, Laser-induced formation of porous silicon 86 (1995) 398
- Bargon, J., see Lätsch, S. 81 (1994) 183
- Barkshire, I.R., M. Prutton and G.C. Smith, Multi-spectral scanning Auger microscopy of tribological surfaces 84 (1995) 331
- Barth, M., see Karstens, H. 86 (1995) 521
- Barthés-Labrousse, M.-G., see Fauquet, C. 81 (1994) 435
- Bas, P., A. Bostel, B. Deconihout and D. Blavette, A general protocol for the reconstruction of 3D atom probe data 87/88 (1995) 298
- Bas, P., see Deconihout, B. 87/88 (1995) 428
- Basiuk, E.V., see Dmitruk, N.L. 90 (1995) 489
- Bastl, Z., see Fajgar, R. 86 (1995) 530
- Bater, S., see Wang, P.W. 90 (1995) 413
- Batirev, I.G., see Leiro, J.A. 90 (1995) 515
- Bäuerle, D., see Heitz, J. 81 (1994) 103
- Bäuerle, D., see Arnold, N. 86 (1995) 457
- Baumgärtner, H., see Jiang, W. 86 (1995) 564
- Bayrachny, B.I., see Skatkov, L.I. 81 (1994) 427
- Beauvois, S., see Viville, P. 86 (1995) 411
- Bedair, S.M. and N.A. El-Masry, Recent advances in atomic layer epitaxy devices 82/83 (1994) 7
- Bedair, S.M., see Hayafuji, N. 82/83 (1994) 18
- Beling, C.D., see Panda, B.K. 85 (1995) 182
- Beling, C.D., see Ling, C.C. 85 (1995) 305
- Bellard, L., see Shafeev, G.A. 86 (1995) 387
- Benítez, J.J., I. Carrizosa and J.A. Odriozola, In situ diffuse reflectance infrared (DRIFTS) identification of active sites in the CO + H₂ reaction over lanthanide-modified Rh/Al₂O₃ catalysts 84 (1995) 391
- Benninghoven, A., see Reihls, K. 84 (1995) 107
- Berardi, V., see Amoroso, S. 86 (1995) 35
- Berger, S., see Tamir, S. 86 (1995) 514
- Bergmann, H.W., K. Schutte, E. Schubert and A. Emmel, Laser-surface processing of metals and ceramics for industrial applications 86 (1995) 259
- Berjeza, N.A., S.P. Velikevitch, V.I. Mazhukin, I. Smurov and G. Flamant, Influence of temperature gradient to solidification velocity ratio on the structure transformation in pulsed- and CW-laser surface treatment 86 (1995) 303
- Berjoan, R., see Aspar, B. 81 (1994) 55
- Bermudez, V.M., Adsorption and co-adsorption of boron and oxygen on ordered α -SiC surfaces 84 (1995) 45
- Bertolini, J.C., see Debauge, Y. 90 (1995) 15
- Bertomeu, J., see Izquierdo, R. 86 (1995) 509
- Bertomeu, J., see Puigdollers, J. 86 (1995) 600
- Bertóti, I., M. Mohai, J.L. Sullivan and S.O. Saied, Surface characterisation of plasma-nitrided titanium: an XPS study 84 (1995) 357
- Bertrais, H., see Arnaud, Y.P. 81 (1994) 69
- Bertrand, P., see Weng, L.T. 84 (1995) 9
- Bertrand, P., see Piyakis, K. 84 (1995) 227
- Bevk, J., see Kosowsky, S.D. 84 (1995) 179
- Bisaro, R., see Aubert, P. 86 (1995) 144
- Blake, R.G., see Miller, M.K. 87/88 (1995) 216
- Błaszczyszyn, R., see Bryl, R. 87/88 (1995) 69
- Blavette, D., see Schmuck, C. 87/88 (1995) 228
- Blavette, D., see Duval, S. 87/88 (1995) 284
- Blavette, D., see Bas, P. 87/88 (1995) 298
- Blavette, D., see Deconihout, B. 87/88 (1995) 428
- Block, J.H., see Cocke, D.L. 84 (1995) 153
- Block, J.H., see Gorodetskii, V. 87/88 (1995) 151
- Block, J.H., see Medvedev, V.K. 87/88 (1995) 159
- Bloss, E., see Coleman, P.G. 85 (1995) 276
- Blum, O. and U. König, Electrochemical and photoelectrochemical modification and characterisation of thin passive films 86 (1995) 417
- Bolmont, D., see Hong, S. 90 (1995) 65
- Bolt, P.H., S.F. Lobner, J.W. Geus and F.H.P.M. Habraken, Interfacial reaction of NiO with Al₂O₃ (11 $\bar{2}$ 0) and polycrystalline α -Al₂O₃ 89 (1995) 339
- Boman, M., see Stenberg, G. 86 (1995) 543
- Bonnet, J., see Lévêque, G. 89 (1995) 211
- Bonser, D.J., see Asami, S. 82/83 (1994) 359
- Borochoy, N. and A. Peled, Aggregation kinetics of photo-excited colloid solutions observed by dynamic photon correlation spectroscopy (PCS) 86 (1995) 533
- Bostel, A., see Bas, P. 87/88 (1995) 298
- Bostel, A., see Deconihout, B. 87/88 (1995) 428
- Bouabid, K., see Maury, F. 86 (1995) 447
- Bouet, M., see Deconihout, B. 87/88 (1995) 428
- Bouillon, F., see Reniers, F. 81 (1994) 151
- Bourbigot, S., M. Le Bras, L. Gengembre and R. Delobel, XPS study of an intumescent coating. Application to the ammonium polyphosphate/pentaerythritol fire-retardant system 81 (1994) 299
- Bourée, J.E., R. Helbing, W. Kuhn and O. Gorochoy, Photoassisted metalorganic vapor-phase epitaxy of ZnSe on GaAs 86 (1995) 437
- Bourée, J.E., see Tonneau, D. 86 (1995) 488
- Bouveresse, E., see Friedbacher, G. 84 (1995) 133
- Boyd, I.W., see Tyrrell, G.C. 86 (1995) 50
- Boyd, I.W., see Craciun, V. 86 (1995) 99
- Boyd, I.W., see King, S. 86 (1995) 134
- Braconi, P., see Buisson, L. 84 (1995) 211
- Bradley, R.H., Surface studies of Cu/Cr/Ag impregnated microporous carbons 90 (1995) 271
- Bradshaw, A.M., see Keil, M. 90 (1995) 377
- Bram, Ch., see Starke, U. 89 (1995) 175

- Brauer, G., see Weiss, A.H. 85 (1995) 82
- Braul, N., see Le Normand, F. 81 (1994) 309
- Brédas, J.L., see Viville, P. 86 (1995) 411
- Bréelle, E., S. Rigo, J.A. Kilner and J.-J. Ganem, SIMS study of rapid thermal nitridation of silicon dioxide thick films in ammonia ambient 81 (1994) 127
- Bremert, O., see Krebs, H.-U. 86 (1995) 86
- Bremert, O., see Krebs, H.-U. 86 (1995) 90
- Brimaud, J.-H., see Durand, H.-A. 86 (1995) 122
- Britton, D.T. and J. Störmer, Application of time-dependent diffusion models to the study of real solids 85 (1995) 1
- Britton, D.T., K. Uhlmann and G. Kögel, Magnetic positron optics 85 (1995) 158
- Brocherieux, A., O. Dessaux, P. Goudmand, L. Gengembre, J. Grimblot, M. Brunel and R. Lazzaroni, Characterization of nickel films deposited by cold remote nitrogen plasma on acrylonitrile-butadiene-styrene copolymer 90 (1995) 47
- Brown, N.M.D. and Z.-H. Liu, An investigation using atomic force microscopy and X-ray photoelectron spectroscopy of the modification of the surface of mica with an argon RF-plasma discharge 90 (1995) 155
- Brübach, J., see Hopkins, J. 84 (1995) 299
- Brunel, M., see Laude, L.D. 86 (1995) 368
- Brunel, M., see Brocherieux, A. 90 (1995) 47
- Bruque, J.M., see Jańczuk, B. 81 (1994) 95
- Brusatin, G., see Caccavale, F. 81 (1994) 443
- Bryl, R., T. Wysocki and R. Błaszczyszyn, Field-induced redistribution and diffusion of water on a Pt field emitter 87/88 (1995) 69
- Bubert, H. and R.P.H. Garten, Matrix factors affecting quantitative analysis of AES for binary alloys 81 (1994) 203
- Buckley, A.N. and R. Woods, Comment on 'Scanning tunnelling microscopy studies of galena: the mechanism of oxidation in air' by B.S. Kim, R.A. Hayes, C.A. Prestidge, J. Ralston and R.St.C. Smart 84 (1995) 223
- Buisson, L., P. Bracconi and X. Claudon, Quantitative analysis of the thermal degassing of a beryllium powder 84 (1995) 211
- Bukhtiyarov, V.I., see Aliev, V.S. 90 (1995) 191
- Bull, S.J., see Rice-Evans, P.C. 85 (1995) 320
- Bull, S.J., see Saleh, A.S. 85 (1995) 325
- Büssenschütt, A., see Zielasek, V. 90 (1995) 117
- Butman, M.F., J. Nakamura, S. Kamidori and H. Kawano, Influence of surface charge on thermal positive ion emission from potassium bromide 89 (1995) 323
- Caccavale, F., G. Brusatin and I. Kleps, A combined use of SIMS and RBS techniques for the investigation of SiC and SiCN films 81 (1994) 443
- Cade, N.A., see King, R.A. 87/88 (1995) 279
- Cade, N.A., see Huang, M. 87/88 (1995) 421
- Cai, G., see Andrén, H.-O. 87/88 (1995) 200
- Cai, S., see Ji, G. 81 (1994) 63
- Calder, I., see Lawther, D.W. 85 (1995) 265
- Callegaro, L., see Vavassori, P. 89 (1995) 93
- Camus, P.P., D.J. Larson and T.F. Kelly, A method for reconstructing and locating atoms on the crystal lattice in three-dimensional atom probe data 87/88 (1995) 305
- Camus, P.P., see Bajikar, S.S. 87/88 (1995) 438
- Camus, P.P., see Larson, D.J. 87/88 (1995) 446
- Cañón, M.G., see L'Argentièrre, P.C. 89 (1995) 63
- Canter, K.F., see Vasumathi, D. 85 (1995) 154
- Canter, K.F., G. Amarendra, D. Vasumathi, S.A. Wesley, R. Xie, A.P. Mills, Jr., R.L. Sabatini and Y. Zhu, Contrast in positron reemission microscopy due to positron trapping by dislocations 85 (1995) 339
- Carley, A.F., P.R. Davies, M.W. Roberts, N. Shukla, Y. Song and K.K. Thomas, The hydroxylation of Cu(111) and Zn(0001) surfaces 81 (1994) 265
- Carline, R.T., C. Pickering, T.J.C. Hosea and D.J. Robbins, Photoreflectance of strained $\text{Si}_{1-x}\text{Ge}_x$ epilayers ($0.07 \leq x \leq 0.26$) and comparison with spectroscopic ellipsometry 81 (1994) 475
- Carlsson, J.-O., see Stenberg, G. 86 (1995) 543
- Carrière, B., see Le Normand, F. 81 (1994) 309
- Carrizosa, I., see Benítez, J.J. 84 (1995) 391
- Castle, J.E., see Salvi, A.M. 90 (1995) 333
- Caudano, R., see Grégoire, Ch. 84 (1995) 163
- Caudano, R., see Lamontagne, B. 90 (1995) 481
- Cerezo, A., see Hyde, J.M. 87/88 (1995) 311
- Cerezo, A., see Miller, M.K. 87/88 (1995) 323
- Cerezo, A., see Sijbrandij, S.J. 87/88 (1995) 414
- Černý, R., V. Vydra, P. Přikryl, I. Ulrych, J. Kočka, K.M.A. El-Kader, Z. Chvoj and V. Cháb, Theoretical and experimental studies of a-Si:H recrystallization by XeCl excimer laser irradiation 86 (1995) 359
- Cerofolini, G.F. and L. Meda, Chemistry at silicon crystalline surfaces 89 (1995) 351
- Cerofolini, G.F., G. La Bruna and L. Meda, Enhanced silicon oxidation in O_2 and $\text{O}_2:\text{F}_2$ 89 (1995) 361
- Cháb, V., see Černý, R. 86 (1995) 359
- Chabrierie, J.-P., see Néron de Surgy, G. 87/88 (1995) 91
- Chambers, S.A., see Tran, T.T. 81 (1994) 161
- Chambreland, S., see Duval, S. 87/88 (1995) 284
- Chan, S.-H., S.M. Sze, C.-Y. Chang and W.-I. Lee, Selective epitaxial growth of GaInP by LP-MOCVD using ethyldimethylindium, trimethylindium, trimethylgallium and triethylgallium as group III sources 82/83 (1994) 85
- Chang, C.-Y., see Chan, S.-H. 82/83 (1994) 85

- Chang, K.-S., see Iwata, T. 87/88 (1995) 31
- Chang, M.F., see Dam, B. 86 (1995) 13
- Charlton, M., see Moxom, J. 85 (1995) 118
- Chattopadhyay, P. and S. Sanyal, Capacitance-voltage characteristics of Schottky barrier diode in the presence of deep-level impurities and series resistance 89 (1995) 205
- Chen, C.S., see Mar, S.Y. 90 (1995) 497
- Chen, H., see Deng, J. 81 (1994) 341
- Chen, X. and Y. Wang, A study of the composition distribution at the Ti/Al₂O₃ interface using the MCs⁺-SIMS technique 89 (1995) 169
- Chen, X.G., see Xiao, X.R. 90 (1995) 321
- Chen, Y.-W., see Li, C. 81 (1994) 465
- Chen, Y.L., see Kelliher, J.T. 86 (1995) 453
- Chenakin, S.P., Initial oxidation kinetics of Fe-Ni single crystals before and after ion bombardment 84 (1995) 91
- Cheng, P., see Xue, G. 89 (1995) 77
- Cheremskoy, P.G., see Skatkov, L.I. 81 (1994) 427
- Chergui, A., see Deiss, J.L. 86 (1995) 149
- Chiurlo, P., see Garbassi, F. 84 (1995) 145
- Chiwaki, M., see Suzuki, R. 85 (1995) 87
- Cho, K., J. Kishimoto, T. Hashizume, H.W. Pickering and T. Sakurai, Adsorption and film growth of BTA on clean and oxygen adsorbed Cu(110) surfaces 87/88 (1995) 380
- Choi, J.-G., see Lee, H.J. 89 (1995) 121
- Chopra, K.L., see Rao, M.V.H. 89 (1995) 417
- Choyke, W.J., see Yates, Jr., J.T. 82/83 (1994) 180
- Chuah, G.K., see Cocke, D.L. 84 (1995) 153
- Chub, A.B., see Khrantsova, E.A. 82/83 (1994) 576
- Chvoj, Z., see Černý, R. 86 (1995) 359
- Cifre, J., see Puigdollers, J. 86 (1995) 600
- Claudon, X., see Buisson, L. 84 (1995) 211
- Clement, M., see Van Veen, A. 85 (1995) 216
- Coble, H.D., see Loo, B.H. 81 (1994) 175
- Coccia, L., see King, S. 86 (1995) 134
- Cocke, D.L., G.K. Chuah, N. Kruse and J.H. Block, Copper oxidation and surface copper oxide stability investigated by pulsed field desorption mass spectrometry 84 (1995) 153
- Cole, D., see Jordan, R. 86 (1995) 24
- Coleman, P.G., see Knights, A.P. 85 (1995) 43
- Coleman, P.G., see Overton, N. 85 (1995) 54
- Coleman, P.G., see Goodyear, A. 85 (1995) 98
- Coleman, P.G., E. Bloss, S. Setzler, S. LaShell, G. Davies and W.D. Sawyer, Slow positron implantation spectroscopy of edge-defined film-fed growth silicon 85 (1995) 276
- Collaud-Coen, M., see Gröning, P. 89 (1995) 83
- Colling, C.W., see Lee, H.J. 89 (1995) 121
- Colón, G., see Navío, J.A. 81 (1994) 325
- Colter, P.C., see Hayafuji, N. 82/83 (1994) 18
- Compaan, A., see Dubowski, J.J. 86 (1995) 548
- Condorelli, G.G., see Gulino, A. 90 (1995) 289
- Cooke, P.W., see Umlor, M.T. 85 (1995) 295
- Corbel, C., see Manuel, A.A. 85 (1995) 301
- Coston, R., see Wee, A.T.S. 81 (1994) 377
- Craciun, D., see Craciun, V. 86 (1995) 99
- Craciun, V., S. Amirhaghi, D. Craciun, J. Elders, J.G.E. Gardeniers and I.W. Boyd, Effects of laser wavelength and fluence on the growth of ZnO thin films by pulsed laser deposition 86 (1995) 99
- Craig, Jr., J.H., see Wang, P.W. 90 (1995) 413
- Creighton, J.R., Surface stoichiometry and the role of adsorbates during GaAs atomic layer epitaxy 82/83 (1994) 171
- Cros, A., see Grégoire, Ch. 84 (1995) 163
- Cros, A., see Shafeev, G.A. 86 (1995) 387
- Culp, R.D., see Jackson, M.S. 81 (1994) 195
- D'Alessio, L., see Teghil, R. 86 (1995) 190
- Dam, B., J. Rector, M.F. Chang, S. Kars, D.G. de Groot and R. Griessen, The laser ablation threshold of YBa₂Cu₃O_{6+x} as revealed by using projection optics 86 (1995) 13
- Danev, G., see Ihlemann, J. 86 (1995) 245
- D'Anna, E., G. Leggieri, A. Luches, M. Martino, A. Perrone, G. Majni, P. Mengucci, R. Alexandrescu, I.N. Mihailescu and J. Zemek, Excimer laser reactive ablation deposition of silicon nitride films 86 (1995) 170
- Danoix, F., see Schmuck, C. 87/88 (1995) 228
- Danoix, F., see Souchet, R. 87/88 (1995) 271
- Dasbach, U., see Arnold, J. 86 (1995) 251
- Daté, M., see Taguchi, Y. 82/83 (1994) 434
- Dauwe, C., see Segers, D. 85 (1995) 172
- David, S.A., see Babu, S.S. 87/88 (1995) 207
- Davies, G., see Coleman, P.G. 85 (1995) 276
- Davies, P.R., see Carley, A.F. 81 (1994) 265
- Davies, R.E., see Smith, G.C. 90 (1995) 357
- De Groot, D.G., see Dam, B. 86 (1995) 13
- De Marco, R. and J. Liesegang, Surface analysis of commercial lead/acid battery grids 84 (1995) 237
- De Maria, G., see Teghil, R. 86 (1995) 190
- De Mierry, P., see Ballutaud, D. 84 (1995) 187
- De Nijs, J.M.M., see Van Veen, A. 85 (1995) 216
- Debauche, C., see Flicstein, J. 86 (1995) 286
- Debauge, Y., M. Abon, J.C. Bertolini, J. Massardier and A. Rochefort, Synergistic alloying behaviour of Pd₅₀Cu₅₀ single crystals upon adsorption and co-adsorption of CO and NO 90 (1995) 15
- Debiemme-Chouvy, C., see Ballutaud, D. 84 (1995) 187
- Declémy, A., see Durand, N. 81 (1994) 119
- Deconihout, B., see Bas, P. 87/88 (1995) 298
- Deconihout, B., A. Bostel, M. Bouet, J.M. Sarrau, P. Bas and D. Blavette, Perfor-

- mance of the multiple events position sensitive detector used in the tomographic atom probe 87/88 (1995) 428
- Deiana, L., see Garbassi, F. 84 (1995) 145
- Deimel, M., see Reihls, K. 84 (1995) 107
- Deiss, J.L., A. Chergui, L. Koutti, J.L. Loison, M. Robino and J.B. Grun, Pulsed laser deposition of epitaxial layers of ZnSe 86 (1995) 149
- Deldime, M., J.-L. Dewez, Y.-J. Schneider and J. Marchand-Brynaert, Reactivity assay of surface carboxyl chain-ends of poly(ethylene terephthalate) (PET) film and track-etched microporous membranes using fluorine labelled- and/or ^3H -labelled derivatization reagents: tandem analysis by X-ray photoelectron spectroscopy (XPS) and liquid scintillation counting (LSC) 90 (1995) 1
- Deleter, P., see Laude, L.D. 86 (1995) 368
- Delgado, A.V., see Durán, J.D.G. 81 (1994) 1
- Delobel, R., see Bourbigot, S. 81 (1994) 299
- Delplancke, M.P., see Reniers, F. 81 (1994) 151
- Demanet, C.M., Atomic force microscopy determination of the topography of fly-ash particles 89 (1995) 97
- Demchuk, A.V. and V.A. Labunov, Surface morphology and structure modification of silicon layers induced by nanosecond laser radiation 86 (1995) 353
- DenBaars, S.P., see Keller, B.P. 82/83 (1994) 126
- Deng, C., see Slaoui, A. 86 (1995) 346
- Deng, J., H. Chen, X. Bao and M. Muhler, The effect of cyclic oxidation-reduction pretreatments on an amorphous $\text{Ni}_{80}\text{P}_{20}$ catalyst: an XPS/UPS/ISS study 81 (1994) 341
- Desimoni, E., see Salvi, A.M. 90 (1995) 333
- Desjardins, P., see Meunier, M. 86 (1995) 475
- Desjonquères, M.C., D. Spanjaard, B. Piveteau and S. Papadia, A simple approach to the calculation of surface defect energies in transition metals 87/88 (1995) 337
- Dessaux, O., see Brocherieux, A. 90 (1995) 47
- Devel, M., C. Girard, C. Joachim and O.J.F. Martin, Field induced manipulation of fullerene molecules with the STM: a self-consistent theoretical study 87/88 (1995) 390
- Devillers, M., O. Dupuis, A. Janosi and J.P. Soumillion, Coordination compounds as precursors for laser deposition of nickel-based conducting films 81 (1994) 83
- Devine, R.A.B., see Parada, E.G. 86 (1995) 294
- Dewez, J.-L., see Deldime, M. 90 (1995) 1
- Dey, S.D., see Ray, N. 84 (1995) 203
- Dhese, K., see Wagner, F.X. 86 (1995) 364
- D'Huysser, A., see Souchet, R. 87/88 (1995) 271
- Di Palma, T.M., S. Orlando, A. Giardini-Guidoni, A.J. Paul, J.W. Hastie and A. Mele, Composition and gas dynamics of laser ablated AlN plumes 86 (1995) 68
- Dieckhoff, S., see Gesang, T. 84 (1995) 273
- Dietler, G., see Gröning, P. 89 (1995) 83
- Dietrich, D., see Schlottig, F. 90 (1995) 129
- Dietz, N., see Kelliher, J.T. 86 (1995) 453
- Dillon, A.C., see George, S.M. 82/83 (1994) 460
- Dimitrakis, P., see Thurzo, I. 90 (1995) 39
- Dimitrova, T., see Atanassova, E. 84 (1995) 193
- Ding, J., see Xue, G. 89 (1995) 77
- Dip, A., see Hayafuji, N. 82/83 (1994) 18
- Dirac, H., see Müllenborn, M. 86 (1995) 568
- Dmitruk, N.L., E.V. Basiuk, G.Ya. Kolbasov, O.A. Yakubtsov, I.A. Molchanovskii and T.A. Taranets, Morphology, atomic composition and photoelectric properties of the microrelief InP-electrolyte interface 90 (1995) 489
- Dodelet, J.P., see Weng, L.T. 84 (1995) 9
- Domingue, A., see Piyakis, K. 84 (1995) 227
- Domínguez, P.S., see Tejedor, P. 89 (1995) 271
- Donaton, R.A., K. Lokere, R. Verbeeck and K. Maex, Etching of CoSi_2 in HF-based solutions 89 (1995) 221
- Dorikens-Vanpraet, L., see Segers, D. 85 (1995) 172
- Drachsel, W., see Gorodetskii, V. 87/88 (1995) 151
- Dragnea, B., see Peled, A. 86 (1995) 538
- Dreyfus, R.W., Why are high- T_c superconductors, HTSC, deposited by 248 nm lasers at 400 MW/cm 2 ? 86 (1995) 29
- Drozd, V.E., A.P. Baraban and I.O. Nikiforova, Electrical properties of $\text{Si-Al}_2\text{O}_3$ structures grown by ML-ALE 82/83 (1994) 583
- Drozd, V.E., A.A. Tulub, V.B. Aleskovski and D.V. Korol'kov, Synthesis of oxide superalloys by ML-ALE method 82/83 (1994) 587
- Drozd, V.E. and V.B. Aleskovski, Synthesis of conducting oxides by ML-ALE 82/83 (1994) 591
- Dubot, P., see Fauquet, C. 81 (1994) 435
- Dubowski, J.J., A. Compaan and M. Prasad, Laser-assisted dry etching ablation of InP 86 (1995) 548
- Dulac, O., see Flicstein, J. 86 (1995) 286
- Dumont, H., Sz. Fujita and Sg. Fujita, Photo-assisted growth and characterization of $\text{Zn}_x\text{Cd}_{1-x}\text{S}$ by MOVPE 86 (1995) 442
- Dupuis, O., see Devillers, M. 81 (1994) 83
- Durán, J.D.G., L. Zurita, M.C. Guindo, A.V. Delgado and F. González-Caballero, Surface thermodynamic properties of cadmium sulfide 81 (1994) 1
- Durand, H.-A., J.-H. Brimaud, O. Hellman, H. Shibata, S. Sakuragi, Y. Makita, D. Gesbert and P. Meyrueis, Excimer laser sputtering deposition of TiO_2 optical coating for solar cells 86 (1995) 122
- Durand, N., K.F. Badawi, A. Declémy and Ph. Goudeau, Origin of residual stress in

- a textured Au thin film on a LiF substrate 81 (1994) 119
- Durbin, S.M., see Gog, Th. 81 (1994) 485
- Durrer, W.G., M. Portillo, P. Wang and D.P. Russell, Temperature dependence of surface charging of NaCl under electron irradiation: role of secondary electron emission 81 (1994) 215
- Duś, R., E. Nowicka, W. Lisowski and Z. Wolfram, Atomic hydrogen adsorption on sintered thin copper films 90 (1995) 277
- Duval, S., S. Chambrelaud, D. Blavette, A. Loiseau and L. Potez, 3D reconstruction of antiphase boundaries in Cu₃Au from field ion images 87/88 (1995) 284
- Dwyer, D.J., X.J. Pang, M. Gao and R.P. Wei, Surface enrichment of niobium on Inconel 718 (100) single crystals 81 (1994) 229
- Dyer, P.E., D.M. Karnakis and G.A. Oldershaw, Analysis and experimental study of one-photon incubated absorption in polymers 86 (1995) 1
- Dyer, P.E., P.H. Key, D. Sands, H.V. Snelling and F.X. Wagner, Blast-wave studies of excimer laser ablation of ZnS 86 (1995) 18
- Dyer, P.E., see Jackson, S.R. 86 (1995) 223
- Eaglesham, D.J., see Weir, B.E. 84 (1995) 413
- Easwarakhanthan, T., S. Ravelet and P. Renard, An ellipsometric procedure for the characterization of very thin surface films on absorbing substrates 90 (1995) 251
- Ebeid, M.R., see Ashour, A. 89 (1995) 159
- Egdell, R.G., see Gulino, A. 90 (1995) 289
- Egdell, R.G., see Taverner, A.E. 90 (1995) 383
- Ehrfeld, W., see Arnold, J. 86 (1995) 251
- Ehrhardt, J.J., see Lobstein, N. 89 (1995) 307
- Eisele, I., see Jiang, W. 86 (1995) 564
- Ekerdt, J.G., see Jackson, M.S. 81 (1994) 195
- Ekerdt, J.G., see Asami, S. 82/83 (1994) 359
- El-Kader, K.M.A., see Černý, R. 86 (1995) 359
- El-Kadry, N., see Ashour, A. 89 (1995) 159
- El-Masry, N.A., see Bedair, S.M. 82/83 (1994) 7
- El-Masry, N.A., see Hayafuji, N. 82/83 (1994) 18
- Eldallal, G.M., see Hayafuji, N. 82/83 (1994) 18
- Elders, J., see Craciun, V. 86 (1995) 99
- Elers, K.-E., M. Ritala, M. Leskelä and E. Rauhala, NbCl₅ as a precursor in atomic layer epitaxy 82/83 (1994) 468
- Elyaagoubi, N., see Meunier, M. 86 (1995) 475
- Emmel, A., see Bergmann, H.W. 86 (1995) 259
- Engelhard, H., F. Stietz, S. Sloboshanin, V. Persch, Th. Allinger, J.A. Schaefer and A. Goldmann, Interfacial reaction of Ag with the InP(100)4 × 2 surface - a photoemission study 90 (1995) 89
- Enomoto, A., see Kurihara, T. 85 (1995) 178
- Enta, Y., N. Miyamoto, Y. Takakuwa and H. Kato, Photoelectron intensity oscillation as a probe to monitor Si layer-by-layer growth 82/83 (1994) 327
- Ernst, N., see Unger, J. 87/88 (1995) 45
- Ernst, N., see Gorodetskii, V. 87/88 (1995) 151
- Esrom, H., J.-Y. Zhang, U. Kogelschatz and A.J. Pedraza, New approach of a laser-induced forward transfer for deposition of patterned thin metal films 86 (1995) 202
- Estève, D., see Maury, F. 86 (1995) 447
- Esteve, J., see Palau, J. 86 (1995) 59
- Etcheberry, A., see Ballutaud, D. 84 (1995) 187
- Evans, J.F., see Schulze, R.K. 81 (1994) 449
- Fähler, S., see Krebs, H.-U. 86 (1995) 86
- Fahy, M.R., K. Sato and B.A. Joyce, Silicon doping with modulated beam epitaxy in the growth of GaAs(111)A 82/83 (1994) 14
- Fajgar, R., M. Jakoubková, Z. Bastl and J. Pola, Germanium-containing coatings by IR laser-induced decomposition of ethoxy(trimethyl)germane and tetramethylgermane 86 (1995) 530
- Fang, J., see Ji, G. 81 (1994) 63
- Fang, Y., C. Bai, T. Wang and Y.-Q. Tang, Characterization of triplex RNA poly[rU] · poly[rA] · poly[rU] adsorbed on silver colloids by Fourier transform surface enhanced Raman scattering and scanning tunneling microscopy 89 (1995) 331
- Fanter, D., see Gesang, T. 84 (1995) 273
- Farrell, T. and J.V. Armstrong, In-situ laser reflectometry of the epitaxial growth of thin semiconductor films 86 (1995) 582
- Fauquet, C., P. Dubot, L. Minel, M.-G. Barthés-Labrousse, M. Rei Vilar and M. Villatte, Adsorption of monoethanolamine on clean, oxidized and hydroxylated aluminium surfaces: a model for amine-cured epoxy/aluminium interfaces 81 (1994) 435
- Fayette, L., see Le Normand, F. 81 (1994) 309
- Fazleev, N.G., J.L. Fry, K. Kuttler and A.H. Weiss, Theoretical study of the positron surface state at an alkali-metal surface 85 (1995) 22
- Fazleev, N.G., J.L. Fry, K. Kuttler, A.R. Koymen and A.H. Weiss, Study of positron surface states on the alkali-metal-covered transition-metal surface 85 (1995) 26
- Fazouan, N., see Maury, F. 86 (1995) 447
- Fedotov, A.K., M.I. Tarasik and A.M. Yanchenko, Carrier transport in heavily doped polycrystalline silicon layers after annealing by a scanning laser beam 84 (1995) 379
- Fei, X., see Wang, J. 84 (1995) 383
- Feldman, L.C., see Weir, B.E. 84 (1995) 413
- Feng, Z.C., see Wee, A.T.S. 81 (1994) 377

- Ferrater, C., see Queral, X. 86 (1995) 95
- Ferro, D., see Teghil, R. 86 (1995) 190
- Fígoli, N.S., see L'Argentièrre, P.C. 89 (1995) 63
- Fitzpatrick, J.J., see Hansen, D.C. 84 (1995) 85
- Flamant, G., see Mazhukin, V.I. 86 (1995) 7
- Flamant, G., see Berjeza, N.A. 86 (1995) 303
- Fleischer, S., see Panda, B.K. 85 (1995) 182
- Flicstein, J., Y. Vitel, O. Dulac, C. Debauche, Y.I. Nissim and C. Licoppe, Tunable UV-flash krypton lamp array useful for large area deposition and in situ UV annealing of Si-based dielectrics 86 (1995) 286
- Flicstein, J., see Parada, E.G. 86 (1995) 294
- Fogarassy, E., see Antoni, F. 86 (1995) 175
- Fogarassy, E., see Mathé, E.L. 86 (1995) 338
- Follis, G.C., see Gog, Th. 81 (1994) 485
- Fontaine, M.-F., see Le Mercier, T. 86 (1995) 382
- Forbes, R.G., Field evaporation theory: a review of basic ideas 87/88 (1995) 1
- Forbes, R.G., G.L.R. Mair, N.N. Ljepojevic and W. Liu, New understandings in the theory of liquid-metal ion sources 87/88 (1995) 99
- Forbes, R.G., see Liu, W. 87/88 (1995) 122
- Fragalà, I., see Gulino, A. 90 (1995) 289
- Freer, B.S., see Kosowsky, S.D. 84 (1995) 179
- Frerichs, H., see Kreutz, E.W. 86 (1995) 266
- Frerichs, H., J. Stricker, D.A. Wesner and E.W. Kreutz, Laser-induced surface modification and metallization of polymers 86 (1995) 405
- Fretwell, J., see Asami, S. 82/83 (1994) 359
- Friedbacher, G., E. Bouveresse, G. Fuchs, M. Grasserbauer, D. Schwarzbach, R. Haubner and B. Lux, Pretreatment of silicon substrates for CVD diamond deposition studied by atomic force microscopy 84 (1995) 133
- Froben, F.W., see Yu, H. 86 (1995) 74
- Frommeyer, G., see Wesemann, J. 87/88 (1995) 179
- Fry, J.L., see Fazleev, N.G. 85 (1995) 22
- Fry, J.L., see Fazleev, N.G. 85 (1995) 26
- Fuchs, C., see Antoni, F. 86 (1995) 175
- Fuchs, G., see Friedbacher, G. 84 (1995) 133
- Fujishima, A., see Loo, B.H. 81 (1994) 175
- Fujita, K., see Hirai, M. 82/83 (1994) 23
- Fujita, Sg., see Fujita, Sz. 86 (1995) 431
- Fujita, Sg., see Dumont, H. 86 (1995) 442
- Fujita, Sz. and Sg. Fujita, Photoassisted growth of II-VI semiconductor films 86 (1995) 431
- Fujita, Sz., see Dumont, H. 86 (1995) 442
- Fukutani, K., see Kanazawa, I. 85 (1995) 124
- Fung, S., see Panda, B.K. 85 (1995) 182
- Fung, S., see Ling, C.C. 85 (1995) 305
- Furukawa, H., see Yoshida, I. 82/83 (1994) 501
- Furukawa, S., see Hwang, S.M. 82/83 (1994) 523
- Fuso, F., see Amoruso, S. 86 (1995) 35
- Gambardella, U., A. Giardini, V. Marotta, A. Morone, S. Orlando and M. Snels, Laser ablation of BiSrCaCuO superconducting thin film: analysis of intermediate species in real time 86 (1995) 45
- Gamo, K., see Meguro, T. 82/83 (1994) 193
- Gamo, K., see Ishii, M. 86 (1995) 554
- Ganem, J.-J., see Bréelle, E. 81 (1994) 127
- Gao, M., see Dwyer, D.J. 81 (1994) 229
- Garbassi, F., L. Balducci, P. Chiurlo and L. Deiana, A study of surface modification of silica using XPS, DRIFT and NMR 84 (1995) 145
- Garcia Lopez, J., see Aubert, P. 86 (1995) 144
- Gardella, Jr., J.A., see Li, J.-X. 90 (1995) 205
- Gardeniers, J.G.E., see Craciun, V. 86 (1995) 99
- Garofalini, S.H., see Hensley, D.A. 81 (1994) 331
- Garry, G., see Aubert, P. 86 (1995) 144
- Garten, R.P.H., see Bubert, H. 81 (1994) 203
- Gasser, A., see Kreutz, E.W. 86 (1995) 310
- Gates, S.M., see Koleske, D.D. 82/83 (1994) 344
- Ge, Q. and P.J. Møller, CO adsorption on clean and atomic-layer-Cu-covered ZnO(10 $\bar{1}$ 0) surfaces 82/83 (1994) 305
- Geber, G.P., An APFIM/TEM investigation of the discontinuous precipitation in a Ni-In alloy 87/88 (1995) 234
- Gengembre, L., see Bourbigot, S. 81 (1994) 299
- Gengembre, L., see Brocherieux, A. 90 (1995) 47
- George, S.M., see Okada, L.A. 82/83 (1994) 410
- George, S.M., O. Sneh, A.C. Dillon, M.L. Wise, A.W. Ott, L.A. Okada and J.D. Way, Atomic layer controlled deposition of SiO₂ and Al₂O₃ using ABAB... binary reaction sequence chemistry 82/83 (1994) 460
- Geretovszky, Zs., L. Kelemen, K. Bali and T. Szörényi, Kinetic model for scanning laser-induced deposition from the liquid phase 86 (1995) 494
- Geretovszky, Zs., see Bali, K. 86 (1995) 500
- Gerola, D., W.B. Waeber and M. Shi, Design and simulation of the PSI electrostatic positron beam 85 (1995) 106
- Gerola, D., see Shi, M. 85 (1995) 143
- Gesang, T., R. Höper, S. Dieckhoff, D. Fanter, A. Hartwig, W. Possart and O.-D. Hennemann, AFM investigations of the initial stages of prepolymer film growth on aluminium 84 (1995) 273
- Gesbert, D., see Durand, H.-A. 86 (1995) 122
- Geus, J.W., see Bolt, P.H. 89 (1995) 339
- Geus, J.W., see Van Kooten, W.E.J. 90 (1995) 137
- Geus, J.W., see Van Wijk, R. 90 (1995) 261
- Gewinner, G., see Hong, S. 90 (1995) 65
- Ghosh, T.B., see Sreemany, M. 81 (1994) 365
- Ghosh, T.B., see Sreemany, M. 90 (1995) 241
- Ghosh, V.J., Positron implantation profiles in elemental and multilayer systems 85 (1995) 187

- Ghosh, V.J., B. Nielsen, K.G. Lynn and D.O. Welch, Defect profiling in elemental and multilayer systems: correlations of fitted defect concentrations with positron implantation profiles 85 (1995) 210
- Giardini, A., see Gambardella, U. 86 (1995) 45
- Giardini-Guidoni, A., see Di Palma, T.M. 86 (1995) 68
- Giardini-Guidoni, A., see Teghil, R. 90 (1995) 505
- Gijzeman, O.L.J., see Van Kooten, W.E.J. 90 (1995) 137
- Gijzeman, O.L.J., see Van Wijk, R. 90 (1995) 261
- Girard, C., see Devel, M. 87/88 (1995) 390
- Givargizov, E.I., V.V. Zhimov, A.N. Stepanova, E.V. Rakova, A.N. Kiselev and P.S. Plekhanov, Microstructure and field emission of diamond particles on silicon tips 87/88 (1995) 24
- Givord, D., see Jordan, R. 86 (1995) 24
- Gleditsch, S., see Reihls, K. 84 (1995) 107
- Gog, Th., G.C. Follis and S.M. Durbin, LiBr on Si(111): an X-ray standing wave measurement 81 (1994) 485
- Gol'berg, S.M., see Sobol, E.N. 90 (1995) 235
- Goldberg, R.D., see Aers, G.C. 85 (1995) 196
- Goldberg, R.D., P.J. Schultz and P.J. Simpson, Determination of the characteristic signal for positron annihilation at divacancies in ion-irradiated silicon 85 (1995) 287
- Goldmann, A., see Kürpick, U. 89 (1995) 383
- Goldmann, A., see Engelhard, H. 90 (1995) 89
- Gomozov, V.P., see Skatkov, L.I. 81 (1994) 427
- Gonda, S., see Kim, J.H. 82/83 (1994) 76
- Gonda, S., see Asahi, H. 82/83 (1994) 109
- González, H., see Néron de Surgy, G. 87/88 (1995) 91
- González, P., see Parada, E.G. 86 (1995) 294
- González, S., see Hernández Creus, A. 81 (1994) 387
- González-Caballero, F., see Durán, J.D.G. 81 (1994) 1
- González-Martín, M.L., see Jańczuk, B. 81 (1994) 95
- Gonzalo, J., C.N. Afonso, F. Vega, D. Martínez García and J. Perrière, Plasma properties and stoichiometry of laser-deposited BiSrCaCuO thin films 86 (1995) 40
- Goodyear, A., see Overton, N. 85 (1995) 54
- Goodyear, A. and P.G. Coleman, Development of a reflection geometry positron reemission microscope 85 (1995) 98
- Gorenstein, A., see Julien, C. 90 (1995) 389
- Gorochov, O., see Bourée, J.E. 86 (1995) 437
- Gorodetskii, V., N. Ernst, W. Drachsel and J.H. Block, Field-induced oxygen layer formation from H₂O and its titration by hydrogen on a Pt-emitter 87/88 (1995) 151
- Gorshkov, V.N., see Vladimirov, V.V. 87/88 (1995) 112
- Görts, P.C., see Van Wijk, R. 90 (1995) 261
- Goto, A., see Itoh, Y. 85 (1995) 165
- Goto, H., see Suzuki, T. 82/83 (1994) 103
- Goto, K., see Takemi, M. 82/83 (1994) 115
- Goto, S., see Ohno, H. 82/83 (1994) 164
- Gotoda, M., H. Sugimoto, S. Maruno, T. Isu, W. Susaki and M. Nunoshita, Fabrication of smooth facets of InP by selective sidewall epitaxy using CBE 82/83 (1994) 80
- Goudeau, Ph., see Durand, N. 81 (1994) 119
- Goudmand, P., see Brocherieux, A. 90 (1995) 47
- Grangeon, F., H. Sassoli, Y. Mathey, M. Autric, D. Pailharey and W. Marine, Pulsed laser deposition of NbTe_x thin films 86 (1995) 160
- Gräsjö, L., G. Hultquist, K.L. Tan and M. Seo, Surface reactions on palladium hydride in vacuum, air and water studied in situ with mass spectrometry 89 (1995) 21
- Grasserbauer, M., see Friedbacher, G. 84 (1995) 133
- Greer, A.L., Diffusion and reactions in thin films 86 (1995) 329
- Grégoire, Ch., J.-J. Pireaux, A. Cros and R. Caudano, High Resolution Electron Energy Loss Spectroscopy investigation of the copper/polyphenylquinoxaline interface formation 84 (1995) 163
- Griessen, R., see Dam, B. 86 (1995) 13
- Griffiths, K., see Kasza, R.V. 84 (1994) 97
- Grimblot, J., see Brocherieux, A. 90 (1995) 47
- Gröning, P., O.M. Küttel, M. Collaud-Coen, G. Dietler and L. Schlapbach, Interaction of low-energy ions (< 10 eV) with polymethylmethacrylate during plasma treatment 89 (1995) 83
- Grozdanov, I., Solution growth and characterization of silver sulfide films 84 (1995) 325
- Grun, J.B., see Deiss, J.L. 86 (1995) 149
- Gu, H.C., see Wang, X.K. 89 (1995) 297
- Gu, S., R. Zhang, P. Han, R. Wang, P. Zhong and Y. Zheng, Raman study of strained SiGe layers 81 (1994) 431
- Guay, D., see Weng, L.T. 84 (1995) 9
- Guay, D., see Lamontagne, B. 90 (1995) 481
- Guczi, L., see Sundararajan, R. 90 (1995) 165
- Gué, A.M., see Maury, F. 86 (1995) 447
- Guesdon, J.P., see Julien, C. 90 (1995) 389
- Guindo, M.C., see Durán, J.D.G. 81 (1994) 1
- Gulino, A., G.G. Condorelli, I. Fragalà and R.G. Egdell, Surface segregation of Sb in doped TiO₂ rutile 90 (1995) 289
- Gulino, A., see Taverner, A.E. 90 (1995) 383
- Gunter, P.L.J., see Van Hardeveld, R.M. 84 (1995) 339
- Gunter, P.L.J. and J.W. Niemantsverdriet, Thickness determination of uniform overlayers on rough substrates by angle-dependent XPS 89 (1995) 69
- Güntherodt, H.-J., see Sum, R. 86 (1995) 140
- Guo, S., G. Xue and Y. Qian, Interfacial modification of polymer/metal joints by a two-component coupling system of polybenzimidazole and 2-mercaptobenzimidazole 84 (1995) 351
- Gurin, V.S. and A.B. Kovrikov, STM-stimulated modification of solids: a quantum chemical study 81 (1994) 43

- Habermehl, S., see Kelliher, J.T. 86 (1995) 453
- Habraken, F.H.P.M., see Bolt, P.H. 89 (1995) 339
- Habraken, F.H.P.M., see Van Wijk, R. 90 (1995) 261
- Hachimi, A., see Lobstein, N. 89 (1995) 307
- Hadj Zoubir, N. and M. Vergnat, Thermal desorption spectroscopy study of chemically etched porous silicon 89 (1995) 35
- Hagenhoff, B., see Reihs, K. 84 (1995) 107
- Hagmann, M.J., Simulations of rectification in a laser-illuminated scanning tunneling microscope 87/88 (1995) 368
- Hague, C.F., see Le Mercier, T. 86 (1995) 382
- Hakvoort, R.A., A. van Veen, P.E. Mijnders and H. Schut, Helium and hydrogen-decorated cavities in silicon 85 (1995) 271
- Hamada, A., see Sueoka, O. 85 (1995) 59
- Hamada, A. and O. Sueoka, Total cross-section measurements for positrons and electrons colliding with molecules: CCl_4 85 (1995) 64
- Hammer, C.F., see Ye, X.R. 89 (1995) 151
- Hammer, L., see Starke, U. 89 (1995) 175
- Han, P., see Gu, S. 81 (1994) 431
- Han, R., see Ling, C.C. 85 (1995) 305
- Hanabusa, M. and A. Komatsu, UV light irradiation effects on nucleation during chemical vapor deposition of Al films 86 (1995) 428
- Hanada, T., see Kawai, M. 82/83 (1994) 487
- Hanebuchi, M., T. Katoh and K. Morita, Characterization of thin Ag films deposited onto $\text{InP}(001)\text{-p}(2 \times 4)$ surface at room temperature by means of LEED, RHEED, AES and RBS-channeling techniques 89 (1995) 113
- Haneman, D., see Wu, S. 89 (1995) 289
- Hansen, D.C., E. McCafferty, C.W. Lins and J.J. Fitzpatrick, An FT-IR investigation of parabactin adsorbed onto aluminum 84 (1995) 85
- Hara, K., see Suzuki, T. 82/83 (1994) 103
- Hara, K., see Kano, N. 82/83 (1994) 132
- Hariharan, K., see Van Bakel, G.P.E.M. 90 (1995) 95
- Hartner, W., see Starke, U. 89 (1995) 175
- Hartwig, A., see Gesang, T. 84 (1995) 273
- Hasegawa, F., see Akamatsu, M. 82/83 (1994) 228
- Hasegawa, M., see Kawasuso, A. 85 (1995) 280
- Hashimoto, K., see Loo, B.H. 81 (1994) 175
- Hashimoto, K., see Arai, M. 89 (1995) 11
- Hashizume, T., see Bakhtizin, R.Z. 87/88 (1995) 347
- Hashizume, T., see Xue, Q. 87/88 (1995) 364
- Hashizume, T., Q.K. Xue, A. Ichimiya and T. Sakurai, Structure of the MBE-grown $\text{GaAs}(001)\text{-(}2 \times 4\text{)}$ phase 87/88 (1995) 373
- Hashizume, T., see Cho, K. 87/88 (1995) 380
- Hashizume, T., see Jeon, D. 87/88 (1995) 386
- Hashizume, T., see Sakurai, T. 87/88 (1995) 405
- Haslingerová, I., see Pingo, M. 90 (1995) 373
- Hastie, J.W., see Di Palma, T.M. 86 (1995) 68
- Hata, K., M. Kumamura, T. Yasuda, Y. Saito and A. Ohshita, A FEM study of liquid lithium on a $\langle 011 \rangle$ -oriented tungsten tip 87/88 (1995) 117
- Hatab, Z.R., S.L. Prins, S.S.H. Naqvi and J.R. McNeil, 16 MB DRAM trench depth characterization using dome scatterometry 86 (1995) 597
- Hatta, A., see Suzuki, Y. 84 (1995) 1
- Hattori, T., see Kanazawa, I. 85 (1995) 124
- Haubner, R., see Friedbacher, G. 84 (1995) 133
- Haukka, S., E.-L. Lakomaa and T. Suntola, Surface coverage of ALE precursors on oxides 82/83 (1994) 548
- Hautojärvi, P., see Vaari, J. 81 (1994) 289
- Hautojärvi, P., see Manuel, A.A. 85 (1995) 301
- Hautojärvi, P., see Vaara, T. 89 (1995) 103
- Hayafuji, N., G.M. Eldallal, A. Dip, P.C. Colter, N.A. El-Masry and S.M. Bedair, Atomic layer epitaxy of device quality AlGaAs and AlAs 82/83 (1994) 18
- Headrick, R.L., see Weir, B.E. 84 (1995) 413
- Heinonen, M.H., see Leiro, J.A. 90 (1995) 515
- Heinz, K., see Starke, U. 89 (1995) 175
- Heitz, J., E. Arenholz, D. Bäuerle and K. Schilcher, Growth of excimer-laser-induced dendritic surface structures on polyethylene-terephthalate 81 (1994) 103
- Heitzinger, J.M., see Jackson, M.S. 81 (1994) 195
- Helbing, R., see Bourée, J.E. 86 (1995) 437
- Hellman, O., see Durand, H.-A. 86 (1995) 122
- Hennemann, O.-D., see Gesang, T. 84 (1995) 273
- Hensley, D.A. and S.H. Garofalini, XPS investigation of lithium borate glass and the Li/LiBO_2 interface 81 (1994) 331
- Henzler, M., see Zielasek, V. 90 (1995) 117
- Hernández Creus, A., R.M. Souto, S. González, M.M. Laz, R.C. Salvarezza and A.J. Arvia, The electrochemical faceting of copper in 85% aqueous orthophosphoric acid by using a potential reversal technique 81 (1994) 387
- Hesch, K., see Arnold, J. 86 (1995) 251
- Hess, P., see Karstens, H. 86 (1995) 521
- Hess, P., see Kolomenskii, A.A. 86 (1995) 591
- Hetherington III, W.M., see Wijekoon, W.M.K.P. 81 (1994) 347
- Heun, S., M. Sugiyama, S. Maeyama, Y. Watanabe and M. Oshima, Morphology of epitaxial SrF_2 films on atomically modified $\text{InP}(100)$ 82/83 (1994) 507
- Hibino, H. and T. Ogino, Scanning tunneling microscopy observations of Ge solid-phase epitaxy on $\text{Si}(111)$ 82/83 (1994) 374
- Himei, H., E. Maruya, M. Kubo, R. Vetrivel and A. Miyamoto, Theoretical estimation of ordered metal species in zeolite pores 82/83 (1994) 543
- Hirabayashi, I., see Matsubara, M. 82/83 (1994) 494
- Hirai, M., H. Ohnishi, K. Fujita and T. Watanabe, Substrate misorientation de-

- pendence of thermal stability of Si atom in Si atomic layer doped GaAs on GaAs(111)A 82/83 (1994) 23
- Hiraoka, H., see Lättsch, S. 81 (1994) 183
- Hirosawa, T., see Yoshida, I. 82/83 (1994) 501
- Hirose, M., M. Washio and K. Takahashi, Production of an intense slow positron beam using a compact cyclotron 85 (1995) 111
- Hirose, M., see Kanazawa, I. 85 (1995) 124
- Hirose, S., see Kano, N. 82/83 (1994) 132
- Hng, H.H., see Wee, A.T.S. 81 (1994) 377
- Hoekje, S.J., see Outlaw, R.A. 81 (1994) 143
- Hofmann, A., see Schlottig, F. 90 (1995) 129
- Hofmann, S. and M.G. Stepanova, Preferential sputtering of argon ion bombarded Ni_3Al and TaSi_2 90 (1995) 227
- Holmes Jr., A.L., see Keller, B.P. 82/83 (1994) 126
- Holt, S.A., R. Zhao and S. Myhra, Aqueous degradation of Bi-2212 single crystals: an AFM study of surface alteration 84 (1995) 125
- Homma, Y., see Yamaguchi, H. 82/83 (1994) 223
- Honda, Y., see Nunogaki, M. 85 (1995) 132
- Hong, J.K., I.-H. Oh, S.-A. Hong and W.Y. Lee, The effect of anodic polarization on a Ag electrode deposited on YSZ solid electrolyte 89 (1995) 229
- Hong, S., C. Pirri, P. Wetzel, D. Bolmont and G. Gewinner, Medium energy electron diffraction and X-ray photoelectron diffraction study of pseudomorphic Fe silicides grown on Si(111). Evidence of Fe vacancy formation 90 (1995) 65
- Hong, S.-A., see Hong, J.K. 89 (1995) 229
- Hongo, S., S. Taniguchi, K. Ojima, T. Urano and T. Kanaji, Adsorption and desorption of H_2O on potassium precovered Si(100) 2×1 surface 82/83 (1994) 437
- Hongo, S., K. Ojima, S. Taniguchi, T. Urano and T. Kanaji, Observation of the interface of Ba/Si(100) by MDS and TDS 82/83 (1994) 537
- Hono, K. and T. Sakurai, Atom probe studies of nanostructured alloys 87/88 (1995) 166
- Hono, K., see Ringer, S.P. 87/88 (1995) 223
- Hono, K., R. Okano, T. Saeda and T. Sakurai, The performance of the IMR three-dimensional atom probe 87/88 (1995) 453
- Hono, K., see Ringer, S.P. 90 (1995) 107
- Hood, G.M., see Zou, H. 90 (1995) 59
- Höper, R., see Gesang, T. 84 (1995) 273
- Hopkins, J., M.R. Leys, J. Brübach, W.C. Van der Vleuten and J.H. Wolter, A RHEED study of the dynamics of GaAs and AlGaAs growth on a (001) surface by MBE 84 (1995) 299
- Horikoshi, Y., see Yamaguchi, H. 82/83 (1994) 223
- Hosea, T.J.C., see Carline, R.T. 81 (1994) 475
- Hou, H.W., see Ye, X.R. 89 (1995) 151
- Hozhabri, N., A.R. Koymen, S.C. Sharma and K. Alavi, Defects and arsenic distribution in low-temperature-grown GaAs 85 (1995) 311
- Hrovatin, R. and J. Možina, Optodynamic aspect of a pulsed laser ablation process 86 (1995) 213
- Hsu, C.-H., see Kosowsky, S.D. 84 (1995) 179
- Hu, R., see Wee, A.T.S. 81 (1994) 377
- Hu, X. and Z. Lin, Hydrogen adsorption induced phase transitions on Si(100)-c(8 \times 8): temperature dependence studied by LEED 90 (1995) 111
- Huang, M., R.A.D. Mackenzie, G.D.W. Smith and N.A. Cade, Development of a FEM, FIM-AP system for studying grid-
ded vacuum microelectronic devices 87/88 (1995) 421
- Huang, M., S. Kaliaguine and S. Suppiah, Surface interaction between H_2 and CO_2 over silicalite-supported platinum 90 (1995) 393
- Huang, Y.S., see Mar, S.Y. 90 (1995) 497
- Huber, M.G., see Yu, H. 86 (1995) 74
- Hübner, A., see Yates, Jr., J.T. 82/83 (1994) 180
- Hulett, Jr., L.D., see Xu, J. 85 (1995) 49
- Hulett, Jr., L.D., S. Wallace, J. Xu, B. Nielsen, Cs. Szeles, K.G. Lynn, J. Pfau and A. Schaub, Assay of weathering effects on protective polymer coatings using positron annihilation spectroscopy 85 (1995) 334
- Hultquist, G., see Gråsjö, L. 89 (1995) 21
- Hwang, S.M., A. Izumi, K. Tsutsui and S. Furukawa, Surface modification of CaF_2 in atomic layer scale by electron beam exposure 82/83 (1994) 523
- Hyde, J.M., M.K. Miller, A. Cerezo and G.D.W. Smith, A study of the effect of ageing temperature on phase separation in Fe-45%Cr alloys 87/88 (1995) 311
- Hyde, J.M., see Miller, M.K. 87/88 (1995) 323
- Ichimiya, A., see Kanazawa, I. 85 (1995) 124
- Ichimiya, A., see Hashizume, T. 87/88 (1995) 373
- Ichimura, S., see Sekine, S. 84 (1995) 401
- Ide, Y. and M. Yamada, Chlorine adsorption on electron beam irradiated GaAs photo-oxides: mechanism of in situ EB lithography 82/83 (1994) 310
- Ignatiev, A., see Zomorrodian, A. 90 (1995) 343
- Ihleemann, J. and B. Wolff-Rottke, Excimer laser ablation patterning of dielectric layers 86 (1995) 228
- Ihleemann, J., B. Wolff-Rottke, G. Danev, K. Petkov and E. Spassova, Structuring of polyimide-metal carbide layer systems by excimer laser ablation 86 (1995) 245
- Ijpma, M.R., see Van Veen, A. 85 (1995) 216
- Ikari, A., Defects in Czochralski-grown silicon crystals investigated by positron annihilation 85 (1995) 253

- Ikeda, H., Y. Miura, N. Takahashi, A. Koukitu and H. Seki, Substitution of surface-adsorbed As atoms to P atoms in atomic layer epitaxy 82/83 (1994) 257
- Ikeda, H., see Suda, Y. 82/83 (1994) 332
- Il'chenko, L.G., Yu.V. Kryuchenko and V.G. Litovchenko, Electron field emission (FE) from quantum size systems 87/88 (1995) 53
- Imai, S. and M. Matsumura, Hydrogen atom assisted ALE of silicon 82/83 (1994) 322
- Imai, S., see Sugahara, S. 82/83 (1994) 380
- Imai, S., see Sugahara, S. 90 (1995) 349
- Inada, T., see Kiyota, Y. 82/83 (1994) 400
- Inoue, N., see Yokoyama, H. 82/83 (1994) 158
- Ionescu, R., C. Moise and A. Vancu, Are modulations of the Schottky surface barrier the only explanation for the gas-sensing effects in sintered SnO_2 ? 84 (1995) 291
- Ishida, H., see Yoshida, S. 89 (1995) 39
- Ishida, M., see Suda, Y. 82/83 (1994) 332
- Ishii, A. and T. Aisaka, Surface barrier sensitivity of positronium formation at surfaces 85 (1995) 33
- Ishii, A., see Kato, M. 85 (1995) 69
- Ishii, M., see Meguro, T. 82/83 (1994) 193
- Ishii, M., T. Meguro, T. Sugano, K. Gamo and Y. Aoyagi, Surface reaction control in digital etching of GaAs by using a tunable UV laser system: reaction control mechanism in layer-by-layer etching 86 (1995) 554
- Ishikawa, K., see Yago, H. 84 (1995) 119
- Isshiki, H., Y. Aoyagi, T. Sugano, S. Iwai and T. Meguro, Surface processes of selective growth by atomic layer epitaxy 82/83 (1994) 57
- Isu, T., see Gotoda, M. 82/83 (1994) 80
- Ito, H., see Suzuki, T. 82/83 (1994) 103
- Ito, S., see Kameoka, S. 89 (1995) 411
- Ito, T., K. Shiraishi and T. Ohno, A Monte Carlo simulation study for adatom migration and resultant atomic arrangements in $\text{Al}_x\text{Ga}_{1-x}\text{As}$ on a GaAs(001) surface 82/83 (1994) 208
- Ito, Y., see Kanazawa, I. 85 (1995) 124
- Ito, Y., see Itoh, Y. 85 (1995) 165
- Ito, Y., see Aruga, T. 85 (1995) 229
- Ito, Y., see Oshima, N. 85 (1995) 329
- Itoh, Y., K.H. Lee, T. Nakajyo, A. Goto, N. Nakanishi, M. Kase, I. Kanazawa, Y. Yamamoto, N. Oshima and Y. Ito, Slow positron production using the RIKEN AVF cyclotron 85 (1995) 165
- Ivanov, I., see Julien, C. 90 (1995) 389
- Ivanov, V.A., see Tumareva, T.A. 87/88 (1995) 18
- Ivchenko, V.A. and N.N. Syutkin, Effect of low-energy (20-40 keV) ion implantation on phase transformations in the sub-surface volume of alloys 87/88 (1995) 257
- Iwai, S., see Isshiki, H. 82/83 (1994) 57
- Iwasa, I., see Otake, S. 82/83 (1994) 263
- Iwashita, T., see Oshima, N. 85 (1995) 329
- Iwata, K., see Kim, J.H. 82/83 (1994) 76
- Iwata, T. and K.-S. Chang, A quantitative estimation of the sensitivity of field-emission pressure-gauge 87/88 (1995) 31
- Izquierdo, R., see Meunier, M. 86 (1995) 475
- Izquierdo, R., J. Bertomeu, M. Suys, E. Sacher and M. Meunier, Excimer laser-induced deposition of copper from $\text{Cu}(\text{hfac})(\text{TMVS})$ 86 (1995) 509
- Izumi, A., see Hwang, S.M. 82/83 (1994) 523
- Jackson, M.S., J.M. Heitzinger, J.W. Nail, R.D. Culp and J.G. Ekerdt, A temperature-programmed desorption/X-ray photoelectron spectroscopy study of ditertiarybutylarsine on GaAs(100) 81 (1994) 195
- Jackson, S.R., W.J. Metheringham and P.E. Dyer, Excimer laser ablation of Nd:YAG and Nd:glass 86 (1995) 223
- Jackson, S.R., see Wagner, F.X. 86 (1995) 364
- Jackson, S.T. and R.G. Nuzzo, Determining hybridization differences for amorphous carbon from the XPS C 1s envelope 90 (1995) 195
- Jain, A., A.K. Razdan, P.N. Kotru and B.M. Wanklyn, Chemical etching of (100) and (110) faces of flux-grown LaBO_3 crystals 84 (1995) 65
- Jakoubková, M., see Fajgar, R. 86 (1995) 530
- Jańczuk, B., M.L. González-Martín and J.M. Bruque, The adsorption of sodium dodecyl sulphate on fluorite and its surface free energy 81 (1994) 95
- Janosi, A., see Devillers, M. 81 (1994) 83
- Jansen, F., see Pflüger, S. 86 (1995) 504
- Jardinier-Offergeld, M., see Reniers, F. 81 (1994) 151
- Jeon, D., H.P. Noh, T. Hashizume, Y. Kuk and T. Sakurai, MnCu surface alloy studied by scanning tunneling microscopy 87/88 (1995) 386
- Ji, G., J. Fang, S. Cai and G. Xue, Grafting onto the surface of plasma-modified fillers 81 (1994) 63
- Jiang, S., D. Peng, X. Zhao, L. Xie and Q. Li, Study on the mechanical and chemical properties of (Ti,Al)N films prepared by DC magnetron sputtering 84 (1995) 373
- Jiang, W., H. Baumgärtner and I. Eisele, Excimer-laser-induced etching of silicon in chlorine atmosphere at a wavelength of 248 nm 86 (1995) 564
- Jimbo, T., see Soga, T. 82/83 (1994) 64
- Jin, B., see Sueoka, O. 85 (1995) 59
- Jo, B.H. and R.W. Vook, Dependence of electromigration rate on applied electric potential 89 (1995) 237
- Joachim, C., see Devel, M. 87/88 (1995) 390

- Joag, D.S., see Adsool, A.D. 87/88 (1995) 37
- Johansen, H., see Reisse, G. 86 (1995) 107
- Johansen, H., see Reisse, G. 86 (1995) 114
- Jordan, R., D. Cole, J.G. Lunney, K. Mackay and D. Givord, Pulsed laser ablation of copper 86 (1995) 24
- Jostsons, A., see Miller, M.K. 87/88 (1995) 216
- Joyce, B.A., see Fahy, M.R. 82/83 (1994) 14
- Julien, C., J.P. Guesdon, A. Gorenstein, A. Khelfa and I. Ivanov, The influence of the substrate material on the growth of V_2O_5 flash-evaporated films 90 (1995) 389
- Jung, E., see Weiss, A.H. 85 (1995) 82
- Kadoshima, M., see Sugahara, S. 90 (1995) 349
- Kafader, U., H. Sirringhaus and H. von Känel, In situ DC-plasma cleaning of silicon surfaces 90 (1995) 297
- Kajiyama, K., Buried-oxide layer formation by high-dose oxygen-ion implantation into Si wafers: SIMOX (separation by implanted oxygen) 85 (1995) 259
- Kaliaguine, S., see Huang, M. 90 (1995) 393
- Kalomiros, J.A., see Kennou, S. 90 (1995) 283
- Kameoka, S., T. Kuriyama, M. Kuroda, S. Ito and K. Kunimori, The chemical interaction between plasma-excited nitrogen and the surface of titanium dioxide 89 (1995) 411
- Kamidoi, S., see Butman, M.F. 89 (1995) 323
- Kanaji, T., see Hongo, S. 82/83 (1994) 437
- Kanaji, T., see Hongo, S. 82/83 (1994) 537
- Kanazawa, I., Y. Ito, M. Hirose, H. Abe, O. Sueoka, S. Takamura, A. Ichimiya, Y. Murata, F. Komori, K. Fukutani, S. Okada and T. Hattori, Production of an intense slow positron beam by using an electron LINAC and its applications 85 (1995) 124
- Kanazawa, I., see Itoh, Y. 85 (1995) 165
- Kanazawa, I., see Oshima, N. 85 (1995) 329
- Kaneko, H., see Okada, S. 85 (1995) 149
- Kano, N., S. Hirose, K. Hara, J. Yoshino, H. Munekata and H. Kukimoto, AlAs layers with low carbon content grown by ALE using ethyldimethylamine alane as a new aluminum source 82/83 (1994) 132
- Kántor, Z., Z. Tóth and T. Szörényi, Metal pattern deposition by laser-induced forward transfer 86 (1995) 196
- Kántor, Z., see Szörényi, T. 86 (1995) 219
- Kantor, Z., see Piglmayer, K. 86 (1995) 484
- Kargl, P.B., see Arnold, N. 86 (1995) 457
- Karnakis, D.M., see Dyer, P.E. 86 (1995) 1
- Kars, S., see Dam, B. 86 (1995) 13
- Karstens, H., J. Knobloch, A. Winkler, A. Pusel, M. Barth and P. Hess, VUV laser (157 nm) chemical vapor deposition of high quality amorphous hydrogenated silicon: gas phase chemistry and modelling 86 (1995) 521
- Kartio, I., see Laajalehto, K. 81 (1994) 11
- Kase, M., see Itoh, Y. 85 (1995) 165
- Kasza, R.V., K. Griffiths, V.P. Zhdanov and P.R. Norton, Nucleation and island growth during water adsorption at sub-monolayer coverages 84 (1994) 97
- Katayama, I., see Ohnishi, H. 82/83 (1994) 444
- Katayama, I., see Tanaka, Y. 82/83 (1994) 528
- Katayama, M., see Kawai, M. 82/83 (1994) 487
- Katayama, Y., see Ohno, H. 82/83 (1994) 164
- Kato, H., see Enta, Y. 82/83 (1994) 327
- Kato, M. and A. Ishii, Positron surface-state trapping induced by surface plasmon excitation under grazing scattering conditions 85 (1995) 69
- Kato, T., see Hanebuchi, M. 89 (1995) 113
- Kawai, M., Z.-Y. Liu, T. Hanada, M. Katayama, M. Aono and C.F. McConville, Layer controlled growth of oxide superconductors 82/83 (1994) 487
- Kawanishi, H., see Takahashi, I. 82/83 (1994) 70
- Kawano, H., see Butman, M.F. 89 (1995) 323
- Kawasaki, M., see Song, Z. 82/83 (1994) 250
- Kawasuso, A., M. Hasegawa, M. Suezawa, S. Yamaguchi and K. Sumino, An annealing study of defects induced by electron irradiation of Czochralski-grown Si using a positron lifetime technique 85 (1995) 280
- Keeble, D.J., see Umlor, M.T. 85 (1995) 295
- Keil, M., J.J. Paggel, Th. Schedel-Niedrig, S. Yokoyama, H. Sotobayashi and A.M. Bradshaw, The structure of PMDA-PDA polyimide monolayers adsorbed on gold surfaces 90 (1995) 377
- Keinonen, J., see Ahlgren, T. 90 (1995) 419
- Keiper, B., see Reisse, G. 86 (1995) 107
- Keiper, B., see Reisse, G. 86 (1995) 114
- Kelber, J.A., see Nuesca, G. 81 (1994) 237
- Kelemen, L., see Geretovszky, Zs. 86 (1995) 494
- Keller, B.P., J.C. Yen, A.L. Holmes Jr., S.P. DenBaars and U.K. Mishra, Flow modulation epitaxy of $Ga_xIn_{1-x}As$ /AlAs heterostructures on InP for resonant tunneling diodes 82/83 (1994) 126
- Kelliher, J.T., A.E. Miller, N. Dietz, S. Habermehl, Y.L. Chen, Z. Lu, G. Lucovsky and K.J. Bachmann, Interrupted cycle chemical beam epitaxy of gallium phosphide on silicon with or without photon assistance 86 (1995) 453
- Kellogg, G.L., Field ion microscope studies of exchange-mediated, atom-displacement processes on metal surfaces 87/88 (1995) 353
- Kelly, T.F., see Camus, P.P. 87/88 (1995) 305
- Kelly, T.F., see Bajikar, S.S. 87/88 (1995) 438

- Kelly, T.F., see Larson, D.J. 87/88 (1995) 446
- Kennou, S., S. Ladas, E.C. Paloura and J.A. Kalomiros, Characterization of ex-situ hydrogenated amorphous SiC thin films by X-ray photoelectron spectroscopy 90 (1995) 283
- Key, P.H., see Dyer, P.E. 86 (1995) 18
- Key, P.H., see Wagner, F.X. 86 (1995) 364
- Khatri, R., see Lawther, D.W. 85 (1995) 265
- Khelfa, A., see Julien, C. 90 (1995) 389
- Khrantsova, E.A., A.V. Zotov, A.A. Saranin, S.V. Ryzhkov, A.B. Chub and V.G. Lifshits, Growth of extra-thin ordered aluminum films on Si(111) surface 82/83 (1994) 576
- Kilner, J.A., see Bréelle, E. 81 (1994) 127
- Kim, C.O., see Kim, T.W. 90 (1995) 75
- Kim, J.H., H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda, Growth temperature dependence of optical properties of gas source MBE grown GaP/AlP short period superlattices 82/83 (1994) 76
- Kim, J.H., see Yang, G. 85 (1995) 77
- Kim, S.G., see Kim, J.H. 82/83 (1994) 76
- Kim, S.G., see Asahi, H. 82/83 (1994) 109
- Kim, T.W., Y.S. Yoon, S.S. Yom and C.O. Kim, Ferroelectric BaTiO₃ films with a high-magnitude dielectric constant grown on p-Si by low-pressure metalorganic chemical vapor deposition 90 (1995) 75
- Kimura, S., see Murakami, E. 82/83 (1994) 338
- Kimura, T., see Takemi, M. 82/83 (1994) 115
- King, R.A., R.A.D. Mackenzie, G.D.W. Smith and N.A. Cade, Atom probe field ion microscope studies of palladium silicide on silicon 87/88 (1995) 279
- King, S., L. Coccia and I.W. Boyd, SEM observations of YBCO on as-received and heat-treated MgO substrates 86 (1995) 134
- Kinser, D.L., see Wang, P.W. 84 (1995) 75
- Kirbitson, R., see Wagner, F.X. 86 (1995) 364
- Kirsanova, T.S., see Tumareva, T.A. 87/88 (1995) 18
- Kiselev, A.N., see Givargizov, E.I. 87/88 (1995) 24
- Kishimoto, J., see Cho, K. 87/88 (1995) 380
- Kitai, M.S., see Sobol, E.N. 90 (1995) 235
- Kitamura, T., see Sugahara, S. 82/83 (1994) 380
- Kitamura, T., see Sugahara, S. 90 (1995) 349
- Kiyota, Y., T. Nakamura and T. Inada, Boron δ -doping in Si using atmospheric pressure CVD 82/83 (1994) 400
- Kleps, I., see Caccavale, F. 81 (1994) 443
- Klotzbücher, T., W. Pfleging, M. Mertin, D.A. Wesner and E.W. Kreutz, Structure and chemical composition of BN thin films grown by pulsed-laser deposition (PLD) 86 (1995) 165
- Knights, A.P. and P.G. Coleman, Secondary electron emission from Ag(100) stimulated by positron and electron impact 85 (1995) 43
- Knights, A.P., see Overton, N. 85 (1995) 54
- Knobloch, J., see Karstens, H. 86 (1995) 521
- Knoll, W., see Piscevic, D. 90 (1995) 425
- Kobayashi, H., F. Mizuno and Y. Nakato, Surface states in the band-gap for Pt-deposited p-InP photoelectrochemical cells 81 (1994) 399
- Kobayashi, H., see Kurihara, T. 85 (1995) 178
- Kobayashi, M., see Yoshikawa, A. 82/83 (1994) 316
- Kobayashi, N. and T. Makimoto, Carbon incorporation mechanism in atomic layer epitaxy of GaAs and AlGaAs 82/83 (1994) 284
- Kobayashi, N., see Uwai, K. 82/83 (1994) 290
- Kobayashi, T., see Akamatsu, M. 82/83 (1994) 228
- Koch, M., see Stoll, H. 85 (1995) 17
- Kočka, J., see Černý, R. 86 (1995) 359
- Koenig, E.W., see Wijekoon, W.M.K.P. 81 (1994) 347
- Kögel, G., see Britton, D.T. 85 (1995) 158
- Kogelschatz, U., see Esrom, H. 86 (1995) 202
- Kolbasov, G.Ya., see Dmitruk, N.L. 90 (1995) 489
- Koleske, D.D. and S.M. Gates, Si ALE using chlorine/hydrogen exchange. Fundamentals and films 82/83 (1994) 344
- Kolev, K., see Laude, L.D. 86 (1995) 368
- Kolev, K., see Viville, P. 86 (1995) 411
- Kolomenskii, A.A., M. Szabadi and P. Hess, Laser diagnostics of C₆₀ and C₇₀ films by broadband surface acoustic wave spectroscopy 86 (1995) 591
- Koltay, E., see Sundararajan, R. 90 (1995) 165
- Komatsu, A., see Hanabusa, M. 86 (1995) 428
- Komolov, S.A., see Møller, P.J. 82/83 (1994) 569
- Komori, F., see Kanazawa, I. 85 (1995) 124
- Komura, T., see Uesugi, K. 82/83 (1994) 367
- König, U., see Blum, O. 86 (1995) 417
- Kono, S., see Sasaki, M. 82/83 (1994) 387
- Kononenko, T.V., V.G. Ralchenko, E.D. Obratsova, V.I. Konov, J. Seth, S.V. Babu and E.N. Loubnin, Excimer laser etching of diamond-like carbon films: spalling effect 86 (1995) 234
- Konotop, V.V., see Skatkov, L.I. 81 (1994) 427
- Konov, V.I., see Pimenov, S.M. 86 (1995) 208
- Konov, V.I., see Kononenko, T.V. 86 (1995) 234
- Koprinarova, J., see Atanassova, E. 84 (1995) 193
- Korol'kov, D.V., see Drozd, V.E. 82/83 (1994) 587
- Kosowsky, S.D., C.-H. Hsu, P.S. Pershan, J. Bevk and B.S. Freer, An X-ray scattering study of SiO_x/Si/Ge(001) 84 (1995) 179
- Kotru, P.N., see Sharma, K.K. 81 (1994) 251
- Kotru, P.N., see Jain, A. 84 (1995) 65
- Koukitu, A., see Ikeda, H. 82/83 (1994) 257
- Koutti, L., see Deiss, J.L. 86 (1995) 149
- Kovrikov, A.B., see Gurin, V.S. 81 (1994) 43
- Koymen, A.R., see Fazleev, N.G. 85 (1995) 26
- Koymen, A.R., see Weiss, A.H. 85 (1995) 82
- Koymen, A.R., see Hozhabri, N. 85 (1995) 311
- Kramer, K.J., see Slaoui, A. 86 (1995) 346
- Krause, H.-P., see Li, B. 86 (1995) 577

- Krebs, H.-U., S. Fähler and O. Bremert, Laser deposition of metallic alloys and multilayers 86 (1995) 86
- Krebs, H.-U., O. Bremert, M. Störmer and Y. Luo, Comparison of the structure of laser deposited and sputtered metallic alloys 86 (1995) 90
- Kreuss, M., see Wesemann, J. 87/88 (1995) 179
- Kreutz, E.W., see Klotzbücher, T. 86 (1995) 165
- Kreutz, E.W., H. Frerichs, M. Mertin, D.A. Wesner and W. Pfleging, Tailoring of surface properties by removal and deposition with laser radiation 86 (1995) 266
- Kreutz, E.W., G. Backes, A. Gasser and K. Wissenbach, Rapid prototyping with CO₂ laser radiation 86 (1995) 310
- Kreutz, E.W., see Frerichs, H. 86 (1995) 405
- Kruck, Th., see Pflüger, S. 86 (1995) 504
- Kruit, P., see Seijbel, L.J. 85 (1995) 92
- Kruse, N., see Cocke, D.L. 84 (1995) 153
- Kruse, N., see Voss, C. 87/88 (1995) 127
- Kruse, N., see Voss, C. 87/88 (1995) 134
- Kruseman, A., see Van Veen, A. 85 (1995) 216
- Kryuchenko, Yu.V., see Il'chenko, L.G. 87/88 (1995) 53
- Kubo, M., see Vetrivel, R. 82/83 (1994) 516
- Kubo, M., see Himei, H. 82/83 (1994) 543
- Kubo, M., R. Yamauchi, R. Vetrivel and A. Miyamoto, Formation processes of ultrafine metal particles on MgO(100) as investigated by molecular dynamics and computer graphics 82/83 (1994) 559
- Kubo, M., R. Miura, R. Yamauchi, R. Vetrivel and A. Miyamoto, Mechanism of the formation of ultrafine gold particles on MgO(100) as investigated by molecular dynamics and computer graphics 89 (1995) 131
- Kubota, H., M. Nagata, R. Miyagawa and M.A. Nicolet, Oxidation of TiN thin films in an ion-beam-assisted deposition process 82/83 (1994) 565
- Kuhn, W., see Bourée, J.E. 86 (1995) 437
- Kuipers, E.W., see Van Hardeveld, R.M. 84 (1995) 339
- Kujirai, H., see Murakami, E. 82/83 (1994) 338
- Kuk, Y., see Jeon, D. 87/88 (1995) 386
- Kukimoto, H., see Kano, N. 82/83 (1994) 132
- Kulkarni, G.U., see Rao, C.N.R. 84 (1995) 285
- Kumagai, H. and K. Toyoda, In situ ellipsometric diagnostics for controlled growth of metal oxides with surface chemical reactions 82/83 (1994) 481
- Kumamura, M., see Hata, K. 87/88 (1995) 117
- Kumeda, M., see Masuda, A. 81 (1994) 277
- Kunimori, K., see Kameoka, S. 89 (1995) 411
- Kurabayashi, T., see Plotka, P. 82/83 (1994) 91
- Kurabayashi, T. and J. Nishizawa, Temperature synchronized molecular layer epitaxy 82/83 (1994) 97
- Kurihara, T., A. Shirakawa, A. Enomoto, T. Shidara, H. Kobayashi and K. Nakahara, An overview of the slow-positron beam facility at the photon factory, KEK 85 (1995) 178
- Kuriyama, T., see Kameoka, S. 89 (1995) 411
- Kuroda, M., see Kameoka, S. 89 (1995) 411
- Kürpick, U., G. Meister and A. Goldmann, Diffusion of Ag on Cu(110) and Cu(111) studied by spatially resolved UV-photoemission 89 (1995) 383
- Kusiński, J., Microstructure, chemical composition and properties of the surface layer of M2 steel after laser melting under different conditions 86 (1995) 317
- Küttel, O.M., see Gröning, P. 89 (1995) 83
- Kuttler, K., see Fazleev, N.G. 85 (1995) 22
- Kuttler, K., see Fazleev, N.G. 85 (1995) 26
- Kuzmichov, A.V., Excimer laser-assisted etching of silicon in chlorine: adsorption and desorption 86 (1995) 559
- Laajalehto, K., I. Kartio and P. Nowak, XPS study of clean metal sulfide surfaces 81 (1994) 11
- La Bruna, G., see Cerofolini, G.F. 89 (1995) 361
- Labatut, C., see Aspar, B. 81 (1994) 55
- Labunov, V.A., see Demchuk, A.V. 86 (1995) 353
- Ladas, S., see Kennou, S. 90 (1995) 283
- Lahtinen, J., see Vaari, J. 81 (1994) 289
- Lahtinen, J., see Vaara, T. 89 (1995) 103
- Lakomaa, E.-L., see Haukka, S. 82/83 (1994) 548
- Lalande, G., see Weng, L.T. 84 (1995) 9
- Lambin, G., see Viville, P. 86 (1995) 411
- Lamontagne, B., F. Semond, A. Adnot and D. Roy, SIMS investigation of the Si(111) oxidation promoted by potassium overlayers 90 (1995) 447
- Lamontagne, B., D. Guay, D. Roy, R. Sporken and R. Caudano, AFM and XPS characterization of the Si(111) surface after thermal treatment 90 (1995) 481
- Lang, B., B. Sefsfaf and G. Allan, An AES study of intrinsic and ion-induced structure in the SiO₂-Si system 81 (1994) 17
- Lang, H.P., see Sum, R. 86 (1995) 140
- LaPierre, R.R., B.J. Robinson and D.A. Thompson, Lateral composition modulation in InGaAsP deposited by gas source molecular beam epitaxy on (100)- and (h11)-oriented InP substrates 90 (1995) 437
- Larena, A., G. Pinto and F. Millán, Using the Lambert-Beer law for thickness evaluation of photoconductor coatings for recording holograms 84 (1995) 407
- L'Argentièrre, P.C., M.G. Cañón and N.S. Fígoli, XPS studies of the effect of Mn on Pd/Al₂O₃ 89 (1995) 63
- Laricchia, G., see Moxom, J. 85 (1995) 118

- Larson, D.J., see Camus, P.P. 87/88 (1995) 305
- Larson, D.J., C.-M. Teng, P.P. Camus and T.F. Kelly, Fabrication of microtips on planar specimens 87/88 (1995) 446
- LaShell, S., see Coleman, P.G. 85 (1995) 276
- Lätsch, S., H. Hiraoka, W. Nieveen and J. Bargon, Interface study on laser-induced material transfer from polymer and quartz surfaces 81 (1994) 183
- Laude, L., see Viville, P. 86 (1995) 411
- Laude, L.D., see Szörényi, T. 86 (1995) 219
- Laude, L.D., K. Kolev, M. Brunel and P. Deleter, Surface properties of excimer-laser-irradiated sintered alumina 86 (1995) 368
- Lauff, U., see Stoll, H. 85 (1995) 17
- Lawall, R., see Piscevic, D. 90 (1995) 425
- Lawther, D.W., R. Khatri, P.J. Simpson, P.J. Schultz, I. Calder and L. Weaver, Variable-energy positron beam study of arsenic diffusion in poly-silicon 85 (1995) 265
- Laz, M.M., see Hernández Creus, A. 81 (1994) 387
- Lazneva, E.F., see Møller, P.J. 82/83 (1994) 569
- Lazzaroni, R., see Viville, P. 86 (1995) 411
- Lazzaroni, R., see Brocherieux, A. 90 (1995) 47
- Le Bras, M., see Bourbigot, S. 81 (1994) 299
- Le Mercier, T., J.-M. Mariot, P. Parent, M.-F. Fontaine, C.F. Hague and M. Querton, Formation of Ti^{3+} ions at the surface of laser-irradiated rutile 86 (1995) 382
- Le Normand, F., A. Ababou, N. Brault, B. Carrière, L. Fayette, B. Marcus, M. Mermoux, M. Romeo and C. Speisser, Diamond nucleation and growth at the early stages on Si(100) monitored by electron spectroscopies 81 (1994) 309
- Leclerc, G., see Piyakis, K. 84 (1995) 227
- Lee, H.J., J.-G. Choi, C.W. Colling, M.S. Mudholkar and L.T. Thompson, Temperature-programmed desorption and decomposition of NH_3 over molybdenum nitride films 89 (1995) 121
- Lee, K.H., see Itoh, Y. 85 (1995) 165
- Lee, S.-P. and M.C. Lin, Laser-induced decomposition of dimethyl cadmium on a quartz substrate 84 (1995) 31
- Lee, T.C., see Ling, C.C. 85 (1995) 305
- Lee, W.-I., see Chan, S.-H. 82/83 (1994) 85
- Lee, W.S., see Outlaw, R.A. 81 (1994) 143
- Lee, W.Y., see Hong, J.K. 89 (1995) 229
- Leggett, G.J. and J.C. Vickerman, Sample charging during static SIMS studies of polymers 84 (1995) 253
- Leggieri, G., see D'Anna, E. 86 (1995) 170
- Leiro, J.A., M.H. Heinonen and I.G. Batirev, Surface segregation and core-level shift of a Pd-Rh alloy studied by XPS 90 (1995) 515
- Leisch, M., see Athenstaedt, W. 87/88 (1995) 318
- LeMone, D.V., see Wang, P.W. 84 (1995) 75
- Lenglet, M., see Souchet, R. 87/88 (1995) 271
- Lennard, W.N., see Massoumi, G.R. 85 (1995) 39
- León, B., see Parada, E.G. 86 (1995) 294
- Leppävuori, S., see Levoska, J. 86 (1995) 180
- Leskelä, M., see Asikainen, T. 82/83 (1994) 122
- Leskelä, M., see Niinistö, L. 82/83 (1994) 454
- Leskelä, M., see Elers, K.-E. 82/83 (1994) 468
- Leskelä, M., see Rautanen, J. 82/83 (1994) 553
- Leung, T.C., see Aers, G.C. 85 (1995) 196
- Leung, T.C., P.J. Simpson, A. Atkinson, I.V. Mitchell and P.J. Schultz, Measurement of oxide thickness using a variable-energy positron beam 85 (1995) 292
- Lévêque, G. and J. Bonnet, Quantitative correction of backscattering in Auger electron spectroscopy of thin films 89 (1995) 211
- Levoska, J. and S. Leppävuori, Effect of laser power density and deposition temperature on electrical and optical properties of pulsed laser ablated diamond-like carbon films 86 (1995) 180
- Lewis, T.A., see Xu, J. 85 (1995) 49
- Leys, M.R., see Hopkins, J. 84 (1995) 299
- Lhoest, J.B., see Piyakis, K. 84 (1995) 227
- Li, B., U. Streller, H.-P. Krause, I. Twesten, N. Schwentner, V. Stepanenko and Yu. Poltoratskii, Desorption in light-induced dry etching of GaAs with Cl_2 around 120 nm 86 (1995) 577
- Li, C., see Wu, J. 81 (1994) 37
- Li, C., Y.-W. Chen, S.-J. Yang and R.-B. Yen, In-situ FTIR investigation of coke formation on USY zeolite 81 (1994) 465
- Li, F.M., see Wu, J.D. 90 (1995) 81
- Li, G., see Wu, J. 81 (1994) 37
- Li, J., see Russell, S.W. 90 (1995) 455
- Li, J.-X., J.A. Gardella, Jr. and P.J. McKeown, A quantitative time-of-flight secondary ion mass spectrometry study of ion formation mechanisms using acid-base alternating Langmuir-Blodgett films 90 (1995) 205
- Li, Q., see Jiang, S. 84 (1995) 373
- Li, S., see Wu, J. 81 (1994) 37
- Li, Y.S., see Wong, P.C. 84 (1995) 245
- Li, Y.S., see Wong, P.C. 89 (1995) 255
- Li, Y.S., P.C. Wong and K.A.R. Mitchell, XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. II. Effects of heating a 26 Å thick film after treatment with a hydrogen plasma 89 (1995) 263
- Licciardello, A., see Torrisi, A. 81 (1994) 259
- Licoppe, C., see Flicstein, J. 86 (1995) 286
- Liesegang, J., see De Marco, R. 84 (1995) 237
- Lifshits, V.G., see Khramtsova, E.A. 82/83 (1994) 576
- Liley, M., see Piscevic, D. 90 (1995) 425
- Lin, M.C., see Lee, S.-P. 84 (1995) 31

- Lin, Y., see Xiao, X.R. 90 (1995) 321
- Lin, Z., see Hu, X. 90 (1995) 111
- Linares-Solano, A., see Muñoz-Guillena, M.J. 81 (1994) 409
- Linares-Solano, A., see Muñoz-Guillena, M.J. 81 (1994) 417
- Linares-Solano, A., see Muñoz-Guillena, M.J. 89 (1995) 197
- Ling, C.C., see Panda, B.K. 85 (1995) 182
- Ling, C.C., T.C. Lee, S. Fung, C.D. Beling, H. Weng, J. Xu, S. Sun and R. Han, Annealing studies of Au/GaAs and Al/GaAs interfaces using a variable energy positron beam 85 (1995) 305
- Lins, C.W., see Hansen, D.C. 84 (1995) 85
- Lisovskii, I.P., V.G. Litovchenko and V.B. Lozinskii, Effect of UV annealing of radiation damage in SiO₂ films 86 (1995) 299
- Lisowski, W., see Duś, R. 90 (1995) 277
- Litovchenko, V.G., see Lisovskii, I.P. 86 (1995) 299
- Litovchenko, V.G., see Il'chenko, L.G. 87/88 (1995) 53
- Liu, W., see Forbes, R.G. 87/88 (1995) 99
- Liu, W. and R.G. Forbes, Modelling the link between emission current and LMIS cusp length 87/88 (1995) 122
- Liu, Z.-H., see Brown, N.M.D. 90 (1995) 155
- Liu, Z.-Y., see Kawai, M. 82/83 (1994) 487
- Liu Yunpeng and Luo Enze, Electron tunneling in double-barrier diode 87/88 (1995) 75
- Ljepojevic, N.N., see Forbes, R.G. 87/88 (1995) 99
- Lloret, A., see Puigdollers, J. 86 (1995) 600
- Lobner, S.F., see Bolt, P.H. 89 (1995) 339
- Lobstein, N., E. Millon, A. Hachimi, J.F. Muller, M. Alnot and J.J. Ehrhardt, Deposition by laser ablation and characterization of titanium dioxide films on polyethylene-terephthalate 89 (1995) 307
- Logothetidis, S., I. Alexandrou and J. Stoenos, In-situ spectroscopic ellipsometry to control the growth of Ti nitride and carbide thin films 86 (1995) 185
- Loh, T.E., see Lu, Y.F. 90 (1995) 217
- Loiseau, A., see Duval, S. 87/88 (1995) 284
- Loison, J.L., see Deiss, J.L. 86 (1995) 149
- Lokere, K., see Donaton, R.A. 89 (1995) 221
- Loo, B.H., J.N. Yao, H.D. Coble, K. Hashimoto and A. Fujishima, A Raman microprobe study of the electrochromic and photochromic thin films of molybdenum trioxide and tungsten trioxide 81 (1994) 175
- Loubnin, E.N., see Kononenko, T.V. 86 (1995) 234
- Loubnin, E.N., see Shafeev, G.A. 86 (1995) 392
- Low, T.S., see Lu, Y.F. 90 (1995) 217
- Löwe, H., see Arnold, J. 86 (1995) 251
- Lozinskii, V.B., see Lisovskii, I.P. 86 (1995) 299
- Lu, L., see Wang, P.W. 84 (1995) 75
- Lu, Y.-F., Square-shaped temperature distribution induced by a Gaussian-shaped laser beam 81 (1994) 357
- Lu, Y.F., T.E. Loh, H.G. Soh and T.S. Low, Laser-induced temperature rise in Gaussian-shaped holes 90 (1995) 217
- Lu, Z., see Kelliher, J.T. 86 (1995) 453
- Lu, Z.-H., see Yang, X.-M. 90 (1995) 175
- Lucas, S.R., see Yates, Jr., J.T. 82/83 (1994) 180
- Luches, A., see D'Anna, E. 86 (1995) 170
- Lucovsky, G., see Kelliher, J.T. 86 (1995) 453
- Luftman, H.S., see Weir, B.E. 84 (1995) 413
- Lujala, V., J. Skarp, M. Tammenmaa and T. Suntola, Atomic layer epitaxy growth of doped zinc oxide thin films from organometals 82/83 (1994) 34
- Lundin, L. and B. Richarz, Atom-probe study of phosphorus segregation to the carbide/matrix interface in an aged 9% chromium steel 87/88 (1995) 194
- Lunney, J.G., see Jordan, R. 86 (1995) 24
- Lunney, J.G., Pulsed laser deposition of metal and metal multilayer films 86 (1995) 79
- Lunney, J.G., see Masterson, H.J. 86 (1995) 154
- Luo, Y., see Krebs, H.-U. 86 (1995) 90
- Luo Enze, see Liu Yunpeng, 87/88 (1995) 75
- Lupp, F., see Pflüger, S. 86 (1995) 504
- Lux, B., see Friedbacher, G. 84 (1995) 133
- Lynn, K.G., see Ghosh, V.J. 85 (1995) 210
- Lynn, K.G., see Umlor, M.T. 85 (1995) 295
- Lynn, K.G., see Hulett, Jr., L.D. 85 (1995) 334
- Macht, M.-P., see Al-Kassab, T. 87/88 (1995) 329
- Macías, M., see Navío, J.A. 81 (1994) 325
- Mackay, K., see Jordan, R. 86 (1995) 24
- Mackenzie, R.A.D., see King, R.A. 87/88 (1995) 279
- Mackenzie, R.A.D., see Huang, M. 87/88 (1995) 421
- Maeda, F., see Watanabe, Y. 82/83 (1994) 136
- Maeda, F., Y. Watanabe and M. Oshima, Surface reactions of Ga and As on Sb-terminated GaAs(001) 82/83 (1994) 276
- Maeda, H., see Nakayama, H. 82/83 (1994) 214
- Maeda, Y., see Watanabe, M. 82/83 (1994) 417
- Maex, K., see Donaton, R.A. 89 (1995) 221
- Maeyama, S., see Heun, S. 82/83 (1994) 507
- Magni, E. and G.A. Somorjai, Preparation of a model Ziegler-Natta catalyst. Surface science studies of magnesium chloride thin film deposited on gold and its interaction with titanium chloride 89 (1995) 187
- Mahajan, A., see Asami, S. 82/83 (1994) 359
- Maier, K., see Stoll, H. 85 (1995) 17
- Mair, G.L.R., see Forbes, R.G. 87/88 (1995) 99
- Majni, G., see D'Anna, E. 86 (1995) 170
- Major, J., see Stoll, H. 85 (1995) 17
- Makimoto, T., see Kobayashi, N. 82/83 (1994) 284
- Makita, Y., see Durand, H.-A. 86 (1995) 122
- Makropoulou, M., see Skordoulis, C.D. 86 (1995) 239
- Manuel, A.A., R. Ambigapathy, K. Saari-nen, P. Hautojärvi and C. Corbel, Defect analysis using 2D-ACAR: GaAs as a test case 85 (1995) 301

- Mar, S.Y., C.S. Chen, Y.S. Huang and K.K. Tiong, Characterization of RuO₂ thin films by Raman spectroscopy 90 (1995) 497
- Marchand-Brynaert, J., see Deldime, M. 90 (1995) 1
- Marcus, B., see Le Normand, F. 81 (1994) 309
- Marine, W., see Grangeon, F. 86 (1995) 160
- Marine, W., see Shafeev, G.A. 86 (1995) 387
- Marino, N., see Baeri, P. 86 (1995) 128
- Mariot, J.-M., see Le Mercier, T. 86 (1995) 382
- Marotta, V., see Gambardella, U. 86 (1995) 45
- Marotta, V., see Teghil, R. 90 (1995) 505
- Marshall, P.A., see Aers, G.C. 85 (1995) 196
- Martin, O.J.F., see Devel, M. 87/88 (1995) 390
- Martínez García, D., see Gonzalo, J. 86 (1995) 40
- Martini, T., see Risse, G. 86 (1995) 107
- Martini, T., see Risse, G. 86 (1995) 114
- Martino, M., see D'Anna, E. 86 (1995) 170
- Maruno, S., see Gotoda, M. 82/83 (1994) 80
- Maruya, E., see Himei, H. 82/83 (1994) 543
- Marx, G., see Schlottig, F. 90 (1995) 129
- Massardier, J., see Debaige, Y. 90 (1995) 15
- Massoumi, G.R., W.N. Lennard, P.J. Schultz, T.A. Porcelli and P.J. Simpson, Energy loss measurements for 20 keV positrons in Al thin films 85 (1995) 39
- Masterson, H.J. and J.G. Lunney, Comparison of epitaxial films of Zn_{1-x}Mn_xTe on (111) and (100) GaAs produced by pulsed laser deposition 86 (1995) 154
- Masuda, A., Y. Yonezawa, A. Morimoto, M. Kumeda and T. Shimizu, Ultrathin SiO₂ films on Si formed by N₂O-plasma oxidation technique 81 (1994) 277
- Masuda, T., see Arai, M. 89 (1995) 11
- Mathé, E.L., A. Naudon, F. Repplinger and E. Fogarassy, Morphology of Si_{1-x}Ge_x thin crystalline films obtained by pulsed-excimer-laser annealing of heavily Ge-implanted Si 86 (1995) 338
- Mathey, Y., see Grangeon, F. 86 (1995) 160
- Mathur, B.K., see Rao, M.V.H. 89 (1995) 417
- Matsubara, M. and I. Hirabayashi, Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition 82/83 (1994) 494
- Matsumiya, Y., see Sakuma, Y. 82/83 (1994) 46
- Matsumura, M., see Imai, S. 82/83 (1994) 322
- Matsumura, M., see Sugahara, S. 82/83 (1994) 380
- Matsumura, M., see Sugahara, S. 90 (1995) 349
- Matsuura, T., see Suzue, K. 82/83 (1994) 422
- Maury, F., K. Bouabid, N. Fazouan, A.M. Gué and D. Estève, GaAs growth by photon-assisted metalorganic molecular beam epitaxy using ethyl derivatives of gallium and arsenic 86 (1995) 447
- Mazhukin, V.I., I. Smurov, C. Surry and G. Flamant, Overheated metastable states in polymer sublimation by laser radiation 86 (1995) 7
- Mazhukin, V.I., see Berjeza, N.A. 86 (1995) 303
- McCafferty, E., see Hansen, D.C. 84 (1995) 85
- McConville, C.F., see Kawai, M. 82/83 (1994) 487
- McKeown, P.J., see Li, J.-X. 90 (1995) 205
- McNeil, J.R., see Hatab, Z.R. 86 (1995) 597
- Meda, L., see Cerofolini, G.F. 89 (1995) 351
- Meda, L., see Cerofolini, G.F. 89 (1995) 361
- Medvedev, A.S., see Shklyayev, A.A. 89 (1995) 49
- Medvedev, V.K., Yu. Suchorski and J.H. Block, Investigation of adsorption and coadsorption of O₂ and CO on Rh by O₂⁺ field ion and Li⁺ field desorption microscopies 87/88 (1995) 159
- Meguro, T., see Isshiki, H. 82/83 (1994) 57
- Meguro, T., M. Ishii, T. Sugano, K. Gamo and Y. Aoyagi, Control of the etching reaction of digital etching using tunable UV laser irradiation 82/83 (1994) 193
- Meguro, T., see Ishii, M. 86 (1995) 554
- Meister, G., see Kürpick, U. 89 (1995) 383
- Mele, A., see Di Palma, T.M. 86 (1995) 68
- Mele, A., see Teghil, R. 90 (1995) 505
- Mengucci, P., see D'Anna, E. 86 (1995) 170
- Mens, A.J.M., see Van Wijk, R. 90 (1995) 261
- Mermoux, M., see Le Normand, F. 81 (1994) 309
- Mertin, M., see Klotzbücher, T. 86 (1995) 165
- Mertin, M., see Kreutz, E.W. 86 (1995) 266
- Mesarwi, A., see Zomorrodian, A. 90 (1995) 343
- Metheringham, W.J., see Jackson, S.R. 86 (1995) 223
- Meunier, M., P. Desjardins, M. Tabbal, N. Elyaagoubi, R. Izquierdo and A. Yelon, Laser processing of tungsten from WF₆ and SiH₄ 86 (1995) 475
- Meunier, M., see Izquierdo, R. 86 (1995) 509
- Meyrueis, P., see Durand, H.-A. 86 (1995) 122
- Michaelsen, C., see Pundt, A. 87/88 (1995) 264
- Miehé, J.A., see Palau, J. 86 (1995) 59
- Mihailescu, I.N., see D'Anna, E. 86 (1995) 170
- Mihashi, Y., see Takemi, M. 82/83 (1994) 115
- Mijnarends, P.E., see Hakvoort, R.A. 85 (1995) 271
- Mikado, T., see Suzuki, R. 85 (1995) 87
- Mikhailov, V.A., F.N. Putilin and D.N. Trubnikov, Study of PbTe(Ga) evaporation using a nanosecond pulsed laser 86 (1995) 64
- Millán, F., see Larena, A. 84 (1995) 407
- Miller, A.E., see Kelliher, J.T. 86 (1995) 453
- Miller, M.K., see Thomson, R.C. 87/88 (1995) 185
- Miller, M.K., see Babu, S.S. 87/88 (1995) 207
- Miller, M.K., K.F. Russell, A. Jostsons and R.G. Blake, Characterization of neutron-irradiated Fe-Au alloys 87/88 (1995) 216
- Miller, M.K. and G.D.W. Smith, Atom probe analysis of interfacial segregation 87/88 (1995) 243
- Miller, M.K., see Hyde, J.M. 87/88 (1995) 311
- Miller, M.K., J.M. Hyde, A. Cerezo and G.D.W. Smith, Comparison of low temperature decomposition in Fe-Cr and duplex stainless steels

- Millon, E., see Lobstein, N. 87/88 (1995) 323
- Mills, Jr., A.P., see Vasumathi, D. 89 (1995) 307
- Mills, Jr., A.P., see Canter, K.F. 85 (1995) 154
- Milun, M., see Valla, T. 85 (1995) 339
- Minel, L., see Fauquet, C. 89 (1995) 375
- Minoura, S., see Sato, S. 81 (1994) 435
- Mishra, U.K., see Keller, B.P. 90 (1995) 29
- Mitchell, I.V., see Leung, T.C. 82/83 (1994) 126
- Mitchell, K.A.R., see Wong, P.C. 85 (1995) 292
- Mitchell, K.A.R., see Wong, P.C. 84 (1995) 245
- Mitchell, K.A.R., see Li, Y.S. 89 (1995) 255
- Mitterauer, J., Microstructured liquid metal ion and electron sources (MILMIS/MILMES) 89 (1995) 263
- Mityukhlyayev, V.B., Electron-beam-induced oxidation of CdS 87/88 (1995) 79
- Miura, H., see Shirai, Y. 81 (1994) 137
- Miura, R., see Kubo, M. 85 (1995) 138
- Miura, Y., see Ikeda, H. 89 (1995) 131
- Miyagawa, R., see Kubota, H. 82/83 (1994) 257
- Miyamoto, A., see Vetrivel, R. 82/83 (1994) 565
- Miyamoto, A., see Himei, H. 82/83 (1994) 516
- Miyamoto, A., see Kubo, M. 82/83 (1994) 543
- Miyamoto, A., see Kubo, M. 82/83 (1994) 559
- Miyamoto, N., see Enta, Y. 89 (1995) 131
- Miyamoto, N., see Suemitsu, M. 82/83 (1994) 327
- Mizuno, F., see Kobayashi, H. 82/83 (1994) 449
- Mizutani, W., A. Ohi, M. Motomatsu and H. Tokumoto, Field evaporation of gold by scanning tunneling microscopy 81 (1994) 399
- Mochizuki, Y., T. Takada and A. Usui, Theoretical studies on the chloride ALE process 87/88 (1995) 398
- Mohai, M., see Bertóti, I. 82/83 (1994) 200
- Mohamed, M.H., M.M. Abdillahi, N.M. Abbas and A.B. Siddiqui, An XPS study of the optimum loading of barium on high-silica MFI zeolite 84 (1995) 357
- Moise, C., see Ionescu, R. 90 (1995) 409
- Molchanovskii, I.A., see Dmitruk, N.L. 84 (1995) 291
- Møller, P.J., see Ge, Q. 90 (1995) 489
- Møller, P.J., S.A. Komolov and E.F. Lazneva, Influence of atomic Cu-layer epitaxy on CO₂ and CO photoinduced desorption from ZnO(0001) 82/83 (1994) 305
- More, M.A., see Adsool, A.D. 82/83 (1994) 569
- Morenza, J.L., see Palau, J. 87/88 (1995) 37
- Mori, K., see Takemi, M. 86 (1995) 59
- Morimoto, A., see Masuda, A. 82/83 (1994) 115
- Morioka, H., see Watamori, M. 81 (1994) 277
- Morishita, H., see Tanaka, Y. 82/83 (1994) 417
- Morishita, T., see Wang, F. 82/83 (1994) 528
- Morishita, Y., see Ohno, H. 90 (1995) 123
- Morita, K., see Hanebuchi, M. 82/83 (1994) 164
- Morone, A., see Gambardella, U. 89 (1995) 113
- Morris, R.E., see Schreifels, J.A. 86 (1995) 45
- Motomatsu, M., see Mizutani, W. 84 (1995) 23
- Moxom, J., G. Laricchia and M. Charlton, A gated positron beam incorporating a scattering cell and novel ion extractor 87/88 (1995) 323
- Možina, J., see Hrovatin, R. 85 (1995) 118
- Mozyrsky, D.V., see Vladimirov, V.V. 86 (1995) 213
- Mudholkar, M.S., see Lee, H.J. 87/88 (1995) 112
- Muhler, M., see Deng, J. 89 (1995) 121
- Müllenborn, M., H. Dirac and J.W. Petersen, Three-dimensional nanostructures by direct laser etching of Si 81 (1994) 341
- Muller, J.F., see Lobstein, N. 86 (1995) 568
- Müller, K., see Starke, U. 89 (1995) 307
- Munekata, H., see Kano, N. 89 (1995) 175
- Muñoz-Guillena, M.J., A. Linares-Solano and C. Salinas-Martínez de Lecea, A study of CaO-SO₂ interaction 82/83 (1994) 132
- Muñoz-Guillena, M.J., A. Linares-Solano and C. Salinas-Martínez de Lecea, A study of CaO-SO₂ interaction in the presence of O₂ 81 (1994) 409
- Muñoz-Guillena, M.J., A. Linares-Solano and C. Salinas-Martínez de Lecea, A new parameter to characterize limestones as SO₂ sorbents 81 (1994) 417
- Murakami, E., H. Kujirai and S. Kimura, Suppression of HBO₂ and Sb adsorption on thin-oxide-covered, H-terminated, or Sb-terminated Si(100) surfaces 89 (1995) 197
- Murata, Y., see Kanazawa, I. 82/83 (1994) 338
- Murota, J., see Sakuraba, M. 85 (1995) 124
- Murota, J., see Suzue, K. 82/83 (1994) 354
- Muto, S., see Sakuma, Y. 82/83 (1994) 422
- Muto, S., see Sakuma, Y. 82/83 (1994) 46
- Myhra, S., see Holt, S.A. 82/83 (1994) 239
- Nagasawa, H. and Y. Yamaguchi, Mechanisms of SiC growth by alternate supply of SiH₂Cl₂ and C₂H₂ 84 (1995) 125
- Nagata, M., see Kubota, H. 82/83 (1994) 405
- Naidu, S., see Weiss, A.H. 82/83 (1994) 565
- Nail, J.W., see Jackson, M.S. 85 (1995) 82
- Naitoh, M., see Watamori, M. 81 (1994) 195
- Nakahara, K., see Kurihara, T. 82/83 (1994) 417
- Nakaji, M., see Takahashi, I. 85 (1995) 178
- Nakajima, K., see Sakuma, Y. 82/83 (1994) 70
- Nakajima, K., see Sakuma, Y. 82/83 (1994) 46
- Nakajyo, T., see Itoh, Y. 82/83 (1994) 239
- Nakajyo, T., see Oshima, N. 85 (1995) 165
- Nakamura, J., see Butman, M.F. 85 (1995) 329
- Nakamura, T., see Kiyota, Y. 89 (1995) 323
- Nakanishi, N., see Itoh, Y. 82/83 (1994) 400
- Nakao, M., see Yoshida, I. 85 (1995) 165
- Nakata, K., see Aruga, T. 82/83 (1994) 501
- Nakato, Y., see Kobayashi, H. 85 (1995) 229
- Nakayama, H., M. Tochigi, H. Maeda and T. Nishino, Configurational atomic ordering caused by stochastic adsorption 81 (1994) 399

- processes in MBE-grown alloy semiconductors 82/83 (1994) 214
- Nakazawa, H., see Suemitsu, M. 82/83 (1994) 449
- Nakazawa, M. and G.A. Somorjai, Coadsorption of water and selected aromatic molecules to model the adhesion of epoxy resins on hydrated surfaces of zinc oxide and iron oxide 84 (1995) 309
- Naqvi, S.S.H., see Hatab, Z.R. 86 (1995) 597
- Narahara, S., see Akamatsu, M. 82/83 (1994) 228
- Naudon, A., see Mathé, E.L. 86 (1995) 338
- Navío, J.A., M. Macías, G. Colón, P.J. Sánchez-Soto, V. Augugliaro and L. Palmisano, Combined use of XPS, IR and EDAX techniques for the characterization of $\text{ZrO}_2\text{-SiO}_2$ powders prepared by a sol-gel process 81 (1994) 325
- Neelissen, R.F.J., see Seijbel, L.J. 85 (1995) 92
- Néron de Surgy, G., H. González and J.-P. Chabrier, Influence of bounded geometry on the initial growth of electrocapillary instability for a liquid metal under electric field 87/88 (1995) 91
- Nicholls, J.E., see Wagner, F.X. 86 (1995) 364
- Nicolaescu, D., Modeling of the field emitter triode (FET) as a displacement/pressure sensor 87/88 (1995) 61
- Nicolet, M.A., see Kubota, H. 82/83 (1994) 565
- Nielsen, B., see Ghosh, V.J. 85 (1995) 210
- Nielsen, B., see Hulett, Jr., L.D. 85 (1995) 334
- Niemantsverdriet, J.W., see Van Hardeveld, R.M. 84 (1995) 339
- Niemantsverdriet, J.W., see Gunter, P.L.J. 89 (1995) 69
- Nieveen, W., see Lätsch, S. 81 (1994) 183
- Niinistö, L. and M. Leskelä, Atomic layer epitaxy in the growth of complex thin film structures for electroluminescent applications 82/83 (1994) 454
- Niinistö, L., see Rautanen, J. 82/83 (1994) 553
- Nikiforova, I.O., see Drozd, V.E. 82/83 (1994) 583
- Nishijima, M., see Taguchi, Y. 82/83 (1994) 434
- Nishikawa, K., see Yamamoto, M. 87/88 (1995) 291
- Nishikawa, O., see Ashino, M. 87/88 (1995) 12
- Nishimura, Y., H. Ujita and M. Tsuji, Tantalum oxide film formation by excimer laser ablation 89 (1995) 393
- Nishinaga, T. and X.Q. Shen, Surface diffusion and adatom stoichiometry in GaAs MBE studied by microprobe-RHEED/SEM MBE 82/83 (1994) 141
- Nishino, T., see Nakayama, H. 82/83 (1994) 214
- Nishiuchi, T., see Yamamoto, M. 87/88 (1995) 291
- Nishiyama, Y., see Arai, M. 89 (1995) 11
- Nishizawa, J., Molecular layer epitaxy of GaAs 82/83 (1994) 1
- Nishizawa, J., see Oyama, Y. 82/83 (1994) 41
- Nishizawa, J., see Plotka, P. 82/83 (1994) 91
- Nishizawa, J., see Kurabayashi, T. 82/83 (1994) 97
- Nissim, Y.I., see Flicstein, J. 86 (1995) 286
- Noh, H.P., see Jeon, D. 87/88 (1995) 386
- Nomura, T., see Yago, H. 84 (1995) 119
- Nomura, Y., see Ohno, H. 82/83 (1994) 164
- Norton, P.R., see Zhdanov, V.P. 81 (1994) 109
- Norton, P.R., see Kasza, R.V. 84 (1994) 97
- Nowak, P., see Laajalehto, K. 81 (1994) 11
- Nowicka, E., see Duś, R. 90 (1995) 277
- Nuesca, G., J. Prasad and J.A. Kelber, Effects of atomic hydrogen on Cu(II)bis-hexafluoroacetylacetonate interactions with a TiN surface 81 (1994) 237
- Nunogaki, M., T. Yamamoto, Y. Honda and T. Okada, A several tens-keV monoenergetic positron surface analyzer with ^{22}Na and electrostatic fields 85 (1995) 132
- Nunoshita, M., see Gotoda, M. 82/83 (1994) 80
- Nuzzo, R.G., see Jackson, S.T. 90 (1995) 195
- Nykänen, E., see Rautanen, J. 82/83 (1994) 553
- Oakey, P.R., see Russell, S.W. 90 (1995) 455
- Obratsova, E.D., see Kononenko, T.V. 86 (1995) 234
- Odriozola, J.A., see Benítez, J.J. 84 (1995) 391
- Ogawa, K., see Wang, F. 90 (1995) 123
- Ogino, T., see Hibino, H. 82/83 (1994) 374
- Ogura, T., see Asahi, H. 82/83 (1994) 109
- Oh, I.-H., see Hong, J.K. 89 (1995) 229
- Ohba, Y., see Ohnishi, H. 82/83 (1994) 444
- Ohgaki, H., see Suzuki, R. 85 (1995) 87
- Ohi, A., see Mizutani, W. 87/88 (1995) 398
- Ohmi, T., see Suzue, K. 82/83 (1994) 422
- Ohnishi, H., see Hirai, M. 82/83 (1994) 23
- Ohnishi, H., Y. Yamamoto, I. Katayama, Y. Ohba and K. Oura, Scanning tunneling microscope observations of $\text{Si}(111)3 \times 1\text{-Ag}$ and $6 \times 1\text{-Ag}$ structures 82/83 (1994) 444
- Ohno, H., S. Goto, Y. Nomura, Y. Morishita and Y. Katayama, Kinetics and mechanism of atomic layer epitaxy of GaAs using trimethylgallium 82/83 (1994) 164
- Ohno, T., see Ito, T. 82/83 (1994) 208
- Ohshita, A., see Hata, K. 87/88 (1995) 117
- Ohta, T., see Vetrivel, R. 82/83 (1994) 516
- Ohtsuka, N., see Sakuma, Y. 82/83 (1994) 46
- Ohtsuka, N., see Ozeki, M. 82/83 (1994) 233
- Ojima, K., see Hongo, S. 82/83 (1994) 437
- Ojima, K., see Hongo, S. 82/83 (1994) 537
- Okada, L.A., M.L. Wise and S.M. George, Isothermal H_2 desorption kinetics from $\text{Si}(100)2 \times 1$: dependence on disilane and atomic hydrogen precursors 82/83 (1994) 410
- Okada, L.A., see George, S.M. 82/83 (1994) 460
- Okada, S., see Kanazawa, I. 85 (1995) 124
- Okada, S. and H. Kaneko, Development of a new Monte Carlo simulation system on positron behavior in matter 85 (1995) 149
- Okada, T., see Nunogaki, M. 85 (1995) 132
- Okahata, Y., see Piscevic, D. 90 (1995) 425

- Okano, R., see Hono, K. 87/88 (1995) 453
- Okuyama, F., see Theiss, A. 87/88 (1995) 146
- Oldershaw, G.A., see Dyer, P.E. 86 (1995) 1
- Ono, S., see Sakuraba, M. 82/83 (1994) 354
- Orlando, S., see Gambardella, U. 86 (1995) 45
- Orlando, S., see Di Palma, T.M. 86 (1995) 68
- Orlando, S., see Teghil, R. 90 (1995) 505
- Oshima, M., see Watanabe, Y. 82/83 (1994) 136
- Oshima, M., see Maeda, F. 82/83 (1994) 276
- Oshima, M., see Heun, S. 82/83 (1994) 507
- Oshima, N., see Itoh, Y. 85 (1995) 165
- Oshima, N., T. Nakajyo, I. Kanazawa, T. Iwashita, Y. Ito, W.-H. Soe and R. Yamamoto, Multilayered Ni/Hf and solid-state amorphization studied using the slow positron beam technique 85 (1995) 329
- Oshiyama, A., M. Saito and O. Sugino, Covalency, elasticity and electron correlation in Si vacancies 85 (1995) 239
- Otake, S., A. Sakamoto, M. Yamamoto and I. Iwasa, In-situ observation of Ga adsorption during TMGa exposure on GaAs(001) surfaces with various As coverages 82/83 (1994) 263
- Ott, A.W., see George, S.M. 82/83 (1994) 460
- Ottosson, M., see Stenberg, G. 86 (1995) 543
- Oura, K., see Watamori, M. 82/83 (1994) 417
- Oura, K., see Ohnishi, H. 82/83 (1994) 444
- Oura, K., see Tanaka, Y. 82/83 (1994) 528
- Outlaw, R.A., W.S. Lee, S.J. Hoekje and S.N. Sankaran, Sulfur segregation in titanium and selected titanium alloys 81 (1994) 143
- Overton, N., A.P. Knights, A. Goodyear and P.G. Coleman, Work function and epithermal positron emission from copper 85 (1995) 54
- Oyama, Y., P. Plotka and J. Nishizawa, Selective MLE growth of GaAs and surface treatment for ideal static induction transistor (ISIT) application 82/83 (1994) 41
- Oyama, Y., see Plotka, P. 82/83 (1994) 91
- Ozeki, M., see Sakuma, Y. 82/83 (1994) 46
- Ozeki, M. and N. Ohtsuka, Atomic layer epitaxy of AlAs: growth mechanism 82/83 (1994) 233
- Paggel, J.J., see Keil, M. 90 (1995) 377
- Pailharey, D., see Grangeon, F. 86 (1995) 160
- Palau, J., M. Sowinska, M. Varela, P. Summ, J. Esteve, P. Serra, J.L. Morenza and J.A. Miehe, Laser wavelength dependence of $\text{YBa}_2\text{Cu}_3\text{O}_y$ laser ablation plumes 86 (1995) 59
- Palau, J., see Queralt, X. 86 (1995) 95
- Palmisano, L., see Navío, J.A. 81 (1994) 325
- Paloura, E.C., see Kennou, S. 90 (1995) 283
- Pancíř, J., see Pingo, M. 90 (1995) 373
- Panda, B.K., S. Fleischer, C.C. Ling, C.D. Beling, S. Fung and S. Panda, Deconvolution of Doppler-broadened positron annihilation lineshapes by the generalised least-squares method 85 (1995) 182
- Panda, S., see Panda, B.K. 85 (1995) 182
- Pande, R., see Adsool, A.D. 87/88 (1995) 37
- Pang, X.J., see Dwyer, D.J. 81 (1994) 229
- Papadia, S., see Desjonquères, M.C. 87/88 (1995) 337
- Papaioannou, G., see Thurzo, I. 90 (1995) 39
- Parada, E.G., P. González, J. Serra, B. León, M. Pérez-Amor, J. Flicstein and R.A.B. Devine, Improvement of silicon oxide film properties by ultraviolet excimer lamp annealing 86 (1995) 294
- Parent, P., see Le Mercier, T. 86 (1995) 382
- Paridaens, J., see Segers, D. 85 (1995) 172
- Park, C., see Bakhtizin, R.Z. 87/88 (1995) 347
- Park, D., see Smith, G.C. 90 (1995) 357
- Partlow, W.D., see Yates, Jr., J.T. 82/83 (1994) 180
- Paul, A.J., see Di Palma, T.M. 86 (1995) 68
- Pauleau, Y., see Tonneau, D. 86 (1995) 488
- Pavlyak, F., Modified relative sensitivity factors for Auger spectra 81 (1994) 351
- Pedraza, A.J., see Esrom, H. 86 (1995) 202
- Peled, A., see Baranauskas, V. 86 (1995) 398
- Peled, A., see Borochoy, N. 86 (1995) 533
- Peled, A., B. Dragnea, R. Alexandrescu and A. Andrei, Laser-induced photodeposition from ZnS colloid solutions 86 (1995) 538
- Peng, D., see Jiang, S. 84 (1995) 373
- Pérez-Amor, M., see Parada, E.G. 86 (1995) 294
- Perrière, J., see Gonzalo, J. 86 (1995) 40
- Perrone, A., see D'Anna, E. 86 (1995) 170
- Persch, V., see Engelhard, H. 90 (1995) 89
- Pershan, P.S., see Kosowsky, S.D. 84 (1995) 179
- Pervan, P., see Valla, T. 89 (1995) 375
- Petersen, J.W., see Müllenborn, M. 86 (1995) 568
- Petkov, K., see Ihlemann, J. 86 (1995) 245
- Petó, G., see Sundararajan, R. 90 (1995) 165
- Pfau, J., see Hulett, Jr., L.D. 85 (1995) 334
- Pfleging, W., see Klotzbücher, T. 86 (1995) 165
- Pfleging, W., see Kreutz, E.W. 86 (1995) 266
- Pflüger, S., M. Wehner, F. Jansen, Th. Kruck and F. Lupp, Deposition of gold on polyimide from solutions 86 (1995) 504
- Pickering, C., see Carline, R.T. 81 (1994) 475
- Pickering, H.W., see Cho, K. 87/88 (1995) 380
- Pickering, H.W., see Sakurai, T. 87/88 (1995) 405
- Piglmayer, K., Z. Tóth and Z. Kantor, Laser-induced etching and deposition of tungsten in $\text{WF}_6\text{-H}_2$ atmosphere 86 (1995) 484
- Pimenov, S.M., G.A. Shafeev, A.A. Smolin, V.I. Konov and B.K. Vodolaga, Laser-induced forward transfer of ultra-fine diamond particles for selective deposition of diamond films 86 (1995) 208
- Pimenov, S.M., see Shafeev, G.A. 86 (1995) 392

- Pincik, E., see Thurzo, I. 90 (1995) 39
- Pingo, M., J. Vošta, J. Pancíř and I. Haslingerová, Topological study of crack growth on iron crystal 90 (1995) 373
- Pinto, G., see Larena, A. 84 (1995) 407
- Pireaux, J.-J., see Grégoire, Ch. 84 (1995) 163
- Pireaux, J.-J., see Piyakis, K. 84 (1995) 227
- Pirri, C., see Hong, S. 90 (1995) 65
- Piscevic, D., R. Lawall, M. Veith, M. Liley, Y. Okahata and W. Knoll, Oligonucleotide hybridization observed by surface plasmon optical techniques 90 (1995) 425
- Piveteau, B., see Desjonquères, M.C. 87/88 (1995) 337
- Piyakis, K., E. Sacher, A. Domingue, J.-J. Pireaux, G. Leclerc, P. Bertrand and J.B. Lhoest, A multitechnique analysis of the outermost layers of the Teflon PFA surface 84 (1995) 227
- Pizzella, G., see Teghil, R. 90 (1995) 505
- Plekhanov, P.S., see Givargizov, E.I. 87/88 (1995) 24
- Plotka, P., see Oyama, Y. 82/83 (1994) 41
- Plotka, P., T. Kurabayashi, Y. Oyama and J. Nishizawa, Ideal static induction transistor implemented with molecular layer epitaxy 82/83 (1994) 91
- Pola, J., see Fajgar, R. 86 (1995) 530
- Polo, M.C., see Puigdollers, J. 86 (1995) 600
- Poltoratskii, Yu., see Li, B. 86 (1995) 577
- Porcelli, T.A., see Massoumi, G.R. 85 (1995) 39
- Poritsky, P.V., see Vladimirov, V.V. 87/88 (1995) 106
- Portillo, M., see Durrer, W.G. 81 (1994) 215
- Porto, A., see Scandurra, A. 89 (1995) 1
- Possart, W., see Gesang, T. 84 (1995) 273
- Potez, L., see Duval, S. 87/88 (1995) 284
- Powell, C.J., Elemental binding energies for X-ray photoelectron spectroscopy 89 (1995) 141
- Prasad, J., see Nuesca, G. 81 (1994) 237
- Prasad, M., see Dubowski, J.J. 86 (1995) 548
- Prévot, B., see Antoni, F. 86 (1995) 175
- Prevot, B., see Slaoui, A. 86 (1995) 346
- Přikryl, P., see Černý, R. 86 (1995) 359
- Prins, S.L., see Hatab, Z.R. 86 (1995) 597
- Prupton, M., see Barkshire, I.R. 84 (1995) 331
- Puglisi, O., see Scandurra, A. 89 (1995) 1
- Puigdollers, J., J. Cifre, M.C. Polo, J.M. Asensi, J. Bertomeu, J. Andreu and A. Lloret, P-doped polycrystalline silicon films obtained at low temperature by hot-wire chemical vapor deposition 86 (1995) 600
- Pundt, A. and C. Michaelsen, APFIM study of the compositional inhomogeneity of sputtered Co-Cr magnetic thin film 87/88 (1995) 264
- Puppin, E., see Vavassori, P. 89 (1995) 93
- Pusel, A., see Karstens, H. 86 (1995) 521
- Puska, M.J., see Weiss, A.H. 85 (1995) 82
- Putilin, F.N., see Mikhailov, V.A. 86 (1995) 64
- Qian, Y., see Guo, S. 84 (1995) 351
- Qiu, S.-L., see Ruckman, M.W. 89 (1995) 401
- Quaeyhaegens, C., see Segers, D. 85 (1995) 172
- Quarton, M., see Le Mercier, T. 86 (1995) 382
- Queralt, X., C. Ferrater, F. Sánchez, R. Aguiar, J. Palau and M. Varela, Erbium oxide thin films on Si(100) obtained by laser ablation and electron beam evaporation 86 (1995) 95
- Räisänen, J., see Ahlgren, T. 90 (1995) 419
- Rajasekar, P., see Ray, N. 84 (1995) 203
- Rajumon, M.K., see Rao, C.N.R. 84 (1995) 285
- Rakova, E.V., see Givargizov, E.I. 87/88 (1995) 24
- Ralchenko, V.G., see Kononenko, T.V. 86 (1995) 234
- Ralston, J., Reply to the "Comment of A.N. Buckley and R. Woods on 'Scanning tunnelling microscopy studies of galena: the mechanism of oxidation in air' by B.S. Kim, R.A. Hayes, C.A. Prestidge, J. Ralston and R.St.C. Smart" 84 (1995) 225
- Ramadan, A.A., see Ashour, A. 89 (1995) 159
- Rao, C.N.R., V. Vijayakrishnan, G.U. Kulkarni and M.K. Rajumon, A comparative study of the interaction of oxygen with clusters and single-crystal surfaces of nickel 84 (1995) 285
- Rao, C.N.R., see Santra, A.K. 84 (1995) 347
- Rao, M.V.H., V. Srinivas, V.V. Rao, B.K. Mathur and K.L. Chopra, Observation of field-induced fragmentation of nickel clusters using Scanning Tunneling Microscopy 89 (1995) 417
- Rao, V.V., see Rao, M.V.H. 89 (1995) 417
- Rauhala, E., see Elers, K.-E. 82/83 (1994) 468
- Rauhala, E., see Ahlgren, T. 90 (1995) 419
- Rautanen, J., M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen, The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy 82/83 (1994) 553
- Ravelet, S., see Easwarakhanthan, T. 90 (1995) 251
- Ray, N., P. Rajasekar and S.D. Dey, A comparative study of primary ion energy dependence of secondary ion yields from Si and Ge surfaces under inert and reactive ion bombardment 84 (1995) 203
- Razdan, A.K., see Jain, A. 84 (1995) 65
- Rector, J., see Dam, B. 86 (1995) 13
- Rei Vilar, M., see Fauquet, C. 81 (1994) 435
- Reihs, K., R. Aguiar Colom, S. Gleditsch, M. Deimel, B. Hagenhoff and A. Benninghoven, Chemisorption of poly(methylhydrogensiloxane) on oxide surfaces: a quantitative investigation using static SIMS 84 (1995) 107
- Reisse, G., S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz, Influence of ion bombardment on the refractive index of laser pulse deposited oxide films 86 (1995) 107

- Reisse, G., S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz, Influence of LN₂ substrate cooling on optical properties of laser-pulse-deposited oxide films 86 (1995) 114
- Reitano, R., see Baeri, P. 86 (1995) 128
- Reitano, R., Thermodynamics and kinetics of solidification of Si-As solutions 86 (1995) 323
- Renard, P., see Easwarakhanthan, T. 90 (1995) 251
- Reniers, F., M.P. Delplancke, A. Asskali, M. Jardinier-Offergeld and F. Bouillon, Surface segregation study of Ib-VIII single-crystal alloys 81 (1994) 151
- Repplinger, F., see Mathé, E.L. 86 (1995) 338
- Rice-Evans, P.C., see Towner, A. 85 (1995) 315
- Rice-Evans, P.C., A.S. Saleh and S.J. Bull, Positron beam spectroscopy for the assessment of the structure and defect density of titanium nitride 85 (1995) 320
- Rice-Evans, P.C., see Saleh, A.S. 85 (1995) 325
- Richarz, B., see Lundin, L. 87/88 (1995) 194
- Rigo, S., see Bréelle, E. 81 (1994) 127
- Ringer, S.P., K. Hono and T. Sakurai, Nucleation and growth of θ' precipitation in Sn-modified Al-Cu alloys: APFIM/TEM observations 87/88 (1995) 223
- Ringer, S.P., K. Hono and T. Sakurai, Erratum to "Nucleation and growth of θ' precipitation in Sn-modified Al-Cu alloys: APFIM/TEM observations" [Appl. Surf. Sci. 87/88 (1995) 223] 90 (1995) 107
- Ritala, M., see Asikainen, T. 82/83 (1994) 122
- Ritala, M., see Elers, K.-E. 82/83 (1994) 468
- Robbins, D.J., see Carline, R.T. 81 (1994) 475
- Roberts, M.W., see Carley, A.F. 81 (1994) 265
- Robino, M., see Deiss, J.L. 86 (1995) 149
- Robinson, B.J., see LaPierre, R.R. 90 (1995) 437
- Rocheffort, A., see Debauge, Y. 90 (1995) 15
- Röllgen, F.W., see Schulze, B. 87/88 (1995) 140
- Röllgen, F.W., see Theiss, A. 87/88 (1995) 146
- Romeo, M., see Le Normand, F. 81 (1994) 309
- Roy, D., see Lamontagne, B. 90 (1995) 447
- Roy, D., see Lamontagne, B. 90 (1995) 481
- Roy, J.A., see Zou, H. 90 (1995) 59
- Ruckman, M.W., S.-L. Qiu and M. Strongin, A photoelectron study of the oxidation of Ta(110) and thin aluminum layers on Ta(110) 89 (1995) 401
- Russell, D.P., see Durrer, W.G. 81 (1994) 215
- Russell, K.F., see Miller, M.K. 87/88 (1995) 216
- Russell, N.M., see Asami, S. 82/83 (1994) 359
- Russell, S.W., J. Li, T.L. Alford, P.R. Oakey and S.C. Shatas, Rapid thermal nitridation of thin chromium films 90 (1995) 455
- Ryzhkov, S.V., see Khramtsova, E.A. 82/83 (1994) 576
- Sacher, E., see Piyakis, K. 84 (1995) 227
- Sacher, E., see Izquierdo, R. 86 (1995) 509
- Saeda, T., see Hono, K. 87/88 (1995) 453
- Sagisaka, K., see Suzuki, Y. 84 (1995) 1
- Saied, S.O., see Bertóti, I. 84 (1995) 357
- Saied, S.O., see Sullivan, J.L. 90 (1995) 309
- Saito, M., see Oshiyama, A. 85 (1995) 239
- Saito, Y., Atomic-hydrogen-induced desorption of fluorine from silicon surfaces 81 (1994) 223
- Saito, Y., see Hata, K. 87/88 (1995) 117
- Sakamoto, A., see Otake, S. 82/83 (1994) 263
- Sakata, T., see Xue, Q. 87/88 (1995) 364
- Sakuma, Y., M. Ozeki, N. Ohtsuka, Y. Matsumiya, H. Shigematsu, O. Ueda, S. Muto, K. Nakajima and N. Yokoyama, Pulsed-jet epitaxy: application to device processes 82/83 (1994) 46
- Sakuma, Y., S. Muto, K. Nakajima and N. Yokoyama, A solution to the surface arsenic stoichiometric problem at the GaAs(001) growth surface in atomic layer epitaxy 82/83 (1994) 239
- Sakuraba, M., J. Murota, T. Watanabe, Y. Sawada and S. Ono, Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH₄ and SiH₄ gases 82/83 (1994) 354
- Sakuragi, S., see Durand, H.-A. 86 (1995) 122
- Sakurai, T., see Hono, K. 87/88 (1995) 166
- Sakurai, T., see Ringer, S.P. 87/88 (1995) 223
- Sakurai, T., see Bakhtizin, R.Z. 87/88 (1995) 347
- Sakurai, T., see Xue, Q. 87/88 (1995) 364
- Sakurai, T., see Hashizume, T. 87/88 (1995) 373
- Sakurai, T., see Cho, K. 87/88 (1995) 380
- Sakurai, T., see Jeon, D. 87/88 (1995) 386
- Sakurai, T., X.D. Wang, T. Hashizume, V. Yurov, H. Shinohara and H.W. Pickering, Adsorption of fullerenes on Cu(111) and Ag(111) surfaces 87/88 (1995) 405
- Sakurai, T., see Hono, K. 87/88 (1995) 453
- Sakurai, T., see Ringer, S.P. 90 (1995) 107
- Salaita, G.N., Determination of the spatial distribution of trace elements in stainless steel by imaging microprobe secondary ion mass spectrometry 90 (1995) 465
- Saleh, A.S., see Rice-Evans, P.C. 85 (1995) 320
- Saleh, A.S., P.C. Rice-Evans and S.J. Bull, Aluminium nitride layers investigated by slow positrons 85 (1995) 325
- Salinas-Martínez de Lecea, C., see Muñoz-Guillena, M.J. 81 (1994) 409
- Salinas-Martínez de Lecea, C., see Muñoz-Guillena, M.J. 81 (1994) 417
- Salinas-Martínez de Lecea, C., see Muñoz-Guillena, M.J. 89 (1995) 197
- Salvarezza, R.C., see Hernández Creus, A. 81 (1994) 387
- Salvi, A.M., J.E. Castle, J.F. Watts and E. Desimoni, Peak fitting of the chromium 2p XPS spectrum 90 (1995) 333
- Salzman, W.R., see Wijekoon, W.M.K.P. 81 (1994) 347
- Saarinen, K., see Manuel, A.A. 85 (1995) 301
- Sabatini, R.L., see Canter, K.F. 85 (1995) 339

- Sánchez, F., see Queral, X. 86 (1995) 95
- Sánchez-Soto, P.J., see Navío, J.A. 81 (1994) 325
- Sands, D., see Dyer, P.E. 86 (1995) 18
- Sands, D., see Wagner, F.X. 86 (1995) 364
- Sankaran, S.N., see Outlaw, R.A. 81 (1994) 143
- Santagata, A., see Teghil, R. 90 (1995) 505
- Santra, A.K. and C.N.R. Rao, Surface alloy formation in Pd/Ag, Cu/Au and Ni/Au bimetallic overlayers 84 (1995) 347
- Sanyal, S., see Chattopadhyay, P. 89 (1995) 205
- Saranin, A.A., see Khramtsova, E.A. 82/83 (1994) 576
- Sarrau, J.M., see Deconihout, B. 87/88 (1995) 428
- Sasaki, M., see Yoshida, S. 82/83 (1994) 28
- Sasaki, M. and S. Yoshida, Pulsed trimethylgallium scattering from As-stabilized and Ga-stabilized surfaces 82/83 (1994) 269
- Sasaki, M., T. Abukawa, H.W. Yeom, M. Yamada, S. Suzuki, S. Sato and S. Kono, Auger electron diffraction study of the initial stage of Ge heteroepitaxy on Si(001) 82/83 (1994) 387
- Sasaoka, C. and A. Usui, Self-limiting adsorption of thermally cracked SiCl₂H₂ on Si surfaces 82/83 (1994) 348
- Sassoli, H., see Grangeon, F. 86 (1995) 160
- Sato, K., see Fahy, M.R. 82/83 (1994) 14
- Sato, M., Surface structure dependence of O₂-W adsorption system 82/83 (1994) 532
- Sato, S., see Sasaki, M. 82/83 (1994) 387
- Sato, S., S. Minoura, T. Urisu and Y. Takasu, IRAS and TDS study on the photolytic decarbonylation of iron pentacarbonyl adsorbed on a SiO₂ film with a buried metal layer 90 (1995) 29
- Sawada, Y., see Sakuraba, M. 82/83 (1994) 354
- Sawada, Y., see Suzue, K. 82/83 (1994) 422
- Sawaki, N., see Suzuki, T. 82/83 (1994) 103
- Sawyer, W.D., see Coleman, P.G. 85 (1995) 276
- Scandurra, A., see Torrisi, A. 81 (1994) 259
- Scandurra, A., A. Porto and O. Puglisi, SIMS microprofiles of Pb-5%Sn solder joints in electronic devices after accelerated life tests 89 (1995) 1
- Schaefer, J., see Yates, Jr., J.T. 82/83 (1994) 180
- Schaefer, J.A., see Engelhard, H. 90 (1995) 89
- Schaub, A., see Hulett, Jr., L.D. 85 (1995) 334
- Schedel-Niedrig, Th., see Keil, M. 90 (1995) 377
- Schilcher, K., see Heitz, J. 81 (1994) 103
- Schlapbach, L., see Gröning, P. 89 (1995) 83
- Schlottig, F., J. Schreckenbach, D. Dietrich, A. Hofmann and G. Marx, Conversion film formation on titanium anodes in acetonitrile at high voltages 90 (1995) 129
- Schmidt, U., see Schulze, B. 87/88 (1995) 140
- Schmuck, C., P. Auger, F. Danoix and D. Blavette, Quantitative analysis of GP zones formed at room temperature in a 7150 Al-based alloy 87/88 (1995) 228
- Schneider, H., see Stoll, H. 85 (1995) 17
- Schneider, Y.-J., see Deldime, M. 90 (1995) 1
- Scholz, R., see Reisse, G. 86 (1995) 107
- Scholz, R., see Reisse, G. 86 (1995) 114
- Schreckenbach, J., see Schlottig, F. 90 (1995) 129
- Schreifels, J.A., N.H. Turner and R.E. Morris, A comparison of X-ray photoelectron spectroscopy and Auger electron spectroscopy depth profiles for magnesium implants 84 (1995) 23
- Schubert, E., see Bergmann, H.W. 86 (1995) 259
- Schultz, P.J., see Massoumi, G.R. 85 (1995) 39
- Schultz, P.J., see Lawther, D.W. 85 (1995) 265
- Schultz, P.J., see Goldberg, R.D. 85 (1995) 287
- Schultz, P.J., see Leung, T.C. 85 (1995) 292
- Schultz, R.J., see Zou, H. 90 (1995) 59
- Schulze, B., A. Theiss, U. Schmidt and F.W. Röllgen, FIM phenomena observed with benzene as image gas 87/88 (1995) 140
- Schulze, R.K. and J.F. Evans, Room-temperature water adsorption on the Si(100) surface examined by UPS, XPS, and static SIMS 81 (1994) 449
- Schut, H., see Seijbel, L.J. 85 (1995) 92
- Schut, H., see Van Veen, A. 85 (1995) 216
- Schut, H. and A. van Veen, Extension of the PC version of VEPFIT with input and output routines running under Windows 85 (1995) 225
- Schut, H., see Hakvoort, R.A. 85 (1995) 271
- Schutte, K., see Bergmann, H.W. 86 (1995) 259
- Schwarzbach, D., see Friedbacher, G. 84 (1995) 133
- Schwentner, N., see Li, B. 86 (1995) 577
- Seeger, A., Positron diffusion in solids and in liquid metals 85 (1995) 8
- Seeger, A., see Stoll, H. 85 (1995) 17
- Sefsaf, B., see Lang, B. 81 (1994) 17
- Segers, D., J. Paridaens, T. Van Hoecke, C. Dauwe, L. Dorikens-Vanpraet, C. Quaeysaegens and L.M. Stals, Positron Doppler broadening measurements with a LINAC-based slow positron beam 85 (1995) 172
- Seidman, D.N., see Van Bakel, G.P.E.M. 90 (1995) 95
- Seijbel, L.J., R.F.J. Neelissen, P. Kruit, A. van Veen and H. Schut, Coupling optics for a combined electron positron scanning microscope 85 (1995) 92
- Seki, H., see Ikeda, H. 82/83 (1994) 257
- Sekine, S., H. Shimizu and S. Ichimura, Composition of sputtered material from Cu-Ni alloy during Xe⁺ ion sputtering at elevated temperatures 84 (1995) 401
- Semond, F., see Lamontagne, B. 90 (1995) 447
- Seo, A. and H. Shindo, Atomic force microscopic study of directional SrSO₄(001) surface and its etching property 82/83 (1994) 475
- Seo, M., see Gråsjö, L. 89 (1995) 21
- Serafetinides, A.A., see Skordoulis, C.D. 86 (1995) 239

- Serra, J., see Parada, E.G. 86 (1995) 294
- Serra, P., see Palau, J. 86 (1995) 59
- Seta, M., see Asahi, H. 82/83 (1994) 109
- Seth, J., see Kononenko, T.V. 86 (1995) 234
- Setzler, S., see Coleman, P.G. 85 (1995) 276
- Shafeev, G.A., see Pimenov, S.M. 86 (1995) 208
- Shafeev, G.A., L. Bellard, J.-M. Themlin, W. Marine and A. Cros, Enhanced adherence of electroless metal deposit on SiO₂ via control of the chemical environment of the Pd seeding layer 86 (1995) 387
- Shafeev, G.A., S.M. Pimenov and E.N. Loubnin, Laser-assisted selective metallisation of diamonds by electroless Ni and Cu plating 86 (1995) 392
- Shafeev, G.A., see Simakin, A.V. 86 (1995) 422
- Sharma, K.K., P.N. Kotru and B.M. Wanklyn, Microindentation studies of flux-grown ErFeO₃ single crystals 81 (1994) 251
- Sharma, R.B., see Adsool, A.D. 87/88 (1995) 37
- Sharma, S.C., see Hozhabri, N. 85 (1995) 311
- Shatas, S.C., see Russell, S.W. 90 (1995) 455
- Shaw, N., see Towner, A. 85 (1995) 315
- Shen, N.F., see Wang, X.K. 89 (1995) 297
- Shen, X.Q., see Nishinaga, T. 82/83 (1994) 141
- Shi, M., see Gerola, D. 85 (1995) 106
- Shi, M., D. Gerola, W.B. Waeber and U. Zimmermann, Slow positron beam extraction from high magnetic fields 85 (1995) 143
- Shibata, H., see Durand, H.-A. 86 (1995) 122
- Shidara, T., see Kurihara, T. 85 (1995) 178
- Shigematsu, H., see Sakuma, Y. 82/83 (1994) 46
- Shimizu, H., see Sekine, S. 84 (1995) 401
- Shimizu, T., see Masuda, A. 81 (1994) 277
- Shindo, H., see Seo, A. 82/83 (1994) 475
- Shinohara, H., see Sakurai, T. 87/88 (1995) 405
- Shinohara, M., see Yokoyama, H. 82/83 (1994) 158
- Shirai, Y., H. Miura and M. Yamaguchi, Construction and performance of a slow positron beam guided by an increasing magnetic field 85 (1995) 138
- Shiraishi, K., see Ito, T. 82/83 (1994) 208
- Shirakawa, A., see Kurihara, T. 85 (1995) 178
- Shklyayev, A.A. and A.S. Medvedev, Plasma-enhanced reactively evaporated deposition of SiO₂ films 89 (1995) 49
- Shogen, S., see Song, Z. 82/83 (1994) 250
- Shukla, N., see Carley, A.F. 81 (1994) 265
- Siddiqui, A.B., see Mohamed, M.H. 90 (1995) 409
- Siegle, A., see Stoll, H. 85 (1995) 17
- Sigmon, T.W., see Slaoui, A. 86 (1995) 346
- Siimon, H., see Aarik, J. 81 (1994) 281
- Siimon, H., see Aarik, J. 90 (1995) 109
- Sijbrandij, S.J., A. Cerezo and G.D.W. Smith, Improvements in the transmission of voltage evaporation pulses in the atom probe 87/88 (1995) 414
- Sil, A. and D.S. Venkateswarlu, Modelling of barium transport in dispenser cathodes 81 (1994) 469
- Simakin, A.V. and G.A. Shafeev, Laser-assisted etching-like damage of Si 86 (1995) 422
- Simpson, P.J., see Massoumi, G.R. 85 (1995) 39
- Simpson, P.J., see Lawther, D.W. 85 (1995) 265
- Simpson, P.J., see Goldberg, R.D. 85 (1995) 287
- Simpson, P.J., see Leung, T.C. 85 (1995) 292
- Sirringhaus, H., see Kafader, U. 90 (1995) 297
- Siuda, R., The smoothing properties of some new shapes for transmission functions in Fourier space. A real case study on exemplary noisy Auger spectra 81 (1994) 27
- Skarp, J., see Lujala, V. 82/83 (1994) 34
- Skatkov, L.I., V.V. Konotop, P.G. Cheremskoy, V.P. Gomofov and B.I. Bayrachny, Surface fractal dimension of sintered porous solid niobium 81 (1994) 427
- Skordoulis, C.D., M. Makropoulou and A.A. Serafetinides, Ablation of nylon-6,6 with UV and IR lasers 86 (1995) 239
- Slaoui, A., C. Deng, S. Talwar, K.J. Kramer, T.W. Sigmon, J.P. Stoquert and B. Prevot, Formation of poly-Si_{1-x}Ge_x using excimer-laser processing 86 (1995) 346
- Sloboshanin, S., see Engelhard, H. 90 (1995) 89
- Smith, G.C., see Barkshire, I.R. 84 (1995) 331
- Smith, G.C., D. Park, K.J. Titchener, R.E. Davies and R.H. West, Surface studies of oil-seal degradation 90 (1995) 357
- Smith, G.D.W., see Miller, M.K. 87/88 (1995) 243
- Smith, G.D.W., see King, R.A. 87/88 (1995) 279
- Smith, G.D.W., see Hyde, J.M. 87/88 (1995) 311
- Smith, G.D.W., see Miller, M.K. 87/88 (1995) 323
- Smith, G.D.W., see Sijbrandij, S.J. 87/88 (1995) 414
- Smith, G.D.W., see Huang, M. 87/88 (1995) 421
- Smolin, A.A., see Pimenov, S.M. 86 (1995) 208
- Smurov, I., see Mazhukin, V.I. 86 (1995) 7
- Smurov, I., see Berjeza, N.A. 86 (1995) 303
- Sneh, O., see George, S.M. 82/83 (1994) 460
- Snelling, H.V., see Dyer, P.E. 86 (1995) 18
- Snels, M., see Gambardella, U. 86 (1995) 45
- Sobol, E.N., M.S. Kitai, S.M. Gol'berg and A.N. Zherikhin, Macro-particle ejection by laser ablation of high-temperature superconductors 90 (1995) 235
- Soe, W.-H., see Oshima, N. 85 (1995) 329
- Soga, T., T. Jimbo and M. Umeno, Epitaxial growth of a two-dimensional structure of GaP on a Si substrate by metalorganic chemical vapor deposition 82/83 (1994) 64
- Soh, H.G., see Lu, Y.F. 90 (1995) 217
- Soininen, P., see Rautanen, J. 82/83 (1994) 553
- Somorjai, G.A., see Nakazawa, M. 84 (1995) 309
- Somorjai, G.A., see Magni, E. 89 (1995) 187
- Song, Y., see Carley, A.F. 81 (1994) 265

- Song, Z., S. Shogen, M. Kawasaki and I. Suemune, X-ray photoelectron spectroscopic and atomic force microscopic study of GaAs etching with a HCl solution 82/83 (1994) 250
- Song, Z.M., see Wu, J.D. 90 (1995) 81
- Sotobayashi, H., see Keil, M. 90 (1995) 377
- Souchet, R., F. Danoix, A. D'Huysser and M. Lenglet, APFIM and XPS study of the first stages of low temperature air oxidation of industrial CuNi alloys 87/88 (1995) 271
- Soumillion, J.P., see Devillers, M. 81 (1994) 83
- Souto, R.M., see Hernández Creus, A. 81 (1994) 387
- Sowinska, M., see Palau, J. 86 (1995) 59
- Spanjaard, D., see Desjonquères, M.C. 87/88 (1995) 337
- Spassova, E., see Ihlemann, J. 86 (1995) 245
- Speisser, C., see Le Normand, F. 81 (1994) 309
- Spinelli, N., see Amoroso, S. 86 (1995) 35
- Sporken, R., see Lamontagne, B. 90 (1995) 481
- Sreemany, M. and T.B. Ghosh, On the XPS peak shape analysis 81 (1994) 365
- Sreemany, M. and T.B. Ghosh, Angle resolved XPS study of inhomogeneous specimens of polycrystalline silver covered with uniform graphite overlayers 90 (1995) 241
- Srinivas, V., see Rao, M.V.H. 89 (1995) 417
- Stals, L.M., see Segers, D. 85 (1995) 172
- Starke, U., Ch. Bram, P.-R. Steiner, W. Hartner, L. Hammer, K. Heinz and K. Müller, The (0001)-surface of 6H-SiC: morphology, composition and structure 89 (1995) 175
- Steiger, B., see Reisse, G. 86 (1995) 107
- Steiger, B., see Reisse, G. 86 (1995) 114
- Steiner, P.-R., see Starke, U. 89 (1995) 175
- Steiner IV, P.A., see Asami, S. 82/83 (1994) 359
- Stenberg, G., M. Boman, M. Ottosson and J.-O. Carlsson, Laser chemical etching of Cu₂O 86 (1995) 543
- Stepanenko, V., see Li, B. 86 (1995) 577
- Stepanova, A.N., see Givargizov, E.I. 87/88 (1995) 24
- Stepanova, M.G., see Hofmann, S. 90 (1995) 227
- Stietz, F., see Engelhard, H. 90 (1995) 89
- Stiller, K., see Thuvander, M. 87/88 (1995) 251
- Stoemenos, J., see Logothetidis, S. 86 (1995) 185
- Stoll, H., M. Koch, U. Lauff, K. Maier, J. Major, H. Schneider, A. Seeger and A. Siegle, Annihilation of incompletely thermalized positronium studied by age-momentum correlation 85 (1995) 17
- Stoquert, J.P., see Antoni, F. 86 (1995) 175
- Stoquert, J.P., see Slaoui, A. 86 (1995) 346
- Störmer, J., see Britton, D.T. 85 (1995) 1
- Störmer, M., see Krebs, H.-U. 86 (1995) 90
- Streller, U., see Li, B. 86 (1995) 577
- Stricker, J., see Frerichs, H. 86 (1995) 405
- Strohmeier, B.R., Comment on 'Influence of surface composition on initial hydration of aluminium in boiling water' by A. Strålin and T. Hjertberg 81 (1994) 273
- Strongin, M., see Ruckman, M.W. 89 (1995) 401
- Suchorski, Yu., see Medvedev, V.K. 87/88 (1995) 159
- Suda, Y., M. Ishida, M. Yamashita and H. Ikeda, Sub-atomic-layer epitaxy of Si using Si₂H₆ 82/83 (1994) 332
- Suemitsu, M., H. Nakazawa and N. Miyamoto, Temperature-programmed-desorption study of the process of atomic deuterium adsorption onto Si(100)2 × 1 82/83 (1994) 449
- Suemune, I., Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs 82/83 (1994) 149
- Suemune, I., see Song, Z. 82/83 (1994) 250
- Sueoka, O., B. Jin and A. Hamada, Threshold behavior of ionization and excitation cross sections of He and Ar by positron impact 85 (1995) 59
- Sueoka, O., see Hamada, A. 85 (1995) 64
- Sueoka, O., see Kanazawa, I. 85 (1995) 124
- Suezawa, M., see Kawasuso, A. 85 (1995) 280
- Sugahara, S., T. Kitamura, S. Imai and M. Matsumura, Atomic layer epitaxy of germanium 82/83 (1994) 380
- Sugahara, S., M. Kadoshima, T. Kitamura, S. Imai and M. Matsumura, Atomic hydrogen-assisted ALE of germanium 90 (1995) 349
- Sugano, T., see Isshiki, H. 82/83 (1994) 57
- Sugano, T., see Meguro, T. 82/83 (1994) 193
- Sugano, T., see Ishii, M. 86 (1995) 554
- Sugimoto, H., see Gotoda, M. 82/83 (1994) 80
- Sugino, O., see Oshiyama, A. 85 (1995) 239
- Sugiyama, M., see Heun, S. 82/83 (1994) 507
- Sullivan, J.L., see Bertóti, I. 84 (1995) 357
- Sullivan, J.L., W. Yu and S.O. Saied, A study of the compositional changes in chemically etched, Ar ion bombarded and reactive ion etched GaAs(100) surfaces by means of ARXPS and LEISS 90 (1995) 309
- Sum, R., H.P. Lang and H.-J. Güntherodt, Pulsed laser deposition and nanometer scale characterization of YBa₂Cu₃O_{7-δ} thin films by scanning probe methods 86 (1995) 140
- Sumino, K., see Kawasuso, A. 85 (1995) 280
- Summ, P., see Palau, J. 86 (1995) 59
- Sun, S., see Ling, C.C. 85 (1995) 305
- Sundararajan, R., G. Pető, E. Koltay and L. Guzzi, Photoemission studies on Pt foil implanted by carbon atoms accelerated in a Van de Graaff generator: nature of the interaction between Pt and carbon 90 (1995) 165
- Suntola, T., see Lujala, V. 82/83 (1994) 34
- Suntola, T., see Haukka, S. 82/83 (1994) 548
- Suppiah, S., see Huang, M. 90 (1995) 393
- Surry, C., see Mazhukin, V.I. 86 (1995) 7
- Susaki, W., see Gotoda, M. 82/83 (1994) 80

- Suys, M., see Izquierdo, R. 86 (1995) 509
- Suzue, K., T. Matsuura, J. Murota, Y. Sawada and T. Ohmi, Substrate orientation dependence of self-limited atomic-layer etching of Si with chlorine adsorption and low-energy Ar⁺ irradiation 82/83 (1994) 422
- Suzuki, R., T. Mikado, M. Chiwaki, H. Ohgaki and T. Yamazaki, Generation of an intense pulsed positron beam for positron lifetime and TOF experiments 85 (1995) 87
- Suzuki, S., see Sasaki, M. 82/83 (1994) 387
- Suzuki, T., H. Goto, N. Sawaki, H. Ito and K. Hara, Autocompensation in Si planar doped GaAs 82/83 (1994) 103
- Suzuki, Y., K. Sagisaka and A. Hatta, Evidence for infrared absorption enhancement of species at the lithium metal/electrolytic solution interface 84 (1995) 1
- Svensson, L.-E., see Andr n, H.-O. 87/88 (1995) 200
- Svob, L., see Ballutaud, D. 84 (1995) 187
- Syutkin, N.N., see Ivchenko, V.A. 87/88 (1995) 257
- Szabadi, M., see Kolomenskii, A.A. 86 (1995) 591
- Sze, S.M., see Chan, S.-H. 82/83 (1994) 85
- Szeles, Cs., see Hulett, Jr., L.D. 85 (1995) 334
- Sz r nyi, T., see K ntor, Z. 86 (1995) 196
- Sz r nyi, T., Z. K ntor and L.D. Laude, Atypical characteristics of KrF excimer laser ablation of indium-tin oxide films 86 (1995) 219
- Sz r nyi, T., see Geretovszky, Zs. 86 (1995) 494
- Sz r nyi, T., see Bali, K. 86 (1995) 500
- Szyszkowski, W., Melting and diffusion under nanosecond laser pulse 90 (1995) 325
- Tabbal, M., see Meunier, M. 86 (1995) 475
- Taguchi, Y., M. Dat , N. Takagi, T. Aruga and M. Nishijima, Chemical reactivity of the Si(111)($\sqrt{3} \times \sqrt{3}$)R30 -B surface: an electron-energy-loss spectroscopy study 82/83 (1994) 434
- Takada, T., see Mochizuki, Y. 82/83 (1994) 200
- Takagi, N., see Taguchi, Y. 82/83 (1994) 434
- Takahashi, I., M. Nakaji and H. Kawanishi, Migration and related buried epitaxy using digital epitaxial growth conditions 82/83 (1994) 70
- Takahashi, K., see Hirose, M. 85 (1995) 111
- Takahashi, N., see Ikeda, H. 82/83 (1994) 257
- Takakuwa, Y., see Enta, Y. 82/83 (1994) 327
- Takamiya, S., see Takemi, M. 82/83 (1994) 115
- Takamura, S., see Kanazawa, I. 85 (1995) 124
- Takamura, S., see Aruga, T. 85 (1995) 229
- Takasu, Y., see Sato, S. 90 (1995) 29
- Takemi, M., T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya, Microscopic analysis of interface structure in InGaAs/InP MQW using Pendell sung oscillation around a satellite peak in high-resolution X-ray diffraction 82/83 (1994) 115
- Takiguchi, T., K. Uesugi, M. Yoshimura and T. Yao, Atomic-scale modification of the AlCl₃-adsorbed Si(111)-7 \times 7 surface 82/83 (1994) 428
- Talwar, S., see Slaoui, A. 86 (1995) 346
- Tamir, S. and S. Berger, Laser induced deposition of nanocrystalline Si with preferred crystallographic orientation 86 (1995) 514
- Tammenmaa, M., see Lujala, V. 82/83 (1994) 34
- Tan, K.L., see Wee, A.T.S. 81 (1994) 377
- Tan, K.L., see Gr sj , L. 89 (1995) 21
- Tanaka, K., see Akinaga, H. 82/83 (1994) 298
- Tanaka, Y., H. Morishita, M. Watamori, K. Oura and I. Katayama, Structural study of SrTiO₃(100) surfaces by low energy ion scattering 82/83 (1994) 528
- Tang, Y.-Q., see Fang, Y. 89 (1995) 331
- Taniguchi, S., see Hongo, S. 82/83 (1994) 437
- Taniguchi, S., see Hongo, S. 82/83 (1994) 537
- Tanimoto, M., see Yokoyama, H. 82/83 (1994) 158
- Taranets, T.A., see Dmitruk, N.L. 90 (1995) 489
- Tarasik, M.I., see Fedotov, A.K. 84 (1995) 379
- Tasch, A., see Asami, S. 82/83 (1994) 359
- Tate, T.J., see Taverner, A.E. 90 (1995) 383
- Taverner, A.E., A. Gulino, R.G. Egdell and T.J. Tate, A photoemission study of electron states in Sb-ion implanted TiO₂(110) 90 (1995) 383
- Teghil, R., L. D'Alessio, G. De Maria and D. Ferro, Pulsed-laser deposition and characterization of TaC films 86 (1995) 190
- Teghil, R., A. Santagata, V. Marotta, S. Orlando, G. Pizzella, A. Giardini-Guidoni and A. Mele, Characterization of the plasma plume and of thin film epitaxially produced during laser ablation of SnSe 90 (1995) 505
- Tejedor, P. and P.S. Dom nguez, Surface kinetics and morphology of ArF laser-assisted etching of (113)A GaAs in a Cl₂ environment 89 (1995) 271
- Teng, C.-M., see Bajikar, S.S. 87/88 (1995) 438
- Teng, C.-M., see Larson, D.J. 87/88 (1995) 446
- Theiss, A., see Schulze, B. 87/88 (1995) 140
- Theiss, A., F. Okuyama and F.W. R llgen, Comparison of NFIM and FIM of polymer layers with tetracyanoethylene and benzene as image gases 87/88 (1995) 146
- Themlin, J.-M., see Shafeev, G.A. 86 (1995) 387
- Thim, G.P., see Baranauskas, V. 86 (1995) 398
- Thoenen, O., see Viville, P. 86 (1995) 411
- Thomas, K.K., see Carley, A.F. 81 (1994) 265
- Thompson, D.A., see LaPierre, R.R. 90 (1995) 437
- Thompson, L.T., see Lee, H.J. 89 (1995) 121
- Thomson, R.C. and M.K. Miller, The partitioning of substitutional solute elements during the tempering of martensite in Cr and Mo containing steels 87/88 (1995) 185

- Thurzo, I., E. Pincik, G. Papaioannou, P. Dimitrakis and N. Arpatzanis, Experimental study of passivating ion-beam-induced distributed energy levels in n-GaAs by hydrogen species from boiling water 90 (1995) 39
- Thuvander, M. and K. Stiller, Structure and chemistry of grain boundaries in Ni-16Cr-9Fe model materials 87/88 (1995) 251
- Tin, C.C., see Wee, A.T.S. 81 (1994) 377
- Tiong, K.K., see Mar, S.Y. 90 (1995) 497
- Titchener, K.J., see Smith, G.C. 90 (1995) 357
- Tochigi, M., see Nakayama, H. 82/83 (1994) 214
- Tokita, S., see Yoshikawa, A. 82/83 (1994) 316
- Tokumoto, H., see Mizutani, W. 87/88 (1995) 398
- Tolk, N.H., see Xu, J. 85 (1995) 49
- Tomitori, M., see Ashino, M. 87/88 (1995) 12
- Tomizuka, H. and A. Ayame, A graphical analysis of transient response curves at an early stage in SIMS depth profiling using a $^{133}\text{Cs}^+$ beam 89 (1995) 281
- Tonneau, D., J.E. Bourée and Y. Pauleau, Kinetics of laser thermal decomposition of trimethylamine alane 86 (1995) 488
- Tontegode, A.Ya. and F.K. Yusifov, Super-efficient diffusion of cesium atoms into rhenium covered by a 2D graphite film 90 (1995) 185
- Torresi, A., A. Scandurra and A. Licciardello, Evaluation of matrix effects in SIMS quantification of $\text{Al}_x\text{Ga}_{1-x}\text{As}$ /GaAs heterostructures: a SNMS approach 81 (1994) 259
- Tóth, A.L., see Bali, K. 86 (1995) 500
- Tóth, Z., see Kántor, Z. 86 (1995) 196
- Tóth, Z., see Piglmayer, K. 86 (1995) 484
- Towner, A., P.C. Rice-Evans and N. Shaw, A positron annihilation study of the formation of defect layers in cadmium mercury telluride 85 (1995) 315
- Toyoda, K., see Kumagai, H. 82/83 (1994) 481
- Tran, T.T. and S.A. Chambers, Auger and X-ray photoelectron diffraction in $\text{MgO}(001)$ 81 (1994) 161
- Trubnikov, D.N., see Mikhailov, V.A. 86 (1995) 64
- Tsuji, M., see Nishimura, Y. 89 (1995) 393
- Tsutsui, K., see Hwang, S.M. 82/83 (1994) 523
- Tulub, A.A., see Drozd, V.E. 82/83 (1994) 587
- Tumareva, T.A., V.A. Ivanov and T.S. Kirsanova, The investigation of the electron energy distribution and the structure of the thin films and microcrystals by field emission methods 87/88 (1995) 18
- Turner, N.H., see Schreifels, J.A. 84 (1995) 23
- Tutov, E.A. and A.A. Baev, Charge transfer processes in a- WO_3/Si heterostructure during electro- and photochromism 90 (1995) 303
- Twisten, I., see Li, B. 86 (1995) 577
- Tyrrell, G.C., T.H. York and I.W. Boyd, Characterisation of ionic species generated during ablation of $\text{Bi}_2\text{Sr}_2\text{Ca}_2\text{Cu}_3\text{O}_{10}$ by frequency-doubled Nd:YAG laser irradiation 86 (1995) 50
- Ueda, O., see Sakuma, Y. 82/83 (1994) 46
- Uesugi, K., T. Komura, M. Yoshimura and T. Yao, Scanning tunneling microscopy study of solid-phase epitaxy processes of amorphous silicon layers on silicon substrates 82/83 (1994) 367
- Uesugi, K., see Takiguchi, T. 82/83 (1994) 428
- Uhlmann, K., see Britton, D.T. 85 (1995) 158
- Ujita, H., see Nishimura, Y. 89 (1995) 393
- Ulrych, I., see Černý, R. 86 (1995) 359
- Umeno, M., see Soga, T. 82/83 (1994) 64
- Umlor, M.T., P. Asoka-Kumar, D.J. Keeble, P.W. Cooke and K.G. Lynn, Positron annihilation studies of defects in molecular beam epitaxy grown III-V layers 85 (1995) 295
- Unger, J., Yu.A. Vlasov and N. Ernst, Probe hole field electron/field ion microscopy and energy spectroscopy of ultrasharp [111]-oriented tungsten tips 87/88 (1995) 45
- Urano, T., see Hongo, S. 82/83 (1994) 437
- Urano, T., see Hongo, S. 82/83 (1994) 537
- Urisu, T., see Sato, S. 90 (1995) 29
- Usui, A., see Mochizuki, Y. 82/83 (1994) 200
- Usui, A., see Sasaoka, C. 82/83 (1994) 348
- Utraiainen, M., see Rautanen, J. 82/83 (1994) 553
- Uwai, K. and N. Kobayashi, Real time observation of surface dielectric responses of GaAs(001) using surface photo-absorption 82/83 (1994) 290
- Vaara, T., see Vaari, J. 81 (1994) 289
- Vaara, T., J. Lahtinen and P. Hautojärvi, Reactions of CO and NO on Mg promoted cobalt 89 (1995) 103
- Vaari, J., T. Vaara, J. Lahtinen and P. Hautojärvi, Adsorption of CO on Mg-promoted Co(poly) 81 (1994) 289
- Väkeväinen, K., see Ahlgren, T. 90 (1995) 419
- Valla, T., P. Pervan and M. Milun, Interaction of oxygen and silver on the V(100) surface 89 (1995) 375
- Van Bakel, G.P.E.M., K. Hariharan and D.N. Seidman, On the structure and chemistry of Ni_3Al on an atomic scale via atom-probe field-ion microscopy 90 (1995) 95
- Van de Leest, R.E., UV photo-annealing of thin sol-gel films 86 (1995) 278
- Van der Vleuten, W.C., see Hopkins, J. 84 (1995) 299
- Van Hardeveld, R.M., P.L.J. Gunter, L.J. van IJzendoorn, W. Wieldraaijer, E.W. Kuipers and J.W. Niemantsverdriet, De-

- position of inorganic salts from solution on flat substrates by spin-coating: theory, quantification and application to model catalysts 84 (1995) 339
- Van Hoecke, T., see Segers, D. 85 (1995) 172
- Van IJzendoorn, L.J., see Van Hardeveld, R.M. 84 (1995) 339
- Van Kooten, W.E.J., J.P.C. van Nispen, O.L.J. Gijzeman and J.W. Geus, The reactivity of O_2/H_2 , O_2/CO and O_2/C_3H_6 gas mixtures on Cu(111) 90 (1995) 137
- Van Nispen, J.P.C., see Van Kooten, W.E.J. 90 (1995) 137
- Van Veen, A., see Seijbel, L.J. 85 (1995) 92
- Van Veen, A., H. Schut, M. Clement, J.M.M. de Nijs, A. Kruseman and M.R. Ijpma, VEPFIT applied to depth profiling problems 85 (1995) 216
- Van Veen, A., see Schut, H. 85 (1995) 225
- Van Veen, A., see Hakvoort, R.A. 85 (1995) 271
- Van Wijk, R., P.C. Görts, A.J.M. Mens, O.L.J. Gijzeman, F.H.P.M. Habraken and J.W. Geus, XPS/NRA investigations of particle size effects during the oxidation of Cu particles supported on oxidised Si(100) 90 (1995) 261
- Vancu, A., see Ionescu, R. 84 (1995) 291
- Varela, M., see Palau, J. 86 (1995) 59
- Varela, M., see Queralt, X. 86 (1995) 95
- Vasumathi, D., G. Amarendra, K.F. Canter and A.P. Mills, Jr., Installation of a Kr moderator in the high-brightness beam at Brandeis 85 (1995) 154
- Vasumathi, D., see Canter, K.F. 85 (1995) 339
- Vavassori, P., L. Callegaro and E. Puppini, Ultraviolet inverse photoemission study of the oxidation of YFe_2 89 (1995) 93
- Vega, F., see Gonzalo, J. 86 (1995) 40
- Veith, M., see Piscevic, D. 90 (1995) 425
- Velikevitch, S.P., see Berjeza, N.A. 86 (1995) 303
- Velotta, R., see Amoruso, S. 86 (1995) 35
- Venkateswarlu, D.S., see Sil, A. 81 (1994) 469
- Verbeeck, R., see Donaton, R.A. 89 (1995) 221
- Vergnat, M., see Hadj Zoubir, N. 89 (1995) 35
- Vettrivel, R., R. Yamauchi, H. Yamano, M. Kubo, A. Miyamoto and T. Ohta, Steric and electronic interactions between source gas and substrate surface during the Al-CVD/Al selective epitaxy process as investigated by quantum chemical calculations 82/83 (1994) 516
- Vettrivel, R., see Himei, H. 82/83 (1994) 543
- Vettrivel, R., see Kubo, M. 82/83 (1994) 559
- Vettrivel, R., see Kubo, M. 89 (1995) 131
- Vickerman, J.C., see Leggett, G.J. 84 (1995) 253
- Vijayakrishnan, V., see Rao, C.N.R. 84 (1995) 285
- Villatte, M., see Fauquet, C. 81 (1994) 435
- Vitek, J.M., see Babu, S.S. 87/88 (1995) 207
- Vitel, Y., see Flicstein, J. 86 (1995) 286
- Viville, P., O. Thoelen, S. Beauvois, R. Lazzaroni, G. Lambin, J.L. Brédas, K. Kolev and L. Laude, Thin films of polymer blends: surface treatment and theoretical modeling 86 (1995) 411
- Vladimirov, V.V. and P.V. Poritsky, On the theory of ion current onset delay in liquid metal ion sources 87/88 (1995) 106
- Vladimirov, V.V., V.N. Gorshkov and D.V. Mozyrsky, The dynamical effects in liquid-metal ion sources 87/88 (1995) 112
- Vlasov, Yu.A., see Unger, J. 87/88 (1995) 45
- Vodolaga, B.K., see Pimenov, S.M. 86 (1995) 208
- Von Känel, H., see Kafader, U. 90 (1995) 297
- Vook, R.W., see Jo, B.H. 89 (1995) 237
- Voss, C. and N. Kruse, Field ion microscopy during an oscillating surface reaction: NO/H_2 on Pt 87/88 (1995) 127
- Voss, C. and N. Kruse, Reaction-induced morphological changes of field emitter tips: NO on Rh and Pt 87/88 (1995) 134
- Vošta, J., see Pingo, M. 90 (1995) 373
- Vydra, V., see Černý, R. 86 (1995) 359
- Wada, K., Defects and material processing in compound semiconductors 85 (1995) 246
- Waeber, W.B., see Gerola, D. 85 (1995) 106
- Waeber, W.B., see Shi, M. 85 (1995) 143
- Wagner, F.X., see Dyer, P.E. 86 (1995) 18
- Wagner, F.X., K. Dhese, P.H. Key, D. Sands, S.R. Jackson, R. Kirbitson and J.E. Nicholls, Photo-luminescence of pulsed excimer laser annealed Sb-implanted CdTe 86 (1995) 364
- Wallace, S., see Hulett, Jr., L.D. 85 (1995) 334
- Wang, F., M. Badaye, K. Ogawa and T. Morishita, Recovery and recrystallization of $SrTiO_3(100)$ surface characterized by ion channeling 90 (1995) 123
- Wang, J., X. Fei, Z. Yu and G. Zhao, Laser-induced selective deposition of Ni-P alloy on silicon 84 (1995) 383
- Wang, P., see Durrer, W.G. 81 (1994) 215
- Wang, P.W., L.P. Zhang, L. Lu, D.V. LeMone and D.L. Kinser, Surface modification of lead silicate glass under X-ray irradiation 84 (1995) 75
- Wang, P.W., S. Bader, L.P. Zhang, M. Ascherl and J.H. Craig, Jr., XPS investigation of electron beam effects on a trimethylsilane dosed Si(100) surface 90 (1995) 413
- Wang, R., see Gu, S. 81 (1994) 431
- Wang, T., see Fang, Y. 89 (1995) 331
- Wang, X.D., see Sakurai, T. 87/88 (1995) 405
- Wang, X.K., N.F. Shen, Z.S. Yang and H.C. Gu, Activation treatments and surface study of amorphous $Fe_{90}Zr_{10}$ and $Fe_{87.8}Zr_{10}Co_2Al_{0.2}$ catalysts 89 (1995) 297

- Wang, Y., see Chen, X. 89 (1995) 169
- Wanklyn, B.M., see Sharma, K.K. 81 (1994) 251
- Wanklyn, B.M., see Jain, A. 84 (1995) 65
- Washio, M., see Hirose, M. 85 (1995) 111
- Watanori, M., M. Naitoh, H. Morioka, Y. Maeda and K. Oura, Low temperature adsorption of hydrogen on Si(111) and (100) surfaces studied by elastic recoil detection analysis 82/83 (1994) 417
- Watanori, M., see Tanaka, Y. 82/83 (1994) 528
- Watanabe, H., see Asahi, H. 82/83 (1994) 109
- Watanabe, T., see Hirai, M. 82/83 (1994) 23
- Watanabe, T., see Sakuraba, M. 82/83 (1994) 354
- Watanabe, Y., F. Maeda and M. Oshima, Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001) 82/83 (1994) 136
- Watanabe, Y., see Maeda, F. 82/83 (1994) 276
- Watanabe, Y., see Heun, S. 82/83 (1994) 507
- Watts, J.F., see Salvi, A.M. 90 (1995) 333
- Way, J.D., see George, S.M. 82/83 (1994) 460
- Weaver, L., see Lawther, D.W. 85 (1995) 265
- Wee, A.T.S., Z.C. Feng, H.H. Hng, K.L. Tan, C.C. Tin, R. Hu and R. Coston, Surface chemical states on 3C-SiC/Si epilayers 81 (1994) 377
- Wehner, M., see Pflüger, S. 86 (1995) 504
- Wei, R.P., see Dwyer, D.J. 81 (1994) 229
- Wei, Y., see Zhang, X.Q. 84 (1995) 267
- Wei, Y., see Yang, X.-M. 90 (1995) 175
- Weir, B.E., D.J. Eaglesham, L.C. Feldman, H.S. Luftman and R.L. Headrick, Electron microscopy of the ordered boron 2×1 structure buried in crystalline silicon 84 (1995) 413
- Weiss, A.H., see Fazleev, N.G. 85 (1995) 22
- Weiss, A.H., see Fazleev, N.G. 85 (1995) 26
- Weiss, A.H., see Yang, G. 85 (1995) 77
- Weiss, A.H., S. Yang, H.Q. Zhou, E. Jung, A.R. Koymen, S. Naidu, G. Brauer and M.J. Puska, Method for the measurement of positron affinities and positron work functions suitable for both positive and negative work function materials 85 (1995) 82
- Weissmantel, S., see Reisse, G. 86 (1995) 107
- Weissmantel, S., see Reisse, G. 86 (1995) 114
- Welch, D.O., see Ghosh, V.J. 85 (1995) 210
- Weng, H., see Ling, C.C. 85 (1995) 305
- Weng, L.T., P. Bertrand, G. Lalande, D. Guay and J.P. Dodelet, Surface characterization by time-of-flight SIMS of a catalyst for oxygen electroreduction: pyrolyzed cobalt phthalocyanine-on-carbon black 84 (1995) 9
- Wesemann, J., G. Frommeyer and M. Kreuss, APFIM investigations on ordered γ -TiAl using single-layer detection method 87/88 (1995) 179
- Wesley, S.A., see Canter, K.F. 85 (1995) 339
- Wesner, D.A., see Klotzbücher, T. 86 (1995) 165
- Wesner, D.A., see Kreutz, E.W. 86 (1995) 266
- Wesner, D.A., see Frerichs, H. 86 (1995) 405
- West, R.H., see Smith, G.C. 90 (1995) 357
- Wetzel, P., see Hong, S. 90 (1995) 65
- White, J.M., see Asami, S. 82/83 (1994) 359
- Wieldraaijer, W., see Van Hardeveld, R.M. 84 (1995) 339
- Wijekoon, W.M.K.P., E.W. Koenig, W.M. Hetherington III and W.R. Salzman, Waveguide CARS spectroscopy of physisorbed methanol on a partially hydroxylated zinc oxide surface 81 (1994) 347
- Winkler, A., see Karstens, H. 86 (1995) 521
- Wise, M.L., see Okada, L.A. 82/83 (1994) 410
- Wise, M.L., see George, S.M. 82/83 (1994) 460
- Wissenbach, K., see Kreutz, E.W. 86 (1995) 310
- Wolff-Rottke, B., see Ihlemann, J. 86 (1995) 228
- Wolff-Rottke, B., see Ihlemann, J. 86 (1995) 245
- Wolfram, Z., see Duś, R. 90 (1995) 277
- Wollenberger, H., see Al-Kassab, T. 87/88 (1995) 329
- Wolter, J.H., see Hopkins, J. 84 (1995) 299
- Wong, P.C., Y.S. Li and K.A.R. Mitchell, Investigations of the interface between magnesium and polyethyleneterephthalate by X-ray photoelectron spectroscopy 84 (1995) 245
- Wong, P.C., Y.S. Li, M.Y. Zhou and K.A.R. Mitchell, XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. I. Hydrogen treatments on a 10 Å thick film 89 (1995) 255
- Wong, P.C., see Li, Y.S. 89 (1995) 263
- Woods, R., see Buckley, A.N. 84 (1995) 223
- Wu, C.Z., see Wu, J.D. 90 (1995) 81
- Wu, J., S. Li, G. Li, C. Li and Q. Xin, FT-IR investigation of methane adsorption on silica 81 (1994) 37
- Wu, J.D., C.Z. Wu, Z.M. Song, L.H. Wu and F.M. Li, Synthesis of molybdenum nitride γ -Mo₂N by multipulse laser irradiation of molybdenum in nitrogen 90 (1995) 81
- Wu, L.H., see Wu, J.D. 90 (1995) 81
- Wu, N.J., see Zomorrodian, A. 90 (1995) 343
- Wu, S. and D. Haneman, Cadmium selenide-amorphous hydrogenated silicon heterostructures 89 (1995) 289
- Wysocki, T., see Bryl, R. 87/88 (1995) 69
- Xiao, D., see Yang, X.-M. 90 (1995) 175
- Xiao, X.R., Y. Lin, Y. Yang, X.G. Chen and J.K. You, Scanned laser spot photocurrent response studies of surface modifications of CdSe thin film electrodes 90 (1995) 321
- Xie, L., see Jiang, S. 84 (1995) 373
- Xie, R., see Canter, K.F. 85 (1995) 339
- Xin, Q., see Wu, J. 81 (1994) 37

- Xin, X.Q., see Ye, X.R. 89 (1995) 151
- Xu, J., L.D. Hulet, Jr., T.A. Lewis and N.H. Tolk, Light emission from polymers under positron and electron bombardment 85 (1995) 49
- Xu, J., see Ling, C.C. 85 (1995) 305
- Xu, J., see Hulet, Jr., L.D. 85 (1995) 334
- Xue, G., see Ji, G. 81 (1994) 63
- Xue, G., see Guo, S. 84 (1995) 351
- Xue, G., J. Ding and P. Cheng, Growth of a surface film on copper from benzotriazole solutions 89 (1995) 77
- Xue, Q., T. Hashizume, J.M. Zhou, T. Sakata and T. Sakurai, MBE-STM study of the Ga-rich 4×2 phase of the GaAs(001) surface 87/88 (1995) 364
- Xue, Q.K., see Hashizume, T. 87/88 (1995) 373
- Yago, H., T. Nomura and K. Ishikawa, Strain relaxation in GaAs islands on GaP(001) 84 (1995) 119
- Yakubtsov, O.A., see Dmitruk, N.L. 90 (1995) 489
- Yamada, M., see Ide, Y. 82/83 (1994) 310
- Yamada, M., see Sasaki, M. 82/83 (1994) 387
- Yamaguchi, H., Y. Homma and Y. Horikoshi, In-situ monitoring of 1st-order phase transition on InAs(001) surfaces by scanning electron surface microscopy 82/83 (1994) 223
- Yamaguchi, M., see Shirai, Y. 85 (1995) 138
- Yamaguchi, S., see Kawasuso, A. 85 (1995) 280
- Yamaguchi, Y., see Nagasawa, H. 82/83 (1994) 405
- Yamamoto, M., see Otake, S. 82/83 (1994) 263
- Yamamoto, M., K. Nishikawa and T. Nishiuuchi, Quantitative analysis of individual atom images in FIM of an ordered Ni_4Mo alloy 87/88 (1995) 291
- Yamamoto, R., see Oshima, N. 85 (1995) 329
- Yamamoto, T., see Nunogaki, M. 85 (1995) 132
- Yamamoto, Y., see Ohnishi, H. 82/83 (1994) 444
- Yamamoto, Y., see Itoh, Y. 85 (1995) 165
- Yamano, H., see Vetrivel, R. 82/83 (1994) 516
- Yamashita, M., see Suda, Y. 82/83 (1994) 332
- Yamauchi, R., see Vetrivel, R. 82/83 (1994) 516
- Yamauchi, R., see Kubo, M. 82/83 (1994) 559
- Yamauchi, R., see Kubo, M. 89 (1995) 131
- Yamazaki, T., see Suzuki, R. 85 (1995) 87
- Yan, P. and S.-Z. Yang, Pulse plasma beam deposition of cubic boron nitride films on GCr15 steel bearing substrate at room temperature 90 (1995) 149
- Yanagisawa, Y., Oxygen exchange between adsorbed NO and MgO surfaces 89 (1995) 251
- Yanchenko, A.M., see Fedotov, A.K. 84 (1995) 379
- Yang, G., J.H. Kim, S. Yang and A.H. Weiss, Adsorption site identification for oxygen molecules on Au/Si(100) by positron annihilation induced Auger electron spectroscopy (PAES) 85 (1995) 77
- Yang, S., see Yang, G. 85 (1995) 77
- Yang, S., see Weiss, A.H. 85 (1995) 82
- Yang, S.-J., see Li, C. 81 (1994) 465
- Yang, S.-Z., see Yan, P. 90 (1995) 149
- Yang, W.Y., see Zhang, X.Q. 84 (1995) 267
- Yang, X.-M., D. Xiao, Z.-H. Lu and Y. Wei, Structural investigation of Langmuir-Blodgett monolayers of L- α -dipalmitoylphosphatidylcholine by atomic force microscopy 90 (1995) 175
- Yang, Y., see Xiao, X.R. 90 (1995) 321
- Yang, Z.S., see Wang, X.K. 89 (1995) 297
- Yao, J.N., see Loo, B.H. 81 (1994) 175
- Yao, T., see Uesugi, K. 82/83 (1994) 367
- Yao, T., see Takiguchi, T. 82/83 (1994) 428
- Yasuda, T., see Hata, K. 87/88 (1995) 117
- Yates, Jr., J.T., A. Hübner, S.R. Lucas, W.D. Partlow, J. Schaefer and W.J. Choyke, Activation of the Ga-CH₃ bond using atomic hydrogen - a possible route to III-V semiconductor films with low carbon levels 82/83 (1994) 180
- Ye, X.R., H.W. Hou, X.Q. Xin and C.F. Hammer, M-S (M = Mo, W) cluster compound films on copper surfaces 89 (1995) 151
- Yelon, A., see Meunier, M. 86 (1995) 475
- Yen, J.C., see Keller, B.P. 82/83 (1994) 126
- Yen, R.-B., see Li, C. 81 (1994) 465
- Yeom, H.W., see Sasaki, M. 82/83 (1994) 387
- Yokoyama, H., M. Tanimoto, M. Shinohara and N. Inoue, Self-limiting and step-propagating nature of GaAs atomic layer epitaxy revealed by atomic force microscopy 82/83 (1994) 158
- Yokoyama, N., see Sakuma, Y. 82/83 (1994) 46
- Yokoyama, N., see Sakuma, Y. 82/83 (1994) 239
- Yokoyama, S., see Keil, M. 90 (1995) 377
- Yom, S.S., see Kim, T.W. 90 (1995) 75
- Yonezawa, Y., see Masuda, A. 81 (1994) 277
- Yoon, Y.S., see Kim, T.W. 90 (1995) 75
- York, T.H., see Tyrrell, G.C. 86 (1995) 50
- Yoshida, I., H. Furukawa, T. Hirose and M. Nakao, Fabrication of CuO₂-plane-based high-temperature superconducting thin films by atomic layer controlled molecular beam epitaxy 82/83 (1994) 501
- Yoshida, S. and M. Sasaki, Investigation of a GaN surface structure for the mask of GaAs selective growth using MOMBE 82/83 (1994) 28
- Yoshida, S., see Sasaki, M. 82/83 (1994) 269
- Yoshida, S. and H. Ishida, An investigation of the thermal stability of undecylimidazole on copper by FT-IR reflection-absorption spectroscopy 89 (1995) 39
- Yoshikawa, A., M. Kobayashi and S. Tokita, Surface reaction mechanism in

- MOMBE-ALE of ZnSe and CdSe as determined by a new in-situ optical probing method 82/83 (1994) 316
- Yoshimura, M., see Uesugi, K. 82/83 (1994) 367
- Yoshimura, M., see Takiguchi, T. 82/83 (1994) 428
- Yoshino, J., see Kano, N. 82/83 (1994) 132
- You, J.K., see Xiao, X.R. 90 (1995) 321
- You, X.Z., see Zhang, X.Q. 84 (1995) 267
- Yu, H., M.G. Huber and F.W. Froben, Laser ablation of refractory material, cluster formation and deposition 86 (1995) 74
- Yu, W., see Sullivan, J.L. 90 (1995) 309
- Yu, Z., see Wang, J. 84 (1995) 383
- Yurov, V., see Sakurai, T. 87/88 (1995) 405
- Yusifov, F.K., see Tontegode, A.Ya. 90 (1995) 185
- Zemek, J., see D'Anna, E. 86 (1995) 170
- Zhang, J.-Y., see Esrom, H. 86 (1995) 202
- Zhang, L.P., see Wang, P.W. 84 (1995) 75
- Zhang, L.P., see Wang, P.W. 90 (1995) 413
- Zhang, R., see Gu, S. 81 (1994) 431
- Zhang, X.Q., W.Y. Yang, X.Z. You and Y. Wei, Preparation and characterization of self-assembly organic multilayer films on silica surface 84 (1995) 267
- Zhao, G., see Wang, J. 84 (1995) 383
- Zhao, R., see Holt, S.A. 84 (1995) 125
- Zhao, X., see Jiang, S. 84 (1995) 373
- Zhdanov, V.P. and P.R. Norton, Nucleation during molecular beam epitaxy 81 (1994) 109
- Zhdanov, V.P., see Kasza, R.V. 84 (1994) 97
- Zheng, Y., see Gu, S. 81 (1994) 431
- Zherikhin, A.N., see Sobol, E.N. 90 (1995) 235
- Zhirnov, V.V., see Givargizov, E.I. 87/88 (1995) 24
- Zhong, P., see Gu, S. 81 (1994) 431
- Zhou, H.Q., see Weiss, A.H. 85 (1995) 82
- Zhou, J.M., see Xue, Q. 87/88 (1995) 364
- Zhou, M.Y., see Wong, P.C. 89 (1995) 255
- Zhu, Y., see Canter, K.F. 85 (1995) 339
- Zielasek, V., A. Büssenschütt and M. Henzler, Multiple losses in off-specular electron energy loss spectra of thin NaCl films individually resolved in energy and momentum 90 (1995) 117
- Zimmermann, U., see Shi, M. 85 (1995) 143
- Zomorrodian, A., A. Mesarwi, N.J. Wu and A. Ignatiev, XPS oxygen line broadening in lead zirconium titanate and related materials 90 (1995) 343
- Zotov, A.V., see Khramtsova, E.A. 82/83 (1994) 576
- Zou, H., G.M. Hood, R.J. Schultz and J.A. Roy, Thermal etching of α -Zr single-crystal surfaces 90 (1995) 59
- Zurita, L., see Durán, J.D.G. 81 (1994) 1



ELSEVIER

Applied Surface Science MI 81-90 (1995) 33-115

applied
surface science

Subject index to volumes 81-90

Ablation

- The laser ablation threshold of $\text{YBa}_2\text{Cu}_3\text{O}_{6+x}$ as revealed by using projection optics, B. Dam, J. Rector, M.F. Chang, S. Kars, D.G. de Groot and R. Griessen 86 (1995) 13
- Blast-wave studies of excimer laser ablation of ZnS, P.E. Dyer, P.H. Key, D. Sands, H.V. Snelling and F.X. Wagner 86 (1995) 18
- Pulsed laser ablation of copper, R. Jordan, D. Cole, J.G. Lunney, K. Mackay and D. Givord 86 (1995) 24
- Why are high- T_c superconductors, HTSC, deposited by 248 nm lasers at 400 MW/cm^2 ?, R.W. Dreyfus 86 (1995) 29
- Time of flight mass spectrometry and covariance mapping technique investigation of charged specie evolution in $\text{Pb}(\text{Ti}_{0.48}\text{Zr}_{0.52})\text{O}_3$ laser ablation, S. Amoruso, V. Berardi, N. Spinelli, R. Velotta, M. Armenante, F. Fusco, M. Allegrini and E. Arimondo 86 (1995) 35
- Plasma properties and stoichiometry of laser-deposited BiSrCaCuO thin films, J. Gonzalo, C.N. Afonso, F. Vega, D. Martínez García and J. Perrière 86 (1995) 40
- Laser ablation of BiSrCaCuO superconducting thin film: analysis of intermediate species in real time, U. Gambardella, A. Giardini, V. Marotta, A. Morone, S. Orlando and M. Snels 86 (1995) 45
- Characterisation of ionic species generated during ablation of $\text{Bi}_2\text{Sr}_2\text{Ca}_2\text{Cu}_3\text{O}_{10}$ by frequency-doubled Nd:YAG laser irradiation, G.C. Tyrrell, T.H. York and I.W. Boyd 86 (1995) 50
- Laser wavelength dependence of $\text{YBa}_2\text{Cu}_3\text{O}_y$ laser ablation plumes, J. Palau, M. Sowinska, M. Varela, P. Summ, J. Esteve, P. Serra, J.L. Morenza and J.A. Miehe 86 (1995) 59
- Study of $\text{PbTe}(\text{Ga})$ evaporation using a nanosecond pulsed laser, V.A. Mikhailov, F.N. Putilin and D.N. Trubnikov 86 (1995) 64
- Composition and gas dynamics of laser ablated AlN plumes, T.M. Di Palma, S. Orlando, A. Giardini-Guidoni, A.J. Paul, J.W. Hastie and A. Mele 86 (1995) 68
- Laser ablation of refractory material, cluster formation and deposition, H. Yu, M.G. Huber and F.W. Froben 86 (1995) 74
- Pulsed laser deposition of metal and metal multilayer films, J.G. Lunney 86 (1995) 79
- Laser deposition of metallic alloys and multilayers, H.-U. Krebs, S. Fähler and O. Bremert 86 (1995) 86
- Comparison of the structure of laser deposited and sputtered metallic alloys, H.-U. Krebs, O. Bremert, M. Störmer and Y. Luo 86 (1995) 90
- Erbium oxide thin films on Si(100) obtained by laser ablation and electron beam evaporation, X. Queralt, C. Ferrater, F. Sánchez, R. Aguiar, J. Palau and M. Varela 86 (1995) 95
- Effects of laser wavelength and fluence on the growth of ZnO thin films by pulsed laser deposition, V. Craciun, S. Amirhaghi, D. Craciun, J. Elders, J.G.E. Gardeniers and I.W. Boyd 86 (1995) 99
- Influence of ion bombardment on the refractive index of laser pulse deposited oxide films, G. Reisse, S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz 86 (1995) 107
- Influence of LN_2 substrate cooling on optical properties of laser-pulse-deposited oxide films, G. Reisse, S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz 86 (1995) 114
- Excimer laser sputtering deposition of TiO_2 optical coating for solar cells, H.-A. Durand, J.-H. Brimaud, O. Hellman, H. Shibata, S. Sakuragi, Y. Makita, D. Gesbert and P. Meyrueis 86 (1995) 122

- SiO₂ film deposition by XeCl laser ablation of fused silica, P. Baeri, R. Reitano and N. Marino 86 (1995) 128
- SEM observations of YBCO on as-received and heat-treated MgO substrates, S. King, L. Coccia and I.W. Boyd 86 (1995) 134
- Pulsed laser deposition and nanometer scale characterization of YBa₂Cu₃O_{7-δ} thin films by scanning probe methods, R. Sum, H.P. Lang and H.-J. Güntherodt 86 (1995) 140
- Structural properties of LiNbO₃ thin films grown by the pulsed laser deposition technique, P. Aubert, G. Garry, R. Bisaro and J. Garcia Lopez 86 (1995) 144
- Pulsed laser deposition of epitaxial layers of ZnSe, J.L. Deiss, A. Chergui, L. Koutti, J.L. Loison, M. Robino and J.B. Grun 86 (1995) 149
- Pulsed laser deposition of NbTe_x thin films, F. Grangeon, H. Sassoli, Y. Mathey, M. Autric, D. Pailharey and W. Marine 86 (1995) 160
- Structure and chemical composition of BN thin films grown by pulsed-laser deposition (PLD), T. Klotzbücher, W. Pfleging, M. Mertin, D.A. Wesner and E.W. Kreutz 86 (1995) 165
- Excimer laser reactive ablation deposition of silicon nitride films, E. D'Anna, G. Leggieri, A. Luches, M. Martino, A. Perrone, G. Majni, P. Mengucci, R. Alexandrescu, I.N. Mihailescu and J. Zemek 86 (1995) 170
- Si_{1-x}Ge_x thin films deposited by the pulsed excimer laser ablation technique, F. Antoni, E. Fogarassy, C. Fuchs, B. Prévot and J.P. Stoquert 86 (1995) 175
- Effect of laser power density and deposition temperature on electrical and optical properties of pulsed laser ablated diamond-like carbon films, J. Levoska and S. Leppävuori 86 (1995) 180
- Pulsed-laser deposition and characterization of TaC films, R. Teghil, L. D'Alessio, G. De Maria and D. Ferro 86 (1995) 190
- Optodynamic aspect of a pulsed laser ablation process, R. Hrovatin and J. Možina 86 (1995) 213
- Atypical characteristics of KrF excimer laser ablation of indium-tin oxide films, T. Szörényi, Z. Kántor and L.D. Laude 86 (1995) 219
- Excimer laser ablation of Nd:YAG and Nd:glass, S.R. Jackson, W.J. Metheringham and P.E. Dyer 86 (1995) 223
- Excimer laser ablation patterning of dielectric layers, J. Ihlemann and B. Wolff-Rottke 86 (1995) 228
- Ablation of nylon-6,6 with UV and IR lasers, C.D. Skordoulis, M. Makropoulou and A.A. Serafetinides 86 (1995) 239
- Structuring of polyimide-metal carbide layer systems by excimer laser ablation, J. Ihlemann, B. Wolff-Rottke, G. Danev, K. Petkov and E. Spassova 86 (1995) 245
- Combination of excimer laser micromachining and replication processes suited for large scale production, J. Arnold, U. Dasbach, W. Ehrfeld, K. Hesch and H. Löwe 86 (1995) 251
- Laser-assisted dry etching ablation of InP, J.J. Dubowski, A. Compaan and M. Prasad 86 (1995) 548
- Deposition by laser ablation and characterization of titanium dioxide films on polyethylene-terephthalate, N. Lobstein, E. Millon, A. Hachimi, J.F. Muller, M. Alnot and J.J. Ehrhardt 89 (1995) 307
- Tantalum oxide film formation by excimer laser ablation, Y. Nishimura, H. Ujita and M. Tsuji 89 (1995) 393
- Macro-particle ejection by laser ablation of high-temperature superconductors, E.N. Sobol, M.S. Kitai, S.M. Gol'berg and A.N. Zherikhin 90 (1995) 235
- Characterization of the plasma plume and of thin film epitaxially produced during laser ablation of SnSe, R. Teghil, A. Santagata, V. Marotta, S. Orlando, G. Pizzella, A. Giardini-Guidoni and A. Mele 90 (1995) 505
- ### Alkali halides
- Origin of residual stress in a textured Au thin film on a LiF substrate, N. Durand, K.F. Badawi, A. Declemy and Ph. Goudeau 81 (1994) 119
- Temperature dependence of surface charging of NaCl under electron irradiation: role of secondary electron emission, W.G. Durrer, M. Portillo, P. Wang and D.P. Russell 81 (1994) 215
- Multiple losses in off-specular electron energy loss spectra of thin NaCl films individually resolved in energy and momentum, V. Zielasek, A. Büssenschütt and M. Henzler 90 (1995) 117
- ### Alkali metals
- The adsorption of sodium dodecyl sulphate on fluorite and its surface free energy, B. Jańczuk, M.L. González-Martín and J.M. Bruque 81 (1994) 95

- Temperature dependence of surface charging of NaCl under electron irradiation: role of secondary electron emission, W.G. Durrer, M. Portillo, P. Wang and D.P. Russell 81 (1994) 215
- XPS investigation of lithium borate glass and the Li/LiBO₂ interface, D.A. Hensley and S.H. Garofalini 81 (1994) 331
- LiBr on Si(111): an X-ray standing wave measurement, Th. Gog, G.C. Follis and S.M. Durbin 81 (1994) 485
- Adsorption and desorption of H₂O on potassium precovered Si(100)2 × 1 surface, S. Hongo, S. Taniguchi, K. Ojima, T. Urano and T. Kanaji 82/83 (1994) 437
- The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen 82/83 (1994) 553
- Evidence for infrared absorption enhancement of species at the lithium metal/electrolytic solution interface, Y. Suzuki, K. Sagisaka and A. Hatta 84 (1995) 1
- Theoretical study of the positron surface state at an alkali-metal surface, N.G. Fazleev, J.L. Fry, K. Kuttler and A.H. Weiss 85 (1995) 22
- Study of positron surface states on the alkali-metal-covered transition-metal surface, N.G. Fazleev, J.L. Fry, K. Kuttler, A.R. Koymen and A.H. Weiss 85 (1995) 26
- Structural properties of LiNbO₃ thin films grown by the pulsed laser deposition technique, P. Aubert, G. Garry, R. Bisaro and J. Garcia Lopez 86 (1995) 144
- A FEM study of liquid lithium on a <011>-oriented tungsten tip, K. Hata, M. Kumamura, T. Yasuda, Y. Saito and A. Ohshita 87/88 (1995) 117
- Scanning tunneling microscopy study of the (3 × 1) reconstruction induced by Li adsorption on the Si(111) surface, R.Z. Bakhtizin, C. Park, T. Hashizume and T. Sakurai 87/88 (1995) 347
- A graphical analysis of transient response curves at an early stage in SIMS depth profiling using a ¹³³Cs⁺ beam, H. Tomizuka and A. Ayame 89 (1995) 281
- Influence of surface charge on thermal positive ion emission from potassium bromide, M.F. Butman, J. Nakamura, S. Kamidoi and H. Kawano 89 (1995) 323
- Superefficient diffusion of cesium atoms into rhenium covered by a 2D graphite film, A.Ya. Tontegode and F.K. Yusifov 90 (1995) 185
- An XPS study of the optimum loading of barium on high-silica MFI zeolite, M.H. Mohamed, M.M. Abdillahi, N.M. Abbas and A.B. Siddiqui 90 (1995) 409
- SIMS investigation of the Si(111) oxidation promoted by potassium overlayers, B. Lamontagne, F. Semond, A. Adnot and D. Roy 90 (1995) 447
- ### Alloys
- Sulfur segregation in titanium and selected titanium alloys, R.A. Outlaw, W.S. Lee, S.J. Hoekje and S.N. Sankaran 81 (1994) 143
- Surface segregation study of Ib-VIII single-crystal alloys, F. Reniers, M.P. Delplancke, A. Asskali, M. Jardinier-Offergeld and F. Bouillon 81 (1994) 151
- Matrix factors affecting quantitative analysis of AES for binary alloys, H. Bubert and R.P.H. Garten 81 (1994) 203
- Surface enrichment of niobium on Inconel 718 (100) single crystals, D.J. Dwyer, X.J. Pang, M. Gao and R.P. Wei 81 (1994) 229
- The effect of cyclic oxidation-reduction pretreatments on an amorphous Ni₈₀P₂₀ catalyst: an XPS/UPS/ISS study, J. Deng, H. Chen, X. Bao and M. Muhler 81 (1994) 341
- Configurational atomic ordering caused by stochastic adsorption processes in MBE-grown alloy semiconductors, H. Nakayama, M. Tochigi, H. Maeda and T. Nishino 82/83 (1994) 214
- Synthesis of oxide superalloys by ML-ALE method, V.E. Drozd, A.A. Tulub, V.B. Aleskovski and D.V. Korol'kov 82/83 (1994) 587
- Surface alloy formation in Pd/Ag, Cu/Au and Ni/Au bimetallic overlayers, A.K. Santra and C.N.R. Rao 84 (1995) 347
- Laser-induced selective deposition of Ni-P alloy on silicon, J. Wang, X. Fei, Z. Yu and G. Zhao 84 (1995) 383
- Composition of sputtered material from Cu-Ni alloy during Xe⁺ ion sputtering at elevated temperatures, S. Sekine, H. Shimizu and S. Ichimura 84 (1995) 401
- Laser deposition of metallic alloys and multilayers, H.-U. Krebs, S. Fähler and O. Bremert 86 (1995) 86
- Comparison of the structure of laser deposited and sputtered metallic alloys, H.-U. Krebs, O. Bremert, M. Störmer and Y. Luo 86 (1995) 90
- Thermodynamics and kinetics of solidification of Si-As solutions, R. Reitano 86 (1995) 323
- Atom probe studies of nanostructured alloys, K. Hono and T. Sakurai 87/88 (1995) 166
- APFIM investigations on ordered γ-TiAl using single-layer detection method, J.

- Wesemann, G. Frommeyer and M. Kreuss 87/88 (1995) 179
- Microstructure of heat resistant chromium steel weld metals, H.-O. Andr  n, G. Cai and L.-E. Svensson 87/88 (1995) 200
- Characterization of neutron-irradiated Fe-Au alloys, M.K. Miller, K.F. Russell, A. Jostons and R.G. Blake 87/88 (1995) 216
- Nucleation and growth of θ' precipitation in Sn-modified Al-Cu alloys: APFIM/TEM observations, S.P. Ringer, K. Hono and T. Sakurai 87/88 (1995) 223
- Quantitative analysis of GP zones formed at room temperature in a 7150 Al-based alloy, C. Schmuck, P. Auger, F. Danoix and D. Blavette 87/88 (1995) 228
- An APFIM/TEM investigation of the discontinuous precipitation in a Ni-In alloy, G.P. Geber 87/88 (1995) 234
- Structure and chemistry of grain boundaries in Ni-16Cr-9Fe model materials, M. Thuvander and K. Stiller 87/88 (1995) 251
- Effect of low-energy (20-40 keV) ion implantation on phase transformations in the subsurface volume of alloys, V.A. Ivchenko and N.N. Syutkin 87/88 (1995) 257
- APFIM study of the compositional inhomogeneity of sputtered Co-Cr magnetic thin film, A. Pundt and C. Michaelsen 87/88 (1995) 264
- APFIM and XPS study of the first stages of low temperature air oxidation of industrial CuNi alloys, R. Souchet, F. Danoix, A. D'Huysser and M. Lenglet 87/88 (1995) 271
- 3D reconstruction of antiphase boundaries in Cu_3Au from field ion images, S. Duval, S. Chambreland, D. Blavette, A. Loiseau and L. Potez 87/88 (1995) 284
- Quantitative analysis of individual atom images in FIM of an ordered Ni_4Mo alloy, M. Yamamoto, K. Nishikawa and T. Nishiuchi 87/88 (1995) 291
- A study of the effect of ageing temperature on phase separation in Fe-45%Cr alloys, J.M. Hyde, M.K. Miller, A. Cerezo and G.D.W. Smith 87/88 (1995) 311
- A three-dimensional atom-probe study of preferential sputtering of a Ni91Pt9 alloy, W. Athenstaedt and M. Leisch 87/88 (1995) 318
- Comparison of low temperature decomposition in Fe-Cr and duplex stainless steels, M.K. Miller, J.M. Hyde, A. Cerezo and G.D.W. Smith 87/88 (1995) 323
- MnCu surface alloy studied by scanning tunneling microscopy, D. Jeon, H.P. Noh, T. Hashizume, Y. Kuk and T. Sakurai 87/88 (1995) 386
- SIMS microprofiles of Pb-5%Sn solder joints in electronic devices after accelerated life tests, A. Scandurra, A. Porto and O. Puglisi 89 (1995) 1
- Ultraviolet inverse photoemission study of the oxidation of YFe_2 , P. Vavassori, L. Callegaro and E. Puppini 89 (1995) 93
- Activation treatments and surface study of amorphous $\text{Fe}_{90}\text{Zr}_{10}$ and $\text{Fe}_{87.8}\text{Zr}_{10}\text{Co}_{2}\text{Al}_{0.2}$ catalysts, X.K. Wang, N.F. Shen, Z.S. Yang and H.C. Gu 89 (1995) 297
- Synergistic alloying behaviour of $\text{Pd}_{50}\text{Cu}_{50}$ single crystals upon adsorption and co-adsorption of CO and NO, Y. Debauge, M. Abon, J.C. Bertolini, J. Massardier and A. Rochefort 90 (1995) 15
- Erratum to "Nucleation and growth of θ' precipitation in Sn-modified Al-Cu alloys: APFIM/TEM observations" [Appl. Surf. Sci. 87/88 (1995) 223], S.P. Ringer, K. Hono and T. Sakurai 90 (1995) 107
- Surface segregation and core-level shift of a Pd-Rh alloy studied by XPS, J.A. Leiro, M.H. Heinonen and I.G. Batirev 90 (1995) 515
- ### Aluminium
- Auger studies of chemical bonds and oxygen minimization in the interfaces between AlN and SiC thin films deposited by LPCVD, B. Aspar, R. Berjoan, C. Labatut and B. Armas 81 (1994) 55
- Interface study on laser-induced material transfer from polymer and quartz surfaces, S. L  tsch, H. Hiraoka, W. Nieveen and J. Bargon 81 (1994) 183
- Evaluation of matrix effects in SIMS quantification of $\text{Al}_x\text{Ga}_{1-x}\text{As}/\text{GaAs}$ heterostructures: a SNMS approach, A. Torrisi, A. Scandurra and A. Licciardello 81 (1994) 259
- Comment on 'Influence of surface composition on initial hydration of aluminium in boiling water' by A. Str  lin and T. Hjertberg, B.R. Strohmeier 81 (1994) 273
- Adsorption of monoethanolamine on clean, oxidized and hydroxylated aluminium surfaces: a model for amine-cured epoxy/aluminium interfaces, C. Fauquet, P. Dubot, L. Minel, M.-G. Barth  s-Labrousse, M. Rei Vilar and M. Villatte 81 (1994) 435
- Atomic layer epitaxy of device quality Al-GaAs and AlAs, N. Hayafuji, G.M. El-dallal, A. Dip, P.C. Colter, N.A. El-Masry and S.M. Bedair 82/83 (1994) 18
- Atomic layer epitaxy growth of doped zinc oxide thin films from organometals, V.

- Lujala, J. Skarp, M. Tammenmaa and T. Suntola 82/83 (1994) 34
- Growth temperature dependence of optical properties of gas source MBE grown GaP/AlP short period superlattices, J.H. Kim, H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda 82/83 (1994) 76
- Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda 82/83 (1994) 109
- Flow modulation epitaxy of $\text{Ga}_x\text{In}_{1-x}\text{As}/\text{AlAs}$ heterostructures on InP for resonant tunneling diodes, B.P. Keller, J.C. Yen, A.L. Holmes Jr., S.P. DenBaars and U.K. Mishra 82/83 (1994) 126
- AlAs layers with low carbon content grown by ALE using ethyldimethylamine alane as a new aluminum source, N. Kano, S. Hirose, K. Hara, J. Yoshino, H. Munekata and H. Kukimoto 82/83 (1994) 132
- Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs, I. Sue-mune 82/83 (1994) 149
- A Monte Carlo simulation study for adatom migration and resultant atomic arrangements in $\text{Al}_x\text{Ga}_{1-x}\text{As}$ on a GaAs(001) surface, T. Ito, K. Shiraishi and T. Ohno 82/83 (1994) 208
- Optical in-situ analysis of GaAs/AlAs/GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using GaCl_3 , AlCl_3 and AsH_3 , M. Akamatsu, S. Narahara, T. Kobayashi and F. Hasegawa 82/83 (1994) 228
- Atomic layer epitaxy of AlAs: growth mechanism, M. Ozeki and N. Ohtsuka 82/83 (1994) 233
- Carbon incorporation mechanism in atomic layer epitaxy of GaAs and AlGaAs, N. Kobayashi and T. Makimoto 82/83 (1994) 284
- Atomic-scale modification of the AlCl_3 -adsorbed Si(111)- 7×7 surface, T. Takiguchi, K. Uesugi, M. Yoshimura and T. Yao 82/83 (1994) 428
- Steric and electronic interactions between source gas and substrate surface during the Al-CVD/Al selective epitaxy process as investigated by quantum chemical calculations, R. Vetrivel, R. Yamauchi, H. Yamano, M. Kubo, A. Miyamoto and T. Ohta 82/83 (1994) 516
- Growth of extra-thin ordered aluminum films on Si(111) surface, E.A. Khramtsova, A.V. Zotov, A.A. Saranin, S.V. Ryzhkov, A.B. Chub and V.G. Lifshits 82/83 (1994) 576
- An FT-IR investigation of parabactin adsorbed onto aluminum, D.C. Hansen, E. McCafferty, C.W. Lins and J.J. Fitzpatrick 84 (1995) 85
- AFM investigations of the initial stages of prepolymer film growth on aluminium, T. Gesang, R. Höper, S. Dieckhoff, D. Fanter, A. Hartwig, W. Possart and O.-D. Hennemann 84 (1995) 273
- A RHEED study of the dynamics of GaAs and AlGaAs growth on a (001) surface by MBE, J. Hopkins, M.R. Leys, J. Brübach, W.C. Van der Vleuten and J.H. Wolter 84 (1995) 299
- Study on the mechanical and chemical properties of (Ti,Al)N films prepared by DC magnetron sputtering, S. Jiang, D. Peng, X. Zhao, L. Xie and Q. Li 84 (1995) 373
- Energy loss measurements for 20 keV positrons in Al thin films, G.R. Massoumi, W.N. Lennard, P.J. Schultz, T.A. Porcelli and P.J. Simpson 85 (1995) 39
- Annealing studies of Au/GaAs and Al/GaAs interfaces using a variable energy positron beam, C.C. Ling, T.C. Lee, S. Fung, C.D. Beling, H. Weng, J. Xu, S. Sun and R. Han 85 (1995) 305
- Aluminium nitride layers investigated by slow positrons, A.S. Saleh, P.C. Rice-Evans and S.J. Bull 85 (1995) 325
- Composition and gas dynamics of laser ablated AlN plumes, T.M. Di Palma, S. Orlando, A. Giardini-Guidoni, A.J. Paul, J.W. Hastie and A. Mele 86 (1995) 68
- Excimer laser ablation of Nd:YAG and Nd:glass, S.R. Jackson, W.J. Metheringham and P.E. Dyer 86 (1995) 223
- UV light irradiation effects on nucleation during chemical vapor deposition of Al films, M. Hanabusa and A. Komatsu 86 (1995) 428
- Kinetics of laser thermal decomposition of trimethylamine alane, D. Tonneau, J.E. Bourée and Y. Pauleau 86 (1995) 488
- Nucleation and growth of θ' precipitation in Sn-modified Al-Cu alloys: APFIM/TEM observations, S.P. Ringer, K. Hono and T. Sakurai 87/88 (1995) 223
- Quantitative analysis of GP zones formed at room temperature in a 7150 Al-based alloy, C. Schmuck, P. Auger, F. Danoix and D. Blavette 87/88 (1995) 228
- X-ray photoelectron spectroscopic study of room-temperature evolution of oxide-covered hydrogenated amorphous silicon/aluminium interface, C. Anandan 89 (1995) 57
- Activation treatments and surface study of amorphous $\text{Fe}_{90}\text{Zr}_{10}$ and $\text{Fe}_{87.8}\text{Zr}_{10}\text{Co}_{2}\text{Al}_{0.2}$ catalysts, X.K. Wang, N.F. Shen, Z.S. Yang and H.C. Gu 89 (1995) 297
- A photoelectron study of the oxidation of Ta(110) and thin aluminum layers on

- Ta(110), M.W. Ruckman, S.-L. Qiu and M. Strongin
On the structure and chemistry of Ni_3Al on an atomic scale via atom-probe field-ion microscopy, G.P.E.M. Van Bakel, K. Hariharan and D.N. Seidman
Erratum to "Nucleation and growth of θ' precipitation in Sn-modified Al-Cu alloys: APFIM/TEM observations" [Appl. Surf. Sci. 87/88 (1995) 223], S.P. Ringer, K. Hono and T. Sakurai

89 (1995) 401

90 (1995) 95

90 (1995) 107

Aluminium oxide

- Atomic layer controlled deposition of SiO_2 and Al_2O_3 using ABAB... binary reaction sequence chemistry, S.M. George, O. Sneh, A.C. Dillon, M.L. Wise, A.W. Ott, L.A. Okada and J.D. Way
In situ ellipsometric diagnostics for controlled growth of metal oxides with surface chemical reactions, H. Kumagai and K. Toyoda
Electrical properties of Si- Al_2O_3 structures grown by ML-ALE, V.E. Drozd, A.P. Baraban and I.O. Nikiforova
In situ diffuse reflectance infrared (DRIFTS) identification of active sites in the $\text{CO} + \text{H}_2$ reaction over lanthanide-modified Rh/ Al_2O_3 catalysts, J.J. Benítez, I. Carrizosa and J.A. Odriozola
Surface properties of excimer-laser-irradiated sintered alumina, L.D. Laude, K. Kolev, M. Brunel and P. Deleter
XPS studies of the effect of Mn on Pd/ Al_2O_3 , P.C. L'Argentièrre, M.G. Cañón and N.S. Fígoli
A study of the composition distribution at the Ti/ Al_2O_3 interface using the MCs^+ -SIMS technique, X. Chen and Y. Wang
Interfacial reaction of NiO with Al_2O_3 - $(11\bar{2}0)$ and polycrystalline α - Al_2O_3 , P.H. Bolt, S.F. Lobner, J.W. Geus and F.H.P.M. Habraken

82/83 (1994) 460

82/83 (1994) 481

82/83 (1994) 583

84 (1995) 391

86 (1995) 368

89 (1995) 63

89 (1995) 169

89 (1995) 339

Ammonia

- SIMS study of rapid thermal nitridation of silicon dioxide thick films in ammonia ambient, E. Bréelle, S. Rigo, J.A. Kilner and J.-J. Ganem
Chemical reactivity of the $\text{Si}(111)\sqrt{3} \times \sqrt{3}$ R30°-B surface: an electron-energy-loss spectroscopy study, Y. Ta-

81 (1994) 127

guchi, M. Daté, N. Takagi, T. Aruga and M. Nishijima

82/83 (1994) 434

Temperature-programmed desorption and decomposition of NH_3 over molybdenum nitride films, H.J. Lee, J.-G. Choi, C.W. Colling, M.S. Mudholkar and L.T. Thompson

89 (1995) 121

Activation treatments and surface study of amorphous $\text{Fe}_{90}\text{Zr}_{10}$ and $\text{Fe}_{87.8}\text{Zr}_{10}\text{Co}_{2}\text{Al}_{0.2}$ catalysts, X.K. Wang, N.F. Shen, Z.S. Yang and H.C. Gu

89 (1995) 297

Annealing

- Helium and hydrogen-decorated cavities in silicon, R.A. Hakvoort, A. van Veen, P.E. Mijnders and H. Schut
An annealing study of defects induced by electron irradiation of Czochralski-grown Si using a positron lifetime technique, A. Kawasuso, M. Hasegawa, M. Suezawa, S. Yamaguchi and K. Sumino
Annealing studies of Au/GaAs and Al/GaAs interfaces using a variable energy positron beam, C.C. Ling, T.C. Lee, S. Fung, C.D. Beling, H. Weng, J. Xu, S. Sun and R. Han
UV photo-annealing of thin sol-gel films, R.E. Van de Leest
Tunable UV-flash krypton lamp array useful for large area deposition and in situ UV annealing of Si-based dielectrics, J. Flicstein, Y. Vitel, O. Dulac, C. Debauche, Y.I. Nissim and C. Licoppe
Improvement of silicon oxide film properties by ultraviolet excimer lamp annealing, E.G. Parada, P. González, J. Serra, B. León, M. Pérez-Amor, J. Flicstein and R.A.B. Devine
Effect of UV annealing of radiation damage in SiO_2 films, I.P. Lisovskii, V.G. Litovchenko and V.B. Lozinskii
Photo-luminescence of pulsed excimer laser annealed Sb-implanted CdTe, F.X. Wagner, K. Dhese, P.H. Key, D. Sands, S.R. Jackson, R. Kirbitson and J.E. Nicholls
Rapid thermal nitridation of thin chromium films, S.W. Russell, J. Li, T.L. Alford, P.R. Oakey and S.C. Shatas

85 (1995) 271

85 (1995) 280

85 (1995) 305

86 (1995) 278

86 (1995) 286

86 (1995) 294

86 (1995) 299

86 (1995) 364

90 (1995) 455

Antimony

- Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy,

- H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda
Surface reactions of Ga and As on Sb-terminated GaAs(001), F. Maeda, Y. Watanabe and M. Oshima
82/83 (1994) 109
- Suppression of HBO_2 and Sb adsorption on thin-oxide-covered, H-terminated, or Sb-terminated Si(100) surfaces, E. Murakami, H. Kujirai and S. Kimura
82/83 (1994) 276
- Auger electron diffraction study of the initial stage of Ge heteroepitaxy on Si(001), M. Sasaki, T. Abukawa, H.W. Yeom, M. Yamada, S. Suzuki, S. Sato and S. Kono
82/83 (1994) 387
- Photo-luminescence of pulsed excimer laser annealed Sb-implanted CdTe, F.X. Wagner, K. Dhese, P.H. Key, D. Sands, S.R. Jackson, R. Kirbitson and J.E. Nicholls
86 (1995) 364
- Surface segregation of Sb in doped TiO_2 rutile, A. Gulino, G.G. Condorelli, I. Fragalà and R.G. Egdell
90 (1995) 289
- A photoemission study of electron states in Sb-ion implanted TiO_2 (110), A.E. Taverner, A. Gulino, R.G. Egdell and T.J. Tate
90 (1995) 383

Argon

- Substrate orientation dependence of self-limited atomic-layer etching of Si with chlorine adsorption and low-energy Ar^+ irradiation, K. Suzue, T. Matsuura, J. Murota, Y. Sawada and T. Ohmi
82/83 (1994) 422
- A comparative study of primary ion energy dependence of secondary ion yields from Si and Ge surfaces under inert and reactive ion bombardment, N. Ray, P. Rajasekar and S.D. Dey
84 (1995) 203
- Threshold behavior of ionization and excitation cross sections of He and Ar by positron impact, O. Sueoka, B. Jin and A. Hamada
85 (1995) 59

Arsenic

- A temperature-programmed desorption/X-ray photoelectron spectroscopy study of ditertiarybutylarsine on GaAs(100), M.S. Jackson, J.M. Heitzinger, J.W. Nail, R.D. Culp and J.G. Ekerdt
81 (1994) 195
- AlAs layers with low carbon content grown by ALE using ethyldimethylamine as a new aluminum source, N. Kano, S. Hirose, K. Hara, J. Yoshino, H. Munekata and H. Kukimoto
82/83 (1994) 132

- Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs, I. Sue-mune
82/83 (1994) 149
- Atomic layer epitaxy of AlAs: growth mechanism, M. Ozeki and N. Ohtsuka
82/83 (1994) 233
- Substitution of surface-adsorbed As atoms to P atoms in atomic layer epitaxy, H. Ikeda, Y. Miura, N. Takahashi, A. Koukitu and H. Seki
82/83 (1994) 257
- Pulsed trimethylgallium scattering from As-stabilized and Ga-stabilized surfaces, M. Sasaki and S. Yoshida
82/83 (1994) 269
- Surface reactions of Ga and As on Sb-terminated GaAs(001), F. Maeda, Y. Watanabe and M. Oshima
82/83 (1994) 276
- Variable-energy positron beam study of arsenic diffusion in poly-silicon, D.W. Lawther, R. Khatri, P.J. Simpson, P.J. Schultz, I. Calder and L. Weaver
85 (1995) 265
- Thermodynamics and kinetics of solidification of Si-As solutions, R. Reitano
86 (1995) 323

Atomic force microscopy

- Growth of excimer-laser-induced dendritic surface structures on polyethylene-terephthalate, J. Heitz, E. Arenholz, D. Bäuerle and K. Schilcher
81 (1994) 103
- Interface study on laser-induced material transfer from polymer and quartz surfaces, S. Lätsch, H. Hiraoka, W. Nieveen and J. Bargon
81 (1994) 183
- Self-limiting and step-propagating nature of GaAs atomic layer epitaxy revealed by atomic force microscopy, H. Yokoyama, M. Tanimoto, M. Shinohara and N. Inoue
82/83 (1994) 158
- X-ray photoelectron spectroscopic and atomic force microscopic study of GaAs etching with a HCl solution, Z. Song, S. Shogen, M. Kawasaki and I. Sue-mune
82/83 (1994) 250
- Atomic force microscopic study of directional SrSO_4 (001) surface and its etching property, A. Seo and H. Shindo
82/83 (1994) 475
- Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi
82/83 (1994) 494
- Morphology of epitaxial SrF_2 films on atomically modified InP (100), S. Heun, M. Sugiyama, S. Maeyama, Y. Watanabe and M. Oshima
82/83 (1994) 507
- The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen
82/83 (1994) 553

- Aqueous degradation of Bi-2212 single crystals: an AFM study of surface alteration, S.A. Holt, R. Zhao and S. Myhra 84 (1995) 125
- Pretreatment of silicon substrates for CVD diamond deposition studied by atomic force microscopy, G. Friedbacher, E. Bouveresse, G. Fuchs, M. Grasserbauer, D. Schwarzbach, R. Haubner and B. Lux 84 (1995) 133
- AFM investigations of the initial stages of prepolymer film growth on aluminium, T. Gesang, R. Höper, S. Dieckhoff, D. Fanter, A. Hartwig, W. Possart and O.-D. Hennemann 84 (1995) 273
- Influence of ion bombardment on the refractive index of laser pulse deposited oxide films, G. Reisse, S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz 86 (1995) 107
- Pulsed laser deposition and nanometer scale characterization of $\text{YBa}_2\text{Cu}_3\text{O}_{7-\delta}$ thin films by scanning probe methods, R. Sum, H.P. Lang and H.-J. Güntherodt 86 (1995) 140
- Laser chemical vapour deposition for microelectronics, G. Auvert 86 (1995) 466
- VUV laser (157 nm) chemical vapor deposition of high quality amorphous hydrogenated silicon: gas phase chemistry and modelling, H. Karstens, J. Knobloch, A. Winkler, A. Pusel, M. Barth and P. Hess 86 (1995) 521
- Laser chemical etching of Cu_2O , G. Stenberg, M. Boman, M. Ottosson and J.-O. Carlsson 86 (1995) 543
- Three-dimensional nanostructures by direct laser etching of Si, M. Müllenborn, H. Dirac and J.W. Petersen 86 (1995) 568
- Thickness determination of uniform overlayers on rough substrates by angle-dependent XPS, P.L.J. Gunter and J.W. Niemantsverdriet 89 (1995) 69
- Atomic force microscopy determination of the topography of fly-ash particles, C.M. Demanet 89 (1995) 97
- Deposition by laser ablation and characterization of titanium dioxide films on polyethylene-terephthalate, N. Lobstein, E. Millon, A. Hachimi, J.F. Muller, M. Alnot and J.J. Ehrhardt 89 (1995) 307
- Characterization of nickel films deposited by cold remote nitrogen plasma on acrylonitrile-butadiene-styrene copolymer, A. Brocherieux, O. Dessaux, P. Goudmand, L. Gengembre, J. Grimblot, M. Brunel and R. Lazzaroni 90 (1995) 47
- An investigation using atomic force microscopy and X-ray photoelectron spectroscopy of the modification of the surface of mica with an argon RF-plasma discharge, N.M.D. Brown and Z.-H. Liu 90 (1995) 155
- Structural investigation of Langmuir-Blodgett monolayers of L- α -dipalmitoylphosphatidylcholine by atomic force microscopy, X.-M. Yang, D. Xiao, Z.-H. Lu and Y. Wei 90 (1995) 175
- AFM and XPS characterization of the Si(111) surface after thermal treatment, B. Lamontagne, D. Guay, D. Roy, R. Sporken and R. Caudano 90 (1995) 481
- ### Atomic probe analysis
- Atom probe and field emission electron spectroscopy studies of semiconductor films on metals, M. Ashino, M. Tomitori and O. Nishikawa 87/88 (1995) 12
- Adsorption studies of iron on tungsten by probe-hole field emission microscopy, A.D. Adsool, R. Pande, R.B. Sharma, M.A. More and D.S. Joag 87/88 (1995) 37
- Atom probe studies of nanostructured alloys, K. Hono and T. Sakurai 87/88 (1995) 166
- APFIM investigations on ordered γ -TiAl using single-layer detection method, J. Wesemann, G. Frommeyer and M. Kreuss 87/88 (1995) 179
- The partitioning of substitutional solute elements during the tempering of martensite in Cr and Mo containing steels, R.C. Thomson and M.K. Miller 87/88 (1995) 185
- Atom-probe study of phosphorus segregation to the carbide/matrix interface in an aged 9% chromium steel, L. Lundin and B. Richarz 87/88 (1995) 194
- Microstructure of heat resistant chromium steel weld metals, H.-O. Andrén, G. Cai and L.-E. Svensson 87/88 (1995) 200
- Atom probe field ion microscopy of type 308 CRE stainless steel welds, S.S. Babu, S.A. David, J.M. Vitek and M.K. Miller 87/88 (1995) 207
- Characterization of neutron-irradiated Fe-Au alloys, M.K. Miller, K.F. Russell, A. Jostons and R.G. Blake 87/88 (1995) 216
- Nucleation and growth of θ' precipitation in Sn-modified Al-Cu alloys: APFIM/TEM observations, S.P. Ringer, K. Hono and T. Sakurai 87/88 (1995) 223
- Quantitative analysis of GP zones formed at room temperature in a 7150 Al-based alloy, C. Schmuck, P. Auger, F. Danoix and D. Blavette 87/88 (1995) 228
- Atom probe analysis of interfacial segregation, M.K. Miller and G.D.W. Smith 87/88 (1995) 243

- Structure and chemistry of grain boundaries in Ni-16Cr-9Fe model materials, M. Thuvander and K. Stiller 87/88 (1995) 251
- APFIM study of the compositional inhomogeneity of sputtered Co-Cr magnetic thin film, A. Pundt and C. Michaelson 87/88 (1995) 264
- APFIM and XPS study of the first stages of low temperature air oxidation of industrial CuNi alloys, R. Souchet, F. Danoix, A. D'Huysser and M. Lenglet 87/88 (1995) 271
- Atom probe field ion microscope studies of palladium silicide on silicon, R.A. King, R.A.D. Mackenzie, G.D.W. Smith and N.A. Cade 87/88 (1995) 279
- A general protocol for the reconstruction of 3D atom probe data, P. Bas, A. Bostel, B. Deconihout and D. Blavette 87/88 (1995) 298
- A method for reconstructing and locating atoms on the crystal lattice in three-dimensional atom probe data, P.P. Camus, D.J. Larson and T.F. Kelly 87/88 (1995) 305
- A study of the effect of ageing temperature on phase separation in Fe-45%Cr alloys, J.M. Hyde, M.K. Miller, A. Cerezo and G.D.W. Smith 87/88 (1995) 311
- A three-dimensional atom-probe study of preferential sputtering of a Ni91Pt9 alloy, W. Athenstaedt and M. Leisch 87/88 (1995) 318
- Comparison of low temperature decomposition in Fe-Cr and duplex stainless steels, M.K. Miller, J.M. Hyde, A. Cerezo and G.D.W. Smith 87/88 (1995) 323
- FIM/AP analysis of Cu-Pd multilayers, T. Al-Kassab, M.-P. Macht and H. Wollenberger 87/88 (1995) 329
- Improvements in the transmission of voltage evaporation pulses in the atom probe, S.J. Sijbrandij, A. Cerezo and G.D.W. Smith 87/88 (1995) 414
- Performance of the multiple events position sensitive detector used in the tomographic atom probe, B. Deconihout, A. Bostel, M. Bouet, J.M. Sarrau, P. Bas and D. Blavette 87/88 (1995) 428
- Microfabrication of extraction electrodes for local-electrode atom probes, S.S. Bajikar, T.F. Kelly, C.-M. Teng and P.P. Camus 87/88 (1995) 438
- Fabrication of microtips on planar specimens, D.J. Larson, C.-M. Teng, P.P. Camus and T.F. Kelly 87/88 (1995) 446
- The performance of the IMR three-dimensional atom probe, K. Hono, R. Okano, T. Saeda and T. Sakurai 87/88 (1995) 453
- On the structure and chemistry of Ni₃Al on an atomic scale via atom-probe field-ion microscopy, G.P.E.M. Van Bakel, K. Hariharan and D.N. Seidman 90 (1995) 95
- Auger electron spectroscopy*
- An AES study of intrinsic and ion-induced structure in the SiO₂-Si system, B. Lang, B. Sefsaf and G. Allan 81 (1994) 17
- The smoothing properties of some new shapes for transmission functions in Fourier space. A real case study on exemplary noisy Auger spectra, R. Siuda 81 (1994) 27
- Auger studies of chemical bonds and oxygen minimization in the interfaces between AlN and SiC thin films deposited by LPCVD, B. Aspar, R. Berjoan, C. Labatut and B. Armas 81 (1994) 55
- Electron-beam-induced oxidation of CdS, V.B. Mityukhlyayev 81 (1994) 137
- Sulfur segregation in titanium and selected titanium alloys, R.A. Outlaw, W.S. Lee, S.J. Hoekje and S.N. Sankaran 81 (1994) 143
- Surface segregation study of Ib-VIII single-crystal alloys, F. Reniers, M.P. Delplancke, A. Asskali, M. Jardinier-Offergeld and F. Bouillon 81 (1994) 151
- Auger and X-ray photoelectron diffraction in MgO(001), T.T. Tran and S.A. Chambers 81 (1994) 161
- Matrix factors affecting quantitative analysis of AES for binary alloys, H. Bubert and R.P.H. Garten 81 (1994) 203
- Temperature dependence of surface charging of NaCl under electron irradiation: role of secondary electron emission, W.G. Durrer, M. Portillo, P. Wang and D.P. Russell 81 (1994) 215
- Atomic-hydrogen-induced desorption of fluorine from silicon surfaces, Y. Saito 81 (1994) 223
- Effects of atomic hydrogen on Cu(II)bis-hexafluoroacetylacetonate interactions with a TiN surface, G. Nuesca, J. Prasad and J.A. Kelber 81 (1994) 237
- Diamond nucleation and growth at the early stages on Si(100) monitored by electron spectroscopies, F. Le Normand, A. Ababou, N. Brault, B. Carrière, L. Fayette, B. Marcus, M. Mermoux, M. Romeo and C. Speisser 81 (1994) 309
- Modified relative sensitivity factors for Auger spectra, F. Pavlyak 81 (1994) 351
- Raman study of strained SiGe layers, S. Gu, R. Zhang, P. Han, R. Wang, P. Zhong and Y. Zheng 81 (1994) 431
- Adsorption of monoethanolamine on clean, oxidized and hydroxylated aluminium surfaces: a model for amine-cured epoxy/aluminium interfaces, C. Fauquet, P. Dubot, L. Minel, M.-G.

- Barthés-Labrousse, M. Rei Vilar and M. Villatte 81 (1994) 435
- Kinetics and mechanism of atomic layer epitaxy of GaAs using trimethylgallium, H. Ohno, S. Goto, Y. Nomura, Y. Morishita and Y. Katayama 82/83 (1994) 164
- Activation of the Ga-CH₃ bond using atomic hydrogen - a possible route to III-V semiconductor films with low carbon levels, J.T. Yates, Jr., A. Hübner, S.R. Lucas, W.D. Partlow, J. Schaefer and W.J. Choyke 82/83 (1994) 180
- Suppression of HBO₂ and Sb adsorption on thin-oxide-covered, H-terminated, or Sb-terminated Si(100) surfaces, E. Murakami, H. Kujirai and S. Kimura 82/83 (1994) 338
- Self-limiting adsorption of thermally cracked SiCl₂H₂ on Si surfaces, C. Sasaoka and A. Usui 82/83 (1994) 348
- Adaptive temperature program ALE of Si_{1-x}Ge_x/Si heterostructures from Si₂H₆/Ge₂H₆, S. Asami, N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt 82/83 (1994) 359
- Atomic layer epitaxy of germanium, S. Sugahara, T. Kitamura, S. Imai and M. Matsumura 82/83 (1994) 380
- Auger electron diffraction study of the initial stage of Ge heteroepitaxy on Si(001), M. Sasaki, T. Abukawa, H.W. Yeom, M. Yamada, S. Suzuki, S. Sato and S. Kono 82/83 (1994) 387
- Growth of extra-thin ordered aluminum films on Si(111) surface, E.A. Khramtsova, A.V. Zotov, A.A. Saranin, S.V. Ryzhkov, A.B. Chub and V.G. Lifshits 82/83 (1994) 576
- A comparison of X-ray photoelectron spectroscopy and Auger electron spectroscopy depth profiles for magnesium implants, J.A. Schreifels, N.H. Turner and R.E. Morris 84 (1995) 23
- Adsorption and co-adsorption of boron and oxygen on ordered α -SiC surfaces, V.M. Bermudez 84 (1995) 45
- Initial oxidation kinetics of Fe-Ni single crystals before and after ion bombardment, S.P. Chenakin 84 (1995) 91
- AES and XPS study of thin RF-sputtered Ta₂O₅ layers, E. Atanassova, T. Dimitrova and J. Koprinarova 84 (1995) 193
- Multi-spectral scanning Auger microscopy of tribological surfaces, I.R. Barkshire, M. Prutton and G.C. Smith 84 (1995) 331
- Surface alloy formation in Pd/Ag, Cu/Au and Ni/Au bimetallic overlayers, A.K. Santra and C.N.R. Rao 84 (1995) 347
- Study on the mechanical and chemical properties of (Ti,Al)N films prepared by DC magnetron sputtering, S. Jiang, D. Peng, X. Zhao, L. Xie and Q. Li 84 (1995) 373
- Laser-induced selective deposition of Ni-P alloy on silicon, J. Wang, X. Fei, Z. Yu and G. Zhao 84 (1995) 383
- Adsorption site identification for oxygen molecules on Au/Si(100) by positron annihilation induced Auger electron spectroscopy (PAES), G. Yang, J.H. Kim, S. Yang and A.H. Weiss 85 (1995) 77
- Laser-assisted selective metallisation of diamonds by electroless Ni and Cu plating, G.A. Shafeev, S.M. Pimenov and E.N. Loubnin 86 (1995) 392
- Interrupted cycle chemical beam epitaxy of gallium phosphide on silicon with or without photon assistance, J.T. Kelliher, A.E. Miller, N. Dietz, S. Habermehl, Y.L. Chen, Z. Lu, G. Lucovsky and K.J. Bachmann 86 (1995) 453
- Characterization of thin Ag films deposited onto InP(001)-p(2 × 4) surface at room temperature by means of LEED, RHEED, AES and RBS-channeling techniques, M. Hanebuchi, T. Katoh and K. Morita 89 (1995) 113
- M-S (M = Mo, W) cluster compound films on copper surfaces, X.R. Ye, H.W. Hou, X.Q. Xin and C.F. Hammer 89 (1995) 151
- Quantitative correction of backscattering in Auger electron spectroscopy of thin films, G. Lévêque and J. Bonnet 89 (1995) 211
- Activation treatments and surface study of amorphous Fe₉₀Zr₁₀ and Fe_{87.8}Zr₁₀Co₂-Al_{0.2} catalysts, X.K. Wang, N.F. Shen, Z.S. Yang and H.C. Gu 89 (1995) 297
- Interaction of oxygen and silver on the V(100) surface, T. Valla, P. Pervan and M. Milun 89 (1995) 375
- Synergistic alloying behaviour of Pd₅₀Cu₅₀ single crystals upon adsorption and co-adsorption of CO and NO, Y. Debauge, M. Abon, J.C. Bertolini, J. Massardier and A. Rochefort 90 (1995) 15
- Ferroelectric BaTiO₃ films with a high-magnitude dielectric constant grown on p-Si by low-pressure metalorganic chemical vapor deposition, T.W. Kim, Y.S. Yoon, S.S. Yom and C.O. Kim 90 (1995) 75
- Synthesis of molybdenum nitride γ -Mo₂N by multipulse laser irradiation of molybdenum in nitrogen, J.D. Wu, C.Z. Wu, Z.M. Song, L.H. Wu and F.M. Li 90 (1995) 81
- Pulse plasma beam deposition of cubic boron nitride films on GCr15 steel bear-

- ing substrate at room temperature, P. Yan and S.-Z. Yang 90 (1995) 149
- Determining hybridization differences for amorphous carbon from the XPS C 1s envelope, S.T. Jackson and R.G. Nuzzo 90 (1995) 195
- XPS/NRA investigations of particle size effects during the oxidation of Cu particles supported on oxidised Si(100), R. Van Wijk, P.C. Görts, A.J.M. Mens, O.L.J. Gijzeman, F.H.P.M. Habraken and J.W. Geus 90 (1995) 261
- Morphology, atomic composition and photoelectric properties of the microrelief InP-electrolyte interface, N.L. Dmitruk, E.V. Basiuk, G.Ya. Kolbasov, O.A. Yakubtsov, I.A. Molchanovskii and T.A. Taranets 90 (1995) 489
- Barium**
- Modelling of barium transport in dispenser cathodes, A. Sil and D.S. Venkateswarlu 81 (1994) 469
- Observation of the interface of Ba/Si(100) by MDS and TDS, S. Hongo, K. Ojima, S. Taniguchi, T. Urano and T. Kanaji 82/83 (1994) 537
- Ferroelectric BaTiO₃ films with a high-magnitude dielectric constant grown on p-Si by low-pressure metalorganic chemical vapor deposition, T.W. Kim, Y.S. Yoon, S.S. Yom and C.O. Kim 90 (1995) 75
- Beryllium**
- Quantitative analysis of the thermal degassing of a beryllium powder, L. Buisson, P. Bracconi and X. Claudon 84 (1995) 211
- Biological materials**
- An FT-IR investigation of parabactin adsorbed onto aluminum, D.C. Hansen, E. McCafferty, C.W. Lins and J.J. Fitzpatrick 84 (1995) 85
- Bismuth**
- Aqueous degradation of Bi-2212 single crystals: an AFM study of surface alteration, S.A. Holt, R. Zhao and S. Myhra 84 (1995) 125
- Borides**
- Chemical etching of (100) and (110) faces of flux-grown LaBO₃ crystals, A. Jain, A.K. Razdan, P.N. Kotru and B.M. Wanklyn 84 (1995) 65
- Boron**
- Boron δ -doping in Si using atmospheric pressure CVD, Y. Kiyota, T. Nakamura and T. Inada 82/83 (1994) 400
- Adsorption and co-adsorption of boron and oxygen on ordered α -SiC surfaces, V.M. Bermudez 84 (1995) 45
- Electron microscopy of the ordered boron 2 \times 1 structure buried in crystalline silicon, B.E. Weir, D.J. Eaglesham, L.C. Feldman, H.S. Luftman and R.L. Headrick 84 (1995) 413
- Boron nitride**
- Structure and chemical composition of BN thin films grown by pulsed-laser deposition (PLD), T. Klotzbücher, W. Pfleging, M. Mertin, D.A. Wesner and E.W. Kreutz 86 (1995) 165
- Pulse plasma beam deposition of cubic boron nitride films on GCr15 steel bearing substrate at room temperature, P. Yan and S.-Z. Yang 90 (1995) 149
- Cadmium**
- Photo-luminescence of pulsed excimer laser annealed Sb-implanted CdTe, F.X. Wagner, K. Dhese, P.H. Key, D. Sands, S.R. Jackson, R. Kirbitson and J.E. Nicholls 86 (1995) 364
- Photo-assisted growth and characterization of Zn_xCd_{1-x}S by MOVPE, H. Dumont, Sz. Fujita and Sg. Fujita 86 (1995) 442
- Cadmium selenide**
- Surface reaction mechanism in MOMBE-ALE of ZnSe and CdSe as determined by a new in-situ optical probing method, A. Yoshikawa, M. Kobayashi and S. Tokita 82/83 (1994) 316
- Cadmium selenide-amorphous hydrogenated silicon heterostructures, S. Wu and D. Haneman 89 (1995) 289
- Scanned laser spot photocurrent response studies of surface modifications of CdSe thin film electrodes, X.R. Xiao, Y. Lin, Y. Yang, X.G. Chen and J.K. You 90 (1995) 321

Cadmium sulphide

- Surface thermodynamic properties of cadmium sulfide, J.D.G. Durán, L. Zurita, M.C. Guindo, A.V. Delgado and F. González-Caballero 81 (1994) 1
- Electron-beam-induced oxidation of CdS, V.B. Mityukhlyayev 81 (1994) 137

Cadmium telluride

- A positron annihilation study of the formation of defect layers in cadmium mercury telluride, A. Towner, P.C. Rice-Evans and N. Shaw 85 (1995) 315
- Thermal effects on structural characterization of evaporated CdTe films during and after deposition, A. Ashour, M.R. Ebeid, N. El-Kadry, M.F. Ahmed and A.A. Ramadan 89 (1995) 159

Calcium

- A study of CaO-SO₂ interaction, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea 81 (1994) 409
- A study of CaO-SO₂ interaction in the presence of O₂, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea 81 (1994) 417
- Surface modification of CaF₂ in atomic layer scale by electron beam exposure, S.M. Hwang, A. Izumi, K. Tsutsui and S. Furukawa 82/83 (1994) 523
- A new parameter to characterize limestones as SO₂ sorbents, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea 89 (1995) 197

Carbides

- Pulsed-laser deposition and characterization of TaC films, R. Teghil, L. D'Alessio, G. De Maria and D. Ferro 86 (1995) 190
- Structuring of polyimide-metal carbide layer systems by excimer laser ablation, J. Ihlemann, B. Wolff-Rottke, G. Danev, K. Petkov and E. Spassova 86 (1995) 245
- Atom-probe study of phosphorus segregation to the carbide/matrix interface in an aged 9% chromium steel, L. Lundin and B. Richarz 87/88 (1995) 194

Carbon

- Grafting onto the surface of plasma-modified fillers, G. Ji, J. Fang, S. Cai and G. Xue 81 (1994) 63
- Carbon incorporation mechanism in atomic layer epitaxy of GaAs and AlGaAs, N. Kobayashi and T. Makimoto 82/83 (1994) 284
- Surface characterization by time-of-flight SIMS of a catalyst for oxygen electroreduction: pyrolyzed cobalt phthalocyanine-on-carbon black, L.T. Weng, P. Bertrand, G. Lalande, D. Guay and J.P. Dodelet 84 (1995) 9
- Laser ablation of refractory material, cluster formation and deposition, H. Yu, M.G. Huber and F.W. Froben 86 (1995) 74
- Laser diagnostics of C₆₀ and C₇₀ films by broadband surface acoustic wave spectroscopy, A.A. Kolomenskii, M. Szabadi and P. Hess 86 (1995) 591
- Field induced manipulation of fullerene molecules with the STM: a self-consistent theoretical study, M. Devel, C. Girard, C. Joachim and O.J.F. Martin 87/88 (1995) 390
- Adsorption of fullerenes on Cu(111) and Ag(111) surfaces, T. Sakurai, X.D. Wang, T. Hashizume, V. Yurov, H. Shinohara and H.W. Pickering 87/88 (1995) 405
- Photoemission studies on Pt foil implanted by carbon atoms accelerated in a Van de Graaff generator: nature of the interaction between Pt and carbon, R. Sundarajan, G. Pető, E. Koltay and L. Guzzi 90 (1995) 165
- Determining hybridization differences for amorphous carbon from the XPS C 1s envelope, S.T. Jackson and R.G. Nuzzo 90 (1995) 195
- Surface studies of Cu/Cr/Ag impregnated microporous carbons, R.H. Bradley 90 (1995) 271

Carbon dioxide

- Influence of atomic Cu-layer epitaxy on CO₂ and CO photoinduced desorption from ZnO(0001), P.J. Møller, S.A. Kholmolov and E.F. Lazneva 82/83 (1994) 569
- Surface interaction between H₂ and CO₂ over silicalite-supported platinum, M. Huang, S. Kaliaguine and S. Suppiah 90 (1995) 393

Carbon monoxide

- Adsorption of CO on Mg-promoted Co-(poly), J. Vaari, T. Vaara, J. Lahtinen and P. Hautajärvi 81 (1994) 289

- CO adsorption on clean and atomic-layer-Cu-covered ZnO(10 $\bar{1}$ 0) surfaces, Q. Ge and P.J. Møller 82/83 (1994) 305
- Influence of atomic Cu-layer epitaxy on CO₂ and CO photoinduced desorption from ZnO(0001), P.J. Møller, S.A. Komolov and E.F. Lazneva 82/83 (1994) 569
- In situ diffuse reflectance infrared (DRIFTS) identification of active sites in the CO + H₂ reaction over lanthanide-modified Rh/Al₂O₃ catalysts, J.J. Benítez, I. Carrizosa and J.A. Odriozola 84 (1995) 391
- Investigation of adsorption and coadsorption of O₂ and CO on Rh by O₂⁺ field ion and Li⁺ field desorption microscopies, V.K. Medvedev, Yu. Suchorski and J.H. Block 87/88 (1995) 159
- Reactions of CO and NO on Mg promoted cobalt, T. Vaara, J. Lahtinen and P. Hautojärvi 89 (1995) 103
- Synergistic alloying behaviour of Pd₅₀Cu₅₀ single crystals upon adsorption and coadsorption of CO and NO, Y. Debauge, M. Abon, J.C. Bertolini, J. Massardier and A. Rochefort 90 (1995) 15
- The reactivity of O₂/H₂, O₂/CO and O₂/C₃H₆ gas mixtures on Cu(111), W.E.J. Van Kooten, J.P.C. Van Nispen, O.L.J. Gijzeman and J.W. Geus 90 (1995) 137

Catalysis

- Identification of active species and theoretical classification of simple catalyst oxides using surface redox couples, Y.P. Arnaud and H. Bertrais 81 (1994) 69
- The effect of cyclic oxidation-reduction pretreatments on an amorphous Ni₈₀P₂₀ catalyst: an XPS/UPS/ISS study, J. Deng, H. Chen, X. Bao and M. Muhler 81 (1994) 341
- In-situ FTIR investigation of coke formation on USY zeolite, C. Li, Y.-W. Chen, S.-J. Yang and R.-B. Yen 81 (1994) 465
- Surface characterization by time-of-flight SIMS of a catalyst for oxygen electroreduction: pyrolyzed cobalt phthalocyanine-on-carbon black, L.T. Weng, P. Bertrand, G. Lalande, D. Guay and J.P. Dodelet 84 (1995) 9
- Deposition of inorganic salts from solution on flat substrates by spin-coating: theory, quantification and application to model catalysts, R.M. Van Hardeveld, P.L.J. Gunter, L.J. Van IJzendoorn, W. Wieldraaijer, E.W. Kuipers and J.W. Niemantsverdriet 84 (1995) 339

- The distribution of activation energy for hydrogen desorption over silica-supported nickel catalysts determined from temperature-programmed desorption spectra, M. Arai, Y. Nishiyama, T. Masuda and K. Hashimoto 89 (1995) 11
- Preparation of a model Ziegler-Natta catalyst. Surface science studies of magnesium chloride thin film deposited on gold and its interaction with titanium chloride, E. Magni and G.A. Somorjai 89 (1995) 187
- Activation treatments and surface study of amorphous Fe₉₀Zr₁₀ and Fe_{87.8}Zr₁₀Co₂-Al_{0.2} catalysts, X.K. Wang, N.F. Shen, Z.S. Yang and H.C. Gu 89 (1995) 297

Ceramics

- Laser-surface processing of metals and ceramics for industrial applications, H.W. Bergmann, K. Schutte, E. Schubert and A. Emmel 86 (1995) 259

Chemical vapour deposition

- Auger studies of chemical bonds and oxygen minimization in the interfaces between AlN and SiC thin films deposited by LPCVD, B. Aspar, R. Berjoan, C. Labatut and B. Armas 81 (1994) 55
- Effects of atomic hydrogen on Cu(II)bis-hexafluoroacetylacetonate interactions with a TiN surface, G. Nuesca, J. Prasad and J.A. Kelber 81 (1994) 237
- Characterization of adsorption in flow type atomic layer epitaxy reactor, J. Aarik and H. Siimon 81 (1994) 281
- Surface chemical states on 3C-SiC/Si epilayers, A.T.S. Wee, Z.C. Feng, H.H. Hng, K.L. Tan, C.C. Tin, R. Hu and R. Coston 81 (1994) 377
- A combined use of SIMS and RBS techniques for the investigation of SiC and SiCN films, F. Caccavale, G. Brusatin and I. Kleps 81 (1994) 443
- Molecular layer epitaxy of GaAs, J. Nishizawa 82/83 (1994) 1
- Recent advances in atomic layer epitaxy devices, S.M. Bedair and N.A. El-Masry 82/83 (1994) 7
- Surface processes of selective growth by atomic layer epitaxy, H. Isshiki, Y. Aoyagi, T. Sugano, S. Iwai and T. Meguro 82/83 (1994) 57
- Epitaxial growth of a two-dimensional structure of GaP on a Si substrate by

- metalorganic chemical vapor deposition, T. Soga, T. Jimbo and M. Umeno 82/83 (1994) 64
- Growth temperature dependence of optical properties of gas source MBE grown GaP/AIP short period superlattices, J.H. Kim, H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda 82/83 (1994) 76
- Fabrication of smooth facets of InP by selective sidewall epitaxy using CBE, M. Gotoda, H. Sugimoto, S. Maruno, T. Isu, W. Susaki and M. Nunoshita 82/83 (1994) 80
- Selective epitaxial growth of GaInP by LP-MOCVD using ethyldimethylindium, trimethylindium, trimethylgallium and triethylgallium as group III sources, S.-H. Chan, S.M. Sze, C.-Y. Chang and W.-I. Lee 82/83 (1994) 85
- Temperature synchronized molecular layer epitaxy, T. Kurabayashi and J. Nishizawa 82/83 (1994) 97
- Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda 82/83 (1994) 109
- Microscopic analysis of interface structure in InGaAs/InP MQW using Pendelösung oscillation around a satellite peak in high-resolution X-ray diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya 82/83 (1994) 115
- Growth of In₂S₃ thin films by atomic layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä 82/83 (1994) 122
- Self-limiting and step-propagating nature of GaAs atomic layer epitaxy revealed by atomic force microscopy, H. Yokoyama, M. Tanimoto, M. Shinohara and N. Inoue 82/83 (1994) 158
- Kinetics and mechanism of atomic layer epitaxy of GaAs using trimethylgallium, H. Ohno, S. Goto, Y. Nomura, Y. Morishita and Y. Katayama 82/83 (1994) 164
- Surface stoichiometry and the role of adsorbates during GaAs atomic layer epitaxy, J.R. Creighton 82/83 (1994) 171
- Theoretical studies on the chloride ALE process, Y. Mochizuki, T. Takada and A. Usui 82/83 (1994) 200
- Optical in-situ analysis of GaAs/AlAs/GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using GaCl₃, AlCl₃ and AsH₃, M. Akamatsu, S. Narahara, T. Kobayashi and F. Hasegawa 82/83 (1994) 228
- Atomic layer epitaxy of AlAs: growth mechanism, M. Ozeki and N. Ohtsuka 82/83 (1994) 233
- A solution to the surface arsenic stoichiometric problem at the GaAs(001) growth surface in atomic layer epitaxy, Y. Sakuma, S. Muto, K. Nakajima and N. Yokoyama 82/83 (1994) 239
- Substitution of surface-adsorbed As atoms to P atoms in atomic layer epitaxy, H. Ikeda, Y. Miura, N. Takahashi, A. Koukitu and H. Seki 82/83 (1994) 257
- In-situ observation of Ga adsorption during TMGa exposure on GaAs(001) surfaces with various As coverages, S. Otake, A. Sakamoto, M. Yamamoto and I. Iwasa 82/83 (1994) 263
- Carbon incorporation mechanism in atomic layer epitaxy of GaAs and AlGaAs, N. Kobayashi and T. Makimoto 82/83 (1994) 284
- Atomic layer epitaxy of ZnSe using reflectance difference spectroscopy, H. Akinaga and K. Tanaka 82/83 (1994) 298
- Surface reaction mechanism in MOMBE-ALE of ZnSe and CdSe as determined by a new in-situ optical probing method, A. Yoshikawa, M. Kobayashi and S. Tokita 82/83 (1994) 316
- Hydrogen atom assisted ALE of silicon, S. Imai and M. Matsumura 82/83 (1994) 322
- Sub-atomic-layer epitaxy of Si using Si₂H₆, Y. Suda, M. Ishida, M. Yamashita and H. Ikeda 82/83 (1994) 332
- Si ALE using chlorine/hydrogen exchange. Fundamentals and films, D.D. Koleske and S.M. Gates 82/83 (1994) 344
- Self-limiting adsorption of thermally cracked SiCl₂H₂ on Si surfaces, C. Sasaoka and A. Usui 82/83 (1994) 348
- Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH₄ and SiH₄ gases, M. Sakuraba, J. Murota, T. Watanabe, Y. Sawada and S. Ono 82/83 (1994) 354
- Adaptive temperature program ALE of Si_{1-x}Ge_x/Si heterostructures from Si₂H₆/Ge₂H₆, S. Asami, N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt 82/83 (1994) 359
- Atomic layer epitaxy of germanium, S. Sugahara, T. Kitamura, S. Imai and M. Matsumura 82/83 (1994) 380
- Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane, H. Akazawa 82/83 (1994) 394
- Boron δ -doping in Si using atmospheric pressure CVD, Y. Kiyota, T. Nakamura and T. Inada 82/83 (1994) 400
- Mechanisms of SiC growth by alternate supply of SiH₂Cl₂ and C₂H₂, H. Nagasawa and Y. Yamaguchi 82/83 (1994) 405
- Isothermal H₂ desorption kinetics from Si(100)2 × 1: dependence on disilane

- and atomic hydrogen precursors, L.A. Okada, M.L. Wise and S.M. George 82/83 (1994) 410
- Atomic layer epitaxy in the growth of complex thin film structures for electroluminescent applications, L. Niinistö and M. Leskelä 82/83 (1994) 454
- Atomic layer controlled deposition of SiO_2 and Al_2O_3 using ABAB... binary reaction sequence chemistry, S.M. George, O. Sneh, A.C. Dillon, M.L. Wise, A.W. Ott, L.A. Okada and J.D. Way 82/83 (1994) 460
- NbCl_5 as a precursor in atomic layer epitaxy, K.-E. Elers, M. Ritala, M. Leskelä and E. Rauhala 82/83 (1994) 468
- Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi 82/83 (1994) 494
- Steric and electronic interactions between source gas and substrate surface during the Al-CVD/Al selective epitaxy process as investigated by quantum chemical calculations, R. Vetrivel, R. Yamauchi, H. Yamano, M. Kubo, A. Miyamoto and T. Ohta 82/83 (1994) 516
- The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen 82/83 (1994) 553
- Pretreatment of silicon substrates for CVD diamond deposition studied by atomic force microscopy, G. Friedbacher, E. Bouveresse, G. Fuchs, M. Grasserbauer, D. Schwarzbach, R. Haubner and B. Lux 84 (1995) 133
- Carrier transport in heavily doped polycrystalline silicon layers after annealing by a scanning laser beam, A.K. Fedotov, M.I. Tarasik and A.M. Yanchenko 84 (1995) 379
- Laser-induced forward transfer of ultra-fine diamond particles for selective deposition of diamond films, S.M. Pimenov, G.A. Shafeev, A.A. Smolin, V.I. Konov and B.K. Vodolaga 86 (1995) 208
- Tunable UV-flash krypton lamp array useful for large area deposition and in situ UV annealing of Si-based dielectrics, J. Flicstein, Y. Vitel, O. Dulac, C. Debauche, Y.I. Nissim and C. Licoppe 86 (1995) 286
- Improvement of silicon oxide film properties by ultraviolet excimer lamp annealing, E.G. Parada, P. González, J. Serra, B. León, M. Pérez-Amor, J. Flicstein and R.A.B. Devine 86 (1995) 294
- UV light irradiation effects on nucleation during chemical vapor deposition of Al films, M. Hanabusa and A. Komatsu 86 (1995) 428
- Photoassisted growth of II-VI semiconductor films, Sz. Fujita and Sg. Fujita 86 (1995) 431
- Photo-assisted growth and characterization of $\text{Zn}_x\text{Cd}_{1-x}\text{S}$ by MOVPE, H. Dumont, Sz. Fujita and Sg. Fujita 86 (1995) 442
- Interrupted cycle chemical beam epitaxy of gallium phosphide on silicon with or without photon assistance, J.T. Kelliher, A.E. Miller, N. Dietz, S. Habermehl, Y.L. Chen, Z. Lu, G. Lucovsky and K.J. Bachmann 86 (1995) 453
- Laser chemical vapour deposition for microelectronics, G. Auvert 86 (1995) 466
- Laser processing of tungsten from WF_6 and SiH_4 , M. Meunier, P. Desjardins, M. Tabbal, N. Elyaagoubi, R. Izquierdo and A. Yelon 86 (1995) 475
- Laser-induced etching and deposition of tungsten in $\text{WF}_6\text{-H}_2$ atmosphere, K. Piglmayer, Z. Tóth and Z. Kantor 86 (1995) 484
- Kinetics of laser thermal decomposition of trimethylamine alane, D. Tonneau, J.E. Bourée and Y. Pauleau 86 (1995) 488
- The effect of process parameters on the O/Mo ratio in laser deposition of molybdenum oxides from aqueous solutions, K. Bali, Zs. Geretovszky, A.L. Tóth and T. Szőrényi 86 (1995) 500
- Excimer laser-induced deposition of copper from $\text{Cu}(\text{hfac})(\text{TMVS})$, R. Izquierdo, J. Bertomeu, M. Suys, E. Sacher and M. Meunier 86 (1995) 509
- Laser induced deposition of nanocrystalline Si with preferred crystallographic orientation, S. Tamir and S. Berger 86 (1995) 514
- VUV laser (157 nm) chemical vapor deposition of high quality amorphous hydrogenated silicon: gas phase chemistry and modelling, H. Karstens, J. Knobloch, A. Winkler, A. Pusel, M. Barth and P. Hess 86 (1995) 521
- Germanium-containing coatings by IR laser-induced decomposition of ethoxy-(trimethyl)germane and tetramethylgermane, R. Fajgar, M. Jakoubková, Z. Bastl and J. Pola 86 (1995) 530
- P-doped polycrystalline silicon films obtained at low temperature by hot-wire chemical vapor deposition, J. Puigdollers, J. Cifre, M.C. Polo, J.M. Asensi, J. Bertomeu, J. Andreu and A. Lloret 86 (1995) 600
- Erratum to "Characterization of adsorption in flow type atomic layer epitaxy reactor" [Appl. Surf. Sci. 81 (1994) 281], J. Aarik and H. Siimon 90 (1995) 109

Chromium

- The partitioning of substitutional solute elements during the tempering of marten-

- site in Cr and Mo containing steels, R.C. Thomson and M.K. Miller 87/88 (1995) 185
- Microstructure of heat resistant chromium steel weld metals, H.-O. Andrén, G. Cai and L.-E. Svensson 87/88 (1995) 200
- Structure and chemistry of grain boundaries in Ni-16Cr-9Fe model materials, M. Thuvander and K. Stiller 87/88 (1995) 251
- APFIM study of the compositional inhomogeneity of sputtered Co-Cr magnetic thin film, A. Pundt and C. Michaelson 87/88 (1995) 264
- A study of the effect of ageing temperature on phase separation in Fe-45%Cr alloys, J.M. Hyde, M.K. Miller, A. Cerezo and G.D.W. Smith 87/88 (1995) 311
- Comparison of low temperature decomposition in Fe-Cr and duplex stainless steels, M.K. Miller, J.M. Hyde, A. Cerezo and G.D.W. Smith 87/88 (1995) 323
- Surface studies of Cu/Cr/Ag impregnated microporous carbons, R.H. Bradley 90 (1995) 271
- Peak fitting of the chromium 2p XPS spectrum, A.M. Salvi, J.E. Castle, J.F. Watts and E. Desimoni 90 (1995) 333
- Rapid thermal nitridation of thin chromium films, S.W. Russell, J. Li, T.L. Alford, P.R. Oakey and S.C. Shatas 90 (1995) 455
- Clusters**
- Formation processes of ultrafine metal particles on MgO(100) as investigated by molecular dynamics and computer graphics, M. Kubo, R. Yamauchi, R. Vetrivel and A. Miyamoto 82/83 (1994) 559
- Cobalt**
- Adsorption of CO on Mg-promoted Co(poly), J. Vaari, T. Vaara, J. Lahtinen and P. Hautojärvi 81 (1994) 289
- Surface characterization by time-of-flight SIMS of a catalyst for oxygen electroreduction: pyrolyzed cobalt phthalocyanine-on-carbon black, L.T. Weng, P. Bertrand, G. Lalande, D. Guay and J.P. Dodelet 84 (1995) 9
- APFIM study of the compositional inhomogeneity of sputtered Co-Cr magnetic thin film, A. Pundt and C. Michaelson 87/88 (1995) 264
- Reactions of CO and NO on Mg promoted cobalt, T. Vaara, J. Lahtinen and P. Hautojärvi 89 (1995) 103
- Etching of CoSi₂ in HF-based solutions, R.A. Donaton, K. Lokere, R. Verbeeck and K. Maex 89 (1995) 221
- Activation treatments and surface study of amorphous Fe₉₀Zr₁₀ and Fe_{87.8}Zr₁₀ Co₂Al_{0.2} catalysts, X.K. Wang, N.F. Shen, Z.S. Yang and H.C. Gu 89 (1995) 297
- Computer simulations**
- Theoretical estimation of ordered metal species in zeolite pores, H. Himei, E. Maruya, M. Kubo, R. Vetrivel and A. Miyamoto 82/83 (1994) 543
- Surface barrier sensitivity of positronium formation at surfaces, A. Ishii and T. Aisaka 85 (1995) 33
- Positron implantation profiles in elemental and multilayer systems, V.J. Ghosh 85 (1995) 187
- VEPFIT applied to depth profiling problems, A. van Veen, H. Schut, M. Clement, J.M.M. de Nijs, A. Kruseman and M.R. Ijpma 85 (1995) 216
- Extension of the PC version of VEPFIT with input and output routines running under Windows, H. Schut and A. van Veen 85 (1995) 225
- Mechanism of the formation of ultrafine gold particles on MgO(100) as investigated by molecular dynamics and computer graphics, M. Kubo, R. Miura, R. Yamauchi, R. Vetrivel and A. Miyamoto 89 (1995) 131
- Preferential sputtering of argon ion bombarded Ni₃Al and TaSi₂, S. Hofmann and M.G. Stepanova 90 (1995) 227
- Copper**
- XPS study of clean metal sulfide surfaces, K. Laajalehto, I. Kartio and P. Nowak 81 (1994) 11
- Surface segregation study of Ib-VIII single-crystal alloys, F. Reniers, M.P. Delplancke, A. Asskali, M. Jardinier-Offergeld and F. Bouillon 81 (1994) 151
- Effects of atomic hydrogen on Cu(II)bis-hexafluoroacetylacetonate interactions with a TiN surface, G. Nuesca, J. Prasad and J.A. Kelber 81 (1994) 237
- The hydroxylation of Cu(111) and Zn(0001) surfaces, A.F. Carley, P.R. Davies, M.W. Roberts, N. Shukla, Y. Song and K.K. Thomas 81 (1994) 265
- The electrochemical faceting of copper in 85% aqueous o-phosphoric acid by using a potential reversal technique, A. Hernández Creus, R.M. Souto, S. González, M.M. Laz, R.C. Salvarezza and A.J. Arvia 81 (1994) 387

- CO adsorption on clean and atomic-layer-Cu-covered ZnO(10 $\bar{1}$ 0) surfaces, Q. Ge and P.J. Møller 82/83 (1994) 305
- Influence of atomic Cu-layer epitaxy on CO₂ and CO photoinduced desorption from ZnO(0001), P.J. Møller, S.A. Komolov and E.F. Lazneva 82/83 (1994) 569
- Copper oxidation and surface copper oxide stability investigated by pulsed field desorption mass spectrometry, D.L. Cocke, G.K. Chuah, N. Kruse and J.H. Block 84 (1995) 153
- High Resolution Electron Energy Loss Spectroscopy investigation of the copper/polyphenylquinoxaline interface formation, Ch. Grégoire, J.-J. Pireaux, A. Cros and R. Caudano 84 (1995) 163
- Surface alloy formation in Pd/Ag, Cu/Au and Ni/Au bimetallic overlayers, A.K. Santra and C.N.R. Rao 84 (1995) 347
- Composition of sputtered material from Cu-Ni alloy during Xe⁺ ion sputtering at elevated temperatures, S. Sekine, H. Shimizu and S. Ichimura 84 (1995) 401
- Study of positron surface states on the alkali-metal-covered transition-metal surface, N.G. Fazleev, J.L. Fry, K. Kuttler, A.R. Koymen and A.H. Weiss 85 (1995) 26
- Work function and epithermal positron emission from copper, N. Overton, A.P. Knights, A. Goodyear and P.G. Coleman 85 (1995) 54
- Pulsed laser ablation of copper, R. Jordan, D. Cole, J.G. Lunney, K. Mackay and D. Givord 86 (1995) 24
- Laser-assisted selective metallisation of diamonds by electroless Ni and Cu plating, G.A. Shafeev, S.M. Pimenov and E.N. Loubnin 86 (1995) 392
- Excimer laser-induced deposition of copper from Cu(hfac)(TMVS), R. Izquierdo, J. Bertomeu, M. Suys, E. Sacher and M. Meunier 86 (1995) 509
- Laser chemical etching of Cu₂O, G. Stenberg, M. Boman, M. Ottosson and J.-O. Carlsson 86 (1995) 543
- Nucleation and growth of θ' precipitation in Sn-modified Al-Cu alloys: APFIM/TEM observations, S.P. Ringer, K. Hono and T. Sakurai 87/88 (1995) 223
- APFIM and XPS study of the first stages of low temperature air oxidation of industrial CuNi alloys, R. Souchet, F. Danoix, A. D'Huysser and M. Lenglet 87/88 (1995) 271
- 3D reconstruction of antiphase boundaries in Cu₃Au from field ion images, S. Duval, S. Chambrelaud, D. Blavette, A. Loiseau and L. Potez 87/88 (1995) 284
- FIM/AP analysis of Cu-Pd multilayers, T. Al-Kassab, M.-P. Macht and H. Wollenberger 87/88 (1995) 329
- Adsorption and film growth of BTA on clean and oxygen adsorbed Cu(110) surfaces, K. Cho, J. Kishimoto, T. Hashizume, H.W. Pickering and T. Sakurai 87/88 (1995) 380
- MnCu surface alloy studied by scanning tunneling microscopy, D. Jeon, H.P. Noh, T. Hashizume, Y. Kuk and T. Sakurai 87/88 (1995) 386
- Adsorption of fullerenes on Cu(111) and Ag(111) surfaces, T. Sakurai, X.D. Wang, T. Hashizume, V. Yurov, H. Shinohara and H.W. Pickering 87/88 (1995) 405
- Fabrication of microtips on planar specimens, D.J. Larson, C.-M. Teng, P.P. Camus and T.F. Kelly 87/88 (1995) 446
- An investigation of the thermal stability of undecylimidazole on copper by FT-IR reflection-absorption spectroscopy, S. Yoshida and H. Ishida 89 (1995) 39
- Growth of a surface film on copper from benzotriazole solutions, G. Xue, J. Ding and P. Cheng 89 (1995) 77
- M-S (M = Mo, W) cluster compound films on copper surfaces, X.R. Ye, H.W. Hou, X.Q. Xin and C.F. Hammer 89 (1995) 151
- Dependence of electromigration rate on applied electric potential, B.H. Jo and R.W. Vook 89 (1995) 237
- Diffusion of Ag on Cu(110) and Cu(111) studied by spatially resolved UV-photoemission, U. Kürpick, G. Meister and A. Goldmann 89 (1995) 383
- Synergistic alloying behaviour of Pd₅₀Cu₅₀ single crystals upon adsorption and co-adsorption of CO and NO, Y. Debauge, M. Abon, J.C. Bertolini, J. Massardier and A. Rochefort 90 (1995) 15
- Erratum to "Nucleation and growth of θ' precipitation in Sn-modified Al-Cu alloys: APFIM/TEM observations" [Appl. Surf. Sci. 87/88 (1995) 223], S.P. Ringer, K. Hono and T. Sakurai 90 (1995) 107
- The reactivity of O₂/H₂, O₂/CO and O₂/C₃H₆ gas mixtures on Cu(111), W.E.J. Van Kooten, J.P.C. Van Nispen, O.L.J. Gijzeman and J.W. Geus 90 (1995) 137
- XPS/NRA investigations of particle size effects during the oxidation of Cu particles supported on oxidised Si(100), R. Van Wijk, P.C. Görts, A.J.M. Mens, O.L.J. Gijzeman, F.H.P.M. Habraken and J.W. Geus 90 (1995) 261
- Surface studies of Cu/Cr/Ag impregnated microporous carbons, R.H. Bradley 90 (1995) 271

- Atomic hydrogen adsorption on sintered thin copper films, R. Duś, E. Nowicka, W. Lisowski and Z. Wolfram

90 (1995) 277

Depth profiling

- Diamond nucleation and growth at the early stages on Si(100) monitored by electron spectroscopies, F. Le Normand, A. Ababou, N. Brault, B. Carrière, L. Fayette, B. Marcus, M. Mermoux, M. Romeo and C. Speisser

81 (1994) 309

- A comparison of X-ray photoelectron spectroscopy and Auger electron spectroscopy depth profiles for magnesium implants, J.A. Schreifels, N.H. Turner and R.E. Morris

84 (1995) 23

- Defect profiling in multilayered systems using mean depth scaling, G.C. Aers, P.A. Marshall, T.C. Leung and R.D. Goldberg

85 (1995) 196

- Defect profiling in elemental and multilayer systems: correlations of fitted defect concentrations with positron implantation profiles, V.J. Ghosh, B. Nielsen, K.G. Lynn and D.O. Welch

85 (1995) 210

- VEPFIT applied to depth profiling problems, A. van Veen, H. Schut, M. Clement, J.M.M. de Nijs, A. Kruseman and M.R. Ijpma

85 (1995) 216

- Depth profiles of defects in Ar-ion-irradiated steels determined by a least-squares fit of *S* parameters from variable-energy positron annihilation, T. Aruga, S. Takamura, K. Nakata and Y. Ito

85 (1995) 229

- Surface segregation of Sb in doped TiO₂ rutile, A. Gulino, G.G. Condorelli, I. Fragalà and R.G. Egdel

90 (1995) 289

Deuterium

- Temperature-programmed-desorption study of the process of atomic deuterium adsorption onto Si(100)2 × 1, M. Sue-mitsu, H. Nakazawa and N. Miyamoto

82/83 (1994) 449

Diamond

- Diamond nucleation and growth at the early stages on Si(100) monitored by electron spectroscopies, F. Le Normand, A. Ababou, N. Brault, B. Carrière, L. Fayette, B. Marcus, M. Mermoux, M. Romeo and C. Speisser

81 (1994) 309

- Pretreatment of silicon substrates for CVD diamond deposition studied by atomic

- force microscopy, G. Friedbacher, E. Bouveresse, G. Fuchs, M. Grasserbauer, D. Schwarzbach, R. Haubner and B. Lux

84 (1995) 133

- Effect of laser power density and deposition temperature on electrical and optical properties of pulsed laser ablated diamond-like carbon films, J. Levoska and S. Leppävuori

86 (1995) 180

- Laser-induced forward transfer of ultra-fine diamond particles for selective deposition of diamond films, S.M. Pimenov, G.A. Shafeev, A.A. Smolin, V.I. Konov and B.K. Vodolaga

86 (1995) 208

- Excimer laser etching of diamond-like carbon films: spalling effect, T.V. Kononenko, V.G. Ralchenko, E.D. Obraztsova, V.I. Konov, J. Seth, S.V. Babu and E.N. Loubnin

86 (1995) 234

- Laser-assisted selective metallisation of diamonds by electroless Ni and Cu plating, G.A. Shafeev, S.M. Pimenov and E.N. Loubnin

86 (1995) 392

- Microstructure and field emission of diamond particles on silicon tips, E.I. Givargizov, V.V. Zhimov, A.N. Stepanova, E.V. Rakova, A.N. Kiselev and P.S. Plekhanov

87/88 (1995) 24

Dielectric constant

- Measurement of oxide thickness using a variable-energy positron beam, T.C. Leung, P.J. Simpson, A. Atkinson, I.V. Mitchell and P.J. Schultz

85 (1995) 292

Diffusion

- Buried-oxide layer formation by high-dose oxygen-ion implantation into Si wafers: SIMOX (separation by implanted oxygen), K. Kajiyama

85 (1995) 259

- Adsorption and film growth of BTA on clean and oxygen adsorbed Cu(110) surfaces, K. Cho, J. Kishimoto, T. Hashizume, H.W. Pickering and T. Sakurai

87/88 (1995) 380

Doping effects

- Silicon doping with modulated beam epitaxy in the growth of GaAs(111)A, M.R. Fahy, K. Sato and B.A. Joyce

82/83 (1994) 14

- Substrate misorientation dependence of thermal stability of Si atom in Si atomic layer doped GaAs on GaAs(111)A, M.

- Hirai, H. Ohnishi, K. Fujita and T. Watanabe 82/83 (1994) 23
- Atomic layer epitaxy growth of doped zinc oxide thin films from organometals, V. Lujala, J. Skarp, M. Tammenmaa and T. Suntola 82/83 (1994) 34
- Carbon incorporation mechanism in atomic layer epitaxy of GaAs and AlGaAs, N. Kobayashi and T. Makimoto 82/83 (1994) 284
- Suppression of HBO₂ and Sb adsorption on thin-oxide-covered, H-terminated, or Sb-terminated Si(100) surfaces, E. Murakami, H. Kujirai and S. Kimura 82/83 (1994) 338
- Boron δ -doping in Si using atmospheric pressure CVD, Y. Kiyota, T. Nakamura and T. Inada 82/83 (1994) 400
- Electron microscopy of the ordered boron 2 \times 1 structure buried in crystalline silicon, B.E. Weir, D.J. Eaglesham, L.C. Feldman, H.S. Luftman and R.L. Headrick 84 (1995) 413
- Elastic recoil detection*
- Low temperature adsorption of hydrogen on Si(111) and (100) surfaces studied by elastic recoil detection analysis, M. Watamori, M. Naitoh, H. Morioka, Y. Maeda and K. Oura 82/83 (1994) 417
- Electrical properties*
- Temperature dependence of surface charging of NaCl under electron irradiation: role of secondary electron emission, W.G. Durrer, M. Portillo, P. Wang and D.P. Russell 81 (1994) 215
- Surface states in the band-gap for Pt-deposited p-InP photoelectrochemical cells, H. Kobayashi, F. Mizuno and Y. Nakato 81 (1994) 399
- Ideal static induction transistor implemented with molecular layer epitaxy, P. Plotka, T. Kurabayashi, Y. Oyama and J. Nishizawa 82/83 (1994) 91
- Flow modulation epitaxy of Ga_xIn_{1-x}As/AlAs heterostructures on InP for resonant tunneling diodes, B.P. Keller, J.C. Yen, A.L. Holmes Jr., S.P. DenBaars and U.K. Mishra 82/83 (1994) 126
- Electrical properties of Si-Al₂O₃ structures grown by ML-ALE, V.E. Drozd, A.P. Baraban and I.O. Nikiforova 82/83 (1994) 583
- Effect of laser power density and deposition temperature on electrical and optical properties of pulsed laser ablated diamond-like carbon films, J. Levoska and S. Leppävuori 86 (1995) 180
- Laser-induced formation of porous silicon, V. Baranauskas, G.P. Thim and A. Peled 86 (1995) 398
- Electrochemical and photoelectrochemical modification and characterisation of thin passive films, O. Blum and U. König 86 (1995) 417
- VUV laser (157 nm) chemical vapor deposition of high quality amorphous hydrogenated silicon: gas phase chemistry and modelling, H. Karstens, J. Knobloch, A. Winkler, A. Pusel, M. Barth and P. Hess 86 (1995) 521
- Capacitance-voltage characteristics of Schottky barrier diode in the presence of deep-level impurities and series resistance, P. Chattopadhyay and S. Sanyal 89 (1995) 205
- Dependence of electromigration rate on applied electric potential, B.H. Jo and R.W. Vook 89 (1995) 237
- Cadmium selenide-amorphous hydrogenated silicon heterostructures, S. Wu and D. Haneman 89 (1995) 289
- Influence of surface charge on thermal positive ion emission from potassium bromide, M.F. Butman, J. Nakamura, S. Kamidoi and H. Kawano 89 (1995) 323
- Experimental study of passivating ion-beam-induced distributed energy levels in n-GaAs by hydrogen species from boiling water, I. Thurzo, E. Pincik, G. Papaioannou, P. Dimitrakakis and N. Arpatzanis 90 (1995) 39
- Atomic hydrogen adsorption on sintered thin copper films, R. Duś, E. Nowicka, W. Lisowski and Z. Wolfram 90 (1995) 277
- Charge transfer processes in a-WO₃/Si heterostructure during electro- and photochromism, E.A. Tutov and A.A. Baev 90 (1995) 303
- Scanned laser spot photocurrent response studies of surface modifications of CdSe thin film electrodes, X.R. Xiao, Y. Lin, Y. Yang, X.G. Chen and J.K. You 90 (1995) 321
- Morphology, atomic composition and photoelectric properties of the microrelief InP-electrolyte interface, N.L. Dmitruk, E.V. Basiuk, G.Ya. Kolbasov, O.A. Yakubtsov, I.A. Molchanovskii and T.A. Taranets 90 (1995) 489
- Characterization of the plasma plume and of thin film epitaxially produced during laser ablation of SnSe, R. Teghil, A. Santagata, V. Marotta, S. Orlando, G. Pizzella, A. Giardini-Guidoni and A. Mele 90 (1995) 505
- Electromigration*
- Dependence of electromigration rate on applied electric potential, B.H. Jo and R.W. Vook 89 (1995) 237

Electron bombardment

- Chlorine adsorption on electron beam irradiated GaAs photo-oxides: mechanism of in situ EB lithography, Y. Ide and M. Yamada

82/83 (1994) 310

Electron diffraction

- Auger and X-ray photoelectron diffraction in MgO(001), T.T. Tran and S.A. Chambers 81 (1994) 161
- Diamond nucleation and growth at the early stages on Si(100) monitored by electron spectroscopies, F. Le Normand, A. Ababou, N. Brault, B. Carrière, L. Fayette, B. Marcus, M. Mermoux, M. Romeo and C. Speisser 81 (1994) 309
- Silicon doping with modulated beam epitaxy in the growth of GaAs(111)A, M.R. Fahy, K. Sato and B.A. Joyce 82/83 (1994) 14
- Investigation of a GaN surface structure for the mask of GaAs selective growth using MOMBE, S. Yoshida and M. Sasaki 82/83 (1994) 28
- Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watanabe, F. Maeda and M. Oshima 82/83 (1994) 136
- Surface diffusion and adatom stoichiometry in GaAs MBE studied by microprobe-RHEED/SEM MBE, T. Nishinaga and X.Q. Shen 82/83 (1994) 141
- Surface reactions of Ga and As on Sb-terminated GaAs(001), F. Maeda, Y. Watanabe and M. Oshima 82/83 (1994) 276
- Real time observation of surface dielectric responses of GaAs(001) using surface photo-absorption, K. Uwai and N. Kobayashi 82/83 (1994) 290
- Atomic layer epitaxy of ZnSe using reflectance difference spectroscopy, H. Akinaga and K. Tanaka 82/83 (1994) 298
- Sub-atomic-layer epitaxy of Si using Si₂H₆, Y. Suda, M. Ishida, M. Yamashita and H. Ikeda 82/83 (1994) 332
- Atomic layer epitaxy of germanium, S. Sugahara, T. Kitamura, S. Imai and M. Matsumura 82/83 (1994) 380
- Auger electron diffraction study of the initial stage of Ge heteroepitaxy on Si(001), M. Sasaki, T. Abukawa, H.W. Yeom, M. Yamada, S. Suzuki, S. Sato and S. Kono 82/83 (1994) 387
- Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane, H. Akazawa 82/83 (1994) 394

- Layer controlled growth of oxide superconductors, M. Kawai, Z.-Y. Liu, T. Hanada, M. Katayama, M. Aono and C.F. McConville

82/83 (1994) 487

- Fabrication of CuO₂-plane-based high-temperature superconducting thin films by atomic layer controlled molecular beam epitaxy, I. Yoshida, H. Furukawa, T. Hirose and M. Nakao

82/83 (1994) 501

- A RHEED study of the dynamics of GaAs and AlGaAs growth on a (001) surface by MBE, J. Hopkins, M.R. Leys, J. Brübach, W.C. Van der Vleuten and J.H. Wolter

84 (1995) 299

- Influence of ion bombardment on the refractive index of laser pulse deposited oxide films, G. Reisse, S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz

86 (1995) 107

- Morphology of Si_{1-x}Ge_x thin crystalline films obtained by pulsed-excimer-laser annealing of heavily Ge-implanted Si, E.L. Mathé, A. Naudon, F. Repplinger and E. Fogarassy

86 (1995) 338

- GaAs growth by photon-assisted metalorganic molecular beam epitaxy using ethyl derivatives of gallium and arsenic, F. Maury, K. Bouabid, N. Fazouan, A.M. Gué and D. Estève

86 (1995) 447

- Germanium-containing coatings by IR laser-induced decomposition of ethoxy-(trimethyl)germane and tetramethylgermane, R. Fajgar, M. Jakoubková, Z. Bastl and J. Pola

86 (1995) 530

- Microstructure and field emission of diamond particles on silicon tips, E.I. Givargizov, V.V. Zhimov, A.N. Stepanova, E.V. Rakova, A.N. Kiselev and P.S. Plekhanov

87/88 (1995) 24

- Structure of the MBE-grown GaAs(001)-(2 × 4) phase, T. Hashizume, Q.K. Xue, A. Ichimiya and T. Sakurai

87/88 (1995) 373

- Characterization of thin Ag films deposited onto InP(001)-p(2 × 4) surface at room temperature by means of LEED, RHEED, AES and RBS-channeling techniques, M. Hanebuchi, T. Katoh and K. Morita

89 (1995) 113

- Medium energy electron diffraction and X-ray photoelectron diffraction study of pseudomorphic Fe silicides grown on Si(111). Evidence of Fe vacancy formation, S. Hong, C. Pirri, P. Wetzel, D. Bolmont and G. Gewinner

90 (1995) 65

- Conversion film formation on titanium anodes in acetonitrile at high voltages, F. Schlottig, J. Schreckenbach, D. Dietrich, A. Hofmann and G. Marx

90 (1995) 129

- In situ DC-plasma cleaning of silicon surfaces, U. Kafader, H. Sirringhaus and H. von Känel 90 (1995) 297
- Electron emission*
- Secondary electron emission from Ag(100) stimulated by positron and electron impact, A.P. Knights and P.G. Coleman 85 (1995) 43
- Electron energy loss spectroscopy*
- The hydroxylation of Cu(111) and Zn(0001) surfaces, A.F. Carley, P.R. Davies, M.W. Roberts, N. Shukla, Y. Song and K.K. Thomas 81 (1994) 265
- Diamond nucleation and growth at the early stages on Si(100) monitored by electron spectroscopies, F. Le Normand, A. Ababou, N. Brault, B. Carrière, L. Fayette, B. Marcus, M. Mermoux, M. Romeo and C. Speisser 81 (1994) 309
- Adsorption of monoethanolamine on clean, oxidized and hydroxylated aluminium surfaces: a model for amine-cured epoxy/aluminium interfaces, C. Fauquet, P. Dubot, L. Minel, M.-G. Barthés-Labrousse, M. Rei Vilar and M. Villatte 81 (1994) 435
- Chemical reactivity of the Si(111)($\sqrt{3} \times \sqrt{3}$)R30°-B surface: an electron-energy-loss spectroscopy study, Y. Taguchi, M. Daté, N. Takagi, T. Aruga and M. Nishijima 82/83 (1994) 434
- Influence of atomic Cu-layer epitaxy on CO₂ and CO photoinduced desorption from ZnO(0001), P.J. Møller, S.A. Komolov and E.F. Lazneva 82/83 (1994) 569
- High Resolution Electron Energy Loss Spectroscopy investigation of the copper/polyphenylquinoxaline interface formation, Ch. Grégoire, J.-J. Pireaux, A. Cros and R. Caudano 84 (1995) 163
- A multitechnique analysis of the outermost layers of the Teflon PFA surface, K. Piyakis, E. Sacher, A. Domingue, J.-J. Pireaux, G. Leclerc, P. Bertrand and J.B. Lhoest 84 (1995) 227
- The (0001)-surface of 6H-SiC: morphology, composition and structure, U. Starke, Ch. Bram, P.-R. Steiner, W. Hartner, L. Hammer, K. Heinz and K. Müller 89 (1995) 175
- Multiple losses in off-specular electron energy loss spectra of thin NaCl films individually resolved in energy and momentum, V. Zielasek, A. Büssenschütt and M. Henzler 90 (1995) 117
- Electron microscopy*
- Interface study on laser-induced material transfer from polymer and quartz surfaces, S. Lätsch, H. Hiraoka, W. Nieveen and J. Bargon 81 (1994) 183
- Diamond nucleation and growth at the early stages on Si(100) monitored by electron spectroscopies, F. Le Normand, A. Ababou, N. Brault, B. Carrière, L. Fayette, B. Marcus, M. Mermoux, M. Romeo and C. Speisser 81 (1994) 309
- The electrochemical faceting of copper in 85% aqueous o-phosphoric acid by using a potential reversal technique, A. Hernández Creus, R.M. Souto, S. González, M.M. Laz, R.C. Salvarezza and A.J. Arvia 81 (1994) 387
- Epitaxial growth of a two-dimensional structure of GaP on a Si substrate by metalorganic chemical vapor deposition, T. Soga, T. Jimbo and M. Umeno 82/83 (1994) 64
- Migration and related buried epitaxy using digital epitaxial growth conditions, I. Takahashi, M. Nakaji and H. Kawanishi 82/83 (1994) 70
- Growth of In₂S₃ thin films by atomic layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä 82/83 (1994) 122
- Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watanabe, F. Maeda and M. Oshima 82/83 (1994) 136
- Surface diffusion and adatom stoichiometry in GaAs MBE studied by microprobe-RHEED/SEM MBE, T. Nishinaga and X.Q. Shen 82/83 (1994) 141
- In-situ monitoring of 1st-order phase transition on InAs(001) surfaces by scanning electron surface microscopy, H. Yamaguchi, Y. Homma and Y. Horikoshi 82/83 (1994) 223
- Adaptive temperature program ALE of Si_{1-x}Ge_x/Si heterostructures from Si₂H₆/Ge₂H₆, S. Asami, N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt 82/83 (1994) 359
- Atomic layer epitaxy of germanium, S. Sugahara, T. Kitamura, S. Imai and M. Matsumura 82/83 (1994) 380
- Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane, H. Akazawa 82/83 (1994) 394

- NbCl₅ as a precursor in atomic layer epitaxy, K.-E. Elers, M. Ritala, M. Leskelä and E. Rauhala 82/83 (1994) 468
- Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi 82/83 (1994) 494
- Chemical etching of (100) and (110) faces of flux-grown LaBO₃ crystals, A. Jain, A.K. Razdan, P.N. Kotru and B.M. Wanklyn 84 (1995) 65
- Solution growth and characterization of silver sulfide films, I. Grozdanov 84 (1995) 325
- Multi-spectral scanning Auger microscopy of tribological surfaces, I.R. Barkshire, M. Prutton and G.C. Smith 84 (1995) 331
- Laser-induced selective deposition of Ni-P alloy on silicon, J. Wang, X. Fei, Z. Yu and G. Zhao 84 (1995) 383
- Electron microscopy of the ordered boron 2 × 1 structure buried in crystalline silicon, B.E. Weir, D.J. Eaglesham, L.C. Feldman, H.S. Luftman and R.L. Headrick 84 (1995) 413
- Coupling optics for a combined electron positron scanning microscope, L.J. Seijbel, R.F.J. Neelissen, P. Kruit, A. van Veen and H. Schut 85 (1995) 92
- Buried-oxide layer formation by high-dose oxygen-ion implantation into Si wafers: SIMOX (separation by implanted oxygen), K. Kajiyama 85 (1995) 259
- Contrast in positron reemission microscopy due to positron trapping by dislocations, K.F. Canter, G. Amarendra, D. Vasumathi, S.A. Wesley, R. Xie, A.P. Mills, Jr., R.L. Sabatini and Y. Zhu 85 (1995) 339
- Analysis and experimental study of one-photon incubated absorption in polymers, P.E. Dyer, D.M. Karnakis and G.A. Oldershaw 86 (1995) 1
- Laser ablation of BiSrCaCuO superconducting thin film: analysis of intermediate species in real time, U. Gambardella, A. Giardini, V. Marotta, A. Morone, S. Orlando and M. Snels 86 (1995) 45
- Laser ablation of refractory material, cluster formation and deposition, H. Yu, M.G. Huber and F.W. Froben 86 (1995) 74
- Effects of laser wavelength and fluence on the growth of ZnO thin films by pulsed laser deposition, V. Craciun, S. Amirhaghi, D. Craciun, J. Elders, J.G.E. Gardeniers and I.W. Boyd 86 (1995) 99
- Influence of ion bombardment on the refractive index of laser pulse deposited oxide films, G. Reisse, S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz 86 (1995) 107
- Excimer laser sputtering deposition of TiO₂ optical coating for solar cells, H.-A. Durand, J.-H. Brimaud, O. Hellman, H. Shibata, S. Sakuragi, Y. Makita, D. Gesbert and P. Meyrueis 86 (1995) 122
- SiO₂ film deposition by XeCl laser ablation of fused silica, P. Baeri, R. Reitano and N. Marino 86 (1995) 128
- SEM observations of YBCO on as-received and heat-treated MgO substrates, S. King, L. Coccia and I.W. Boyd 86 (1995) 134
- Pulsed laser deposition of epitaxial layers of ZnSe, J.L. Deiss, A. Chergui, L. Koutti, J.L. Loison, M. Robino and J.B. Grun 86 (1995) 149
- Comparison of epitaxial films of Zn_{1-x}Mn_xTe on (111) and (100) GaAs produced by pulsed laser deposition, H.J. Masterson and J.G. Lunney 86 (1995) 154
- Si_{1-x}Ge_x thin films deposited by the pulsed excimer laser ablation technique, F. Antoni, E. Fogarassy, C. Fuchs, B. Prévot and J.P. Stoquert 86 (1995) 175
- Pulsed-laser deposition and characterization of TaC films, R. Teghil, L. D'Alessio, G. De Maria and D. Ferro 86 (1995) 190
- Laser-induced forward transfer of ultra-fine diamond particles for selective deposition of diamond films, S.M. Pimenov, G.A. Shafeev, A.A. Smolin, V.I. Konov and B.K. Vodolaga 86 (1995) 208
- Excimer laser ablation patterning of dielectric layers, J. Ihlemann and B. Wolff-Rottke 86 (1995) 228
- Ablation of nylon-6,6 with UV and IR lasers, C.D. Skordoulis, M. Makropoulou and A.A. Serafetinides 86 (1995) 239
- Tailoring of surface properties by removal and deposition with laser radiation, E.W. Kreutz, H. Frerichs, M. Mertin, D.A. Wesner and W. Pfleging 86 (1995) 266
- Microstructure, chemical composition and properties of the surface layer of M2 steel after laser melting under different conditions, J. Kusiński 86 (1995) 317
- Morphology of Si_{1-x}Ge_x thin crystalline films obtained by pulsed-excimer-laser annealing of heavily Ge-implanted Si, E.L. Mathé, A. Naudon, F. Repplinger and E. Fogarassy 86 (1995) 338
- Formation of poly-Si_{1-x}Ge_x using excimer-laser processing, A. Slaoui, C. Deng, S. Talwar, K.J. Kramer, T.W. Sigmon, J.P. Stoquert and B. Prevot 86 (1995) 346
- Surface morphology and structure modification of silicon layers induced by nanosecond laser radiation, A.V. Demchuk and V.A. Labunov 86 (1995) 353

- Laser-assisted selective metallisation of diamonds by electroless Ni and Cu plating, G.A. Shafeev, S.M. Pimenov and E.N. Loubnin 86 (1995) 392
- Laser-assisted etching-like damage of Si, A.V. Simakin and G.A. Shafeev 86 (1995) 422
- GaAs growth by photon-assisted metalorganic molecular beam epitaxy using ethyl derivatives of gallium and arsenic, F. Maury, K. Bouabid, N. Fazouan, A.M. Gué and D. Estève 86 (1995) 447
- Interrupted cycle chemical beam epitaxy of gallium phosphide on silicon with or without photon assistance, J.T. Kelliher, A.E. Miller, N. Dietz, S. Habermehl, Y.L. Chen, Z. Lu, G. Lucovsky and K.J. Bachmann 86 (1995) 453
- Laser chemical vapour deposition for microelectronics, G. Auvert 86 (1995) 466
- Laser processing of tungsten from WF_6 and SiH_4 , M. Meunier, P. Desjardins, M. Tabbal, N. Elyaagoubi, R. Izquierdo and A. Yelon 86 (1995) 475
- Laser-induced etching and deposition of tungsten in WF_6 - H_2 atmosphere, K. Piglmayer, Z. Tóth and Z. Kantor 86 (1995) 484
- Kinetic model for scanning laser-induced deposition from the liquid phase, Zs. Geretovszky, L. Kelemen, K. Bali and T. Szörényi 86 (1995) 494
- Laser induced deposition of nanocrystalline Si with preferred crystallographic orientation, S. Tamir and S. Berger 86 (1995) 514
- Germanium-containing coatings by IR laser-induced decomposition of ethoxy-(trimethyl)germane and tetramethylgermane, R. Fajgar, M. Jakoubková, Z. Bastl and J. Pola 86 (1995) 530
- Excimer-laser-induced etching of silicon in chlorine atmosphere at a wavelength of 248 nm, W. Jiang, H. Baumgärtner and I. Eisele 86 (1995) 564
- Three-dimensional nanostructures by direct laser etching of Si, M. Müllenborn, H. Dirac and J.W. Petersen 86 (1995) 568
- P-doped polycrystalline silicon films obtained at low temperature by hot-wire chemical vapor deposition, J. Puigdollers, J. Cifre, M.C. Polo, J.M. Asensi, J. Bertomeu, J. Andreu and A. Lloret 86 (1995) 600
- Microstructure and field emission of diamond particles on silicon tips, E.I. Givargizov, V.V. Zhimov, A.N. Stepanova, E.V. Rakova, A.N. Kiselev and P.S. Plekhanov 87/88 (1995) 24
- Microstructure of heat resistant chromium steel weld metals, H.-O. Andrén, G. Cai and L.-E. Svensson 87/88 (1995) 200
- Characterization of neutron-irradiated Fe-Au alloys, M.K. Miller, K.F. Russell, A. Jostsons and R.G. Blake 87/88 (1995) 216
- Nucleation and growth of θ' precipitation in Sn-modified Al-Cu alloys: APFIM/TEM observations, S.P. Ringer, K. Hono and T. Sakurai 87/88 (1995) 223
- An APFIM/TEM investigation of the discontinuous precipitation in a Ni-In alloy, G.P. Geber 87/88 (1995) 234
- Structure and chemistry of grain boundaries in Ni-16Cr-9Fe model materials, M. Thuvander and K. Stiller 87/88 (1995) 251
- 3D reconstruction of antiphase boundaries in Cu_3Au from field ion images, S. Duval, S. Chambrelaud, D. Blavette, A. Loiseau and L. Potez 87/88 (1995) 284
- Microfabrication of extraction electrodes for local-electrode atom probes, S.S. Bajikar, T.F. Kelly, C.-M. Teng and P.P. Camus 87/88 (1995) 438
- Etching of $CoSi_2$ in HF-based solutions, R.A. Donaton, K. Lokere, R. Verbeeck and K. Maex 89 (1995) 221
- The effect of anodic polarization on a Ag electrode deposited on YSZ solid electrolyte, J.K. Hong, I.-H. Oh, S.-A. Hong and W.Y. Lee 89 (1995) 229
- Dependence of electromigration rate on applied electric potential, B.H. Jo and R.W. Vook 89 (1995) 237
- Activation treatments and surface study of amorphous $Fe_{90}Zr_{10}$ and $Fe_{87.8}Zr_{10}Co_{2-}Al_{0.2}$ catalysts, X.K. Wang, N.F. Shen, Z.S. Yang and H.C. Gu 89 (1995) 297
- Deposition by laser ablation and characterization of titanium dioxide films on polyethylene-terephthalate, N. Lobstein, E. Millon, A. Hachimi, J.F. Muller, M. Alnot and J.J. Ehrhardt 89 (1995) 307
- Interfacial reaction of NiO with Al_2O_3 ($11\bar{2}0$) and polycrystalline $\alpha-Al_2O_3$, P.H. Bolt, S.F. Lobner, J.W. Geus and F.H.P.M. Habraken 89 (1995) 339
- Characterization of nickel films deposited by cold remote nitrogen plasma on acrylonitrile-butadiene-styrene copolymer, A. Brocherieux, O. Dessaux, P. Goudmand, L. Gengembre, J. Grimblot, M. Brunel and R. Lazzaroni 90 (1995) 47
- Thermal etching of $\alpha-Zr$ single-crystal surfaces, H. Zou, G.M. Hood, R.J. Schultz and J.A. Roy 90 (1995) 59
- Ferroelectric $BaTiO_3$ films with a high-magnitude dielectric constant grown on p-Si by low-pressure metalorganic chemical vapor deposition, T.W. Kim, Y.S. Yoon, S.S. Yom and C.O. Kim 90 (1995) 75

- Synthesis of molybdenum nitride $\gamma\text{-Mo}_2\text{N}$ by multipulse laser irradiation of molybdenum in nitrogen, J.D. Wu, C.Z. Wu, Z.M. Song, L.H. Wu and F.M. Li 90 (1995) 81
- Erratum to "Nucleation and growth of θ' precipitation in Sn-modified Al-Cu alloys: APFIM/TEM observations" [Appl. Surf. Sci. 87/88 (1995) 223], S.P. Ringer, K. Hono and T. Sakurai 90 (1995) 107
- Pulse plasma beam deposition of cubic boron nitride films on GCr15 steel bearing substrate at room temperature, P. Yan and S.-Z. Yang 90 (1995) 149
- Surface studies of oil-seal degradation, G.C. Smith, D. Park, K.J. Titchener, R.E. Davies and R.H. West 90 (1995) 357
- Morphology, atomic composition and photoelectric properties of the microrelief InP-electrolyte interface, N.L. Dmitruk, E.V. Basiuk, G.Ya. Kolbasov, O.A. Yakubtsov, I.A. Molchanovskii and T.A. Taranets 90 (1995) 489
- Characterization of the plasma plume and of thin film epitaxially produced during laser ablation of SnSe, R. Teghil, A. Santagata, V. Marotta, S. Orlando, G. Pizzella, A. Giardini-Guidoni and A. Mele 90 (1995) 505
- Electron spin resonance*
- Improvement of silicon oxide film properties by ultraviolet excimer lamp annealing, E.G. Parada, P. González, J. Serra, B. León, M. Pérez-Amor, J. Flicstein and R.A.B. Devine 86 (1995) 294
- Ellipsometry*
- Photoreflectance of strained $\text{Si}_{1-x}\text{Ge}_x$ epilayers ($0.07 \leq x \leq 0.26$) and comparison with spectroscopic ellipsometry, R.T. Carline, C. Pickering, T.J.C. Hosea and D.J. Robbins 81 (1994) 475
- In situ ellipsometric diagnostics for controlled growth of metal oxides with surface chemical reactions, H. Kumagai and K. Toyoda 82/83 (1994) 481
- Synthesis of oxide superalloys by ML-ALE method, V.E. Drozd, A.A. Tulub, V.B. Aleskovski and D.V. Korol'kov 82/83 (1994) 587
- In-situ spectroscopic ellipsometry to control the growth of Ti nitride and carbide thin films, S. Logothetidis, I. Alexandrou and J. Stoemenos 86 (1995) 185
- Effect of UV annealing of radiation damage in SiO_2 films, I.P. Lisovskii, V.G. Litovchenko and V.B. Lozinskii 86 (1995) 299
- Plasma-enhanced reactively evaporated deposition of SiO_2 films, A.A. Shklyayev and A.S. Medvedev 89 (1995) 49
- Deposition by laser ablation and characterization of titanium dioxide films on polyethylene-terephthalate, N. Lobstein, E. Millon, A. Hachimi, J.F. Muller, M. Alnot and J.J. Ehrhardt 89 (1995) 307
- Tantalum oxide film formation by excimer laser ablation, Y. Nishimura, H. Ujita and M. Tsuji 89 (1995) 393
- The reactivity of O_2/H_2 , O_2/CO and $\text{O}_2/\text{C}_3\text{H}_6$ gas mixtures on Cu(111), W.E.J. Van Kooten, J.P.C. Van Nispen, O.L.J. Gijzeman and J.W. Geus 90 (1995) 137
- An ellipsometric procedure for the characterization of very thin surface films on absorbing substrates, T. Easwarakhanthan, S. Ravelet and P. Renard 90 (1995) 251
- Epitaxy*
- Nucleation during molecular beam epitaxy, V.P. Zhdanov and P.R. Norton 81 (1994) 109
- Surface segregation study of Ib-VIII single-crystal alloys, F. Reniers, M.P. Delplancke, A. Asskali, M. Jardinier-Offergeld and F. Bouillon 81 (1994) 151
- Characterization of adsorption in flow type atomic layer epitaxy reactor, J. Aarik and H. Siimon 81 (1994) 281
- Photoreflectance of strained $\text{Si}_{1-x}\text{Ge}_x$ epilayers ($0.07 \leq x \leq 0.26$) and comparison with spectroscopic ellipsometry, R.T. Carline, C. Pickering, T.J.C. Hosea and D.J. Robbins 81 (1994) 475
- Molecular layer epitaxy of GaAs, J. Nishizawa 82/83 (1994) 1
- Recent advances in atomic layer epitaxy devices, S.M. Bedair and N.A. El-Masry 82/83 (1994) 7
- Silicon doping with modulated beam epitaxy in the growth of GaAs(111)A, M.R. Fahy, K. Sato and B.A. Joyce 82/83 (1994) 14
- Atomic layer epitaxy of device quality Al-GaAs and AlAs, N. Hayafuji, G.M. El-dallal, A. Dip, P.C. Colter, N.A. El-Masry and S.M. Bedair 82/83 (1994) 18
- Atomic layer epitaxy growth of doped zinc oxide thin films from organometals, V. Lujala, J. Skarp, M. Tammenmaa and T. Suntola 82/83 (1994) 34
- Selective MLE growth of GaAs and surface treatment for ideal static induction tran-

- sistor (ISIT) application, Y. Oyama, P. Plotka and J. Nishizawa 82/83 (1994) 41
- Pulsed-jet epitaxy: application to device processes, Y. Sakuma, M. Ozeki, N. Ohtsuka, Y. Matsumiya, H. Shigematsu, O. Ueda, S. Muto, K. Nakajima and N. Yokoyama 82/83 (1994) 46
- Surface processes of selective growth by atomic layer epitaxy, H. Isshiki, Y. Aoyagi, T. Sugano, S. Iwai and T. Meguro 82/83 (1994) 57
- Epitaxial growth of a two-dimensional structure of GaP on a Si substrate by metalorganic chemical vapor deposition, T. Soga, T. Jimbo and M. Umeno 82/83 (1994) 64
- Migration and related buried epitaxy using digital epitaxial growth conditions, I. Takahashi, M. Nakaji and H. Kawanishi 82/83 (1994) 70
- Growth temperature dependence of optical properties of gas source MBE grown GaP/AIP short period superlattices, J.H. Kim, H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda 82/83 (1994) 76
- Fabrication of smooth facets of InP by selective sidewall epitaxy using CBE, M. Gotoda, H. Sugimoto, S. Maruno, T. Isu, W. Susaki and M. Nunoshita 82/83 (1994) 80
- Selective epitaxial growth of GaInP by LP-MOCVD using ethyldimethylindium, trimethylindium, trimethylgallium and triethylgallium as group III sources, S.-H. Chan, S.M. Sze, C.-Y. Chang and W.-I. Lee 82/83 (1994) 85
- Ideal static induction transistor implemented with molecular layer epitaxy, P. Plotka, T. Kurabayashi, Y. Oyama and J. Nishizawa 82/83 (1994) 91
- Temperature synchronized molecular layer epitaxy, T. Kurabayashi and J. Nishizawa 82/83 (1994) 97
- Autocompensation in Si planar doped GaAs, T. Suzuki, H. Goto, N. Sawaki, H. Ito and K. Hara 82/83 (1994) 103
- Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda 82/83 (1994) 109
- Growth of In_2S_3 thin films by atomic layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä 82/83 (1994) 122
- Flow modulation epitaxy of $\text{Ga}_x\text{In}_{1-x}\text{As}$ /AlAs heterostructures on InP for resonant tunneling diodes, B.P. Keller, J.C. Yen, A.L. Holmes Jr., S.P. DenBaars and U.K. Mishra 82/83 (1994) 126
- AlAs layers with low carbon content grown by ALE using ethyldimethylamine alane as a new aluminum source, N. Kano, S. Hirose, K. Hara, J. Yoshino, H. Munekata and H. Kukimoto 82/83 (1994) 132
- Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watanabe, F. Maeda and M. Oshima 82/83 (1994) 136
- Surface diffusion and adatom stoichiometry in GaAs MBE studied by microprobe-RHEED/SEM MBE, T. Nishinaga and X.Q. Shen 82/83 (1994) 141
- Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs, I. Sue-mune 82/83 (1994) 149
- Self-limiting and step-propagating nature of GaAs atomic layer epitaxy revealed by atomic force microscopy, H. Yokoyama, M. Tanimoto, M. Shinohara and N. Inoue 82/83 (1994) 158
- Kinetics and mechanism of atomic layer epitaxy of GaAs using trimethylgallium, H. Ohno, S. Goto, Y. Nomura, Y. Morishita and Y. Katayama 82/83 (1994) 164
- Surface stoichiometry and the role of adsorbates during GaAs atomic layer epitaxy, J.R. Creighton 82/83 (1994) 171
- Theoretical studies on the chloride ALE process, Y. Mochizuki, T. Takada and A. Usui 82/83 (1994) 200
- Configurational atomic ordering caused by stochastic adsorption processes in MBE-grown alloy semiconductors, H. Nakayama, M. Tochigi, H. Maeda and T. Nishino 82/83 (1994) 214
- Optical in-situ analysis of GaAs/AlAs/GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using GaCl_3 , AlCl_3 and AsH_3 , M. Akamatsu, S. Narahara, T. Kobayashi and F. Hasegawa 82/83 (1994) 228
- Atomic layer epitaxy of AlAs: growth mechanism, M. Ozeki and N. Ohtsuka 82/83 (1994) 233
- A solution to the surface arsenic stoichiometric problem at the GaAs(001) growth surface in atomic layer epitaxy, Y. Sakuma, S. Muto, K. Nakajima and N. Yokoyama 82/83 (1994) 239
- Substitution of surface-adsorbed As atoms to P atoms in atomic layer epitaxy, H. Ikeda, Y. Miura, N. Takahashi, A. Koukitu and H. Seki 82/83 (1994) 257
- Real time observation of surface dielectric responses of GaAs(001) using surface photo-absorption, K. Uwai and N. Kobayashi 82/83 (1994) 290

- Atomic layer epitaxy of ZnSe using reflectance difference spectroscopy, H. Akinaga and K. Tanaka 82/83 (1994) 298
- Photoelectron intensity oscillation as a probe to monitor Si layer-by-layer growth, Y. Enta, N. Miyamoto, Y. Takakuwa and H. Kato 82/83 (1994) 327
- Sub-atomic-layer epitaxy of Si using Si_2H_6 , Y. Suda, M. Ishida, M. Yamashita and H. Ikeda 82/83 (1994) 332
- Si ALE using chlorine/hydrogen exchange. Fundamentals and films, D.D. Koleske and S.M. Gates 82/83 (1994) 344
- Self-limiting adsorption of thermally cracked SiCl_2H_2 on Si surfaces, C. Sasaoka and A. Usui 82/83 (1994) 348
- Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH_4 and SiH_4 gases, M. Sakuraba, J. Murota, T. Watanabe, Y. Sawada and S. Ono 82/83 (1994) 354
- Scanning tunneling microscopy study of solid-phase epitaxy processes of amorphous silicon layers on silicon substrates, K. Uesugi, T. Komura, M. Yoshimura and T. Yao 82/83 (1994) 367
- Atomic layer epitaxy of germanium, S. Sugahara, T. Kitamura, S. Imai and M. Matsumura 82/83 (1994) 380
- Auger electron diffraction study of the initial stage of Ge heteroepitaxy on Si(001), M. Sasaki, T. Abukawa, H.W. Yeom, M. Yamada, S. Suzuki, S. Sato and S. Kono 82/83 (1994) 387
- Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane, H. Akazawa 82/83 (1994) 394
- Mechanisms of SiC growth by alternate supply of SiH_2Cl_2 and C_2H_2 , H. Nagasawa and Y. Yamaguchi 82/83 (1994) 405
- Atomic layer epitaxy in the growth of complex thin film structures for electroluminescent applications, L. Niinistö and M. Leskelä 82/83 (1994) 454
- NbCl_5 as a precursor in atomic layer epitaxy, K.-E. Elers, M. Ritala, M. Leskelä and E. Rauhala 82/83 (1994) 468
- Layer controlled growth of oxide superconductors, M. Kawai, Z.-Y. Liu, T. Hanada, M. Katayama, M. Aono and C.F. McConville 82/83 (1994) 487
- Fabrication of CuO_2 -plane-based high-temperature superconducting thin films by atomic layer controlled molecular beam epitaxy, I. Yoshida, H. Furukawa, T. Hirosawa and M. Nakao 82/83 (1994) 501
- Morphology of epitaxial SrF_2 films on atomically modified $\text{InP}(100)$, S. Heun, M. Sugiyama, S. Maeyama, Y. Watanabe and M. Oshima 82/83 (1994) 507
- Steric and electronic interactions between source gas and substrate surface during the Al-CVD/Al selective epitaxy process as investigated by quantum chemical calculations, R. Vetrivel, R. Yamauchi, H. Yamano, M. Kubo, A. Miyamoto and T. Ohta 82/83 (1994) 516
- The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen 82/83 (1994) 553
- Influence of atomic Cu-layer epitaxy on CO_2 and CO photoinduced desorption from $\text{ZnO}(0001)$, P.J. Møller, S.A. Komolov and E.F. Lazneva 82/83 (1994) 569
- Electrical properties of Si- Al_2O_3 structures grown by ML-ALE, V.E. Drozd, A.P. Baraban and I.O. Nikiforova 82/83 (1994) 583
- Strain relaxation in GaAs islands on GaP(001), H. Yago, T. Nomura and K. Ishikawa 84 (1995) 119
- A RHEED study of the dynamics of GaAs and AlGaAs growth on a (001) surface by MBE, J. Hopkins, M.R. Leys, J. Brübach, W.C. Van der Vleuten and J.H. Wolter 84 (1995) 299
- Application of time-dependent diffusion models to the study of real solids, D.T. Britton and J. Störmer 85 (1995) 1
- Positron annihilation studies of defects in molecular beam epitaxy grown III-V layers, M.T. Umlor, P. Asoka-Kumar, D.J. Keeble, P.W. Cooke and K.G. Lynn 85 (1995) 295
- Pulsed laser deposition of epitaxial layers of ZnSe, J.L. Deiss, A. Chergui, L. Koutti, J.L. Loison, M. Robino and J.B. Grun 86 (1995) 149
- Comparison of epitaxial films of $\text{Zn}_{1-x}\text{Mn}_x\text{Te}$ on (111) and (100) GaAs produced by pulsed laser deposition, H.J. Masterson and J.G. Lunney 86 (1995) 154
- Photoassisted growth of II-VI semiconductor films, Sz. Fujita and Sg. Fujita 86 (1995) 431
- Photoassisted metalorganic vapor-phase epitaxy of ZnSe on GaAs, J.E. Bourée, R. Helbing, W. Kuhn and O. Gorochoy 86 (1995) 437
- Photo-assisted growth and characterization of $\text{Zn}_x\text{Cd}_{1-x}\text{S}$ by MOVPE, H. Dumont, Sz. Fujita and Sg. Fujita 86 (1995) 442
- GaAs growth by photon-assisted metalorganic molecular beam epitaxy using

- ethyl derivatives of gallium and arsenic, F. Maury, K. Bouabid, N. Fazouan, A.M. Gué and D. Estève 86 (1995) 447
- Interrupted cycle chemical beam epitaxy of gallium phosphide on silicon with or without photon assistance, J.T. Kelliher, A.E. Miller, N. Dietz, S. Habermehl, Y.L. Chen, Z. Lu, G. Lucovsky and K.J. Bachmann 86 (1995) 453
- In-situ laser reflectometry of the epitaxial growth of thin semiconductor films, T. Farrell and J.V. Armstrong 86 (1995) 582
- MBE-STM study of the Ga-rich 4×2 phase of the GaAs(001) surface, Q. Xue, T. Hashizume, J.M. Zhou, T. Sakata and T. Sakurai 87/88 (1995) 364
- Structure of the MBE-grown GaAs(001)-(2 \times 4) phase, T. Hashizume, Q.K. Xue, A. Ichimiya and T. Sakurai 87/88 (1995) 373
- Diffusion of Ag on Cu(110) and Cu(111) studied by spatially resolved UV-photoemission, U. Kürpick, G. Meister and A. Goldmann 89 (1995) 383
- Erratum to "Characterization of adsorption in flow type atomic layer epitaxy reactor" [Appl. Surf. Sci. 81 (1994) 281], J. Aarik and H. Siimon 90 (1995) 109
- Multiple losses in off-specular electron energy loss spectra of thin NaCl films individually resolved in energy and momentum, V. Zielasek, A. Büssenschütt and M. Henzler 90 (1995) 117
- Atomic hydrogen-assisted ALE of germanium, S. Sugahara, M. Kadoshima, T. Kitamura, S. Imai and M. Matsumura 90 (1995) 349
- Lateral composition modulation in InGaAsP deposited by gas source molecular beam epitaxy on (100)- and (111)-oriented InP substrates, R.R. LaPierre, B.J. Robinson and D.A. Thompson 90 (1995) 437
- Characterization of the plasma plume and of thin film epitaxially produced during laser ablation of SnSe, R. Teghil, A. Santagata, V. Marotta, S. Orlando, G. Pizzella, A. Giardini-Guidoni and A. Mele 90 (1995) 505

Erbium

- Erbium oxide thin films on Si(100) obtained by laser ablation and electron beam evaporation, X. Queralt, C. Ferrater, F. Sánchez, R. Aguiar, J. Palau and M. Varela 86 (1995) 95

Etching

- Control of the etching reaction of digital etching using tunable UV laser irradiation, T. Meguro, M. Ishii, T. Sugano, K. Gamo and Y. Aoyagi 82/83 (1994) 193
- X-ray photoelectron spectroscopic and atomic force microscopic study of GaAs etching with a HCl solution, Z. Song, S. Shogen, M. Kawasaki and I. Suemune 82/83 (1994) 250
- Substrate orientation dependence of self-limited atomic-layer etching of Si with chlorine adsorption and low-energy Ar⁺ irradiation, K. Suzue, T. Matsuura, J. Murota, Y. Sawada and T. Ohmi 82/83 (1994) 422
- Chemical etching of (100) and (110) faces of flux-grown LaBO₃ crystals, A. Jain, A.K. Razdan, P.N. Kotru and B.M. Wanklyn 84 (1995) 65
- Excimer laser etching of diamond-like carbon films: spalling effect, T.V. Kononenko, V.G. Ralchenko, E.D. Obratsova, V.I. Konov, J. Seth, S.V. Babu and E.N. Loubnin 86 (1995) 234
- Laser-assisted etching-like damage of Si, A.V. Simakin and G.A. Shafeev 86 (1995) 422
- Laser-induced etching and deposition of tungsten in WF₆-H₂ atmosphere, K. Piglmayer, Z. Tóth and Z. Kantor 86 (1995) 484
- Laser chemical etching of Cu₂O, G. Stenberg, M. Boman, M. Ottosson and J.-O. Carlsson 86 (1995) 543
- Laser-assisted dry etching ablation of InP, J.J. Dubowski, A. Compaan and M. Prasad 86 (1995) 548
- Surface reaction control in digital etching of GaAs by using a tunable UV laser system: reaction control mechanism in layer-by-layer etching, M. Ishii, T. Meguro, T. Sugano, K. Gamo and Y. Aoyagi 86 (1995) 554
- Excimer laser-assisted etching of silicon in chlorine: adsorption and desorption, A.V. Kuzmichov 86 (1995) 559
- Excimer-laser-induced etching of silicon in chlorine atmosphere at a wavelength of 248 nm, W. Jiang, H. Baumgärtner and I. Eisele 86 (1995) 564
- Three-dimensional nanostructures by direct laser etching of Si, M. Müllenborn, H. Dirac and J.W. Petersen 86 (1995) 568
- Desorption in light-induced dry etching of GaAs with Cl₂ around 120 nm, B. Li, U. Streller, H.-P. Krause, I. Twesten, N. Schwentner, V. Stepanenko and Yu. Poltoratskii 86 (1995) 577

Etching of CoSi_2 in HF-based solutions, R.A. Donaton, K. Lokere, R. Verbeeck and K. Maex

89 (1995) 221

Surface kinetics and morphology of ArF laser-assisted etching of (113)A GaAs in a Cl_2 environment, P. Tejedor and P.S. Domínguez

89 (1995) 271

Experimental study of passivating ion-beam-induced distributed energy levels in n-GaAs by hydrogen species from boiling water, I. Thurzo, E. Pincik, G. Papaioannou, P. Dimitrakakis and N. Arpatzakis

90 (1995) 39

Thermal etching of α -Zr single-crystal surfaces, H. Zou, G.M. Hood, R.J. Schultz and J.A. Roy

90 (1995) 59

A study of the compositional changes in chemically etched, Ar ion bombarded and reactive ion etched GaAs(100) surfaces by means of ARXPS and LEISS, J.L. Sullivan, W. Yu and S.O. Saied

90 (1995) 309

Evaporation

Annealing studies of Au/GaAs and Al/GaAs interfaces using a variable energy positron beam, C.C. Ling, T.C. Lee, S. Fung, C.D. Beling, H. Weng, J. Xu, S. Sun and R. Han

85 (1995) 305

Study of PbTe(Ga) evaporation using a nanosecond pulsed laser, V.A. Mikhailov, F.N. Putilin and D.N. Trubnikov

86 (1995) 64

Erbium oxide thin films on Si(100) obtained by laser ablation and electron beam evaporation, X. Queral, C. Ferrater, F. Sánchez, R. Aguiar, J. Palau and M. Varela

86 (1995) 95

Thermal effects on structural characterization of evaporated CdTe films during and after deposition, A. Ashour, M.R. Ebeid, N. El-Kadry, M.F. Ahmed and A.A. Ramadan

89 (1995) 159

Dependence of electromigration rate on applied electric potential, B.H. Jo and R.W. Vook

89 (1995) 237

Cadmium selenide-amorphous hydrogenated silicon heterostructures, S. Wu and D. Haneman

89 (1995) 289

Interfacial reaction of NiO with Al_2O_3 (11 $\bar{2}$ 0) and polycrystalline α - Al_2O_3 , P.H. Bolt, S.F. Lobner, J.W. Geus and F.H.P.M. Habraken

89 (1995) 339

The influence of the substrate material on the growth of V_2O_5 flash-evaporated films, C. Julien, J.P. Guesdon, A. Gorenstein, A. Khelfa and I. Ivanov

90 (1995) 389

Field desorption

Investigation of adsorption and coadsorption of O_2 and CO on Rh by O_2^+ field ion and Li^+ field desorption microscopies, V.K. Medvedev, Yu. Suchorski and J.H. Block

87/88 (1995) 159

Field effect

Probe hole field electron/field ion microscopy and energy spectroscopy of ultrasharp [111]-oriented tungsten tips, J. Unger, Yu.A. Vlasov and N. Ernst

87/88 (1995) 45

Field-induced redistribution and diffusion of water on a Pt field emitter, R. Bryl, T. Wysocki and R. Błaszczyszyn

87/88 (1995) 69

Microstructured liquid metal ion and electron sources (MILMIS/MILMES), J. Mitterauer

87/88 (1995) 79

Reaction-induced morphological changes of field emitter tips: NO on Rh and Pt, C. Voss and N. Kruse

87/88 (1995) 134

Field-induced oxygen layer formation from H_2O and its titration by hydrogen on a Pt-emitter, V. Gorodetskii, N. Ernst, W. Drachsel and J.H. Block

87/88 (1995) 151

Field ion microscope studies of exchange-mediated, atom-displacement processes on metal surfaces, G.L. Kellogg

87/88 (1995) 353

Field induced manipulation of fullerene molecules with the STM: a self-consistent theoretical study, M. Devel, C. Girard, C. Joachim and O.J.F. Martin

87/88 (1995) 390

Field electron microscopy

Surface structure dependence of O_2 -W adsorption system, M. Sato

82/83 (1994) 532

Field emission

Microstructure and field emission of diamond particles on silicon tips, E.I. Givargizov, V.V. Zhimov, A.N. Stepanova, E.V. Rakova, A.N. Kiselev and P.S. Plekhanov

87/88 (1995) 24

A quantitative estimation of the sensitivity of field-emission pressure-gauge, T. Iwata and K.-S. Chang

87/88 (1995) 31

Probe hole field electron/field ion microscopy and energy spectroscopy of ultrasharp [111]-oriented tungsten tips, J. Unger, Yu.A. Vlasov and N. Ernst

87/88 (1995) 45

- Electron field emission (FE) from quantum size systems, L.G. Il'chenko, Yu.V. Kryuchenko and V.G. Litovchenko 87/88 (1995) 53
- Modeling of the field emitter triode (FET) as a displacement/pressure sensor, D. Nicolaescu 87/88 (1995) 61
- Microstructured liquid metal ion and electron sources (MILMIS/MILMES), J. Mitterauer 87/88 (1995) 79
- Field-induced oxygen layer formation from H_2O and its titration by hydrogen on a Pt-emitter, V. Gorodetskii, N. Ernst, W. Drachsel and J.H. Block 87/88 (1995) 151

Field emission microscopy

- Atom probe and field emission electron spectroscopy studies of semiconductor films on metals, M. Ashino, M. Tomitori and O. Nishikawa 87/88 (1995) 12
- Adsorption studies of iron on tungsten by probe-hole field emission microscopy, A.D. Adsool, R. Pande, R.B. Sharma, M.A. More and D.S. Joag 87/88 (1995) 37
- Development of a FEM, FIM-AP system for studying gridded vacuum microelectronic devices, M. Huang, R.A.D. Mackenzie, G.D.W. Smith and N.A. Cade 87/88 (1995) 421

Field evaporation

- Field evaporation theory: a review of basic ideas, R.G. Forbes 87/88 (1995) 1
- Field evaporation of gold by scanning tunneling microscopy, W. Mizutani, A. Ohi, M. Motomatsu and H. Tokumoto 87/88 (1995) 398

Field ion microscopy

- Probe hole field electron/field ion microscopy and energy spectroscopy of ultrasharp [111]-oriented tungsten tips, J. Unger, Yu.A. Vlasov and N. Ernst 87/88 (1995) 45
- A FEM study of liquid lithium on a <011>-oriented tungsten tip, K. Hata, M. Kumamura, T. Yasuda, Y. Saito and A. Ohshita 87/88 (1995) 117
- Field ion microscopy during an oscillating surface reaction: NO/H_2 on Pt, C. Voss and N. Kruse 87/88 (1995) 127
- Reaction-induced morphological changes of field emitter tips: NO on Rh and Pt, C. Voss and N. Kruse 87/88 (1995) 134

- FIM phenomena observed with benzene as image gas, B. Schulze, A. Theiss, U. Schmidt and F.W. Röhlgen 87/88 (1995) 140
- Comparison of NFIM and FIM of polymer layers with tetracyanoethylene and benzene as image gases, A. Theiss, F. Okuyama and F.W. Röhlgen 87/88 (1995) 146
- Field-induced oxygen layer formation from H_2O and its titration by hydrogen on a Pt-emitter, V. Gorodetskii, N. Ernst, W. Drachsel and J.H. Block 87/88 (1995) 151
- APFIM investigations on ordered γ -TiAl using single-layer detection method, J. Wesemann, G. Frommeyer and M. Kreuss 87/88 (1995) 179
- Atom-probe study of phosphorus segregation to the carbide/matrix interface in an aged 9% chromium steel, L. Lundin and B. Richarz 87/88 (1995) 194
- Microstructure of heat resistant chromium steel weld metals, H.-O. Andrén, G. Cai and L.-E. Svensson 87/88 (1995) 200
- Atom probe field ion microscopy of type 308 CRE stainless steel welds, S.S. Babu, S.A. David, J.M. Vitek and M.K. Miller 87/88 (1995) 207
- Characterization of neutron-irradiated Fe-Au alloys, M.K. Miller, K.F. Russell, A. Jostsons and R.G. Blake 87/88 (1995) 216
- Nucleation and growth of θ' precipitation in Sn-modified Al-Cu alloys: APFIM/TEM observations, S.P. Ringer, K. Hono and T. Sakurai 87/88 (1995) 223
- An APFIM/TEM investigation of the discontinuous precipitation in a Ni-In alloy, G.P. Geber 87/88 (1995) 234
- Structure and chemistry of grain boundaries in Ni-16Cr-9Fe model materials, M. Thuvander and K. Stiller 87/88 (1995) 251
- Effect of low-energy (20-40 keV) ion implantation on phase transformations in the subsurface volume of alloys, V.A. Ivchenko and N.N. Syutkin 87/88 (1995) 257
- APFIM study of the compositional inhomogeneity of sputtered Co-Cr magnetic thin film, A. Pundt and C. Michaelsen 87/88 (1995) 264
- APFIM and XPS study of the first stages of low temperature air oxidation of industrial CuNi alloys, R. Souchet, F. Danoix, A. D'Huysser and M. Lenglet 87/88 (1995) 271
- Atom probe field ion microscope studies of palladium silicide on silicon, R.A. King, R.A.D. Mackenzie, G.D.W. Smith and N.A. Cade 87/88 (1995) 279
- 3D reconstruction of antiphase boundaries in Cu_3Au from field ion images, S. Duval, S. Chambrelaud, D. Blavette, A. Loiseau and L. Potez 87/88 (1995) 284

- Quantitative analysis of individual atom images in FIM of an ordered Ni_4Mo alloy, M. Yamamoto, K. Nishikawa and T. Nishiuchi 87/88 (1995) 291
- FIM/AP analysis of Cu-Pd multilayers, T. Al-Kassab, M.-P. Macht and H. Wollenberger 87/88 (1995) 329
- Field ion microscope studies of exchange-mediated, atom-displacement processes on metal surfaces, G.L. Kellogg 87/88 (1995) 353
- Adsorption of fullerenes on Cu(111) and Ag(111) surfaces, T. Sakurai, X.D. Wang, T. Hashizume, V. Yurov, H. Shinohara and H.W. Pickering 87/88 (1995) 405
- Development of a FEM, FIM-AP system for studying gridded vacuum microelectronic devices, M. Huang, R.A.D. Mackenzie, G.D.W. Smith and N.A. Cade 87/88 (1995) 421
- On the structure and chemistry of Ni_3Al on an atomic scale via atom-probe field-ion microscopy, G.P.E.M. Van Bakel, K. Hariharan and D.N. Seidman 90 (1995) 95
- Erratum to "Nucleation and growth of θ' precipitation in Sn-modified Al-Cu alloys: APFIM/TEM observations" [Appl. Surf. Sci. 87/88 (1995) 223], S.P. Ringer, K. Hono and T. Sakurai 90 (1995) 107
- ### Gallium
- Activation of the Ga- CH_3 bond using atomic hydrogen - a possible route to III-V semiconductor films with low carbon levels, J.T. Yates, Jr., A. Hübner, S.R. Lucas, W.D. Partlow, J. Schaefer and W.J. Choyke 82/83 (1994) 180
- Pulsed trimethylgallium scattering from As-stabilized and Ga-stabilized surfaces, M. Sasaki and S. Yoshida 82/83 (1994) 269
- Surface reactions of Ga and As on Sb-terminated GaAs(001), F. Maeda, Y. Watanabe and M. Oshima 82/83 (1994) 276
- ### Gallium arsenide
- A temperature-programmed desorption/X-ray photoelectron spectroscopy study of ditertiarybutylarsine on GaAs(100), M.S. Jackson, J.M. Heitzinger, J.W. Nail, R.D. Culp and J.G. Ekerdt 81 (1994) 195
- Evaluation of matrix effects in SIMS quantification of $\text{Al}_x\text{Ga}_{1-x}\text{As}$ /GaAs heterostructures: a SNMS approach, A. Torrisi, A. Scandurra and A. Licciardello 81 (1994) 259
- Molecular layer epitaxy of GaAs, J. Nishizawa 82/83 (1994) 1
- Silicon doping with modulated beam epitaxy in the growth of GaAs(111)A, M.R. Fahy, K. Sato and B.A. Joyce 82/83 (1994) 14
- Atomic layer epitaxy of device quality Al-GaAs and AlAs, N. Hayafuji, G.M. El-dallal, A. Dip, P.C. Colter, N.A. El-Masry and S.M. Bedair 82/83 (1994) 18
- Substrate misorientation dependence of thermal stability of Si atom in Si atomic layer doped GaAs on GaAs(111)A, M. Hirai, H. Ohnishi, K. Fujita and T. Watanabe 82/83 (1994) 23
- Investigation of a GaN surface structure for the mask of GaAs selective growth using MOMBE, S. Yoshida and M. Sasaki 82/83 (1994) 28
- Selective MLE growth of GaAs and surface treatment for ideal static induction transistor (ISIT) application, Y. Oyama, P. Plotka and J. Nishizawa 82/83 (1994) 41
- Pulsed-jet epitaxy: application to device processes, Y. Sakuma, M. Ozeki, N. Ohtsuka, Y. Matsumiya, H. Shigematsu, O. Ueda, S. Muto, K. Nakajima and N. Yokoyama 82/83 (1994) 46
- Surface processes of selective growth by atomic layer epitaxy, H. Isshiki, Y. Aoyagi, T. Sugano, S. Iwai and T. Meguro 82/83 (1994) 57
- Migration and related buried epitaxy using digital epitaxial growth conditions, I. Takahashi, M. Nakaji and H. Kawanishi 82/83 (1994) 70
- Ideal static induction transistor implemented with molecular layer epitaxy, P. Plotka, T. Kurabayashi, Y. Oyama and J. Nishizawa 82/83 (1994) 91
- Temperature synchronized molecular layer epitaxy, T. Kurabayashi and J. Nishizawa 82/83 (1994) 97
- Autocompensation in Si planar doped GaAs, T. Suzuki, H. Goto, N. Sawaki, H. Ito and K. Hara 82/83 (1994) 103
- Microscopic analysis of interface structure in InGaAs/InP MQW using Pendelösung oscillation around a satellite peak in high-resolution X-ray diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya 82/83 (1994) 115
- Flow modulation epitaxy of $\text{Ga}_x\text{In}_{1-x}\text{As}$ /AlAs heterostructures on InP for resonant tunneling diodes, B.P. Keller, J.C. Yen, A.L. Holmes Jr., S.P. DenBaars and U.K. Mishra 82/83 (1994) 126
- Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watanabe, F. Maeda and M. Oshima 82/83 (1994) 136

- Surface diffusion and adatom stoichiometry in GaAs MBE studied by microprobe-RHEED/SEM MBE, T. Nishinaga and X.Q. Shen 82/83 (1994) 141
- Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs, I. Sue-mune 82/83 (1994) 149
- Self-limiting and step-propagating nature of GaAs atomic layer epitaxy revealed by atomic force microscopy, H. Yokoyama, M. Tanimoto, M. Shinohara and N. Inoue 82/83 (1994) 158
- Kinetics and mechanism of atomic layer epitaxy of GaAs using trimethylgallium, H. Ohno, S. Goto, Y. Nomura, Y. Morishita and Y. Katayama 82/83 (1994) 164
- Surface stoichiometry and the role of adsorbates during GaAs atomic layer epitaxy, J.R. Creighton 82/83 (1994) 171
- Control of the etching reaction of digital etching using tunable UV laser irradiation, T. Meguro, M. Ishii, T. Sugano, K. Gamo and Y. Aoyagi 82/83 (1994) 193
- Theoretical studies on the chloride ALE process, Y. Mochizuki, T. Takada and A. Usui 82/83 (1994) 200
- A Monte Carlo simulation study for adatom migration and resultant atomic arrangements in $\text{Al}_x\text{Ga}_{1-x}\text{As}$ on a GaAs(001) surface, T. Ito, K. Shiraishi and T. Ohno 82/83 (1994) 208
- Optical in-situ analysis of GaAs/AlAs/GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using GaCl_3 , AlCl_3 and AsH_3 , M. Akamatsu, S. Narahara, T. Kobayashi and F. Hasegawa 82/83 (1994) 228
- A solution to the surface arsenic stoichiometric problem at the GaAs(001) growth surface in atomic layer epitaxy, Y. Sakuma, S. Muto, K. Nakajima and N. Yokoyama 82/83 (1994) 239
- X-ray photoelectron spectroscopic and atomic force microscopic study of GaAs etching with a HCl solution, Z. Song, S. Shogen, M. Kawasaki and I. Suemune 82/83 (1994) 250
- In-situ observation of Ga adsorption during TMGa exposure on GaAs(001) surfaces with various As coverages, S. Otake, A. Sakamoto, M. Yamamoto and I. Iwasa 82/83 (1994) 263
- Pulsed trimethylgallium scattering from As-stabilized and Ga-stabilized surfaces, M. Sasaki and S. Yoshida 82/83 (1994) 269
- Surface reactions of Ga and As on Sb-terminated GaAs(001), F. Maeda, Y. Watanabe and M. Oshima 82/83 (1994) 276
- Carbon incorporation mechanism in atomic layer epitaxy of GaAs and AlGaAs, N. Kobayashi and T. Makimoto 82/83 (1994) 284
- Real time observation of surface dielectric responses of GaAs(001) using surface photo-absorption, K. Uwai and N. Kobayashi 82/83 (1994) 290
- Chlorine adsorption on electron beam irradiated GaAs photo-oxides: mechanism of in situ EB lithography, Y. Ide and M. Yamada 82/83 (1994) 310
- Strain relaxation in GaAs islands on GaP(001), H. Yago, T. Nomura and K. Ishikawa 84 (1995) 119
- Reactivity of III-V and II-VI semiconductors toward hydrogen: surface modification and evolution in air, D. Ballutaud, C. Debiemme-Chouvy, A. Etcheberry, P. De Mierry and L. Svob 84 (1995) 187
- A RHEED study of the dynamics of GaAs and AlGaAs growth on a (001) surface by MBE, J. Hopkins, M.R. Leys, J. Brübach, W.C. Van der Vleuten and J.H. Wolter 84 (1995) 299
- Defects and material processing in compound semiconductors, K. Wada 85 (1995) 246
- Defect analysis using 2D-ACAR: GaAs as a test case, A.A. Manuel, R. Ambigapathy, K. Saarinen, P. Hautojärvi and C. Corbel 85 (1995) 301
- Annealing studies of Au/GaAs and Al/GaAs interfaces using a variable energy positron beam, C.C. Ling, T.C. Lee, S. Fung, C.D. Beling, H. Weng, J. Xu, S. Sun and R. Han 85 (1995) 305
- Defects and arsenic distribution in low-temperature-grown GaAs, N. Hozhabri, A.R. Koymen, S.C. Sharma and K. Alavi 85 (1995) 311
- Comparison of epitaxial films of $\text{Zn}_{1-x}\text{Mn}_x\text{Te}$ on (111) and (100) GaAs produced by pulsed laser deposition, H.J. Masterson and J.G. Lunney 86 (1995) 154
- Photoassisted metalorganic vapor-phase epitaxy of ZnSe on GaAs, J.E. Bourée, R. Helbing, W. Kuhn and O. Gorochov 86 (1995) 437
- GaAs growth by photon-assisted metalorganic molecular beam epitaxy using ethyl derivatives of gallium and arsenic, F. Maury, K. Bouabid, N. Fazouan, A.M. Gué and D. Estève 86 (1995) 447
- Surface reaction control in digital etching of GaAs by using a tunable UV laser system: reaction control mechanism in layer-by-layer etching, M. Ishii, T. Meguro, T. Sugano, K. Gamo and Y. Aoyagi 86 (1995) 554
- Desorption in light-induced dry etching of GaAs with Cl_2 around 120 nm, B. Li, U. Streller, H.-P. Krause, I. Twesten, N.

- Schwentner, V. Stepanenko and Yu. Poltoratskii 86 (1995) 577
- MBE-STM study of the Ga-rich 4×2 phase of the GaAs(001) surface, Q. Xue, T. Hashizume, J.M. Zhou, T. Sakata and T. Sakurai 87/88 (1995) 364
- Structure of the MBE-grown GaAs(001)-(2 \times 4) phase, T. Hashizume, Q.K. Xue, A. Ichimiya and T. Sakurai 87/88 (1995) 373
- Surface kinetics and morphology of ArF laser-assisted etching of (113)A GaAs in a Cl_2 environment, P. Tejedor and P.S. Domínguez 89 (1995) 271
- Experimental study of passivating ion-beam-induced distributed energy levels in n-GaAs by hydrogen species from boiling water, I. Thurzo, E. Pincik, G. Papaioannou, P. Dimitrakis and N. Arpatzanis 90 (1995) 39
- A study of the compositional changes in chemically etched, Ar ion bombarded and reactive ion etched GaAs(100) surfaces by means of ARXPS and LEISS, J.L. Sullivan, W. Yu and S.O. Saied 90 (1995) 309
- Lateral composition modulation in InGaAsP deposited by gas source molecular beam epitaxy on (100)- and ($h11$)-oriented InP substrates, R.R. LaPierre, B.J. Robinson and D.A. Thompson 90 (1995) 437
- Gallium phosphide*
- Epitaxial growth of a two-dimensional structure of GaP on a Si substrate by metalorganic chemical vapor deposition, T. Soga, T. Jimbo and M. Umeno 82/83 (1994) 64
- Growth temperature dependence of optical properties of gas source MBE grown GaP/AlP short period superlattices, J.H. Kim, H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda 82/83 (1994) 76
- Selective epitaxial growth of GaInP by LP-MOCVD using ethyldimethylindium, trimethylindium, trimethylgallium and triethylgallium as group III sources, S.-H. Chan, S.M. Sze, C.-Y. Chang and W.-I. Lee 82/83 (1994) 85
- Strain relaxation in GaAs islands on GaP(001), H. Yago, T. Nomura and K. Ishikawa 84 (1995) 119
- Interrupted cycle chemical beam epitaxy of gallium phosphide on silicon with or without photon assistance, J.T. Kelliher, A.E. Miller, N. Dietz, S. Habermehl, Y.L. Chen, Z. Lu, G. Lucovsky and K.J. Bachmann 86 (1995) 453
- Germanium*
- Raman study of strained SiGe layers, S. Gu, R. Zhang, P. Han, R. Wang, P. Zhong and Y. Zheng 81 (1994) 431
- Photoreflectance of strained $\text{Si}_{1-x}\text{Ge}_x$ epilayers ($0.07 \leq x \leq 0.26$) and comparison with spectroscopic ellipsometry, R.T. Carline, C. Pickering, T.J.C. Hosea and D.J. Robbins 81 (1994) 475
- Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH_4 and SiH_4 gases, M. Sakuraba, J. Murota, T. Watanabe, Y. Sawada and S. Ono 82/83 (1994) 354
- Adaptive temperature program ALE of $\text{Si}_{1-x}\text{Ge}_x/\text{Si}$ heterostructures from $\text{Si}_2\text{H}_6/\text{Ge}_2\text{H}_6$, S. Asami, N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt 82/83 (1994) 359
- Scanning tunneling microscopy observations of Ge solid-phase epitaxy on Si(111), H. Hibino and T. Ogino 82/83 (1994) 374
- Atomic layer epitaxy of germanium, S. Sugahara, T. Kitamura, S. Imai and M. Matsumura 82/83 (1994) 380
- Auger electron diffraction study of the initial stage of Ge heteroepitaxy on Si(001), M. Sasaki, T. Abukawa, H.W. Yeom, M. Yamada, S. Suzuki, S. Sato and S. Kono 82/83 (1994) 387
- An X-ray scattering study of $\text{SiO}_x/\text{Si}/\text{Ge}(001)$, S.D. Kosowsky, C.-H. Hsu, P.S. Pershan, J. Bevk and B.S. Freer 84 (1995) 179
- A comparative study of primary ion energy dependence of secondary ion yields from Si and Ge surfaces under inert and reactive ion bombardment, N. Ray, P. Rajasekar and S.D. Dey 84 (1995) 203
- $\text{Si}_{1-x}\text{Ge}_x$ thin films deposited by the pulsed excimer laser ablation technique, F. Antoni, E. Fogarassy, C. Fuchs, B. Prévot and J.P. Stoquert 86 (1995) 175
- Morphology of $\text{Si}_{1-x}\text{Ge}_x$ thin crystalline films obtained by pulsed-excimer-laser annealing of heavily Ge-implanted Si, E.L. Mathé, A. Naudon, F. Repplinger and E. Fogarassy 86 (1995) 338
- Formation of poly- $\text{Si}_{1-x}\text{Ge}_x$ using excimer-laser processing, A. Slaoui, C. Deng, S. Talwar, K.J. Kramer, T.W. Sigmon, J.P. Stoquert and B. Prevot 86 (1995) 346
- Germanium-containing coatings by IR laser-induced decomposition of ethoxy-(trimethyl)germane and tetramethylgermane, R. Fajgar, M. Jakoubková, Z. Bastl and J. Pola 86 (1995) 530

- Multiple losses in off-specular electron energy loss spectra of thin NaCl films individually resolved in energy and momentum, V. Zielasek, A. Büssenschütt and M. Henzler 90 (1995) 117
- Atomic hydrogen-assisted ALE of germanium, S. Sugahara, M. Kadoshima, T. Kitamura, S. Imai and M. Matsumura 90 (1995) 349
- ### Glass
- XPS investigation of lithium borate glass and the Li/LiBO₂ interface, D.A. Hensley and S.H. Garofalini 81 (1994) 331
- Surface modification of lead silicate glass under X-ray irradiation, P.W. Wang, L.P. Zhang, L. Lu, D.V. LeMone and D.L. Kinser 84 (1995) 75
- Excimer laser ablation of Nd:YAG and Nd:glass, S.R. Jackson, W.J. Metheringham and P.E. Dyer 86 (1995) 223
- Enhanced adherence of electroless metal deposit on SiO₂ via control of the chemical environment of the Pd seeding layer, G.A. Shafeev, L. Bellard, J.-M. Themlin, W. Marine and A. Cros 86 (1995) 387
- ### Gold
- Origin of residual stress in a textured Au thin film on a LiF substrate, N. Durand, K.F. Badawi, A. Declémy and Ph. Goudeau 81 (1994) 119
- Interface study on laser-induced material transfer from polymer and quartz surfaces, S. Lätsch, H. Hiraoka, W. Nieveen and J. Bargon 81 (1994) 183
- Surface alloy formation in Pd/Ag, Cu/Au and Ni/Au bimetallic overlayers, A.K. Santra and C.N.R. Rao 84 (1995) 347
- Adsorption site identification for oxygen molecules on Au/Si(100) by positron annihilation induced Auger electron spectroscopy (PAES), G. Yang, J.H. Kim, S. Yang and A.H. Weiss 85 (1995) 77
- Annealing studies of Au/GaAs and Al/GaAs interfaces using a variable energy positron beam, C.C. Ling, T.C. Lee, S. Fung, C.D. Beling, H. Weng, J. Xu, S. Sun and R. Han 85 (1995) 305
- Deposition of gold on polyimide from solutions, S. Pflüger, M. Wehner, F. Jansen, Th. Kruck and F. Lupp 86 (1995) 504
- Characterization of neutron-irradiated Fe-Au alloys, M.K. Miller, K.F. Russell, A. Jostsons and R.G. Blake 87/88 (1995) 216
- 3D reconstruction of antiphase boundaries in Cu₃Au from field ion images, S. Duval, S. Chambrelaud, D. Blavette, A. Loiseau and L. Potez 87/88 (1995) 284
- Field evaporation of gold by scanning tunneling microscopy, W. Mizutani, A. Ohi, M. Motomatsu and H. Tokumoto 87/88 (1995) 398
- Mechanism of the formation of ultrafine gold particles on MgO(100) as investigated by molecular dynamics and computer graphics, M. Kubo, R. Miura, R. Yamauchi, R. Vetrivel and A. Miyamoto 89 (1995) 131
- Preparation of a model Ziegler-Natta catalyst. Surface science studies of magnesium chloride thin film deposited on gold and its interaction with titanium chloride, E. Magni and G.A. Somorjai 89 (1995) 187
- ### Graphite
- Superefficient diffusion of cesium atoms into rhenium covered by a 2D graphite film, A.Ya. Tontegode and F.K. Yusifov 90 (1995) 185
- Angle resolved XPS study of inhomogeneous specimens of polycrystalline silver covered with uniform graphite overlayers, M. Sreemany and T.B. Ghosh 90 (1995) 241
- ### Hafnium
- Multilayered Ni/Hf and solid-state amorphization studied using the slow positron beam technique, N. Oshima, T. Nakajyo, I. Kanazawa, T. Iwashita, Y. Ito, W.-H. Soe and R. Yamamoto 85 (1995) 329
- ### Halides
- LiBr on Si(111): an X-ray standing wave measurement, Th. Gog, G.C. Follis and S.M. Durbin 81 (1994) 485
- ### Halogenides
- Temperature dependence of surface charging of NaCl under electron irradiation: role of secondary electron emission, W.G. Durrer, M. Portillo, P. Wang and D.P. Russell 81 (1994) 215
- Optical in-situ analysis of GaAs/AlAs/GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using GaCl₃, AlCl₃ and AsH₃, M. Akamatsu, S. Narahara, T. Kobayashi and F. Hasegawa 82/83 (1994) 228

- Atomic-scale modification of the AlCl_3 -adsorbed $\text{Si}(111)-7 \times 7$ surface, T. Takiguchi, K. Uesugi, M. Yoshimura and T. Yao 82/83 (1994) 428
- NbCl_5 as a precursor in atomic layer epitaxy, K.-E. Elers, M. Ritala, M. Leskelä and E. Rauhala 82/83 (1994) 468
- Morphology of epitaxial SrF_2 films on atomically modified $\text{InP}(100)$, S. Heun, M. Sugiyama, S. Maeyama, Y. Watanabe and M. Oshima 82/83 (1994) 507
- Surface modification of CaF_2 in atomic layer scale by electron beam exposure, S.M. Hwang, A. Izumi, K. Tsutsui and S. Furukawa 82/83 (1994) 523
- Preparation of a model Ziegler-Natta catalyst. Surface science studies of magnesium chloride thin film deposited on gold and its interaction with titanium chloride, E. Magni and G.A. Somorjai 89 (1995) 187
- Influence of surface charge on thermal positive ion emission from potassium bromide, M.F. Butman, J. Nakamura, S. Kamidoi and H. Kawano 89 (1995) 323
- Silicon surface cleaning using XeF_2 gas treatment, V.S. Aliev, M.R. Baklanov and V.I. Bukhtiyarov 90 (1995) 191
- ### Halogens
- The adsorption of sodium dodecyl sulphate on fluorite and its surface free energy, B. Jańczuk, M.L. González-Martín and J.M. Bruque 81 (1994) 95
- Atomic-hydrogen-induced desorption of fluorine from silicon surfaces, Y. Saito 81 (1994) 223
- Theoretical studies on the chloride ALE process, Y. Mochizuki, T. Takada and A. Usui 82/83 (1994) 200
- Chlorine adsorption on electron beam irradiated GaAs photo-oxides: mechanism of in situ EB lithography, Y. Ide and M. Yamada 82/83 (1994) 310
- Si ALE using chlorine/hydrogen exchange. Fundamentals and films, D.D. Koleske and S.M. Gates 82/83 (1994) 344
- Substrate orientation dependence of self-limited atomic-layer etching of Si with chlorine adsorption and low-energy Ar^+ irradiation, K. Suzue, T. Matsuura, J. Murota, Y. Sawada and T. Ohmi 82/83 (1994) 422
- Excimer-laser-induced etching of silicon in chlorine atmosphere at a wavelength of 248 nm, W. Jiang, H. Baumgärtner and I. Eisele 86 (1995) 564
- Desorption in light-induced dry etching of GaAs with Cl_2 around 120 nm, B. Li, U. Streller, H.-P. Krause, I. Twesten, N. Schwentner, V. Stepanenko and Yu. Poltoratskii 86 (1995) 577
- ### Helium
- Threshold behavior of ionization and excitation cross sections of He and Ar by positron impact, O. Sueoka, B. Jin and A. Hamada 85 (1995) 59
- Helium and hydrogen-decorated cavities in silicon, R.A. Hakvoort, A. van Veen, P.E. Mijnen and H. Schut 85 (1995) 271
- ### Hydrides
- Adsorption of monoethanolamine on clean, oxidized and hydroxylated aluminium surfaces: a model for amine-cured epoxy/aluminium interfaces, C. Fauquet, P. Dubot, L. Minel, M.-G. Barthés-Labrousse, M. Rei Vilar and M. Villatte 81 (1994) 435
- Optical in-situ analysis of GaAs/AlAs/GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using GaCl_3 , AlCl_3 and AsH_3 , M. Akamatsu, S. Narahara, T. Kobayashi and F. Hasegawa 82/83 (1994) 228
- Surface reactions on palladium hydride in vacuum, air and water studied in situ with mass spectrometry, L. Gråsjö, G. Hultquist, K.L. Tan and M. Seo 89 (1995) 21
- ### Hydrocarbons
- A temperature-programmed desorption/X-ray photoelectron spectroscopy study of ditertiarybutylarsine on GaAs(100), M.S. Jackson, J.M. Heitzinger, J.W. Nail, R.D. Culp and J.G. Ekerdt 81 (1994) 195
- Chemisorption of poly(methylhydrogen-siloxane) on oxide surfaces: a quantitative investigation using static SIMS, K. Reihs, R. Aguiar Colom, S. Gleditsch, M. Deimel, B. Hagenhoff and A. Benninghoven 84 (1995) 107
- FIM phenomena observed with benzene as image gas, B. Schulze, A. Theiss, U. Schmidt and F.W. Röllgen 87/88 (1995) 140
- Comparison of NFIM and FIM of polymer layers with tetracyanoethylene and benzene as image gases, A. Theiss, F. Okuyama and F.W. Röllgen 87/88 (1995) 146
- Adsorption and film growth of BTA on clean and oxygen adsorbed Cu(110) surfaces, K. Cho, J. Kishimoto, T.

- Hashizume, H.W. Pickering and T. Sakurai 87/88 (1995) 380
- An investigation of the thermal stability of undecylimidazole on copper by FT-IR reflection-absorption spectroscopy, S. Yoshida and H. Ishida 89 (1995) 39
- Growth of a surface film on copper from benzotriazole solutions, G. Xue, J. Ding and P. Cheng 89 (1995) 77
- The reactivity of O_2/H_2 , O_2/CO and O_2/C_3H_6 gas mixtures on Cu(111), W.E.J. Van Kooten, J.P.C. Van Nispen, O.L.J. Gijzeman and J.W. Geus 90 (1995) 137
- ### Hydrogen
- Atomic-hydrogen-induced desorption of fluorine from silicon surfaces, Y. Saito 81 (1994) 223
- Effects of atomic hydrogen on Cu(II)bis-hexafluoroacetylacetonate interactions with a TiN surface, G. Nuesca, J. Prasad and J.A. Kelber 81 (1994) 237
- Comment on 'Influence of surface composition on initial hydration of aluminium in boiling water' by A. Strålin and T. Hjertberg, B.R. Strohmeier 81 (1994) 273
- The effect of cyclic oxidation-reduction pretreatments on an amorphous $Ni_{80}P_{20}$ catalyst: an XPS/UPS/ISS study, J. Deng, H. Chen, X. Bao and M. Muhler 81 (1994) 341
- Activation of the Ga- CH_3 bond using atomic hydrogen - a possible route to III-V semiconductor films with low carbon levels, J.T. Yates, Jr., A. Hübner, S.R. Lucas, W.D. Partlow, J. Schaefer and W.J. Choyke 82/83 (1994) 180
- Hydrogen atom assisted ALE of silicon, S. Imai and M. Matsumura 82/83 (1994) 322
- Suppression of HBO_2 and Sb adsorption on thin-oxide-covered, H-terminated, or Sb-terminated Si(100) surfaces, E. Murakami, H. Kujirai and S. Kimura 82/83 (1994) 338
- Si ALE using chlorine/hydrogen exchange. Fundamentals and films, D.D. Koleske and S.M. Gates 82/83 (1994) 344
- Isothermal H_2 desorption kinetics from Si(100)2 × 1: dependence on disilane and atomic hydrogen precursors, L.A. Okada, M.L. Wise and S.M. George 82/83 (1994) 410
- Low temperature adsorption of hydrogen on Si(111) and (100) surfaces studied by elastic recoil detection analysis, M. Watamori, M. Naitoh, H. Morioka, Y. Maeda and K. Oura 82/83 (1994) 417
- Reactivity of III-V and II-VI semiconductors toward hydrogen: surface modification and evolution in air, D. Ballutaud, C. Debiemme-Chouvy, A. Etcheberry, P. De Mierry and L. Svob 84 (1995) 187
- Quantitative analysis of the thermal degassing of a beryllium powder, L. Buisson, P. Bracconi and X. Claudon 84 (1995) 211
- In situ diffuse reflectance infrared (DRIFTS) identification of active sites in the $CO + H_2$ reaction over lanthanide-modified Rh/ Al_2O_3 catalysts, J.J. Benítez, I. Carrizosa and J.A. Odriozola 84 (1995) 391
- Helium and hydrogen-decorated cavities in silicon, R.A. Hakvoort, A. van Veen, P.E. Mijnen and H. Schut 85 (1995) 271
- VUV laser (157 nm) chemical vapor deposition of high quality amorphous hydrogenated silicon: gas phase chemistry and modelling, H. Karstens, J. Knobloch, A. Winkler, A. Pusel, M. Barth and P. Hess 86 (1995) 521
- Field ion microscopy during an oscillating surface reaction: NO/H_2 on Pt, C. Voss and N. Kruse 87/88 (1995) 127
- Field-induced oxygen layer formation from H_2O and its titration by hydrogen on a Pt-emitter, V. Gorodetskii, N. Ernst, W. Drachsel and J.H. Block 87/88 (1995) 151
- The distribution of activation energy for hydrogen desorption over silica-supported nickel catalysts determined from temperature-programmed desorption spectra, M. Arai, Y. Nishiyama, T. Masuda and K. Hashimoto 89 (1995) 11
- XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. I. Hydrogen treatments on a 10 Å thick film, P.C. Wong, Y.S. Li, M.Y. Zhou and K.A.R. Mitchell 89 (1995) 255
- XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. II. Effects of heating a 26 Å thick film after treatment with a hydrogen plasma, Y.S. Li, P.C. Wong and K.A.R. Mitchell 89 (1995) 263
- Cadmium selenide-amorphous hydrogenated silicon heterostructures, S. Wu and D. Haneman 89 (1995) 289
- Experimental study of passivating ion-beam-induced distributed energy levels in n-GaAs by hydrogen species from boiling water, I. Thurzo, E. Pincik, G. Papaioannou, P. Dimitrakakis and N. Arpatzanis 90 (1995) 39
- Hydrogen adsorption induced phase transitions on Si(100)-c(8 × 8): temperature dependence studied by LEED, X. Hu and Z. Lin 90 (1995) 111
- The reactivity of O_2/H_2 , O_2/CO and O_2/C_3H_6 gas mixtures on Cu(111), W.E.J.

- Van Kooten, J.P.C. Van Nispen, O.L.J. Gijzeman and J.W. Geus 90 (1995) 137
- Atomic hydrogen adsorption on sintered thin copper films, R. Duś, E. Nowicka, W. Lisowski and Z. Wolfram 90 (1995) 277
- Atomic hydrogen-assisted ALE of germanium, S. Sugahara, M. Kadoshima, T. Kitamura, S. Imai and M. Matsumura 90 (1995) 349
- Surface interaction between H_2 and CO_2 over silicalite-supported platinum, M. Huang, S. Kaliaguine and S. Suppiah 90 (1995) 393

Indium

- Selective epitaxial growth of GaInP by LP-MOCVD using ethyldimethylindium, trimethylindium, trimethylgallium and triethylgallium as group III sources, S.-H. Chan, S.M. Sze, C.-Y. Chang and W.-I. Lee 82/83 (1994) 85
- Microscopic analysis of interface structure in InGaAs/InP MQW using Pendelösung oscillation around a satellite peak in high-resolution X-ray diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya 82/83 (1994) 115
- Growth of In_2S_3 thin films by atomic layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä 82/83 (1994) 122
- Atypical characteristics of KrF excimer laser ablation of indium-tin oxide films, T. Szörényi, Z. Kántor and L.D. Laude 86 (1995) 219
- An APFIM/TEM investigation of the discontinuous precipitation in a Ni-In alloy, G.P. Geber 87/88 (1995) 234

Indium antimonide

- Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watanabe, F. Maeda and M. Oshima 82/83 (1994) 136

Indium arsenide

- Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda 82/83 (1994) 109
- In-situ monitoring of 1st-order phase transition on InAs(001) surfaces by scanning electron surface microscopy, H. Yamaguchi, Y. Homma and Y. Horikoshi 82/83 (1994) 223

Indium phosphide

- Surface states in the band-gap for Pt-deposited p-InP photoelectrochemical cells, H. Kobayashi, F. Mizuno and Y. Nakato 81 (1994) 399
- Pulsed-jet epitaxy: application to device processes, Y. Sakuma, M. Ozeki, N. Ohtsuka, Y. Matsumiya, H. Shigematsu, O. Ueda, S. Muto, K. Nakajima and N. Yokoyama 82/83 (1994) 46
- Migration and related buried epitaxy using digital epitaxial growth conditions, I. Takahashi, M. Nakaji and H. Kawanishi 82/83 (1994) 70
- Fabrication of smooth facets of InP by selective sidewall epitaxy using CBE, M. Gotoda, H. Sugimoto, S. Maruno, T. Isu, W. Susaki and M. Nunoshita 82/83 (1994) 80
- Microscopic analysis of interface structure in InGaAs/InP MQW using Pendelösung oscillation around a satellite peak in high-resolution X-ray diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya 82/83 (1994) 115
- Flow modulation epitaxy of $Ga_xIn_{1-x}As$ /AlAs heterostructures on InP for resonant tunneling diodes, B.P. Keller, J.C. Yen, A.L. Holmes Jr., S.P. DenBaars and U.K. Mishra 82/83 (1994) 126
- Morphology of epitaxial SrF_2 films on atomically modified InP(100), S. Heun, M. Sugiyama, S. Maeyama, Y. Watanabe and M. Oshima 82/83 (1994) 507
- Application of time-dependent diffusion models to the study of real solids, D.T. Britton and J. Störmer 85 (1995) 1
- Laser-assisted dry etching ablation of InP, J.J. Dubowski, A. Compaan and M. Prasad 86 (1995) 548
- Characterization of thin Ag films deposited onto InP(001)-p(2 × 4) surface at room temperature by means of LEED, RHEED, AES and RBS-channeling techniques, M. Hanebuchi, T. Katoh and K. Morita 89 (1995) 113
- Interfacial reaction of Ag with the InP (100)4 × 2 surface - a photoemission study, H. Engelhard, F. Stietz, S. Sloboshanin, V. Persch, Th. Allinger, J.A. Schaefer and A. Goldmann 90 (1995) 89
- Lateral composition modulation in InGaAsP deposited by gas source molecular beam epitaxy on (100)- and (h11)-oriented InP substrates, R.R. LaPierre, B.J. Robinson and D.A. Thompson 90 (1995) 437
- Morphology, atomic composition and photoelectric properties of the microrelief InP-electrolyte interface, N.L. Dmitruk,

E.V. Basiuk, G.Ya. Kolbasov, O.A. Yakubtsov, I.A. Molchanovskii and T.A. Taranets

90 (1995) 489

Infrared spectroscopy

FT-IR investigation of methane adsorption on silica, J. Wu, S. Li, G. Li, C. Li and Q. Xin

81 (1994) 37

Coordination compounds as precursors for laser deposition of nickel-based conducting films, M. Devillers, O. Dupuis, A. Janosi and J.P. Soumillion

81 (1994) 83

Combined use of XPS, IR and EDAX techniques for the characterization of ZrO_2 - SiO_2 powders prepared by a sol-gel process, J.A. Navío, M. Macías, G. Colón, P.J. Sánchez-Soto, V. Augugliaro and L. Palmisano

81 (1994) 325

In-situ FTIR investigation of coke formation on USY zeolite, C. Li, Y.-W. Chen, S.-J. Yang and R.-B. Yen

81 (1994) 465

Surface stoichiometry and the role of adsorbates during GaAs atomic layer epitaxy, J.R. Creighton

82/83 (1994) 171

Atomic layer controlled deposition of SiO_2 and Al_2O_3 using ABAB... binary reaction sequence chemistry, S.M. George, O. Sneh, A.C. Dillon, M.L. Wise, A.W. Ott, L.A. Okada and J.D. Way

82/83 (1994) 460

Surface coverage of ALE precursors on oxides, S. Haukka, E.-L. Lakomaa and T. Suntola

82/83 (1994) 548

Evidence for infrared absorption enhancement of species at the lithium metal/electrolytic solution interface, Y. Suzuki, K. Sagisaka and A. Hatta

84 (1995) 1

An FT-IR investigation of parabactin adsorbed onto aluminum, D.C. Hansen, E. McCafferty, C.W. Lins and J.J. Fitzpatrick

84 (1995) 85

A study of surface modification of silica using XPS, DRIFT and NMR, F. Garbassi, L. Balducci, P. Chiurlo and L. Deiana

84 (1995) 145

A multitechnique analysis of the outermost layers of the Teflon PFA surface, K. Piyakis, E. Sacher, A. Domingue, J.-J. Pireaux, G. Leclerc, P. Bertrand and J.B. Lhoest

84 (1995) 227

In situ diffuse reflectance infrared (DRIFTS) identification of active sites in the $CO + H_2$ reaction over lanthanide-modified Rh/Al_2O_3 catalysts, J.J. Benítez, I. Carrizosa and J.A. Odriozola

84 (1995) 391

Using the Lambert-Beer law for thickness evaluation of photoconductor coatings for recording holograms, A. Larena, G. Pinto and F. Millán

84 (1995) 407

Analysis and experimental study of one-photon incubated absorption in polymers, P.E. Dyer, D.M. Karnakis and G.A. Oldershaw

86 (1995) 1

Excimer laser reactive ablation deposition of silicon nitride films, E. D'Anna, G. Leggieri, A. Luches, M. Martino, A. Perrone, G. Majni, P. Mengucci, R. Alexandrescu, I.N. Mihailescu and J. Zemek

86 (1995) 170

UV photo-annealing of thin sol-gel films, R.E. Van de Leest

86 (1995) 278

Improvement of silicon oxide film properties by ultraviolet excimer lamp annealing, E.G. Parada, P. González, J. Serra, B. León, M. Pérez-Amor, J. Flicstein and R.A.B. Devine

86 (1995) 294

Effect of UV annealing of radiation damage in SiO_2 films, I.P. Lisovskii, V.G. Litovchenko and V.B. Lozinskii

86 (1995) 299

An investigation of the thermal stability of undecylimidazole on copper by FT-IR reflection-absorption spectroscopy, S. Yoshida and H. Ishida

89 (1995) 39

Plasma-enhanced reactively evaporated deposition of SiO_2 films, A.A. Shklyayev and A.S. Medvedev

89 (1995) 49

Growth of a surface film on copper from benzotriazole solutions, G. Xue, J. Ding and P. Cheng

89 (1995) 77

M-S (M = Mo, W) cluster compound films on copper surfaces, X.R. Ye, H.W. Hou, X.Q. Xin and C.F. Hammer

89 (1995) 151

The chemical interaction between plasma-excited nitrogen and the surface of titanium dioxide, S. Kameoka, T. Kuriyama, M. Kuroda, S. Ito and K. Kunimori

89 (1995) 411

IRAS and TDS study on the photolytic decarbonylation of iron pentacarbonyl adsorbed on a SiO_2 film with a buried metal layer, S. Sato, S. Minoura, T. Urisu and Y. Takasu

90 (1995) 29

Pulse plasma beam deposition of cubic boron nitride films on GCr15 steel bearing substrate at room temperature, P. Yan and S.-Z. Yang

90 (1995) 149

A quantitative time-of-flight secondary ion mass spectrometry study of ion formation mechanisms using acid-base alternating Langmuir-Blodgett films, J.-X. Li, J.A. Gardella, Jr. and P.J. McKeown

90 (1995) 205

Surface interaction between H_2 and CO_2 over silicalite-supported platinum, M. Huang, S. Kaliaguine and S. Suppiah

90 (1995) 393

Interfaces

- Interface study on laser-induced material transfer from polymer and quartz surfaces, S. Lätsch, H. Hiraoka, W. Nieveen and J. Bargon 81 (1994) 183
- Adsorption of monoethanolamine on clean, oxidized and hydroxylated aluminium surfaces: a model for amine-cured epoxy/aluminium interfaces, C. Fauquet, P. Dubot, L. Minel, M.-G. Barthés-Labrousse, M. Rei Vilar and M. Villatte 81 (1994) 435
- Microscopic analysis of interface structure in InGaAs/InP MQW using Pendelösung oscillation around a satellite peak in high-resolution X-ray diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya 82/83 (1994) 115
- Adaptive temperature program ALE of $\text{Si}_{1-x}\text{Ge}_x/\text{Si}$ heterostructures from $\text{Si}_2\text{H}_6/\text{Ge}_2\text{H}_6$, S. Asami, N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt 82/83 (1994) 359
- Observation of the interface of Ba/Si(100) by MDS and TDS, S. Hongo, K. Ojima, S. Taniguchi, T. Urano and T. Kanaji 82/83 (1994) 537
- An X-ray scattering study of $\text{SiO}_x/\text{Si}/\text{Ge}(001)$, S.D. Kosowsky, C.-H. Hsu, P.S. Pershan, J. Bevk and B.S. Freer 84 (1995) 179
- Interfacial modification of polymer/metal joints by a two-component coupling system of polybenzimidazole and 2-mercaptobenzimidazole, S. Guo, G. Xue and Y. Qian 84 (1995) 351
- Annealing studies of Au/GaAs and Al/GaAs interfaces using a variable energy positron beam, C.C. Ling, T.C. Lee, S. Fung, C.D. Beling, H. Weng, J. Xu, S. Sun and R. Han 85 (1995) 305
- Atom probe analysis of interfacial segregation, M.K. Miller and G.D.W. Smith 87/88 (1995) 243
- X-ray photoelectron spectroscopic study of room-temperature evolution of oxide-covered hydrogenated amorphous silicon/aluminium interface, C. Anandan 89 (1995) 57
- A study of the composition distribution at the $\text{Ti}/\text{Al}_2\text{O}_3$ interface using the MCs^+ -SIMS technique, X. Chen and Y. Wang 89 (1995) 169
- irradiation, K. Suzue, T. Matsuura, J. Murota, Y. Sawada and T. Ohmi 82/83 (1994) 422
- Oxidation of TiN thin films in an ion-beam-assisted deposition process, H. Kubota, M. Nagata, R. Miyagawa and M.A. Nicolet 82/83 (1994) 565
- Initial oxidation kinetics of Fe-Ni single crystals before and after ion bombardment, S.P. Chenakin 84 (1995) 91
- A comparative study of primary ion energy dependence of secondary ion yields from Si and Ge surfaces under inert and reactive ion bombardment, N. Ray, P. Rajasekar and S.D. Dey 84 (1995) 203
- Determination of the characteristic signal for positron annihilation at divacancies in ion-irradiated silicon, R.D. Goldberg, P.J. Schultz and P.J. Simpson 85 (1995) 287
- Influence of ion bombardment on the refractive index of laser pulse deposited oxide films, G. Reisse, S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz 86 (1995) 107
- Effect of UV annealing of radiation damage in SiO_2 films, I.P. Lisovskii, V.G. Litovchenko and V.B. Lozinskii 86 (1995) 299
- Preferential sputtering of argon ion bombarded Ni_3Al and TaSi_2 , S. Hofmann and M.G. Stepanova 90 (1995) 227
- A study of the compositional changes in chemically etched, Ar ion bombarded and reactive ion etched GaAs(100) surfaces by means of ARXPS and LEISS, J.L. Sullivan, W. Yu and S.O. Saied 90 (1995) 309

Ion implantation

- Buried-oxide layer formation by high-dose oxygen-ion implantation into Si wafers: SIMOX (separation by implanted oxygen), K. Kajiyama 85 (1995) 259
- Helium and hydrogen-decorated cavities in silicon, R.A. Hakvoort, A. van Veen, P.E. Mijnders and H. Schut 85 (1995) 271
- Photo-luminescence of pulsed excimer laser annealed Sb-implanted CdTe, F.X. Wagner, K. Dhese, P.H. Key, D. Sands, S.R. Jackson, R. Kirbitson and J.E. Nicholls 86 (1995) 364
- Effect of low-energy (20-40 keV) ion implantation on phase transformations in the subsurface volume of alloys, V.A. Ivchenko and N.N. Syutkin 87/88 (1995) 257
- A photoemission study of electron states in Sb-ion implanted $\text{TiO}_2(110)$, A.E. Tavernier, A. Gulino, R.G. Egdell and T.J. Tate 90 (1995) 383

Ion bombardment

- Substrate orientation dependence of self-limited atomic-layer etching of Si with chlorine adsorption and low-energy Ar^+

- Range profiles of 6-10 MeV ^{15}N ions implanted in silicon, T. Ahlgren, K. Väkeväinen, J. Räisänen, E. Rauhala and J. Keinonen 90 (1995) 419
- Ion scattering*
- The effect of cyclic oxidation-reduction pretreatments on an amorphous $\text{Ni}_{80}\text{P}_{20}$ catalyst: an XPS/UPS/ISS study, J. Deng, H. Chen, X. Bao and M. Muhler 81 (1994) 341
- A combined use of SIMS and RBS techniques for the investigation of SiC and SiCN films, F. Caccavale, G. Brusatin and I. Kleps 81 (1994) 443
- Growth of In_2S_3 thin films by atomic layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä 82/83 (1994) 122
- NbCl_5 as a precursor in atomic layer epitaxy, K.-E. Elers, M. Ritala, M. Leskelä and E. Rauhala 82/83 (1994) 468
- Surface modification of CaF_2 in atomic layer scale by electron beam exposure, S.M. Hwang, A. Izumi, K. Tsutsui and S. Furukawa 82/83 (1994) 523
- Structural study of $\text{SrTiO}_3(100)$ surfaces by low energy ion scattering, Y. Tanaka, H. Morishita, M. Watamori, K. Oura and I. Katayama 82/83 (1994) 528
- Surface coverage of ALE precursors on oxides, S. Haukka, E.-L. Lakomaa and T. Suntola 82/83 (1994) 548
- Deposition of inorganic salts from solution on flat substrates by spin-coating: theory, quantification and application to model catalysts, R.M. Van Hardeveld, P.L.J. Gunter, L.J. Van IJzendoorn, W. Wieldraaijer, E.W. Kuipers and J.W. Niemantsverdriet 84 (1995) 339
- Laser-induced selective deposition of Ni-P alloy on silicon, J. Wang, X. Fei, Z. Yu and G. Zhao 84 (1995) 383
- Buried-oxide layer formation by high-dose oxygen-ion implantation into Si wafers: SIMOX (separation by implanted oxygen), K. Kajiyama 85 (1995) 259
- The laser ablation threshold of $\text{YBa}_2\text{Cu}_3\text{O}_{6+x}$ as revealed by using projection optics, B. Dam, J. Rector, M.F. Chang, S. Kars, D.G. de Groot and R. Griessen 86 (1995) 13
- Plasma properties and stoichiometry of laser-deposited BiSrCaCuO thin films, J. Gonzalo, C.N. Afonso, F. Vega, D. Martínez García and J. Perrière 86 (1995) 40
- SiO_2 film deposition by XeCl laser ablation of fused silica, P. Baeri, R. Reitano and N. Marino 86 (1995) 128
- Structural properties of LiNbO_3 thin films grown by the pulsed laser deposition technique, P. Aubert, G. Garry, R. Bisaro and J. Garcia Lopez 86 (1995) 144
- Pulsed laser deposition of epitaxial layers of ZnSe, J.L. Deiss, A. Chergui, L. Koutti, J.L. Loison, M. Robino and J.B. Grun 86 (1995) 149
- $\text{Si}_{1-x}\text{Ge}_x$ thin films deposited by the pulsed excimer laser ablation technique, F. Antoni, E. Fogarassy, C. Fuchs, B. Prévot and J.P. Stoquert 86 (1995) 175
- Characterization of thin Ag films deposited onto $\text{InP}(001)\text{-p}(2 \times 4)$ surface at room temperature by means of LEED, RHEED, AES and RBS-channeling techniques, M. Hanebuchi, T. Katoh and K. Morita 89 (1995) 113
- Etching of CoSi_2 in HF-based solutions, R.A. Donaton, K. Lokere, R. Verbeeck and K. Maex 89 (1995) 221
- Interfacial reaction of NiO with $\text{Al}_2\text{O}_3(11\bar{2}0)$ and polycrystalline $\alpha\text{-Al}_2\text{O}_3$, P.H. Bolt, S.F. Lobner, J.W. Geus and F.H.P.M. Habraken 89 (1995) 339
- Synergistic alloying behaviour of $\text{Pd}_{50}\text{Cu}_{50}$ single crystals upon adsorption and co-adsorption of CO and NO, Y. Debaugé, M. Abon, J.C. Bertolini, J. Massardier and A. Rochefort 90 (1995) 15
- Recovery and recrystallization of $\text{SrTiO}_3(100)$ surface characterized by ion channeling, F. Wang, M. Badaye, K. Ogawa and T. Morishita 90 (1995) 123
- XPS/NRA investigations of particle size effects during the oxidation of Cu particles supported on oxidised $\text{Si}(100)$, R. Van Wijk, P.C. Görts, A.J.M. Mens, O.L.J. Gijzeman, F.H.P.M. Habraken and J.W. Geus 90 (1995) 261
- A study of the compositional changes in chemically etched, Ar ion bombarded and reactive ion etched $\text{GaAs}(100)$ surfaces by means of ARXPS and LEISS, J.L. Sullivan, W. Yu and S.O. Saied 90 (1995) 309
- Iron*
- XPS study of clean metal sulfide surfaces, K. Laajalehto, I. Kartio and P. Nowak 81 (1994) 11
- Initial oxidation kinetics of Fe-Ni single crystals before and after ion bombardment, S.P. Chenakin 84 (1995) 91
- Coadsorption of water and selected aromatic molecules to model the adhesion of epoxy resins on hydrated surfaces of zinc oxide and iron oxide, M. Nakazawa and G.A. Somorjai 84 (1995) 309

- Adsorption studies of iron on tungsten by probe-hole field emission microscopy, A.D. Adsool, R. Pande, R.B. Sharma, M.A. More and D.S. Joag 87/88 (1995) 37
- Characterization of neutron-irradiated Fe-Au alloys, M.K. Miller, K.F. Russell, A. Jostsons and R.G. Blake 87/88 (1995) 216
- Structure and chemistry of grain boundaries in Ni-16Cr-9Fe model materials, M. Thuvander and K. Stiller 87/88 (1995) 251
- A study of the effect of ageing temperature on phase separation in Fe-45%Cr alloys, J.M. Hyde, M.K. Miller, A. Cerezo and G.D.W. Smith 87/88 (1995) 311
- Comparison of low temperature decomposition in Fe-Cr and duplex stainless steels, M.K. Miller, J.M. Hyde, A. Cerezo and G.D.W. Smith 87/88 (1995) 323
- Ultraviolet inverse photoemission study of the oxidation of YFe₂, P. Vavassori, L. Callegaro and E. Puppini 89 (1995) 93
- Activation treatments and surface study of amorphous Fe₉₀Zr₁₀ and Fe_{87.8}Zr₁₀Co₂-Al_{0.2} catalysts, X.K. Wang, N.F. Shen, Z.S. Yang and H.C. Gu 89 (1995) 297
- Medium energy electron diffraction and X-ray photoelectron diffraction study of pseudomorphic Fe silicides grown on Si(111). Evidence of Fe vacancy formation, S. Hong, C. Pirri, P. Wetzels, D. Bolmont and G. Gewinner 90 (1995) 65
- Topological study of crack growth on iron crystal, M. Pingo, J. Vošta, J. Pancíř and I. Haslingerová 90 (1995) 373
- Krypton*
- Installation of a Kr moderator in the high-brightness beam at Brandeis, D. Vasumathi, G. Amarendra, K.F. Canter and A.P. Mills, Jr. 85 (1995) 154
- Langmuir-Blodgett structures*
- Structural investigation of Langmuir-Blodgett monolayers of L- α -dipalmitoylphosphatidylcholine by atomic force microscopy, X.-M. Yang, D. Xiao, Z.-H. Lu and Y. Wei 90 (1995) 175
- A quantitative time-of-flight secondary ion mass spectrometry study of ion formation mechanisms using acid-base alternating Langmuir-Blodgett films, J.-X. Li, J.A. Gardella, Jr. and P.J. McKeown 90 (1995) 205
- Lanthanides*
- Chemical etching of (100) and (110) faces of flux-grown LaBO₃ crystals, A. Jain, A.K. Razdan, P.N. Kotru and B.M. Wanklyn 84 (1995) 65
- Laser processing*
- Coordination compounds as precursors for laser deposition of nickel-based conducting films, M. Devillers, O. Dupuis, A. Janosi and J.P. Soumillion 81 (1994) 83
- Growth of excimer-laser-induced dendritic surface structures on polyethylene-terephthalate, J. Heitz, E. Arenholz, D. Bäuerle and K. Schilcher 81 (1994) 103
- Interface study on laser-induced material transfer from polymer and quartz surfaces, S. Lätsch, H. Hiraoka, W. Nieveen and J. Bargon 81 (1994) 183
- Square-shaped temperature distribution induced by a Gaussian-shaped laser beam, Y.-F. Lu 81 (1994) 357
- Control of the etching reaction of digital etching using tunable UV laser irradiation, T. Meguro, M. Ishii, T. Sugano, K. Gamo and Y. Aoyagi 82/83 (1994) 193
- Laser-induced decomposition of dimethyl cadmium on a quartz substrate, S.-P. Lee and M.C. Lin 84 (1995) 31
- Carrier transport in heavily doped polycrystalline silicon layers after annealing by a scanning laser beam, A.K. Fedotov, M.I. Tarasik and A.M. Yanchenko 84 (1995) 379
- Laser-induced selective deposition of Ni-P alloy on silicon, J. Wang, X. Fei, Z. Yu and G. Zhao 84 (1995) 383
- Analysis and experimental study of one-photon incubated absorption in polymers, P.E. Dyer, D.M. Karnakis and G.A. Oldershaw 86 (1995) 1
- Overheated metastable states in polymer sublimation by laser radiation, V.I. Mazhukin, I. Smurov, C. Surry and G. Flamant 86 (1995) 7
- The laser ablation threshold of YBa₂Cu₃O_{6+x} as revealed by using projection optics, B. Dam, J. Rector, M.F. Chang, S. Kars, D.G. de Groot and R. Griessen 86 (1995) 13
- Blast-wave studies of excimer laser ablation of ZnS, P.E. Dyer, P.H. Key, D. Sands, H.V. Snelling and F.X. Wagner 86 (1995) 18
- Pulsed laser ablation of copper, R. Jordan, D. Cole, J.G. Lunney, K. Mackay and D. Givord 86 (1995) 24

- Why are high- T_c superconductors, HTSC, deposited by 248 nm lasers at 400 MW/cm²?, R.W. Dreyfus 86 (1995) 29
- Time of flight mass spectrometry and covariance mapping technique investigation of charged specie evolution in Pb(Ti_{0.48}Zr_{0.52})O₃ laser ablation, S. Amoroso, V. Berardi, N. Spinelli, R. Velotta, M. Armenante, F. Fusco, M. Allegrini and E. Arimondo 86 (1995) 35
- Plasma properties and stoichiometry of laser-deposited BiSrCaCuO thin films, J. Gonzalo, C.N. Afonso, F. Vega, D. Martínez García and J. Perrière 86 (1995) 40
- Laser ablation of BiSrCaCuO superconducting thin film: analysis of intermediate species in real time, U. Gambardella, A. Giardini, V. Marotta, A. Morone, S. Orlando and M. Snels 86 (1995) 45
- Characterisation of ionic species generated during ablation of Bi₂Sr₂Ca₂Cu₃O₁₀ by frequency-doubled Nd:YAG laser irradiation, G.C. Tyrrell, T.H. York and I.W. Boyd 86 (1995) 50
- Laser wavelength dependence of YBa₂Cu₃O_y laser ablation plumes, J. Palau, M. Sowinska, M. Varela, P. Summ, J. Esteve, P. Serra, J.L. Morenza and J.A. Miehe 86 (1995) 59
- Study of PbTe(Ga) evaporation using a nanosecond pulsed laser, V.A. Mikhailov, F.N. Putilin and D.N. Trubnikov 86 (1995) 64
- Composition and gas dynamics of laser ablated AlN plumes, T.M. Di Palma, S. Orlando, A. Giardini-Guidoni, A.J. Paul, J.W. Hastie and A. Mele 86 (1995) 68
- Laser ablation of refractory material, cluster formation and deposition, H. Yu, M.G. Huber and F.W. Froben 86 (1995) 74
- Pulsed laser deposition of metal and metal multilayer films, J.G. Lunney 86 (1995) 79
- Laser deposition of metallic alloys and multilayers, H.-U. Krebs, S. Fähler and O. Bremert 86 (1995) 86
- Comparison of the structure of laser deposited and sputtered metallic alloys, H.-U. Krebs, O. Bremert, M. Störmer and Y. Luo 86 (1995) 90
- Erbium oxide thin films on Si(100) obtained by laser ablation and electron beam evaporation, X. Queral, C. Ferrater, F. Sánchez, R. Aguiar, J. Palau and M. Varela 86 (1995) 95
- Effects of laser wavelength and fluence on the growth of ZnO thin films by pulsed laser deposition, V. Craciun, S. Amirhaghi, D. Craciun, J. Elders, J.G.E. Gardieniers and I.W. Boyd 86 (1995) 99
- Influence of LN₂ substrate cooling on optical properties of laser-pulse-deposited oxide films, G. Reisse, S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz 86 (1995) 114
- Excimer laser sputtering deposition of TiO₂ optical coating for solar cells, H.-A. Durand, J.-H. Brimaud, O. Hellman, H. Shibata, S. Sakuragi, Y. Makita, D. Gesbert and P. Meyrueis 86 (1995) 122
- SiO₂ film deposition by XeCl laser ablation of fused silica, P. Baeri, R. Reitano and N. Marino 86 (1995) 128
- SEM observations of YBCO on as-received and heat-treated MgO substrates, S. King, L. Coccia and I.W. Boyd 86 (1995) 134
- Pulsed laser deposition and nanometer scale characterization of YBa₂Cu₃O_{7-δ} thin films by scanning probe methods, R. Sum, H.P. Lang and H.-J. Güntherodt 86 (1995) 140
- Structural properties of LiNbO₃ thin films grown by the pulsed laser deposition technique, P. Aubert, G. Garry, R. Bisaro and J. Garcia Lopez 86 (1995) 144
- Pulsed laser deposition of epitaxial layers of ZnSe, J.L. Deiss, A. Chergui, L. Koutti, J.L. Loison, M. Robino and J.B. Grun 86 (1995) 149
- Comparison of epitaxial films of Zn_{1-x}Mn_xTe on (111) and (100) GaAs produced by pulsed laser deposition, H.J. Masterson and J.G. Lunney 86 (1995) 154
- Pulsed laser deposition of NbTe_x thin films, F. Grangeon, H. Sassoli, Y. Mathey, M. Autric, D. Pailharey and W. Marine 86 (1995) 160
- Structure and chemical composition of BN thin films grown by pulsed-laser deposition (PLD), T. Klotzbücher, W. Pfleging, M. Mertin, D.A. Wesner and E.W. Kreutz 86 (1995) 165
- Excimer laser reactive ablation deposition of silicon nitride films, E. D'Anna, G. Leggieri, A. Luches, M. Martino, A. Perrone, G. Majni, P. Mengucci, R. Alexandrescu, I.N. Mihailescu and J. Zemek 86 (1995) 170
- Si_{1-x}Ge_x thin films deposited by the pulsed excimer laser ablation technique, F. Antoni, E. Fogarassy, C. Fuchs, B. Prévot and J.P. Stoquert 86 (1995) 175
- Effect of laser power density and deposition temperature on electrical and optical properties of pulsed laser ablated diamond-like carbon films, J. Levoska and S. Leppävuori 86 (1995) 180

- Pulsed-laser deposition and characterization of TaC films, R. Teghil, L. D'Alessio, G. De Maria and D. Ferro 86 (1995) 190
- Metal pattern deposition by laser-induced forward transfer, Z. Kántor, Z. Tóth and T. Szörényi 86 (1995) 196
- New approach of a laser-induced forward transfer for deposition of patterned thin metal films, H. Esrom, J.-Y. Zhang, U. Kogelschatz and A.J. Pedraza 86 (1995) 202
- Laser-induced forward transfer of ultra-fine diamond particles for selective deposition of diamond films, S.M. Pimenov, G.A. Shafeev, A.A. Smolin, V.I. Konov and B.K. Vodolaga 86 (1995) 208
- Optodynamic aspect of a pulsed laser ablation process, R. Hrovatin and J. Možina 86 (1995) 213
- Atypical characteristics of KrF excimer laser ablation of indium-tin oxide films, T. Szörényi, Z. Kántor and L.D. Laude 86 (1995) 219
- Excimer laser ablation of Nd:YAG and Nd:glass, S.R. Jackson, W.J. Metheringham and P.E. Dyer 86 (1995) 223
- Excimer laser ablation patterning of dielectric layers, J. Ihlemann and B. Wolff-Rottke 86 (1995) 228
- Excimer laser etching of diamond-like carbon films: spalling effect, T.V. Kononenko, V.G. Ralchenko, E.D. Obratsova, V.I. Konov, J. Seth, S.V. Babu and E.N. Loubnin 86 (1995) 234
- Ablation of nylon-6,6 with UV and IR lasers, C.D. Skordoulis, M. Makropoulou and A.A. Serafetinides 86 (1995) 239
- Structuring of polyimide-metal carbide layer systems by excimer laser ablation, J. Ihlemann, B. Wolff-Rottke, G. Danev, K. Petkov and E. Spassova 86 (1995) 245
- Combination of excimer laser micromachining and replication processes suited for large scale production, J. Arnold, U. Dasbach, W. Ehrfeld, K. Hesch and H. Löwe 86 (1995) 251
- Laser-surface processing of metals and ceramics for industrial applications, H.W. Bergmann, K. Schutte, E. Schubert and A. Emmel 86 (1995) 259
- Tailoring of surface properties by removal and deposition with laser radiation, E.W. Kreutz, H. Frerichs, M. Mertin, D.A. Wesner and W. Pfleging 86 (1995) 266
- Improvement of silicon oxide film properties by ultraviolet excimer lamp annealing, E.G. Parada, P. González, J. Serra, B. León, M. Pérez-Amor, J. Flicstein and R.A.B. Devine 86 (1995) 294
- Influence of temperature gradient to solidification velocity ratio on the structure transformation in pulsed- and CW-laser surface treatment, N.A. Berjeza, S.P. Velikevitch, V.I. Mazhukin, I. Smurov and G. Flamant 86 (1995) 303
- Rapid prototyping with CO₂ laser radiation, E.W. Kreutz, G. Backes, A. Gasser and K. Wissenbach 86 (1995) 310
- Microstructure, chemical composition and properties of the surface layer of M2 steel after laser melting under different conditions, J. Kusiński 86 (1995) 317
- Morphology of Si_{1-x}Ge_x thin crystalline films obtained by pulsed-excimer-laser annealing of heavily Ge-implanted Si, E.L. Mathé, A. Naudon, F. Repplinger and E. Fogarassy 86 (1995) 338
- Formation of poly-Si_{1-x}Ge_x using excimer-laser processing, A. Slaoui, C. Deng, S. Talwar, K.J. Kramer, T.W. Sigmon, J.P. Stoquert and B. Prevot 86 (1995) 346
- Surface morphology and structure modification of silicon layers induced by nanosecond laser radiation, A.V. Demchuk and V.A. Labunov 86 (1995) 353
- Theoretical and experimental studies of a-Si:H recrystallization by XeCl excimer laser irradiation, R. Černý, V. Vydra, P. Přikryl, I. Ulrych, J. Kočka, K.M.A. El-Kader, Z. Chvoj and V. Cháb 86 (1995) 359
- Photo-luminescence of pulsed excimer laser annealed Sb-implanted CdTe, F.X. Wagner, K. Dhese, P.H. Key, D. Sands, S.R. Jackson, R. Kirbitson and J.E. Nicholls 86 (1995) 364
- Surface properties of excimer-laser-irradiated sintered alumina, L.D. Laude, K. Kolev, M. Brunel and P. Deleter 86 (1995) 368
- Formation of Ti³⁺ ions at the surface of laser-irradiated rutile, T. Le Mercier, J.-M. Mariot, P. Parent, M.-F. Fontaine, C.F. Hague and M. Quarton 86 (1995) 382
- Enhanced adherence of electroless metal deposit on SiO₂ via control of the chemical environment of the Pd seeding layer, G.A. Shafeev, L. Bellard, J.-M. Thémelin, W. Marine and A. Cros 86 (1995) 387
- Laser-assisted selective metallisation of diamonds by electroless Ni and Cu plating, G.A. Shafeev, S.M. Pimenov and E.N. Loubnin 86 (1995) 392
- Laser-induced formation of porous silicon, V. Baranauskas, G.P. Thim and A. Peled 86 (1995) 398
- Laser-induced surface modification and metallization of polymers, H. Frerichs, J. Stricker, D.A. Wesner and E.W. Kreutz 86 (1995) 405
- Thin films of polymer blends: surface treatment and theoretical modeling, P.

- Viville, O. Thoelen, S. Beauvois, R. Lazzaroni, G. Lambin, J.L. Brédas, K. Kolev and L. Laude 86 (1995) 411
- Laser-assisted etching-like damage of Si, A.V. Simakin and G.A. Shafeev 86 (1995) 422
- Laser direct writing and instabilities: a one-dimensional approach, N. Arnold, P.B. Kargl and D. Bäuerle 86 (1995) 457
- Laser chemical vapour deposition for micro-electronics, G. Auvert 86 (1995) 466
- Laser processing of tungsten from WF_6 and SiH_4 , M. Meunier, P. Desjardins, M. Tabbal, N. Elyaagoubi, R. Izquierdo and A. Yelon 86 (1995) 475
- Laser-induced etching and deposition of tungsten in WF_6 - H_2 atmosphere, K. Piglmayer, Z. Tóth and Z. Kantor 86 (1995) 484
- Kinetics of laser thermal decomposition of trimethylamine alane, D. Tonneau, J.E. Bourée and Y. Pauleau 86 (1995) 488
- Kinetic model for scanning laser-induced deposition from the liquid phase, Zs. Geretovszky, L. Kelemen, K. Bali and T. Szörényi 86 (1995) 494
- The effect of process parameters on the O/Mo ratio in laser deposition of molybdenum oxides from aqueous solutions, K. Bali, Zs. Geretovszky, A.L. Tóth and T. Szörényi 86 (1995) 500
- Deposition of gold on polyimide from solutions, S. Pflüger, M. Wehner, F. Jansen, Th. Kruck and F. Lupp 86 (1995) 504
- Excimer laser-induced deposition of copper from $Cu(hfac)(TMVS)$, R. Izquierdo, J. Bertomeu, M. Suys, E. Sacher and M. Meunier 86 (1995) 509
- Laser induced deposition of nanocrystalline Si with preferred crystallographic orientation, S. Tamir and S. Berger 86 (1995) 514
- VUV laser (157 nm) chemical vapor deposition of high quality amorphous hydrogenated silicon: gas phase chemistry and modelling, H. Karstens, J. Knobloch, A. Winkler, A. Pusel, M. Barth and P. Hess 86 (1995) 521
- Germanium-containing coatings by IR laser-induced decomposition of ethoxy-(trimethyl)germane and tetramethylgermane, R. Fajgar, M. Jakoubková, Z. Bastl and J. Pola 86 (1995) 530
- Laser-induced photodeposition from ZnS colloid solutions, A. Peled, B. Dragnea, R. Alexandrescu and A. Andrei 86 (1995) 538
- Laser chemical etching of Cu_2O , G. Stenberg, M. Boman, M. Ottosson and J.-O. Carlsson 86 (1995) 543
- Laser-assisted dry etching ablation of InP, J.J. Dubowski, A. Compaa and M. Prasad 86 (1995) 548
- Surface reaction control in digital etching of GaAs by using a tunable UV laser system: reaction control mechanism in layer-by-layer etching, M. Ishii, T. Meguro, T. Sugano, K. Gamo and Y. Aoyagi 86 (1995) 554
- Excimer laser-assisted etching of silicon in chlorine: adsorption and desorption, A.V. Kuzmichov 86 (1995) 559
- Excimer-laser-induced etching of silicon in chlorine atmosphere at a wavelength of 248 nm, W. Jiang, H. Baumgärtner and I. Eisele 86 (1995) 564
- Three-dimensional nanostructures by direct laser etching of Si, M. Müllenborn, H. Dirac and J.W. Petersen 86 (1995) 568
- Desorption in light-induced dry etching of GaAs with Cl_2 around 120 nm, B. Li, U. Steller, H.-P. Krause, I. Twesten, N. Schwentner, V. Stepanenko and Yu. Poltoratskii 86 (1995) 577
- Surface kinetics and morphology of ArF laser-assisted etching of (113)A GaAs in a Cl_2 environment, P. Tejedor and P.S. Domínguez 89 (1995) 271
- Tantalum oxide film formation by excimer laser ablation, Y. Nishimura, H. Ujita and M. Tsuji 89 (1995) 393
- Synthesis of molybdenum nitride γ - Mo_2N by multipulse laser irradiation of molybdenum in nitrogen, J.D. Wu, C.Z. Wu, Z.M. Song, L.H. Wu and F.M. Li 90 (1995) 81
- Laser-induced temperature rise in Gaussian-shaped holes, Y.F. Lu, T.E. Loh, H.G. Soh and T.S. Low 90 (1995) 217
- Melting and diffusion under nanosecond laser pulse, W. Szyszko 90 (1995) 325
- ### Lead
- XPS study of clean metal sulfide surfaces, K. Laajalehto, I. Kartio and P. Nowak 81 (1994) 11
- Surface modification of lead silicate glass under X-ray irradiation, P.W. Wang, L.P. Zhang, L. Lu, D.V. LeMone and D.L. Kinser 84 (1995) 75
- Comment on 'Scanning tunnelling microscopy studies of galena: the mechanism of oxidation in air' by B.S. Kim, R.A. Hayes, C.A. Prestidge, J. Ralston and R.St.C. Smart, A.N. Buckley and R. Woods 84 (1995) 223
- Surface analysis of commercial lead/acid battery grids, R. De Marco and J. Liesegang 84 (1995) 237
- Time of flight mass spectrometry and covariance mapping technique investiga-

- tion of charged specie evolution in $\text{Pb}(\text{Ti}_{0.48}\text{Zr}_{0.52})\text{O}_3$ laser ablation, S. Amoruso, V. Berardi, N. Spinelli, R. Velotta, M. Armenante, F. Fuso, M. Allegrini and E. Arimondo 86 (1995) 35
- Study of $\text{PbTe}(\text{Ga})$ evaporation using a nanosecond pulsed laser, V.A. Mikhailov, F.N. Putilin and D.N. Trubnikov 86 (1995) 64
- SIMS microprofiles of Pb-5\%Sn solder joints in electronic devices after accelerated life tests, A. Scandurra, A. Porto and O. Puglisi 89 (1995) 1
- XPS oxygen line broadening in lead zirconium titanate and related materials, A. Zomorrodian, A. Mesarwi, N.J. Wu and A. Ignatiev 90 (1995) 343
- ### Low energy electron diffraction
- Low temperature adsorption of hydrogen on $\text{Si}(111)$ and (100) surfaces studied by elastic recoil detection analysis, M. Watamori, M. Naitoh, H. Morioka, Y. Maeda and K. Oura 82/83 (1994) 417
- Atomic layer controlled deposition of SiO_2 and Al_2O_3 using ABAB... binary reaction sequence chemistry, S.M. George, O. Sneh, A.C. Dillon, M.L. Wise, A.W. Ott, L.A. Okada and J.D. Way 82/83 (1994) 460
- Structural study of $\text{SrTiO}_3(100)$ surfaces by low energy ion scattering, Y. Tanaka, H. Morishita, M. Watamori, K. Oura and I. Katayama 82/83 (1994) 528
- Influence of atomic Cu-layer epitaxy on CO_2 and CO photoinduced desorption from $\text{ZnO}(0001)$, P.J. Møller, S.A. Komolov and E.F. Lazneva 82/83 (1994) 569
- Growth of extra-thin ordered aluminum films on $\text{Si}(111)$ surface, E.A. Khramtsova, A.V. Zotov, A.A. Saranin, S.V. Ryzhkov, A.B. Chub and V.G. Lifshits 82/83 (1994) 576
- Adsorption and co-adsorption of boron and oxygen on ordered $\alpha\text{-SiC}$ surfaces, V.M. Bermudez 84 (1995) 45
- Characterization of thin Ag films deposited onto $\text{InP}(001)\text{-p}(2 \times 4)$ surface at room temperature by means of LEED, RHEED, AES and RBS-channeling techniques, M. Hanebuchi, T. Katoh and K. Morita 89 (1995) 113
- The (0001) -surface of 6H-SiC : morphology, composition and structure, U. Starke, Ch. Bram, P.-R. Steiner, W. Hartner, L. Hammer, K. Heinz and K. Müller 89 (1995) 175
- Synergistic alloying behaviour of $\text{Pd}_{50}\text{Cu}_{50}$ single crystals upon adsorption and co-adsorption of CO and NO, Y. Debauge, M. Abon, J.C. Bertolini, J. Massardier and A. Rochefort 90 (1995) 15
- Ferroelectric BaTiO_3 films with a high-magnitude dielectric constant grown on p-Si by low-pressure metalorganic chemical vapor deposition, T.W. Kim, Y.S. Yoon, S.S. Yom and C.O. Kim 90 (1995) 75
- Hydrogen adsorption induced phase transitions on $\text{Si}(100)\text{-c}(8 \times 8)$: temperature dependence studied by LEED, X. Hu and Z. Lin 90 (1995) 111
- ### Luminescence
- Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda 82/83 (1994) 109
- Flow modulation epitaxy of $\text{Ga}_x\text{In}_{1-x}\text{As}/\text{AlAs}$ heterostructures on InP for resonant tunneling diodes, B.P. Keller, J.C. Yen, A.L. Holmes Jr., S.P. DenBaars and U.K. Mishra 82/83 (1994) 126
- Atomic layer epitaxy in the growth of complex thin film structures for electroluminescent applications, L. Niinistö and M. Leskelä 82/83 (1994) 454
- Electrical properties of $\text{Si-Al}_2\text{O}_3$ structures grown by ML-ALE, V.E. Drozd, A.P. Baraban and I.O. Nikiforova 82/83 (1994) 583
- Photo-luminescence of pulsed excimer laser annealed Sb-implanted CdTe, F.X. Wagner, K. Dhese, P.H. Key, D. Sands, S.R. Jackson, R. Kirbitson and J.E. Nicholls 86 (1995) 364
- GaAs growth by photon-assisted metalorganic molecular beam epitaxy using ethyl derivatives of gallium and arsenic, F. Maury, K. Bouabid, N. Fazouan, A.M. Gué and D. Estève 86 (1995) 447
- Lateral composition modulation in InGaAsP deposited by gas source molecular beam epitaxy on (100) - and $(h11)$ -oriented InP substrates, R.R. LaPierre, B.J. Robinson and D.A. Thompson 90 (1995) 437
- ### Magnesium
- Adsorption of CO on Mg-promoted $\text{Co}(\text{poly})$, J. Vaari, T. Vaara, J. Lahtinen and P. Hautojärvi 81 (1994) 289
- Investigations of the interface between magnesium and polyethyleneterephthalate by

- X-ray photoelectron spectroscopy, P.C. Wong, Y.S. Li and K.A.R. Mitchell 84 (1995) 245
- Reactions of CO and NO on Mg promoted cobalt, T. Vaara, J. Lahtinen and P. Hautojärvi 89 (1995) 103
- Preparation of a model Ziegler-Natta catalyst. Surface science studies of magnesium chloride thin film deposited on gold and its interaction with titanium chloride, E. Magni and G.A. Somorjai 89 (1995) 187

Magnesium oxide

- Surface segregation study of Ib-VIII single-crystal alloys, F. Reniers, M.P. Delplancke, A. Asskali, M. Jardinier-Offergeld and F. Bouillon 81 (1994) 151
- Auger and X-ray photoelectron diffraction in MgO(001), T.T. Tran and S.A. Chambers 81 (1994) 161
- Formation processes of ultrafine metal particles on MgO(100) as investigated by molecular dynamics and computer graphics, M. Kubo, R. Yamauchi, R. Vetrivel and A. Miyamoto 82/83 (1994) 559
- Mechanism of the formation of ultrafine gold particles on MgO(100) as investigated by molecular dynamics and computer graphics, M. Kubo, R. Miura, R. Yamauchi, R. Vetrivel and A. Miyamoto 89 (1995) 131
- Oxygen exchange between adsorbed NO and MgO surfaces, Y. Yanagisawa 89 (1995) 251

Magnetic properties

- Atom probe studies of nanostructured alloys, K. Hono and T. Sakurai 87/88 (1995) 166

Manganese

- Comparison of epitaxial films of $Zn_{1-x}Mn_xTe$ on (111) and (100) GaAs produced by pulsed laser deposition, H.J. Masterson and J.G. Lunney 86 (1995) 154
- MnCu surface alloy studied by scanning tunneling microscopy, D. Jeon, H.P. Noh, T. Hashizume, Y. Kuk and T. Sakurai 87/88 (1995) 386
- XPS studies of the effect of Mn on Pd/ Al_2O_3 , P.C. L'Argentière, M.G. Cañón and N.S. Fígoli 89 (1995) 63

Mass spectroscopy

- Molecular layer epitaxy of GaAs, J. Nishizawa 82/83 (1994) 1
- Selective MLE growth of GaAs and surface treatment for ideal static induction transistor (ISIT) application, Y. Oyama, P. Plotka and J. Nishizawa 82/83 (1994) 41
- Activation of the Ga-CH₃ bond using atomic hydrogen - a possible route to III-V semiconductor films with low carbon levels, J.T. Yates, Jr., A. Hübner, S.R. Lucas, W.D. Partlow, J. Schaefer and W.J. Choyke 82/83 (1994) 180
- Influence of atomic Cu-layer epitaxy on CO₂ and CO photoinduced desorption from ZnO(0001), P.J. Møller, S.A. Komolov and E.F. Lazneva 82/83 (1994) 569
- Copper oxidation and surface copper oxide stability investigated by pulsed field desorption mass spectrometry, D.L. Cocke, G.K. Chuah, N. Kruse and J.H. Block 84 (1995) 153
- Quantitative analysis of the thermal degassing of a beryllium powder, L. Buisson, P. Bracconi and X. Claudon 84 (1995) 211
- Composition of sputtered material from Cu-Ni alloy during Xe⁺ ion sputtering at elevated temperatures, S. Sekine, H. Shimizu and S. Ichimura 84 (1995) 401
- Time of flight mass spectrometry and covariance mapping technique investigation of charged specie evolution in Pb(Ti_{0.48}Zr_{0.52})O₃ laser ablation, S. Amoroso, V. Berardi, N. Spinelli, R. Velotta, M. Armenante, F. Fuso, M. Allegri and E. Arimondo 86 (1995) 35
- Characterisation of ionic species generated during ablation of Bi₂Sr₂Ca₂Cu₃O₁₀ by frequency-doubled Nd:YAG laser irradiation, G.C. Tyrrell, T.H. York and I.W. Boyd 86 (1995) 50
- Study of PbTe(Ga) evaporation using a nanosecond pulsed laser, V.A. Mikhailov, F.N. Putlin and D.N. Trubnikov 86 (1995) 64
- Composition and gas dynamics of laser ablated AlN plumes, T.M. Di Palma, S. Orlando, A. Giardini-Guidoni, A.J. Paul, J.W. Hastie and A. Mele 86 (1995) 68
- Surface reaction control in digital etching of GaAs by using a tunable UV laser system: reaction control mechanism in layer-by-layer etching, M. Ishii, T. Meguro, T. Sugano, K. Gamo and Y. Aoyagi 86 (1995) 554
- Surface reactions on palladium hydride in vacuum, air and water studied in situ

- with mass spectrometry, L. Gråsjö, G. Hultquist, K.L. Tan and M. Seo 89 (1995) 21
- The reactivity of O_2/H_2 , O_2/CO and O_2/C_3H_6 gas mixtures on Cu(111), W.E.J. Van Kooten, J.P.C. Van Nispen, O.L.J. Gijzeman and J.W. Geus 90 (1995) 137
- Superefficient diffusion of cesium atoms into rhenium covered by a 2D graphite film, A.Ya. Tontegode and F.K. Yusifov 90 (1995) 185
- Atomic hydrogen adsorption on sintered thin copper films, R. Duś, E. Nowicka, W. Lisowski and Z. Wolfram 90 (1995) 277
- Characterization of the plasma plume and of thin film epitaxially produced during laser ablation of SnSe, R. Teghil, A. Santagata, V. Marotta, S. Orlando, G. Pizzella, A. Giardini-Guidoni and A. Mele 90 (1995) 505
- Mercury telluride*
- A positron annihilation study of the formation of defect layers in cadmium mercury telluride, A. Towner, P.C. Rice-Evans and N. Shaw 85 (1995) 315
- Metals*
- XPS study of clean metal sulfide surfaces, K. Laajalehto, I. Kartio and P. Nowak 81 (1994) 11
- Formation processes of ultrafine metal particles on MgO(100) as investigated by molecular dynamics and computer graphics, M. Kubo, R. Yamauchi, R. Vetrivel and A. Miyamoto 82/83 (1994) 559
- Interfacial modification of polymer/metal joints by a two-component coupling system of polybenzimidazole and 2-mercaptobenzimidazole, S. Guo, G. Xue and Y. Qian 84 (1995) 351
- Pulsed laser deposition of metal and metal multilayer films, J.G. Lunney 86 (1995) 79
- Laser deposition of metallic alloys and multilayers, H.-U. Krebs, S. Fähler and O. Bremert 86 (1995) 86
- Comparison of the structure of laser deposited and sputtered metallic alloys, H.-U. Krebs, O. Bremert, M. Störmer and Y. Luo 86 (1995) 90
- Metal pattern deposition by laser-induced forward transfer, Z. Kántor, Z. Tóth and T. Szörényi 86 (1995) 196
- New approach of a laser-induced forward transfer for deposition of patterned thin metal films, H. Esrom, J.-Y. Zhang, U. Kogelschatz and A.J. Pedraza 86 (1995) 202
- Structuring of polyimide-metal carbide layer systems by excimer laser ablation, J. Ihlemann, B. Wolff-Rottke, G. Danev, K. Petkov and E. Spassova 86 (1995) 245
- Laser-surface processing of metals and ceramics for industrial applications, H.W. Bergmann, K. Schutte, E. Schubert and A. Emmel 86 (1995) 259
- Enhanced adherence of electroless metal deposit on SiO_2 via control of the chemical environment of the Pd seeding layer, G.A. Shafeev, L. Bellard, J.-M. Themlin, W. Marine and A. Cros 86 (1995) 387
- Laser-induced surface modification and metallization of polymers, H. Frerichs, J. Stricker, D.A. Wesner and E.W. Kreutz 86 (1995) 405
- Atom probe and field emission electron spectroscopy studies of semiconductor films on metals, M. Ashino, M. Tomitori and O. Nishikawa 87/88 (1995) 12
- Field ion microscope studies of exchange-mediated, atom-displacement processes on metal surfaces, G.L. Kellogg 87/88 (1995) 353
- Methane*
- FT-IR investigation of methane adsorption on silica, J. Wu, S. Li, G. Li, C. Li and Q. Xin 81 (1994) 37
- Quantitative analysis of the thermal degassing of a beryllium powder, L. Buisson, P. Bracconi and X. Claudon 84 (1995) 211
- Methanol*
- Waveguide CARS spectroscopy of physisorbed methanol on a partially hydroxylated zinc oxide surface, W.M.K.P. Wijekoon, E.W. Koenig, W.M. Hetherington III and W.R. Salzman 81 (1994) 347
- Mica*
- An investigation using atomic force microscopy and X-ray photoelectron spectroscopy of the modification of the surface of mica with an argon RF-plasma discharge, N.M.D. Brown and Z.-H. Liu 90 (1995) 155
- Molecular dynamics*
- Theoretical estimation of ordered metal species in zeolite pores, H. Himeji, E.

Maruya, M. Kubo, R. Vetrivel and A. Miyamoto

82/83 (1994) 543

Formation processes of ultrafine metal particles on MgO(100) as investigated by molecular dynamics and computer graphics, M. Kubo, R. Yamauchi, R. Vetrivel and A. Miyamoto

82/83 (1994) 559

Molybdenum

A Raman microprobe study of the electrochromic and photochromic thin films of molybdenum trioxide and tungsten trioxide, B.H. Loo, J.N. Yao, H.D. Coble, K. Hashimoto and A. Fujishima

81 (1994) 175

The effect of process parameters on the O/Mo ratio in laser deposition of molybdenum oxides from aqueous solutions, K. Bali, Zs. Geretovszky, A.L. Tóth and T. Szörényi

86 (1995) 500

The partitioning of substitutional solute elements during the tempering of martensite in Cr and Mo containing steels, R.C. Thomson and M.K. Miller

87/88 (1995) 185

Quantitative analysis of individual atom images in FIM of an ordered Ni₄Mo alloy, M. Yamamoto, K. Nishikawa and T. Nishiuchi

87/88 (1995) 291

Temperature-programmed desorption and decomposition of NH₃ over molybdenum nitride films, H.J. Lee, J.-G. Choi, C.W. Colling, M.S. Mudholkar and L.T. Thompson

89 (1995) 121

M-S (M = Mo, W) cluster compound films on copper surfaces, X.R. Ye, H.W. Hou, X.Q. Xin and C.F. Hammer

89 (1995) 151

Synthesis of molybdenum nitride γ -Mo₂N by multipulse laser irradiation of molybdenum in nitrogen, J.D. Wu, C.Z. Wu, Z.M. Song, L.H. Wu and F.M. Li

90 (1995) 81

Monte Carlo simulations

A Monte Carlo simulation study for adatom migration and resultant atomic arrangements in Al_xGa_{1-x}As on a GaAs(001) surface, T. Ito, K. Shiraishi and T. Ohno

82/83 (1994) 208

Development of a new Monte Carlo simulation system on positron behavior in matter, S. Okada and H. Kaneko

85 (1995) 149

Positron implantation profiles in elemental and multilayer systems, V.J. Ghosh

85 (1995) 187

Mössbauer spectroscopy

Laser deposition of metallic alloys and multilayers, H.-U. Krebs, S. Fähler and O. Bremert

86 (1995) 86

Comparison of the structure of laser deposited and sputtered metallic alloys, H.-U. Krebs, O. Bremert, M. Störmer and Y. Luo

86 (1995) 90

Multilayers

Preparation and characterization of self-assembly organic multilayer films on silica surface, X.Q. Zhang, W.Y. Yang, X.Z. You and Y. Wei

84 (1995) 267

Positron implantation profiles in elemental and multilayer systems, V.J. Ghosh

85 (1995) 187

Defect profiling in multilayered systems using mean depth scaling, G.C. Aers, P.A. Marshall, T.C. Leung and R.D. Goldberg

85 (1995) 196

Defect profiling in elemental and multilayer systems: correlations of fitted defect concentrations with positron implantation profiles, V.J. Ghosh, B. Nielsen, K.G. Lynn and D.O. Welch

85 (1995) 210

Multilayered Ni/Hf and solid-state amorphization studied using the slow positron beam technique, N. Oshima, T. Nakajyo, I. Kanazawa, T. Iwashita, Y. Ito, W.-H. Soe and R. Yamamoto

85 (1995) 329

Pulsed laser deposition of metal and metal multilayer films, J.G. Lunney

86 (1995) 79

Laser deposition of metallic alloys and multilayers, H.-U. Krebs, S. Fähler and O. Bremert

86 (1995) 86

FIM/AP analysis of Cu-Pd multilayers, T. Al-Kassab, M.-P. Macht and H. Wollenberger

87/88 (1995) 329

Nickel

Coordination compounds as precursors for laser deposition of nickel-based conducting films, M. Devillers, O. Dupuis, A. Janosi and J.P. Soumillion

81 (1994) 83

The effect of cyclic oxidation-reduction pretreatments on an amorphous Ni₈₀P₂₀ catalyst: an XPS/UPS/ISS study, J. Deng, H. Chen, X. Bao and M. Muhler

81 (1994) 341

Initial oxidation kinetics of Fe-Ni single crystals before and after ion bombardment, S.P. Chenakin

84 (1995) 91

A comparative study of the interaction of oxygen with clusters and single-crystal

- surfaces of nickel, C.N.R. Rao, V. Vijayakrishnan, G.U. Kulkarni and M.K. Rajumon 84 (1995) 285
- Surface alloy formation in Pd/Ag, Cu/Au and Ni/Au bimetallic overlayers, A.K. Santra and C.N.R. Rao 84 (1995) 347
- Laser-induced selective deposition of Ni-P alloy on silicon, J. Wang, X. Fei, Z. Yu and G. Zhao 84 (1995) 383
- Composition of sputtered material from Cu-Ni alloy during Xe⁺ ion sputtering at elevated temperatures, S. Sekine, H. Shimizu and S. Ichimura 84 (1995) 401
- Multilayered Ni/Hf and solid-state amorphization studied using the slow positron beam technique, N. Oshima, T. Nakajyo, I. Kanazawa, T. Iwashita, Y. Ito, W.-H. Soe and R. Yamamoto 85 (1995) 329
- Enhanced adherence of electroless metal deposit on SiO₂ via control of the chemical environment of the Pd seeding layer, G.A. Shafeev, L. Bellard, J.-M. Thémelin, W. Marine and A. Cros 86 (1995) 387
- Laser-assisted selective metallisation of diamonds by electroless Ni and Cu plating, G.A. Shafeev, S.M. Pimenov and E.N. Loubnin 86 (1995) 392
- An APFIM/TEM investigation of the discontinuous precipitation in a Ni-In alloy, G.P. Geber 87/88 (1995) 234
- Structure and chemistry of grain boundaries in Ni-16Cr-9Fe model materials, M. Thuvander and K. Stiller 87/88 (1995) 251
- APFIM and XPS study of the first stages of low temperature air oxidation of industrial CuNi alloys, R. Souchet, F. Danoix, A. D'Huysser and M. Lenglet 87/88 (1995) 271
- Quantitative analysis of individual atom images in FIM of an ordered Ni₄Mo alloy, M. Yamamoto, K. Nishikawa and T. Nishiuchi 87/88 (1995) 291
- A three-dimensional atom-probe study of preferential sputtering of a Ni₉₁Pt₉ alloy, W. Athenstaedt and M. Leisch 87/88 (1995) 318
- Interfacial reaction of NiO with Al₂O₃ (11 $\bar{2}$ 0) and polycrystalline α -Al₂O₃, P.H. Bolt, S.F. Lobner, J.W. Geus and F.H.P.M. Habraken 89 (1995) 339
- Observation of field-induced fragmentation of nickel clusters using Scanning Tunneling Microscopy, M.V.H. Rao, V. Srinivas, V.V. Rao, B.K. Mathur and K.L. Chopra 89 (1995) 417
- Characterization of nickel films deposited by cold remote nitrogen plasma on acrylonitrile-butadiene-styrene copolymer, A. Brocherieux, O. Dessaux, P. Goudmand, L. Gengembre, J. Grimblot, M. Brunel and R. Lazzaroni 90 (1995) 47
- On the structure and chemistry of Ni₃Al on an atomic scale via atom-probe field-ion microscopy, G.P.E.M. Van Bakel, K. Hariharan and D.N. Seidman 90 (1995) 95
- ### Niobium
- Surface enrichment of niobium on Inconel 718 (100) single crystals, D.J. Dwyer, X.J. Pang, M. Gao and R.P. Wei 81 (1994) 229
- Surface fractal dimension of sintered porous solid niobium, L.I. Skatkov, V.V. Konotop, P.G. Cheremskoy, V.P. Gomofov and B.I. Bayrachny 81 (1994) 427
- NbCl₅ as a precursor in atomic layer epitaxy, K.-E. Elers, M. Ritala, M. Leskelä and E. Rauhala 82/83 (1994) 468
- Pulsed laser deposition of NbTe_x thin films, F. Grangeon, H. Sassoli, Y. Mathey, M. Autric, D. Pailharey and W. Marine 86 (1995) 160
- ### Niobium oxide
- Structural properties of LiNbO₃ thin films grown by the pulsed laser deposition technique, P. Aubert, G. Garry, R. Bisaro and J. Garcia Lopez 86 (1995) 144
- ### Nitric oxide
- Ultrathin SiO₂ films on Si formed by N₂O-plasma oxidation technique, A. Masuda, Y. Yonezawa, A. Morimoto, M. Kumeda and T. Shimizu 81 (1994) 277
- Field ion microscopy during an oscillating surface reaction: NO/H₂ on Pt, C. Voss and N. Kruse 87/88 (1995) 127
- Reaction-induced morphological changes of field emitter tips: NO on Rh and Pt, C. Voss and N. Kruse 87/88 (1995) 134
- Reactions of CO and NO on Mg promoted cobalt, T. Vaara, J. Lahtinen and P. Hautojärvi 89 (1995) 103
- Oxygen exchange between adsorbed NO and MgO surfaces, Y. Yanagisawa 89 (1995) 251
- Synergistic alloying behaviour of Pd₅₀Cu₅₀ single crystals upon adsorption and co-adsorption of CO and NO, Y. Debaugé, M. Abon, J.C. Bertolini, J. Massardier and A. Rochefort 90 (1995) 15

Nitrides

- Auger studies of chemical bonds and oxygen minimization in the interfaces between AlN and SiC thin films deposited by LPCVD, B. Aspar, R. Berjoan, C. Labatut and B. Armas 81 (1994) 55
- Investigation of a GaN surface structure for the mask of GaAs selective growth using MOMBE, S. Yoshida and M. Sasaki 82/83 (1994) 28
- Study on the mechanical and chemical properties of (Ti,Al)N films prepared by DC magnetron sputtering, S. Jiang, D. Peng, X. Zhao, L. Xie and Q. Li 84 (1995) 373
- Aluminium nitride layers investigated by slow positrons, A.S. Saleh, P.C. Rice-Evans and S.J. Bull 85 (1995) 325
- Composition and gas dynamics of laser ablated AlN plumes, T.M. Di Palma, S. Orlando, A. Giardini-Guidoni, A.J. Paul, J.W. Hastie and A. Mele 86 (1995) 68
- Temperature-programmed desorption and decomposition of NH₃ over molybdenum nitride films, H.J. Lee, J.-G. Choi, C.W. Colling, M.S. Mudholkar and L.T. Thompson 89 (1995) 121
- Synthesis of molybdenum nitride γ -Mo₂N by multipulse laser irradiation of molybdenum in nitrogen, J.D. Wu, C.Z. Wu, Z.M. Song, L.H. Wu and F.M. Li 90 (1995) 81
- Rapid thermal nitridation of thin chromium films, S.W. Russell, J. Li, T.L. Alford, P.R. Oakey and S.C. Shatas 90 (1995) 455

Nitrogen

- SIMS study of rapid thermal nitridation of silicon dioxide thick films in ammonia ambient, E. Bréelle, S. Rigo, J.A. Kilner and J.-J. Ganem 81 (1994) 127
- A comparative study of primary ion energy dependence of secondary ion yields from Si and Ge surfaces under inert and reactive ion bombardment, N. Ray, P. Rajasekar and S.D. Dey 84 (1995) 203
- Surface characterisation of plasma-nitrided titanium: an XPS study, I. Bertóti, M. Mohai, J.L. Sullivan and S.O. Saied 84 (1995) 357
- The chemical interaction between plasma-excited nitrogen and the surface of titanium dioxide, S. Kameoka, T. Kuriyama, M. Kuroda, S. Ito and K. Kunimori 89 (1995) 411
- Range profiles of 6-10 MeV ¹⁵N ions implanted in silicon, T. Ahlgren, K. Väkeväinen, J. Räisänen, E. Rauhala and J. Keinonen 90 (1995) 419

Noble gases

- Composition of sputtered material from Cu-Ni alloy during Xe⁺ ion sputtering at elevated temperatures, S. Sekine, H. Shimizu and S. Ichimura 84 (1995) 401

Nuclear magnetic resonance

- Coordination compounds as precursors for laser deposition of nickel-based conducting films, M. Devillers, O. Dupuis, A. Janosi and J.P. Soumillion 81 (1994) 83
- A study of surface modification of silica using XPS, DRIFT and NMR, F. Garbassi, L. Balducci, P. Chiurlo and L. Deiana 84 (1995) 145

Nuclear reaction analysis

- XPS/NRA investigations of particle size effects during the oxidation of Cu particles supported on oxidised Si(100), R. Van Wijk, P.C. Görts, A.J.M. Mens, O.L.J. Gijzeman, F.H.P.M. Habraken and J.W. Geus 90 (1995) 261

Nucleation

- Nucleation and island growth during water adsorption at sub-monolayer coverages, R.V. Kasza, K. Griffiths, V.P. Zhdanov and P.R. Norton 84 (1994) 97

Optical properties

- A Raman microprobe study of the electrochromic and photochromic thin films of molybdenum trioxide and tungsten trioxide, B.H. Loo, J.N. Yao, H.D. Coble, K. Hashimoto and A. Fujishima 81 (1994) 175
- Growth temperature dependence of optical properties of gas source MBE grown GaP/AlP short period superlattices, J.H. Kim, H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda 82/83 (1994) 76
- Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda 82/83 (1994) 109
- Optical in-situ analysis of GaAs/AlAs/GaAs and GaAs/(Al)GaAs/GaAs atomic layer growth using GaCl₃, AlCl₃

- and AsH₃, M. Akamatsu, S. Narahara, T. Kobayashi and F. Hasegawa 82/83 (1994) 228
- In-situ observation of Ga adsorption during TMGa exposure on GaAs(001) surfaces with various As coverages, S. Otake, A. Sakamoto, M. Yamamoto and I. Iwasa 82/83 (1994) 263
- Carbon incorporation mechanism in atomic layer epitaxy of GaAs and AlGaAs, N. Kobayashi and T. Makimoto 82/83 (1994) 284
- Atomic layer epitaxy of ZnSe using reflectance difference spectroscopy, H. Akinaga and K. Tanaka 82/83 (1994) 298
- Surface reaction mechanism in MOMBE-ALE of ZnSe and CdSe as determined by a new in-situ optical probing method, A. Yoshikawa, M. Kobayashi and S. Tokita 82/83 (1994) 316
- The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen 82/83 (1994) 553
- Preparation and characterization of self-assembly organic multilayer films on silica surface, X.Q. Zhang, W.Y. Yang, X.Z. You and Y. Wei 84 (1995) 267
- Analysis and experimental study of one-photon incubated absorption in polymers, P.E. Dyer, D.M. Karnakis and G.A. Oldershaw 86 (1995) 1
- Influence of LN₂ substrate cooling on optical properties of laser-pulse-deposited oxide films, G. Reisse, S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz 86 (1995) 114
- Excimer laser sputtering deposition of TiO₂ optical coating for solar cells, H.-A. Durand, J.-H. Brimaud, O. Hellman, H. Shibata, S. Sakuragi, Y. Makita, D. Gesbert and P. Meyrueis 86 (1995) 122
- Effect of laser power density and deposition temperature on electrical and optical properties of pulsed laser ablated diamond-like carbon films, J. Levoska and S. Leppävuori 86 (1995) 180
- Oligonucleotide hybridization observed by surface plasmon optical techniques, D. Piscevic, R. Lawall, M. Veith, M. Liley, Y. Okahata and W. Knoll 90 (1995) 425
- Organic substances*
- Grafting onto the surface of plasma-modified fillers, G. Ji, J. Fang, S. Cai and G. Xue 81 (1994) 63
- Preparation and characterization of self-assembly organic multilayer films on silica surface, X.Q. Zhang, W.Y. Yang, X.Z. You and Y. Wei 84 (1995) 267
- Structural investigation of Langmuir-Blodgett monolayers of L- α -dipalmitoylphosphatidylcholine by atomic force microscopy, X.-M. Yang, D. Xiao, Z.-H. Lu and Y. Wei 90 (1995) 175
- XPS investigation of electron beam effects on a trimethylsilane dosed Si(100) surface, P.W. Wang, S. Bader, L.P. Zhang, M. Ascherl and J.H. Craig, Jr. 90 (1995) 413
- Organometallic vapour deposition*
- Effects of atomic hydrogen on Cu(II)bis-hexafluoroacetylacetonate interactions with a TiN surface, G. Nuesca, J. Prasad and J.A. Kelber 81 (1994) 237
- Atomic layer epitaxy of device quality AlGaAs and AlAs, N. Hayafuji, G.M. El-dallal, A. Dip, P.C. Colter, N.A. El-Masry and S.M. Bedair 82/83 (1994) 18
- Investigation of a GaN surface structure for the mask of GaAs selective growth using MOMBE, S. Yoshida and M. Sasaki 82/83 (1994) 28
- Atomic layer epitaxy growth of doped zinc oxide thin films from organometals, V. Lujala, J. Skarp, M. Tammenmaa and T. Suntola 82/83 (1994) 34
- AlAs layers with low carbon content grown by ALE using ethyldimethylamine alane as a new aluminum source, N. Kano, S. Hirose, K. Hara, J. Yoshino, H. Munkata and H. Kukimoto 82/83 (1994) 132
- Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs, I. Sue-mune 82/83 (1994) 149
- Carbon incorporation mechanism in atomic layer epitaxy of GaAs and AlGaAs, N. Kobayashi and T. Makimoto 82/83 (1994) 284
- Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi 82/83 (1994) 494
- Steric and electronic interactions between source gas and substrate surface during the Al-CVD/Al selective epitaxy process as investigated by quantum chemical calculations, R. Vetrivel, R. Yamauchi, H. Yamano, M. Kubo, A. Miyamoto and T. Ohta 82/83 (1994) 516
- Surface coverage of ALE precursors on oxides, S. Haukka, E.-L. Lakomaa and T. Suntola 82/83 (1994) 548
- Electrical properties of Si-Al₂O₃ structures grown by ML-ALE, V.E. Drozd, A.P. Baraban and I.O. Nikiforova 82/83 (1994) 583

- Synthesis of oxide superalloys by ML-ALE method, V.E. Drozd, A.A. Tulub, V.B. Aleskovski and D.V. Korol'kov 82/83 (1994) 587
- Synthesis of conducting oxides by ML-ALE, V.E. Drozd and V.B. Aleskovski 82/83 (1994) 591
- Photoassisted metalorganic vapor-phase epitaxy of ZnSe on GaAs, J.E. Bourée, R. Helbing, W. Kuhn and O. Gorochov 86 (1995) 437
- GaAs growth by photon-assisted metalorganic molecular beam epitaxy using ethyl derivatives of gallium and arsenic, F. Maury, K. Bouabid, N. Fazouan, A.M. Gué and D. Estève 86 (1995) 447
- Characterization of nickel films deposited by cold remote nitrogen plasma on acrylonitrile-butadiene-styrene copolymer, A. Brocherieux, O. Dessaux, P. Goudmand, L. Gengembre, J. Grimblot, M. Brunel and R. Lazzaroni 90 (1995) 47
- Ferroelectric BaTiO₃ films with a high-magnitude dielectric constant grown on p-Si by low-pressure metalorganic chemical vapor deposition, T.W. Kim, Y.S. Yoon, S.S. Yom and C.O. Kim 90 (1995) 75

Oxidation

- Electron-beam-induced oxidation of CdS, V.B. Mityukhlyayev 81 (1994) 137
- The hydroxylation of Cu(111) and Zn(0001) surfaces, A.F. Carley, P.R. Davies, M.W. Roberts, N. Shukla, Y. Song and K.K. Thomas 81 (1994) 265
- Initial oxidation kinetics of Fe-Ni single crystals before and after ion bombardment, S.P. Chenakin 84 (1995) 91
- Copper oxidation and surface copper oxide stability investigated by pulsed field desorption mass spectrometry, D.L. Cocke, G.K. Chuah, N. Kruse and J.H. Block 84 (1995) 153
- APFIM and XPS study of the first stages of low temperature air oxidation of industrial CuNi alloys, R. Souchet, F. Danoix, A. D'Huysser and M. Lenglet 87/88 (1995) 271
- Ultraviolet inverse photoemission study of the oxidation of YFe₂, P. Vavassori, L. Callegaro and E. Puppini 89 (1995) 93
- Enhanced silicon oxidation in O₂ and O₂:F₂, G.F. Cerofolini, G. La Bruna and L. Meda 89 (1995) 361
- A photoelectron study of the oxidation of Ta(110) and thin aluminum layers on Ta(110), M.W. Ruckman, S.-L. Qiu and M. Strongin 89 (1995) 401

Oxides

- Identification of active species and theoretical classification of simple catalyst oxides using surface redox couples, Y.P. Arnaud and H. Bertrais 81 (1994) 69
- A Raman microprobe study of the electrochromic and photochromic thin films of molybdenum trioxide and tungsten trioxide, B.H. Loo, J.N. Yao, H.D. Coble, K. Hashimoto and A. Fujishima 81 (1994) 175
- A study of CaO-SO₂ interaction, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea 81 (1994) 409
- A study of CaO-SO₂ interaction in the presence of O₂, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea 81 (1994) 417
- Adsorption of monoethanolamine on clean, oxidized and hydroxylated aluminium surfaces: a model for amine-cured epoxy/aluminium interfaces, C. Fauquet, P. Dubot, L. Minel, M.-G. Barthés-Labrousse, M. Rei Vilar and M. Villatte 81 (1994) 435
- Chlorine adsorption on electron beam irradiated GaAs photo-oxides: mechanism of in situ EB lithography, Y. Ide and M. Yamada 82/83 (1994) 310
- Structural study of SrTiO₃(100) surfaces by low energy ion scattering, Y. Tanaka, H. Morishita, M. Watamori, K. Oura and I. Katayama 82/83 (1994) 528
- Synthesis of oxide superalloys by ML-ALE method, V.E. Drozd, A.A. Tulub, V.B. Aleskovski and D.V. Korol'kov 82/83 (1994) 587
- Synthesis of conducting oxides by ML-ALE, V.E. Drozd and V.B. Aleskovski 82/83 (1994) 591
- Chemisorption of poly(methylhydrogensiloxane) on oxide surfaces: a quantitative investigation using static SIMS, K. Reihs, R. Aguiar Colom, S. Gleditsch, M. Deimel, B. Hagenhoff and A. Benninghoven 84 (1995) 107
- AES and XPS study of thin RF-sputtered Ta₂O₅ layers, E. Atanassova, T. Dimitrova and J. Koprinarova 84 (1995) 193
- Coadsorption of water and selected aromatic molecules to model the adhesion of epoxy resins on hydrated surfaces of zinc oxide and iron oxide, M. Nakazawa and G.A. Somorjai 84 (1995) 309
- Time of flight mass spectrometry and covariance mapping technique investigation of charged specie evolution in Pb(Ti_{0.48}Zr_{0.52})O₃ laser ablation, S. Amoruso, V. Berardi, N. Spinelli, R.

- Velotta, M. Armenante, F. Fuso, M. Alegrini and E. Arimondo
Erbium oxide thin films on Si(100) obtained by laser ablation and electron beam evaporation, X. Queralt, C. Ferrater, F. Sánchez, R. Aguiar, J. Palau and M. Varela
86 (1995) 35
- Influence of ion bombardment on the refractive index of laser pulse deposited oxide films, G. Reisse, S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz
86 (1995) 95
- Influence of LN₂ substrate cooling on optical properties of laser-pulse-deposited oxide films, G. Reisse, S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz
86 (1995) 107
- The effect of process parameters on the O/Mo ratio in laser deposition of molybdenum oxides from aqueous solutions, K. Bali, Zs. Geretovszky, A.L. Tóth and T. Szörényi
86 (1995) 114
- Laser chemical etching of Cu₂O, G. Stenberg, M. Boman, M. Ottosson and J.-O. Carlsson
86 (1995) 500
- A new parameter to characterize limestones as SO₂ sorbents, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea
86 (1995) 543
- XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. I. Hydrogen treatments on a 10 Å thick film, P.C. Wong, Y.S. Li, M.Y. Zhou and K.A.R. Mitchell
89 (1995) 197
- XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. II. Effects of heating a 26 Å thick film after treatment with a hydrogen plasma, Y.S. Li, P.C. Wong and K.A.R. Mitchell
89 (1995) 255
- Interfacial reaction of NiO with Al₂O₃ (11 $\bar{2}$ 0) and polycrystalline α -Al₂O₃, P.H. Bolt, S.F. Lobner, J.W. Geus and F.H.P.M. Habraken
89 (1995) 263
- Tantalum oxide film formation by excimer laser ablation, Y. Nishimura, H. Ujita and M. Tsuji
89 (1995) 339
- Ferroelectric BaTiO₃ films with a high-magnitude dielectric constant grown on p-Si by low-pressure metalorganic chemical vapor deposition, T.W. Kim, Y.S. Yoon, S.S. Yom and C.O. Kim
89 (1995) 393
- Recovery and recrystallization of SrTiO₃(100) surface characterized by ion channeling, F. Wang, M. Badaye, K. Ogawa and T. Morishita
90 (1995) 75
- XPS/NRA investigations of particle size effects during the oxidation of Cu particles supported on oxidised Si(100), R. Van Wijk, P.C. Görts, A.J.M. Mens, O.L.J. Gijzeman, F.H.P.M. Habraken and J.W. Geus
90 (1995) 123
- SIMS investigation of the Si(111) oxidation promoted by potassium overlayers, B. Lamontagne, F. Semond, A. Adnot and D. Roy
90 (1995) 261
- Characterization of RuO₂ thin films by Raman spectroscopy, S.Y. Mar, C.S. Chen, Y.S. Huang and K.K. Tiong
90 (1995) 447
- 90 (1995) 497
- ### Oxygen
- Auger studies of chemical bonds and oxygen minimization in the interfaces between AlN and SiC thin films deposited by LPCVD, B. Aspar, R. Berjoan, C. Labatut and B. Armas
81 (1994) 55
- A study of CaO-SO₂ interaction in the presence of O₂, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea
81 (1994) 417
- Surface structure dependence of O₂-W adsorption system, M. Sato
82/83 (1994) 532
- Adsorption and co-adsorption of boron and oxygen on ordered α -SiC surfaces, V.M. Bermudez
84 (1995) 45
- A comparative study of primary ion energy dependence of secondary ion yields from Si and Ge surfaces under inert and reactive ion bombardment, N. Ray, P. Rajasekar and S.D. Dey
84 (1995) 203
- A comparative study of the interaction of oxygen with clusters and single-crystal surfaces of nickel, C.N.R. Rao, V. Vijaykrishnan, G.U. Kulkarni and M.K. Rajumon
84 (1995) 285
- Adsorption site identification for oxygen molecules on Au/Si(100) by positron annihilation induced Auger electron spectroscopy (PAES), G. Yang, J.H. Kim, S. Yang and A.H. Weiss
85 (1995) 77
- The effect of process parameters on the O/Mo ratio in laser deposition of molybdenum oxides from aqueous solutions, K. Bali, Zs. Geretovszky, A.L. Tóth and T. Szörényi
86 (1995) 500
- Field-induced oxygen layer formation from H₂O and its titration by hydrogen on a Pt-emitter, V. Gorodetskii, N. Ernst, W. Drachsel and J.H. Block
87/88 (1995) 151
- Investigation of adsorption and coadsorption of O₂ and CO on Rh by O₂⁺ field ion and Li⁺ field desorption microscopies, V.K. Medvedev, Yu. Suchorski and J.H. Block
87/88 (1995) 159

Interaction of oxygen and silver on the V(100) surface, T. Valla, P. Pervan and M. Milun

89 (1995) 375

The reactivity of O_2/H_2 , O_2/CO and O_2/C_3H_6 gas mixtures on Cu(111), W.E.J. Van Kooten, J.P.C. Van Nispen, O.L.J. Gijzeman and J.W. Geus

90 (1995) 137

XPS oxygen line broadening in lead zirconium titanate and related materials, A. Zomorrodian, A. Mesarwi, N.J. Wu and A. Ignatiev

90 (1995) 343

Palladium

Surface segregation study of Ib-VIII single-crystal alloys, F. Reniers, M.P. Delplancke, A. Asskali, M. Jardinier-Offergeld and F. Bouillon

81 (1994) 151

Surface alloy formation in Pd/Ag, Cu/Au and Ni/Au bimetallic overlayers, A.K. Santra and C.N.R. Rao

84 (1995) 347

Enhanced adherence of electroless metal deposit on SiO_2 via control of the chemical environment of the Pd seeding layer, G.A. Shafeev, L. Bellard, J.-M. Themlin, W. Marine and A. Cros

86 (1995) 387

Atom probe field ion microscope studies of palladium silicide on silicon, R.A. King, R.A.D. Mackenzie, G.D.W. Smith and N.A. Cade

87/88 (1995) 279

FIM/AP analysis of Cu-Pd multilayers, T. Al-Kassab, M.-P. Macht and H. Wollenberger

87/88 (1995) 329

Surface reactions on palladium hydride in vacuum, air and water studied in situ with mass spectrometry, L. Gråsjö, G. Hultquist, K.L. Tan and M. Seo

89 (1995) 21

XPS studies of the effect of Mn on Pd/ Al_2O_3 , P.C. L'Argentièrre, M.G. Cañón and N.S. Fígoli

89 (1995) 63

Synergistic alloying behaviour of $Pd_{50}Cu_{50}$ single crystals upon adsorption and co-adsorption of CO and NO, Y. Debauge, M. Abon, J.C. Bertolini, J. Massardier and A. Rochefort

90 (1995) 15

Surface segregation and core-level shift of a Pd-Rh alloy studied by XPS, J.A. Leiro, M.H. Heinonen and I.G. Batirev

90 (1995) 515

Phase transitions

In-situ monitoring of 1st-order phase transition on InAs(001) surfaces by scanning electron surface microscopy, H. Yamaguchi, Y. Homma and Y. Horikoshi

82/83 (1994) 223

Atomic layer epitaxy of AlAs: growth mechanism, M. Ozeki and N. Ohtsuka

82/83 (1994) 233

Effect of low-energy (20-40 keV) ion implantation on phase transformations in the subsurface volume of alloys, V.A. Ivchenko and N.N. Syutkin

87/88 (1995) 257

Hydrogen adsorption induced phase transitions on Si(100)-c(8 × 8): temperature dependence studied by LEED, X. Hu and Z. Lin

90 (1995) 111

Phosphorus

The effect of cyclic oxidation-reduction pretreatments on an amorphous $Ni_{80}P_{20}$ catalyst: an XPS/UPS/ISS study, J. Deng, H. Chen, X. Bao and M. Muhler

81 (1994) 341

Substitution of surface-adsorbed As atoms to P atoms in atomic layer epitaxy, H. Ikeda, Y. Miura, N. Takahashi, A. Koukitu and H. Seki

82/83 (1994) 257

Laser-induced selective deposition of Ni-P alloy on silicon, J. Wang, X. Fei, Z. Yu and G. Zhao

84 (1995) 383

Photochemistry

Selective MLE growth of GaAs and surface treatment for ideal static induction transistor (ISIT) application, Y. Oyama, P. Plotka and J. Nishizawa

82/83 (1994) 41

Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane, H. Akazawa

82/83 (1994) 394

Laser-induced decomposition of dimethyl cadmium on a quartz substrate, S.-P. Lee and M.C. Lin

84 (1995) 31

Tailoring of surface properties by removal and deposition with laser radiation, E.W. Kreutz, H. Frerichs, M. Mertin, D.A. Wesner and W. Pfleging

86 (1995) 266

Aggregation kinetics of photo-excited colloid solutions observed by dynamic photon correlation spectroscopy (PCS), N. Borochoy and A. Peled

86 (1995) 533

IRAS and TDS study on the photolytic decarbonylation of iron pentacarbonyl adsorbed on a SiO_2 film with a buried metal layer, S. Sato, S. Minoura, T. Urisu and Y. Takasu

90 (1995) 29

Photoelectron spectroscopy

XPS study of clean metal sulfide surfaces, K. Laajalehto, I. Kartio and P. Nowak

81 (1994) 11

- Coordination compounds as precursors for laser deposition of nickel-based conducting films, M. Devillers, O. Dupuis, A. Janosi and J.P. Soumillion 81 (1994) 83
- Auger and X-ray photoelectron diffraction in MgO(001), T.T. Tran and S.A. Chambers 81 (1994) 161
- Interface study on laser-induced material transfer from polymer and quartz surfaces, S. Lätsch, H. Hiraoka, W. Nieveen and J. Bargon 81 (1994) 183
- A temperature-programmed desorption/X-ray photoelectron spectroscopy study of ditertiarybutylarsine on GaAs(100), M.S. Jackson, J.M. Heitzinger, J.W. Nail, R.D. Culp and J.G. Ekerdt 81 (1994) 195
- Surface enrichment of niobium on Inconel 718 (100) single crystals, D.J. Dwyer, X.J. Pang, M. Gao and R.P. Wei 81 (1994) 229
- Effects of atomic hydrogen on Cu(II)bis-hexafluoroacetylacetonate interactions with a TiN surface, G. Nuesca, J. Prasad and J.A. Kelber 81 (1994) 237
- The hydroxylation of Cu(111) and Zn(0001) surfaces, A.F. Carley, P.R. Davies, M.W. Roberts, N. Shukla, Y. Song and K.K. Thomas 81 (1994) 265
- Ultrathin SiO₂ films on Si formed by N₂O-plasma oxidation technique, A. Masuda, Y. Yonezawa, A. Morimoto, M. Kumeda and T. Shimizu 81 (1994) 277
- Adsorption of CO on Mg-promoted Co(poly), J. Vaari, T. Vaara, J. Lahtinen and P. Hautojärvi 81 (1994) 289
- XPS study of an intumescent coating. Application to the ammonium polyphosphate/pentaerythritol fire-retardant system, S. Bourbigot, M. Le Bras, L. Gengembre and R. Delobel 81 (1994) 299
- Diamond nucleation and growth at the early stages on Si(100) monitored by electron spectroscopies, F. Le Normand, A. Ababou, N. Brault, B. Carrière, L. Fayette, B. Marcus, M. Mermoux, M. Romeo and C. Speisser 81 (1994) 309
- Combined use of XPS, IR and EDAX techniques for the characterization of ZrO₂-SiO₂ powders prepared by a sol-gel process, J.A. Navío, M. Macías, G. Colón, P.J. Sánchez-Soto, V. Augugliaro and L. Palmisano 81 (1994) 325
- XPS investigation of lithium borate glass and the Li/LiBO₂ interface, D.A. Hensley and S.H. Garofalini 81 (1994) 331
- The effect of cyclic oxidation-reduction pretreatments on an amorphous Ni₈₀P₂₀ catalyst: an XPS/UPS/ISS study, J. Deng, H. Chen, X. Bao and M. Muhler 81 (1994) 341
- On the XPS peak shape analysis, M. Sreemany and T.B. Ghosh 81 (1994) 365
- Surface chemical states on 3C-SiC/Si epilayers, A.T.S. Wee, Z.C. Feng, H.H. Hng, K.L. Tan, C.C. Tin, R. Hu and R. Coston 81 (1994) 377
- Room-temperature water adsorption on the Si(100) surface examined by UPS, XPS, and static SIMS, R.K. Schulze and J.F. Evans 81 (1994) 449
- Selective MLE growth of GaAs and surface treatment for ideal static induction transistor (ISIT) application, Y. Oyama, P. Plotka and J. Nishizawa 82/83 (1994) 41
- Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watanabe, F. Maeda and M. Oshima 82/83 (1994) 136
- X-ray photoelectron spectroscopic and atomic force microscopic study of GaAs etching with a HCl solution, Z. Song, S. Shogen, M. Kawasaki and I. Suemune 82/83 (1994) 250
- Surface reactions of Ga and As on Sb-terminated GaAs(001), F. Maeda, Y. Watanabe and M. Oshima 82/83 (1994) 276
- Chlorine adsorption on electron beam irradiated GaAs photo-oxides: mechanism of in situ EB lithography, Y. Ide and M. Yamada 82/83 (1994) 310
- Photoelectron intensity oscillation as a probe to monitor Si layer-by-layer growth, Y. Enta, N. Miyamoto, Y. Takakuwa and H. Kato 82/83 (1994) 327
- Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH₄ and SiH₄ gases, M. Sakuraba, J. Murota, T. Watanabe, Y. Sawada and S. Ono 82/83 (1994) 354
- Auger electron diffraction study of the initial stage of Ge heteroepitaxy on Si(001), M. Sasaki, T. Abukawa, H.W. Yeom, M. Yamada, S. Suzuki, S. Sato and S. Kono 82/83 (1994) 387
- Substrate orientation dependence of self-limited atomic-layer etching of Si with chlorine adsorption and low-energy Ar⁺ irradiation, K. Suzue, T. Matsuura, J. Murota, Y. Sawada and T. Ohmi 82/83 (1994) 422
- Morphology of epitaxial SrF₂ films on atomically modified InP(100), S. Heun, M. Sugiyama, S. Maeyama, Y. Watanabe and M. Oshima 82/83 (1994) 507
- Surface modification of CaF₂ in atomic layer scale by electron beam exposure, S.M. Hwang, A. Izumi, K. Tsutsui and S. Furukawa 82/83 (1994) 523
- Synthesis of oxide superalloys by ML-ALE method, V.E. Drozd, A.A. Tulub, V.B. Aleskovski and D.V. Korol'kov 82/83 (1994) 587

- A comparison of X-ray photoelectron spectroscopy and Auger electron spectroscopy depth profiles for magnesium implants, J.A. Schreifels, N.H. Turner and R.E. Morris 84 (1995) 23
- Surface modification of lead silicate glass under X-ray irradiation, P.W. Wang, L.P. Zhang, L. Lu, D.V. LeMone and D.L. Kinser 84 (1995) 75
- A study of surface modification of silica using XPS, DRIFT and NMR, F. Garbassi, L. Balducci, P. Chiurlo and L. Deiana 84 (1995) 145
- An X-ray scattering study of $\text{SiO}_x/\text{Si}/\text{Ge}(001)$, S.D. Kosowsky, C.-H. Hsu, P.S. Pershan, J. Bevk and B.S. Freer 84 (1995) 179
- Reactivity of III-V and II-VI semiconductors toward hydrogen: surface modification and evolution in air, D. Ballutaud, C. Debiemme-Chouvy, A. Etcheberry, P. De Mierry and L. Svob 84 (1995) 187
- AES and XPS study of thin RF-sputtered Ta_2O_5 layers, E. Atanassova, T. Dimitrova and J. Koprinarova 84 (1995) 193
- Comment on 'Scanning tunnelling microscopy studies of galena: the mechanism of oxidation in air' by B.S. Kim, R.A. Hayes, C.A. Prestidge, J. Ralston and R.St.C. Smart, A.N. Buckley and R. Woods 84 (1995) 223
- Surface analysis of commercial lead/acid battery grids, R. De Marco and J. Liesegang 84 (1995) 237
- Investigations of the interface between magnesium and polyethyleneterephthalate by X-ray photoelectron spectroscopy, P.C. Wong, Y.S. Li and K.A.R. Mitchell 84 (1995) 245
- A comparative study of the interaction of oxygen with clusters and single-crystal surfaces of nickel, C.N.R. Rao, V. Vijayakrishnan, G.U. Kulkarni and M.K. Rajumon 84 (1995) 285
- Surface characterisation of plasma-nitrided titanium: an XPS study, I. Bertóti, M. Mohai, J.L. Sullivan and S.O. Saied 84 (1995) 357
- Laser-induced selective deposition of Ni-P alloy on silicon, J. Wang, X. Fei, Z. Yu and G. Zhao 84 (1995) 383
- Defects and arsenic distribution in low-temperature-grown GaAs, N. Hozhabri, A.R. Koymen, S.C. Sharma and K. Alavi 85 (1995) 311
- Erbium oxide thin films on Si(100) obtained by laser ablation and electron beam evaporation, X. Queralt, C. Ferrater, F. Sánchez, R. Aguiar, J. Palau and M. Varela 86 (1995) 95
- Pulsed-laser deposition and characterization of TaC films, R. Teghil, L. D'Alessio, G. De Maria and D. Ferro 86 (1995) 190
- Formation of Ti^{3+} ions at the surface of laser-irradiated rutile, T. Le Mercier, J.-M. Mariot, P. Parent, M.-F. Fontaine, C.F. Hague and M. Quarton 86 (1995) 382
- Excimer laser-induced deposition of copper from $\text{Cu}(\text{hfac})(\text{TMVS})$, R. Izquierdo, J. Bertomeu, M. Suys, E. Sacher and M. Meunier 86 (1995) 509
- Laser-induced photodeposition from ZnS colloid solutions, A. Peled, B. Dragnea, R. Alexandrescu and A. Andrei 86 (1995) 538
- Desorption in light-induced dry etching of GaAs with Cl_2 around 120 nm, B. Li, U. Streller, H.-P. Krause, I. Twesten, N. Schwentner, V. Stepanenko and Yu. Poltoratskii 86 (1995) 577
- APFIM and XPS study of the first stages of low temperature air oxidation of industrial CuNi alloys, R. Souchet, F. Danoix, A. D'Huysser and M. Lenglet 87/88 (1995) 271
- Plasma-enhanced reactively evaporated deposition of SiO_2 films, A.A. Shklyayev and A.S. Medvedev 89 (1995) 49
- X-ray photoelectron spectroscopic study of room-temperature evolution of oxide-covered hydrogenated amorphous silicon/aluminium interface, C. Anandan 89 (1995) 57
- XPS studies of the effect of Mn on Pd/ Al_2O_3 , P.C. L'Argentièrre, M.G. Cañón and N.S. Figoli 89 (1995) 63
- Thickness determination of uniform overlayers on rough substrates by angle-dependent XPS, P.L.J. Gunter and J.W. Niemantsverdriet 89 (1995) 69
- Interaction of low-energy ions (< 10 eV) with polymethylmethacrylate during plasma treatment, P. Gröning, O.M. Küttel, M. Collaud-Coen, G. Dietler and L. Schlappbach 89 (1995) 83
- Reactions of CO and NO on Mg promoted cobalt, T. Vaara, J. Lahtinen and P. Hautojärvi 89 (1995) 103
- Elemental binding energies for X-ray photoelectron spectroscopy, C.J. Powell 89 (1995) 141
- M-S (M = Mo, W) cluster compound films on copper surfaces, X.R. Ye, H.W. Hou, X.Q. Xin and C.F. Hammer 89 (1995) 151
- The effect of anodic polarization on a Ag electrode deposited on YSZ solid electrolyte, J.K. Hong, I.-H. Oh, S.-A. Hong and W.Y. Lee 89 (1995) 229
- XPS investigations of the interactions of hydrogen with thin films of zirconium

- oxide. I. Hydrogen treatments on a 10 Å thick film, P.C. Wong, Y.S. Li, M.Y. Zhou and K.A.R. Mitchell 89 (1995) 255
- XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. II. Effects of heating a 26 Å thick film after treatment with a hydrogen plasma, Y.S. Li, P.C. Wong and K.A.R. Mitchell 89 (1995) 263
- A graphical analysis of transient response curves at an early stage in SIMS depth profiling using a $^{133}\text{Cs}^+$ beam, H. Tomizuka and A. Ayame 89 (1995) 281
- Activation treatments and surface study of amorphous $\text{Fe}_{90}\text{Zr}_{10}$ and $\text{Fe}_{87.8}\text{Zr}_{10}\text{Co}_{2-}\text{Al}_{0.2}$ catalysts, X.K. Wang, N.F. Shen, Z.S. Yang and H.C. Gu 89 (1995) 297
- Deposition by laser ablation and characterization of titanium dioxide films on polyethylene-terephthalate, N. Lobstein, E. Millon, A. Hachimi, J.F. Muller, M. Alnot and J.J. Ehrhardt 89 (1995) 307
- Interaction of oxygen and silver on the V(100) surface, T. Valla, P. Pervan and M. Milun 89 (1995) 375
- Diffusion of Ag on Cu(110) and Cu(111) studied by spatially resolved UV-photoemission, U. Kürpick, G. Meister and A. Goldmann 89 (1995) 383
- Tantalum oxide film formation by excimer laser ablation, Y. Nishimura, H. Ujita and M. Tsuji 89 (1995) 393
- A photoelectron study of the oxidation of Ta(110) and thin aluminum layers on Ta(110), M.W. Ruckman, S.-L. Qiu and M. Strongin 89 (1995) 401
- Reactivity assay of surface carboxyl chain-ends of poly(ethylene terephthalate) (PET) film and track-etched microporous membranes using fluorine labelled- and/or ^3H -labelled derivatization reagents: tandem analysis by X-ray photoelectron spectroscopy (XPS) and liquid scintillation counting (LSC), M. Deldime, J.-L. Dewez, Y.-J. Schneider and J. Marchand-Brynaert 90 (1995) 1
- Characterization of nickel films deposited by cold remote nitrogen plasma on acrylonitrile-butadiene-styrene copolymer, A. Brocherieux, O. Dessaux, P. Goudmand, L. Gengembre, J. Grimblot, M. Brunel and R. Lazzaroni 90 (1995) 47
- Medium energy electron diffraction and X-ray photoelectron diffraction study of pseudomorphic Fe silicides grown on Si(111). Evidence of Fe vacancy formation, S. Hong, C. Pirri, P. Wetzel, D. Bolmont and G. Gewinner 90 (1995) 65
- Interfacial reaction of Ag with the InP (100) 4×2 surface - a photoemission study, H. Engelhard, F. Stietz, S. Sloboshanin, V. Persch, Th. Allinger, J.A. Schaefer and A. Goldmann 90 (1995) 89
- Conversion film formation on titanium anodes in acetonitrile at high voltages, F. Schlottig, J. Schreckenbach, D. Dietrich, A. Hofmann and G. Marx 90 (1995) 129
- Pulse plasma beam deposition of cubic boron nitride films on GCr15 steel bearing substrate at room temperature, P. Yan and S.-Z. Yang 90 (1995) 149
- An investigation using atomic force microscopy and X-ray photoelectron spectroscopy of the modification of the surface of mica with an argon RF-plasma discharge, N.M.D. Brown and Z.-H. Liu 90 (1995) 155
- Photoemission studies on Pt foil implanted by carbon atoms accelerated in a Van de Graaff generator: nature of the interaction between Pt and carbon, R. Sundararajan, G. Pető, E. Koltay and L. Guzzi 90 (1995) 165
- Determining hybridization differences for amorphous carbon from the XPS C 1s envelope, S.T. Jackson and R.G. Nuzzo 90 (1995) 195
- Angle resolved XPS study of inhomogeneous specimens of polycrystalline silver covered with uniform graphite overlayers, M. Sreemany and T.B. Ghosh 90 (1995) 241
- XPS/NRA investigations of particle size effects during the oxidation of Cu particles supported on oxidised Si(100), R. Van Wijk, P.C. Görts, A.J.M. Mens, O.L.J. Gijzeman, F.H.P.M. Habraken and J.W. Geus 90 (1995) 261
- Surface studies of Cu/Cr/Ag impregnated microporous carbons, R.H. Bradley 90 (1995) 271
- Characterization of ex-situ hydrogenated amorphous SiC thin films by X-ray photoelectron spectroscopy, S. Kennou, S. Ladas, E.C. Paloura and J.A. Kalomiros 90 (1995) 283
- Surface segregation of Sb in doped TiO_2 rutile, A. Gulino, G.G. Condorelli, I. Fragalà and R.G. Egdell 90 (1995) 289
- In situ DC-plasma cleaning of silicon surfaces, U. Kafader, H. Sirringhaus and H. von Känel 90 (1995) 297
- A study of the compositional changes in chemically etched, Ar ion bombarded and reactive ion etched GaAs(100) surfaces by means of ARXPS and LEISS, J.L. Sullivan, W. Yu and S.O. Saied 90 (1995) 309

- Peak fitting of the chromium 2p XPS spectrum, A.M. Salvi, J.E. Castle, J.F. Watts and E. Desimoni 90 (1995) 333
- XPS oxygen line broadening in lead zirconium titanate and related materials, A. Zomorrodian, A. Mesarwi, N.J. Wu and A. Ignatiev 90 (1995) 343
- Surface studies of oil-seal degradation, G.C. Smith, D. Park, K.J. Titchener, R.E. Davies and R.H. West 90 (1995) 357
- The structure of PMDA-PDA polyimide monolayers adsorbed on gold surfaces, M. Keil, J.J. Paggel, Th. Schedel-Niedrig, S. Yokoyama, H. Sotobayashi and A.M. Bradshaw 90 (1995) 377
- A photoemission study of electron states in Sb-ion implanted $\text{TiO}_2(110)$, A.E. Taverner, A. Gulino, R.G. Egdell and T.J. Tate 90 (1995) 383
- An XPS study of the optimum loading of barium on high-silica MFI zeolite, M.H. Mohamed, M.M. Abdillahi, N.M. Abbas and A.B. Siddiqui 90 (1995) 409
- XPS investigation of electron beam effects on a trimethylsilane dosed $\text{Si}(100)$ surface, P.W. Wang, S. Bater, L.P. Zhang, M. Ascherl and J.H. Craig, Jr. 90 (1995) 413
- AFM and XPS characterization of the $\text{Si}(111)$ surface after thermal treatment, B. Lamontagne, D. Guay, D. Roy, R. Sporken and R. Caudano 90 (1995) 481
- Surface segregation and core-level shift of a Pd-Rh alloy studied by XPS, J.A. Leiro, M.H. Heinonen and I.G. Batirev 90 (1995) 515

Photoemission

- Surface alloy formation in Pd/Ag, Cu/Au and Ni/Au bimetallic overlayers, A.K. Santra and C.N.R. Rao 84 (1995) 347
- Ultraviolet inverse photoemission study of the oxidation of YFe_2 , P. Vavassori, L. Callegaro and E. Puppini 89 (1995) 93
- Photoemission studies on Pt foil implanted by carbon atoms accelerated in a Van de Graaff generator: nature of the interaction between Pt and carbon, R. Sundararajan, G. Pető, E. Koltay and L. Gucci 90 (1995) 165

Photon emission

- Light emission from polymers under positron and electron bombardment, J. Xu, L.D. Hulet, Jr., T.A. Lewis and N.H. Tolk 85 (1995) 49

Plasma processing

- Grafting onto the surface of plasma-modified fillers, G. Ji, J. Fang, S. Cai and G. Xue 81 (1994) 63
- Ultrathin SiO_2 films on Si formed by N_2O -plasma oxidation technique, A. Masuda, Y. Yonezawa, A. Morimoto, M. Kumeda and T. Shimizu 81 (1994) 277
- Surface characterisation of plasma-nitrided titanium: an XPS study, I. Bertóti, M. Mohai, J.L. Sullivan and S.O. Saied 84 (1995) 357
- Plasma-enhanced reactively evaporated deposition of SiO_2 films, A.A. Shklyayev and A.S. Medvedev 89 (1995) 49
- Interaction of low-energy ions (< 10 eV) with polymethylmethacrylate during plasma treatment, P. Gröning, O.M. Küttel, M. Collaud-Coen, G. Dietler and L. Schlapbach 89 (1995) 83
- XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. I. Hydrogen treatments on a 10 Å thick film, P.C. Wong, Y.S. Li, M.Y. Zhou and K.A.R. Mitchell 89 (1995) 255
- XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. II. Effects of heating a 26 Å thick film after treatment with a hydrogen plasma, Y.S. Li, P.C. Wong and K.A.R. Mitchell 89 (1995) 263
- Cadmium selenide-amorphous hydrogenated silicon heterostructures, S. Wu and D. Haneman 89 (1995) 289
- The chemical interaction between plasma-excited nitrogen and the surface of titanium dioxide, S. Kameoka, T. Kuriyama, M. Kuroda, S. Ito and K. Kunimori 89 (1995) 411
- Pulse plasma beam deposition of cubic boron nitride films on GCr15 steel bearing substrate at room temperature, P. Yan and S.-Z. Yang 90 (1995) 149
- An investigation using atomic force microscopy and X-ray photoelectron spectroscopy of the modification of the surface of mica with an argon RF-plasma discharge, N.M.D. Brown and Z.-H. Liu 90 (1995) 155
- In situ DC-plasma cleaning of silicon surfaces, U. Kafader, H. Sirringhaus and H. von Känel 90 (1995) 297

Platinum

- Surface states in the band-gap for Pt-deposited p-InP photoelectrochemical cells, H. Kobayashi, F. Mizuno and Y. Nakato 81 (1994) 399

- Field-induced redistribution and diffusion of water on a Pt field emitter, R. Bryl, T. Wysocki and R. Błaszczyszyn 87/88 (1995) 69
- Field ion microscopy during an oscillating surface reaction: NO/H₂ on Pt, C. Voss and N. Kruse 87/88 (1995) 127
- Reaction-induced morphological changes of field emitter tips: NO on Rh and Pt, C. Voss and N. Kruse 87/88 (1995) 134
- Field-induced oxygen layer formation from H₂O and its titration by hydrogen on a Pt-emitter, V. Gorodetskii, N. Ernst, W. Drachsel and J.H. Block 87/88 (1995) 151
- A three-dimensional atom-probe study of preferential sputtering of a Ni91Pt9 alloy, W. Athenstaedt and M. Leisch 87/88 (1995) 318
- Photoemission studies on Pt foil implanted by carbon atoms accelerated in a Van de Graaff generator: nature of the interaction between Pt and carbon, R. Sundararajan, G. Pető, E. Koltay and L. Guzzi 90 (1995) 165
- Surface interaction between H₂ and CO₂ over silicalite-supported platinum, M. Huang, S. Kaliaguine and S. Suppiah 90 (1995) 393
- ### Polymers
- Grafting onto the surface of plasma-modified fillers, G. Ji, J. Fang, S. Cai and G. Xue 81 (1994) 63
- Growth of excimer-laser-induced dendritic surface structures on polyethyleneterephthalate, J. Heitz, E. Arenholz, D. Bäuerle and K. Schilcher 81 (1994) 103
- Interface study on laser-induced material transfer from polymer and quartz surfaces, S. Lätsch, H. Hiraoka, W. Nieveen and J. Bargon 81 (1994) 183
- XPS study of an intumescent coating. Application to the ammonium polyphosphate/pentaerythritol fire-retardant system, S. Bourbigot, M. Le Bras, L. Gengembre and R. Delobel 81 (1994) 299
- Adsorption of monoethanolamine on clean, oxidized and hydroxylated aluminium surfaces: a model for amine-cured epoxy/aluminium interfaces, C. Fauquet, P. Dubot, L. Minel, M.-G. Barthés-Labrousse, M. Rei Vilar and M. Villatte 81 (1994) 435
- Surface characterization by time-of-flight SIMS of a catalyst for oxygen electroreduction: pyrolyzed cobalt phthalocyanine-on-carbon black, L.T. Weng, P. Bertrand, G. Lalande, D. Guay and J.P. Dodelet 84 (1995) 9
- High Resolution Electron Energy Loss Spectroscopy investigation of the copper/polyphenylquinoxaline interface formation, Ch. Grégoire, J.-J. Pireaux, A. Cros and R. Caudano 84 (1995) 163
- A multitechnique analysis of the outermost layers of the Teflon PFA surface, K. Piyakis, E. Sacher, A. Domingue, J.-J. Pireaux, G. Leclerc, P. Bertrand and J.B. Lhoest 84 (1995) 227
- Investigations of the interface between magnesium and polyethyleneterephthalate by X-ray photoelectron spectroscopy, P.C. Wong, Y.S. Li and K.A.R. Mitchell 84 (1995) 245
- Sample charging during static SIMS studies of polymers, G.J. Leggett and J.C. Vickerman 84 (1995) 253
- AFM investigations of the initial stages of prepolymer film growth on aluminium, T. Gesang, R. Höper, S. Dieckhoff, D. Fanter, A. Hartwig, W. Possart and O.-D. Hennemann 84 (1995) 273
- Coadsorption of water and selected aromatic molecules to model the adhesion of epoxy resins on hydrated surfaces of zinc oxide and iron oxide, M. Nakazawa and G.A. Somorjai 84 (1995) 309
- Interfacial modification of polymer/metal joints by a two-component coupling system of polybenzimidazole and 2-mercaptobenzimidazole, S. Guo, G. Xue and Y. Qian 84 (1995) 351
- Using the Lambert-Beer law for thickness evaluation of photoconductor coatings for recording holograms, A. Larena, G. Pinto and F. Millán 84 (1995) 407
- Light emission from polymers under positron and electron bombardment, J. Xu, L.D. Hulett, Jr., T.A. Lewis and N.H. Tolk 85 (1995) 49
- Assay of weathering effects on protective polymer coatings using positron annihilation spectroscopy, L.D. Hulett, Jr., S. Wallace, J. Xu, B. Nielsen, Cs. Szeles, K.G. Lynn, J. Pfau and A. Schaub 85 (1995) 334
- Analysis and experimental study of one-photon incubated absorption in polymers, P.E. Dyer, D.M. Karnakis and G.A. Oldershaw 86 (1995) 1
- Overheated metastable states in polymer sublimation by laser radiation, V.I. Mazhukin, I. Smurov, C. Surry and G. Flamant 86 (1995) 7
- Ablation of nylon-6,6 with UV and IR lasers, C.D. Skordoulis, M. Makropoulou and A.A. Serafetinides 86 (1995) 239
- Structuring of polyimide-metal carbide layer systems by excimer laser ablation,

- J. Ihlemann, B. Wolff-Rottke, G. Danev, K. Petkov and E. Spassova 86 (1995) 245
- Laser-induced surface modification and metallization of polymers, H. Frerichs, J. Stricker, D.A. Wesner and E.W. Kreutz 86 (1995) 405
- Thin films of polymer blends: surface treatment and theoretical modeling, P. Viville, O. Thoelen, S. Beauvois, R. Lazzaroni, G. Lambin, J.L. Brédas, K. Kolev and L. Laude 86 (1995) 411
- Deposition of gold on polyimide from solutions, S. Pflüger, M. Wehner, F. Jansen, Th. Kruck and F. Lupp 86 (1995) 504
- Comparison of NFIM and FIM of polymer layers with tetracyanoethylene and benzene as image gases, A. Theiss, F. Okuyama and F.W. Röllgen 87/88 (1995) 146
- An investigation of the thermal stability of undecylimidazole on copper by FT-IR reflection-absorption spectroscopy, S. Yoshida and H. Ishida 89 (1995) 39
- Growth of a surface film on copper from benzotriazole solutions, G. Xue, J. Ding and P. Cheng 89 (1995) 77
- Interaction of low-energy ions (< 10 eV) with polymethylmethacrylate during plasma treatment, P. Gröning, O.M. Küttel, M. Collaud-Coen, G. Dietler and L. Schlapbach 89 (1995) 83
- Deposition by laser ablation and characterization of titanium dioxide films on polyethylene-terephthalate, N. Lobstein, E. Millon, A. Hachimi, J.F. Muller, M. Alnot and J.J. Ehrhardt 89 (1995) 307
- Characterization of triplex RNA poly[rU]·poly[rA]·poly[rU] adsorbed on silver colloids by Fourier transform surface enhanced Raman scattering and scanning tunneling microscopy, Y. Fang, C. Bai, T. Wang and Y.-Q. Tang 89 (1995) 331
- Reactivity assay of surface carboxyl chain-ends of poly(ethylene terephthalate) (PET) film and track-etched microporous membranes using fluorine labelled- and/or ³H-labelled derivatization reagents: tandem analysis by X-ray photoelectron spectroscopy (XPS) and liquid scintillation counting (LSC), M. Deldime, J.-L. Dewez, Y.-J. Schneider and J. Marchand-Brynaert 90 (1995) 1
- Characterization of nickel films deposited by cold remote nitrogen plasma on acrylonitrile-butadiene-styrene copolymer, A. Brocherieux, O. Dessaux, P. Goudmand, L. Gengembre, J. Grimblot, M. Brunel and R. Lazzaroni 90 (1995) 47
- Surface studies of oil-seal degradation, G.C. Smith, D. Park, K.J. Titchener, R.E. Davies and R.H. West 90 (1995) 357
- The structure of PMDA-PDA polyimide monolayers adsorbed on gold surfaces, M. Keil, J.J. Paggel, Th. Schedel-Niedrig, S. Yokoyama, H. Sotobayashi and A.M. Bradshaw 90 (1995) 377
- ### Positron beams
- Positron diffusion in solids and in liquid metals, A. Seeger 85 (1995) 8
- Design and simulation of the PSI electrostatic positron beam, D. Gerola, W.B. Waeber and M. Shi 85 (1995) 106
- A gated positron beam incorporating a scattering cell and novel ion extractor, J. Moxom, G. Laricchia and M. Charlton 85 (1995) 118
- Production of an intense slow positron beam by using an electron LINAC and its applications, I. Kanazawa, Y. Ito, M. Hirose, H. Abe, O. Sueoka, S. Takamura, A. Ichimiya, Y. Murata, F. Komori, K. Fukutani, S. Okada and T. Hattori 85 (1995) 124
- A several tens-keV monoenergetic positron surface analyzer with ²²Na and electrostatic fields, M. Nunogaki, T. Yamamoto, Y. Honda and T. Okada 85 (1995) 132
- Construction and performance of a slow positron beam guided by an increasing magnetic field, Y. Shirai, H. Miura and M. Yamaguchi 85 (1995) 138
- Magnetic positron optics, D.T. Britton, K. Uhlmann and G. Kögel 85 (1995) 158
- ### Positron diffraction
- Positron surface-state trapping induced by surface plasmon excitation under grazing scattering conditions, M. Kato and A. Ishii 85 (1995) 69
- ### Positron microscopy
- Development of a reflection geometry positron reemission microscope, A. Goodyear and P.G. Coleman 85 (1995) 98
- ### Positron scattering
- Total cross-section measurements for positrons and electrons colliding with

- molecules: CCl_4 , A. Hamada and O. Sueoka 85 (1995) 64
- Positron surface-state trapping induced by surface plasmon excitation under grazing scattering conditions, M. Kato and A. Ishii 85 (1995) 69
- Development of a new Monte Carlo simulation system on positron behavior in matter, S. Okada and H. Kaneko 85 (1995) 149
- Positron spectroscopy*
- Application of time-dependent diffusion models to the study of real solids, D.T. Britton and J. Störmer 85 (1995) 1
- Annihilation of incompletely thermalized positronium studied by age-momentum correlation, H. Stoll, M. Koch, U. Lauff, K. Maier, J. Major, H. Schneider, A. Seeger and A. Siegle 85 (1995) 17
- Theoretical study of the positron surface state at an alkali-metal surface, N.G. Fazleev, J.L. Fry, K. Kuttler and A.H. Weiss 85 (1995) 22
- Study of positron surface states on the alkali-metal-covered transition-metal surface, N.G. Fazleev, J.L. Fry, K. Kuttler, A.R. Koymen and A.H. Weiss 85 (1995) 26
- Energy loss measurements for 20 keV positrons in Al thin films, G.R. Massoumi, W.N. Lennard, P.J. Schultz, T.A. Porcelli and P.J. Simpson 85 (1995) 39
- Work function and epithermal positron emission from copper, N. Overton, A.P. Knights, A. Goodyear and P.G. Coleman 85 (1995) 54
- Method for the measurement of positron affinities and positron work functions suitable for both positive and negative work function materials, A.H. Weiss, S. Yang, H.Q. Zhou, E. Jung, A.R. Koymen, S. Naidu, G. Brauer and M.J. Puska 85 (1995) 82
- Generation of an intense pulsed positron beam for positron lifetime and TOF experiments, R. Suzuki, T. Mikado, M. Chiwaki, H. Ohgaki and T. Yamazaki 85 (1995) 87
- Production of an intense slow positron beam using a compact cyclotron, M. Hirose, M. Washio and K. Takahashi 85 (1995) 111
- Slow positron beam extraction from high magnetic fields, M. Shi, D. Gerola, W.B. Waeber and U. Zimmermann 85 (1995) 143
- Installation of a Kr moderator in the high-brightness beam at Brandeis, D. Vasumathi, G. Amarendra, K.F. Canter and A.P. Mills, Jr. 85 (1995) 154
- Slow positron production using the RIKEN AVF cyclotron, Y. Itoh, K.H. Lee, T. Nakajyo, A. Goto, N. Nakanishi, M. Kase, I. Kanazawa, Y. Yamamoto, N. Oshima and Y. Ito 85 (1995) 165
- Positron Doppler broadening measurements with a LINAC-based slow positron beam, D. Segers, J. Paridaens, T. Van Hoecke, C. Dauwe, L. Dorikens-Vanpraet, C. Quaeysaegens and L.M. Stals 85 (1995) 172
- An overview of the slow-positron beam facility at the photon factory, KEK, T. Kurihara, A. Shirakawa, A. Enomoto, T. Shidara, H. Kobayashi and K. Nakahara 85 (1995) 178
- Deconvolution of Doppler-broadened positron annihilation lineshapes by the generalised least-squares method, B.K. Panda, S. Fleischer, C.C. Ling, C.D. Beling, S. Fung and S. Panda 85 (1995) 182
- Positron implantation profiles in elemental and multilayer systems, V.J. Ghosh 85 (1995) 187
- Defect profiling in multilayered systems using mean depth scaling, G.C. Aers, P.A. Marshall, T.C. Leung and R.D. Goldberg 85 (1995) 196
- Defect profiling in elemental and multilayer systems: correlations of fitted defect concentrations with positron implantation profiles, V.J. Ghosh, B. Nielsen, K.G. Lynn and D.O. Welch 85 (1995) 210
- VEPFIT applied to depth profiling problems, A. van Veen, H. Schut, M. Clement, J.M.M. de Nijs, A. Kruseman and M.R. Ijpma 85 (1995) 216
- Extension of the PC version of VEPFIT with input and output routines running under Windows, H. Schut and A. van Veen 85 (1995) 225
- Depth profiles of defects in Ar-ion-irradiated steels determined by a least-squares fit of S parameters from variable-energy positron annihilation, T. Aruga, S. Takamura, K. Nakata and Y. Ito 85 (1995) 229
- Defects in Czochralski-grown silicon crystals investigated by positron annihilation, A. Ikari 85 (1995) 253
- Variable-energy positron beam study of arsenic diffusion in poly-silicon, D.W. Lawther, R. Khatri, P.J. Simpson, P.J. Schultz, I. Calder and L. Weaver 85 (1995) 265
- Slow positron implantation spectroscopy of edge-defined film-fed growth silicon, P.G. Coleman, E. Bloss, S. Setzler, S. LaShell, G. Davies and W.D. Sawyer 85 (1995) 276
- An annealing study of defects induced by electron irradiation of Czochralski-grown Si using a positron lifetime tech-

- nique, A. Kawasuso, M. Hasegawa, M. Suezawa, S. Yamaguchi and K. Sumino 85 (1995) 280
- Determination of the characteristic signal for positron annihilation at divacancies in ion-irradiated silicon, R.D. Goldberg, P.J. Schultz and P.J. Simpson 85 (1995) 287
- Measurement of oxide thickness using a variable-energy positron beam, T.C. Leung, P.J. Simpson, A. Atkinson, I.V. Mitchell and P.J. Schultz 85 (1995) 292
- Positron annihilation studies of defects in molecular beam epitaxy grown III-V layers, M.T. Umlor, P. Asoka-Kumar, D.J. Keeble, P.W. Cooke and K.G. Lynn 85 (1995) 295
- Annealing studies of Au/GaAs and Al/GaAs interfaces using a variable energy positron beam, C.C. Ling, T.C. Lee, S. Fung, C.D. Beling, H. Weng, J. Xu, S. Sun and R. Han 85 (1995) 305
- Defects and arsenic distribution in low-temperature-grown GaAs, N. Hozhabri, A.R. Koymen, S.C. Sharma and K. Alavi 85 (1995) 311
- A positron annihilation study of the formation of defect layers in cadmium mercury telluride, A. Towner, P.C. Rice-Evans and N. Shaw 85 (1995) 315
- Positron beam spectroscopy for the assessment of the structure and defect density of titanium nitride, P.C. Rice-Evans, A.S. Saleh and S.J. Bull 85 (1995) 320
- Aluminium nitride layers investigated by slow positrons, A.S. Saleh, P.C. Rice-Evans and S.J. Bull 85 (1995) 325
- Multilayered Ni/Hf and solid-state amorphization studied using the slow positron beam technique, N. Oshima, T. Nakajyo, I. Kanazawa, T. Iwashita, Y. Ito, W.-H. Soe and R. Yamamoto 85 (1995) 329
- Assay of weathering effects on protective polymer coatings using positron annihilation spectroscopy, L.D. Hulett, Jr., S. Wallace, J. Xu, B. Nielsen, Cs. Szeles, K.G. Lynn, J. Pfau and A. Schaub 85 (1995) 334
- Contrast in positron reemission microscopy due to positron trapping by dislocations, K.F. Canter, G. Amarendra, D. Vasumathi, S.A. Wesley, R. Xie, A.P. Mills, Jr., R.L. Sabatini and Y. Zhu 85 (1995) 339

Quantum effects

- Optical properties of atomic layer grown InAs/AlSb quantum well structures by gas source migration enhanced epitaxy, H. Asahi, S.G. Kim, M. Seta, K. Asami, H. Watanabe, T. Ogura and S. Gonda 82/83 (1994) 109

- Microscopic analysis of interface structure in InGaAs/InP MQW using Pendelösung oscillation around a satellite peak in high-resolution X-ray diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya 82/83 (1994) 115
- Electron field emission (FE) from quantum size systems, L.G. Il'chenko, Yu.V. Kryuchenko and V.G. Litovchenko 87/88 (1995) 53

Quartz

- Enhanced adherence of electroless metal deposit on SiO₂ via control of the chemical environment of the Pd seeding layer, G.A. Shafeev, L. Bellard, J.-M. Thémelin, W. Marine and A. Cros 86 (1995) 387

Radiation damage

- Surface modification of CaF₂ in atomic layer scale by electron beam exposure, S.M. Hwang, A. Izumi, K. Tsutsui and S. Furukawa 82/83 (1994) 523
- Surface modification of lead silicate glass under X-ray irradiation, P.W. Wang, L.P. Zhang, L. Lu, D.V. LeMone and D.L. Kinser 84 (1995) 75
- Depth profiles of defects in Ar-ion-irradiated steels determined by a least-squares fit of *S* parameters from variable-energy positron annihilation, T. Aruga, S. Takamura, K. Nakata and Y. Ito 85 (1995) 229
- An annealing study of defects induced by electron irradiation of Czochralski-grown Si using a positron lifetime technique, A. Kawasuso, M. Hasegawa, M. Suezawa, S. Yamaguchi and K. Sumino 85 (1995) 280
- Determination of the characteristic signal for positron annihilation at divacancies in ion-irradiated silicon, R.D. Goldberg, P.J. Schultz and P.J. Simpson 85 (1995) 287
- Characterization of neutron-irradiated Fe-Au alloys, M.K. Miller, K.F. Russell, A. Jostons and R.G. Blake 87/88 (1995) 216
- Experimental study of passivating ion-beam-induced distributed energy levels in n-GaAs by hydrogen species from boiling water, I. Thurzo, E. Pincik, G. Papaioannou, P. Dimitrakakis and N. Arpatzanis 90 (1995) 39

Raman scattering

- A Raman microprobe study of the electrochromic and photochromic thin films

- of molybdenum trioxide and tungsten trioxide, B.H. Loo, J.N. Yao, H.D. Coble, K. Hashimoto and A. Fujishima 81 (1994) 175
- Diamond nucleation and growth at the early stages on Si(100) monitored by electron spectroscopies, F. Le Normand, A. Ababou, N. Brault, B. Carrière, L. Fayette, B. Marcus, M. Mermoux, M. Romeo and C. Speisser 81 (1994) 309
- Waveguide CARS spectroscopy of physisorbed methanol on a partially hydroxylated zinc oxide surface, W.M.K.P. Wijekoon, E.W. Koenig, W.M. Hetherington III and W.R. Salzman 81 (1994) 347
- Raman study of strained SiGe layers, S. Gu, R. Zhang, P. Han, R. Wang, P. Zhong and Y. Zheng 81 (1994) 431
- Interfacial modification of polymer/metal joints by a two-component coupling system of polybenzimidazole and 2-mercaptobenzimidazole, S. Guo, G. Xue and Y. Qian 84 (1995) 351
- Structure and chemical composition of BN thin films grown by pulsed-laser deposition (PLD), T. Klotzbücher, W. Pfleging, M. Mertin, D.A. Wesner and E.W. Kreutz 86 (1995) 165
- Si_{1-x}Ge_x thin films deposited by the pulsed excimer laser ablation technique, F. Antoni, E. Fogarassy, C. Fuchs, B. Prévot and J.P. Stoquert 86 (1995) 175
- Excimer laser etching of diamond-like carbon films: spalling effect, T.V. Kononenko, V.G. Ralchenko, E.D. Obratsova, V.I. Konov, J. Seth, S.V. Babu and E.N. Loubnin 86 (1995) 234
- Formation of poly-Si_{1-x}Ge_x using excimer-laser processing, A. Slaoui, C. Deng, S. Talwar, K.J. Kramer, T.W. Sigmon, J.P. Stoquert and B. Prevot 86 (1995) 346
- P-doped polycrystalline silicon films obtained at low temperature by hot-wire chemical vapor deposition, J. Puigdollers, J. Cifre, M.C. Polo, J.M. Asensi, J. Bertomeu, J. Andreu and A. Lloret 86 (1995) 600
- Growth of a surface film on copper from benzotriazole solutions, G. Xue, J. Ding and P. Cheng 89 (1995) 77
- Characterization of triplex RNA poly[rU]·poly[rA]·poly[rU] adsorbed on silver colloids by Fourier transform surface enhanced Raman scattering and scanning tunneling microscopy, Y. Fang, C. Bai, T. Wang and Y.-Q. Tang 89 (1995) 331
- The influence of the substrate material on the growth of V₂O₅ flash-evaporated films, C. Julien, J.P. Guesdon, A. Gorenstein, A. Khelfa and I. Ivanov 90 (1995) 389
- Characterization of RuO₂ thin films by Raman spectroscopy, S.Y. Mar, C.S. Chen, Y.S. Huang and K.K. Tiong 90 (1995) 497
- ### Rhenium
- Superefficient diffusion of cesium atoms into rhenium covered by a 2D graphite film, A.Ya. Tontegode and F.K. Yusifov 90 (1995) 185
- ### Rhodium
- Surface segregation study of Ib-VIII single-crystal alloys, F. Reniers, M.P. Delplancke, A. Asskali, M. Jardinier-Offergeld and F. Bouillon 81 (1994) 151
- In situ diffuse reflectance infrared (DRIFTS) identification of active sites in the CO + H₂ reaction over lanthanide-modified Rh/Al₂O₃ catalysts, J.J. Benítez, I. Carrizosa and J.A. Odriozola 84 (1995) 391
- Reaction-induced morphological changes of field emitter tips: NO on Rh and Pt, C. Voss and N. Kruse 87/88 (1995) 134
- Investigation of adsorption and coadsorption of O₂ and CO on Rh by O₂⁺ field ion and Li⁺ field desorption microscopies, V.K. Medvedev, Yu. Suchorski and J.H. Block 87/88 (1995) 159
- Surface segregation and core-level shift of a Pd-Rh alloy studied by XPS, J.A. Leiro, M.H. Heinonen and I.G. Batirev 90 (1995) 515
- ### Ruthenium
- Characterization of RuO₂ thin films by Raman spectroscopy, S.Y. Mar, C.S. Chen, Y.S. Huang and K.K. Tiong 90 (1995) 497
- ### Scanning tunneling microscopy
- STM-stimulated modification of solids: a quantum chemical study, V.S. Gurin and A.B. Kovrikov 81 (1994) 43
- Scanning tunneling microscopy study of solid-phase epitaxy processes of amorphous silicon layers on silicon substrates, K. Uesugi, T. Komura, M. Yoshimura and T. Yao 82/83 (1994) 367
- Scanning tunneling microscopy observations of Ge solid-phase epitaxy on Si(111), H. Hibino and T. Ogino 82/83 (1994) 374
- Atomic-scale modification of the AlCl₃-adsorbed Si(111)-7 × 7 surface, T.

- Takiguchi, K. Uesugi, M. Yoshimura and T. Yao 82/83 (1994) 428
- Scanning tunneling microscope observations of Si(111)3 × 1-Ag and 6 × 1-Ag structures, H. Ohnishi, Y. Yamamoto, I. Katayama, Y. Ohba and K. Oura 82/83 (1994) 444
- Comment on 'Scanning tunnelling microscopy studies of galena: the mechanism of oxidation in air' by B.S. Kim, R.A. Hayes, C.A. Prestidge, J. Ralston and R.St.C. Smart, A.N. Buckley and R. Woods 84 (1995) 223
- Reply to the "Comment of A.N. Buckley and R. Woods on 'Scanning tunnelling microscopy studies of galena: the mechanism of oxidation in air' by B.S. Kim, R.A. Hayes, C.A. Prestidge, J. Ralston and R.St.C. Smart", J. Ralston 84 (1995) 225
- Pulsed laser deposition and nanometer scale characterization of YBa₂Cu₃O_{7-δ} thin films by scanning probe methods, R. Sum, H.P. Lang and H.-J. Güntherodt 86 (1995) 140
- Surface properties of excimer-laser-irradiated sintered alumina, L.D. Laude, K. Kolev, M. Brunel and P. Deleter 86 (1995) 368
- Scanning tunneling microscopy study of the (3 × 1) reconstruction induced by Li adsorption on the Si(111) surface, R.Z. Bakhtizin, C. Park, T. Hashizume and T. Sakurai 87/88 (1995) 347
- MBE-STM study of the Ga-rich 4 × 2 phase of the GaAs(001) surface, Q. Xue, T. Hashizume, J.M. Zhou, T. Sakata and T. Sakurai 87/88 (1995) 364
- Simulations of rectification in a laser-illuminated scanning tunneling microscope, M.J. Hagmann 87/88 (1995) 368
- Structure of the MBE-grown GaAs(001)-(2 × 4) phase, T. Hashizume, Q.K. Xue, A. Ichimiya and T. Sakurai 87/88 (1995) 373
- Adsorption and film growth of BTA on clean and oxygen adsorbed Cu(110) surfaces, K. Cho, J. Kishimoto, T. Hashizume, H.W. Pickering and T. Sakurai 87/88 (1995) 380
- MnCu surface alloy studied by scanning tunneling microscopy, D. Jeon, H.P. Noh, T. Hashizume, Y. Kuk and T. Sakurai 87/88 (1995) 386
- Field induced manipulation of fullerene molecules with the STM: a self-consistent theoretical study, M. Devel, C. Girard, C. Joachim and O.J.F. Martin 87/88 (1995) 390
- Field evaporation of gold by scanning tunneling microscopy, W. Mizutani, A. Ohi, M. Motomatsu and H. Tokumoto 87/88 (1995) 398
- Adsorption of fullerenes on Cu(111) and Ag(111) surfaces, T. Sakurai, X.D. Wang, T. Hashizume, V. Yurov, H. Shinohara and H.W. Pickering 87/88 (1995) 405
- The (0001)-surface of 6H-SiC: morphology, composition and structure, U. Starke, Ch. Bram, P.-R. Steiner, W. Hartner, L. Hammer, K. Heinz and K. Müller 89 (1995) 175
- Characterization of triplex RNA poly[rU]·poly[rA]·poly[rU] adsorbed on silver colloids by Fourier transform surface enhanced Raman scattering and scanning tunneling microscopy, Y. Fang, C. Bai, T. Wang and Y.-Q. Tang 89 (1995) 331
- Observation of field-induced fragmentation of nickel clusters using Scanning Tunneling Microscopy, M.V.H. Rao, V. Srinivas, V.V. Rao, B.K. Mathur and K.L. Chopra 89 (1995) 417
- In situ DC-plasma cleaning of silicon surfaces, U. Kafader, H. Sirringhaus and H. von Känel 90 (1995) 297
- The structure of PMDA-PDA polyimide monolayers adsorbed on gold surfaces, M. Keil, J.J. Paggel, Th. Schedel-Niedrig, S. Yokoyama, H. Sotobayashi and A.M. Bradshaw 90 (1995) 377
- ### Schottky barrier
- Are modulations of the Schottky surface barrier the only explanation for the gas-sensing effects in sintered SnO₂?, R. Ionescu, C. Moise and A. Vancu 84 (1995) 291
- Annealing studies of Au/GaAs and Al/GaAs interfaces using a variable energy positron beam, C.C. Ling, T.C. Lee, S. Fung, C.D. Beling, H. Weng, J. Xu, S. Sun and R. Han 85 (1995) 305
- Capacitance-voltage characteristics of Schottky barrier diode in the presence of deep-level impurities and series resistance, P. Chattopadhyay and S. Sanyal 89 (1995) 205
- ### Secondary ion mass spectrometry
- SIMS study of rapid thermal nitridation of silicon dioxide thick films in ammonia ambient, E. Bréelle, S. Rigo, J.A. Kilner and J.-J. Ganem 81 (1994) 127
- Interface study on laser-induced material transfer from polymer and quartz surfaces, S. Lätsch, H. Hiraoka, W. Nieveen and J. Bargon 81 (1994) 183
- Evaluation of matrix effects in SIMS quantification of Al_xGa_{1-x}As/GaAs heterostructures: a SNMS approach, A.

- Torrisi, A. Scandurra and A. Licciardello 81 (1994) 259
- Surface chemical states on 3C-SiC/Si epilayers, A.T.S. Wee, Z.C. Feng, H.H. Hng, K.L. Tan, C.C. Tin, R. Hu and R. Coston 81 (1994) 377
- A combined use of SIMS and RBS techniques for the investigation of SiC and SiCN films, F. Caccavale, G. Brusatin and I. Kleps 81 (1994) 443
- Room-temperature water adsorption on the Si(100) surface examined by UPS, XPS, and static SIMS, R.K. Schulze and J.F. Evans 81 (1994) 449
- Substrate misorientation dependence of thermal stability of Si atom in Si atomic layer doped GaAs on GaAs(111)A, M. Hirai, H. Ohnishi, K. Fujita and T. Watanabe 82/83 (1994) 23
- Autocompensation in Si planar doped GaAs, T. Suzuki, H. Goto, N. Sawaki, H. Ito and K. Hara 82/83 (1994) 103
- Boron δ -doping in Si using atmospheric pressure CVD, Y. Kiyota, T. Nakamura and T. Inada 82/83 (1994) 400
- Surface characterization by time-of-flight SIMS of a catalyst for oxygen electroreduction: pyrolyzed cobalt phthalocyanine-on-carbon black, L.T. Weng, P. Bertrand, G. Lalande, D. Guay and J.P. Dodelet 84 (1995) 9
- Chemisorption of poly(methylhydrogen-siloxane) on oxide surfaces: a quantitative investigation using static SIMS, K. Reihs, R. Aguiar Colom, S. Gleditsch, M. Deimel, B. Hagenhoff and A. Benninghoven 84 (1995) 107
- A multitechnique analysis of the outermost layers of the Teflon PFA surface, K. Piyakis, E. Sacher, A. Domingue, J.-J. Pireaux, G. Leclerc, P. Bertrand and J.B. Lhoest 84 (1995) 227
- Sample charging during static SIMS studies of polymers, G.J. Leggett and J.C. Vickerman 84 (1995) 253
- Electron microscopy of the ordered boron 2×1 structure buried in crystalline silicon, B.E. Weir, D.J. Eaglesham, L.C. Feldman, H.S. Luftman and R.L. Headrick 84 (1995) 413
- Excimer laser etching of diamond-like carbon films: spalling effect, T.V. Kononenko, V.G. Ralchenko, E.D. Obraztsova, V.I. Konov, J. Seth, S.V. Babu and E.N. Loubnin 86 (1995) 234
- Interrupted cycle chemical beam epitaxy of gallium phosphide on silicon with or without photon assistance, J.T. Kelliher, A.E. Miller, N. Dietz, S. Habermehl, Y.L. Chen, Z. Lu, G. Lucovsky and K.J. Bachmann 86 (1995) 453
- Excimer-laser-induced etching of silicon in chlorine atmosphere at a wavelength of 248 nm, W. Jiang, H. Baumgärtner and I. Eisele 86 (1995) 564
- P-doped polycrystalline silicon films obtained at low temperature by hot-wire chemical vapor deposition, J. Puigdollers, J. Cifre, M.C. Polo, J.M. Asensi, J. Bertomeu, J. Andreu and A. Lloret 86 (1995) 600
- SIMS microprofiles of Pb-5%Sn solder joints in electronic devices after accelerated life tests, A. Scandurra, A. Porto and O. Puglisi 89 (1995) 1
- A study of the composition distribution at the Ti/Al₂O₃ interface using the MCs⁺-SIMS technique, X. Chen and Y. Wang 89 (1995) 169
- A graphical analysis of transient response curves at an early stage in SIMS depth profiling using a ¹³³Cs⁺ beam, H. Tomizuka and A. Ayame 89 (1995) 281
- A quantitative time-of-flight secondary ion mass spectrometry study of ion formation mechanisms using acid-base alternating Langmuir-Blodgett films, J.-X. Li, J.A. Gardella, Jr. and P.J. McKeown 90 (1995) 205
- In situ DC-plasma cleaning of silicon surfaces, U. Kafader, H. Sirringhaus and H. von Känel 90 (1995) 297
- SIMS investigation of the Si(111) oxidation promoted by potassium overlayers, B. Lamontagne, F. Semond, A. Adnot and D. Roy 90 (1995) 447
- Determination of the spatial distribution of trace elements in stainless steel by imaging microprobe secondary ion mass spectrometry, G.N. Salaita 90 (1995) 465

Selenium

- Comparative study between MEE- and MBE-grown InSb-nanocrystals on Se-terminated GaAs(001), Y. Watanabe, F. Maeda and M. Oshima 82/83 (1994) 136
- Atomic layer epitaxy of ZnSe using reflectance difference spectroscopy, H. Akinaga and K. Tanaka 82/83 (1994) 298
- Surface reaction mechanism in MOMBE-ALE of ZnSe and CdSe as determined by a new in-situ optical probing method, A. Yoshikawa, M. Kobayashi and S. Tokita 82/83 (1994) 316

- Pulsed laser deposition of epitaxial layers of ZnSe, J.L. Deiss, A. Chergui, L. Koutti, J.L. Loison, M. Robino and J.B. Grun 86 (1995) 149
- Photoassisted metalorganic vapor-phase epitaxy of ZnSe on GaAs, J.E. Bourée, R. Helbing, W. Kuhn and O. Gorochov 86 (1995) 437
- Characterization of the plasma plume and of thin film epitaxially produced during laser ablation of SnSe, R. Teghil, A. Santagata, V. Marotta, S. Orlando, G. Pizzella, A. Giardini-Guidoni and A. Mele 90 (1995) 505

Semiconductors

- Activation of the Ga-CH₃ bond using atomic hydrogen - a possible route to III-V semiconductor films with low carbon levels, J.T. Yates, Jr., A. Hübner, S.R. Lucas, W.D. Partlow, J. Schaefer and W.J. Choyke 82/83 (1994) 180
- Configurational atomic ordering caused by stochastic adsorption processes in MBE-grown alloy semiconductors, H. Nakayama, M. Tochigi, H. Maeda and T. Nishino 82/83 (1994) 214
- Reactivity of III-V and II-VI semiconductors toward hydrogen: surface modification and evolution in air, D. Ballutaud, C. Debiemme-Chouvy, A. Etcheberry, P. De Mierry and L. Svob 84 (1995) 187
- Photoassisted growth of II-VI semiconductor films, Sz. Fujita and Sg. Fujita 86 (1995) 431
- In-situ laser reflectometry of the epitaxial growth of thin semiconductor films, T. Farrell and J.V. Armstrong 86 (1995) 582
- Atom probe and field emission electron spectroscopy studies of semiconductor films on metals, M. Ashino, M. Tomitori and O. Nishikawa 87/88 (1995) 12

Silane

- Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH₄ and SiH₄ gases, M. Sakuraba, J. Murota, T. Watanabe, Y. Sawada and S. Ono 82/83 (1994) 354
- Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane, H. Akazawa 82/83 (1994) 394
- Isothermal H₂ desorption kinetics from Si(100)2 × 1: dependence on disilane and atomic hydrogen precursors, L.A. Okada, M.L. Wise and S.M. George 82/83 (1994) 410
- A study of surface modification of silica using XPS, DRIFT and NMR, F. Gar-

- bassi, L. Balducci, P. Chiurlo and L. Deiana 84 (1995) 145

Silicides

- Atom probe field ion microscope studies of palladium silicide on silicon, R.A. King, R.A.D. Mackenzie, G.D.W. Smith and N.A. Cade 87/88 (1995) 279
- Etching of CoSi₂ in HF-based solutions, R.A. Donaton, K. Lokere, R. Verbeeck and K. Maex 89 (1995) 221
- Medium energy electron diffraction and X-ray photoelectron diffraction study of pseudomorphic Fe silicides grown on Si(111). Evidence of Fe vacancy formation, S. Hong, C. Pirri, P. Wetzel, D. Bolmont and G. Gewinner 90 (1995) 65

Silicon

- An AES study of intrinsic and ion-induced structure in the SiO₂-Si system, B. Lang, B. Sefsaf and G. Allan 81 (1994) 17
- Atomic-hydrogen-induced desorption of fluorine from silicon surfaces, Y. Saito 81 (1994) 223
- Surface chemical states on 3C-SiC/Si epilayers, A.T.S. Wee, Z.C. Feng, H.H. Hng, K.L. Tan, C.C. Tin, R. Hu and R. Coston 81 (1994) 377
- Raman study of strained SiGe layers, S. Gu, R. Zhang, P. Han, R. Wang, P. Zhong and Y. Zheng 81 (1994) 431
- A combined use of SIMS and RBS techniques for the investigation of SiC and SiCN films, F. Caccavale, G. Brusatin and I. Kleps 81 (1994) 443
- Room-temperature water adsorption on the Si(100) surface examined by UPS, XPS, and static SIMS, R.K. Schulze and J.F. Evans 81 (1994) 449
- Photoreflectance of strained Si_{1-x}Ge_x epilayers (0.07 ≤ x ≤ 0.26) and comparison with spectroscopic ellipsometry, R.T. Carline, C. Pickering, T.J.C. Hosea and D.J. Robbins 81 (1994) 475
- Silicon doping with modulated beam epitaxy in the growth of GaAs(111)A, M.R. Fahy, K. Sato and B.A. Joyce 82/83 (1994) 14
- Substrate misorientation dependence of thermal stability of Si atom in Si atomic layer doped GaAs on GaAs(111)A, M. Hirai, H. Ohnishi, K. Fujita and T. Watanabe 82/83 (1994) 23
- Epitaxial growth of a two-dimensional structure of GaP on a Si substrate by

- metalorganic chemical vapor deposition, T. Soga, T. Jimbo and M. Umeno 82/83 (1994) 64
- Autocompensation in Si planar doped GaAs, T. Suzuki, H. Goto, N. Sawaki, H. Ito and K. Hara 82/83 (1994) 103
- Hydrogen atom assisted ALE of silicon, S. Imai and M. Matsumura 82/83 (1994) 322
- Photoelectron intensity oscillation as a probe to monitor Si layer-by-layer growth, Y. Enta, N. Miyamoto, Y. Takakuwa and H. Kato 82/83 (1994) 327
- Sub-atomic-layer epitaxy of Si using Si_2H_6 , Y. Suda, M. Ishida, M. Yamashita and H. Ikeda 82/83 (1994) 332
- Suppression of HBO_2 and Sb adsorption on thin-oxide-covered, H-terminated, or Sb-terminated Si(100) surfaces, E. Murakami, H. Kujirai and S. Kimura 82/83 (1994) 338
- Si ALE using chlorine/hydrogen exchange. Fundamentals and films, D.D. Koleske and S.M. Gates 82/83 (1994) 344
- Self-limiting adsorption of thermally cracked SiCl_2H_2 on Si surfaces, C. Sasaoka and A. Usui 82/83 (1994) 348
- Atomic-layer epitaxy control of Ge and Si in flash-heating CVD using GeH_4 and SiH_4 gases, M. Sakuraba, J. Murota, T. Watanabe, Y. Sawada and S. Ono 82/83 (1994) 354
- Adaptive temperature program ALE of $\text{Si}_{1-x}\text{Ge}_x/\text{Si}$ heterostructures from $\text{Si}_2\text{H}_6/\text{Ge}_2\text{H}_6$, S. Asami, N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt 82/83 (1994) 359
- Scanning tunneling microscopy study of solid-phase epitaxy processes of amorphous silicon layers on silicon substrates, K. Uesugi, T. Komura, M. Yoshimura and T. Yao 82/83 (1994) 367
- Scanning tunneling microscopy observations of Ge solid-phase epitaxy on Si(111), H. Hibino and T. Ogino 82/83 (1994) 374
- Temperature effects on synchrotron-radiation-excited Si atomic layer epitaxy using disilane, H. Akazawa 82/83 (1994) 394
- Boron δ -doping in Si using atmospheric pressure CVD, Y. Kiyota, T. Nakamura and T. Inada 82/83 (1994) 400
- Isothermal H_2 desorption kinetics from Si(100) 2×1 : dependence on disilane and atomic hydrogen precursors, L.A. Okada, M.L. Wise and S.M. George 82/83 (1994) 410
- Low temperature adsorption of hydrogen on Si(111) and (100) surfaces studied by elastic recoil detection analysis, M. Watamori, M. Naitoh, H. Morioka, Y. Maeda and K. Oura 82/83 (1994) 417
- Substrate orientation dependence of self-limited atomic-layer etching of Si with chlorine adsorption and low-energy Ar^+ irradiation, K. Suzue, T. Matsuura, J. Murota, Y. Sawada and T. Ohmi 82/83 (1994) 422
- Atomic-scale modification of the AlCl_3 -adsorbed Si(111)- 7×7 surface, T. Takiguchi, K. Uesugi, M. Yoshimura and T. Yao 82/83 (1994) 428
- Chemical reactivity of the Si(111)($\sqrt{3} \times \sqrt{3}$) $\text{R}30^\circ$ -B surface: an electron-energy-loss spectroscopy study, Y. Taguchi, M. Daté, N. Takagi, T. Aruga and M. Nishijima 82/83 (1994) 434
- Adsorption and desorption of H_2O on potassium precovered Si(100) 2×1 surface, S. Hongo, S. Taniguchi, K. Ojima, T. Urano and T. Kanaji 82/83 (1994) 437
- Scanning tunneling microscope observations of Si(111) 3×1 -Ag and 6×1 -Ag structures, H. Ohnishi, Y. Yamamoto, I. Katayama, Y. Ohba and K. Oura 82/83 (1994) 444
- Temperature-programmed-desorption study of the process of atomic deuterium adsorption onto Si(100) 2×1 , M. Suemitsu, H. Nakazawa and N. Miyamoto 82/83 (1994) 449
- Observation of the interface of Ba/Si(100) by MDS and TDS, S. Hongo, K. Ojima, S. Taniguchi, T. Urano and T. Kanaji 82/83 (1994) 537
- Growth of extra-thin ordered aluminum films on Si(111) surface, E.A. Khramtsova, A.V. Zotov, A.A. Saranin, S.V. Ryzhkov, A.B. Chub and V.G. Lifshits 82/83 (1994) 576
- Electrical properties of Si- Al_2O_3 structures grown by ML-ALE, V.E. Drozd, A.P. Baraban and I.O. Nikiforova 82/83 (1994) 583
- Pretreatment of silicon substrates for CVD diamond deposition studied by atomic force microscopy, G. Friedbacher, E. Bouveresse, G. Fuchs, M. Grasserbauer, D. Schwarzbach, R. Haubner and B. Lux 84 (1995) 133
- A study of surface modification of silica using XPS, DRIFT and NMR, F. Garbassi, L. Balducci, P. Chiurlo and L. Deiana 84 (1995) 145
- An X-ray scattering study of $\text{SiO}_x/\text{Si}/\text{Ge}(001)$, S.D. Kosowsky, C.-H. Hsu, P.S. Pershan, J. Bevk and B.S. Freer 84 (1995) 179
- A comparative study of primary ion energy dependence of secondary ion yields from Si and Ge surfaces under inert and reactive ion bombardment, N. Ray, P. Rajasekar and S.D. Dey 84 (1995) 203
- Carrier transport in heavily doped polycrystalline silicon layers after annealing by a scanning laser beam, A.K. Fedotov, M.I. Tarasik and A.M. Yanchenko 84 (1995) 379
- Laser-induced selective deposition of Ni-P alloy on silicon, J. Wang, X. Fei, Z. Yu and G. Zhao 84 (1995) 383

- Electron microscopy of the ordered boron 2×1 structure buried in crystalline silicon, B.E. Weir, D.J. Eaglesham, L.C. Feldman, H.S. Luftman and R.L. Headrick 84 (1995) 413
- Adsorption site identification for oxygen molecules on Au/Si(100) by positron annihilation induced Auger electron spectroscopy (PAES), G. Yang, J.H. Kim, S. Yang and A.H. Weiss 85 (1995) 77
- Covalency, elasticity and electron correlation in Si vacancies, A. Oshiyama, M. Saito and O. Sugino 85 (1995) 239
- Defects in Czochralski-grown silicon crystals investigated by positron annihilation, A. Ikari 85 (1995) 253
- Buried-oxide layer formation by high-dose oxygen-ion implantation into Si wafers: SIMOX (separation by implanted oxygen), K. Kajiyama 85 (1995) 259
- Variable-energy positron beam study of arsenic diffusion in poly-silicon, D.W. Lawther, R. Khatri, P.J. Simpson, P.J. Schultz, I. Calder and L. Weaver 85 (1995) 265
- Helium and hydrogen-decorated cavities in silicon, R.A. Hakvoort, A. van Veen, P.E. Mijnen and H. Schut 85 (1995) 271
- Slow positron implantation spectroscopy of edge-defined film-fed growth silicon, P.G. Coleman, E. Bloss, S. Setzler, S. LaShell, G. Davies and W.D. Sawyer 85 (1995) 276
- An annealing study of defects induced by electron irradiation of Czochralski-grown Si using a positron lifetime technique, A. Kawasuso, M. Hasegawa, M. Suezawa, S. Yamaguchi and K. Sumino 85 (1995) 280
- Determination of the characteristic signal for positron annihilation at divacancies in ion-irradiated silicon, R.D. Goldberg, P.J. Schultz and P.J. Simpson 85 (1995) 287
- Erbium oxide thin films on Si(100) obtained by laser ablation and electron beam evaporation, X. Queralt, C. Ferrater, F. Sánchez, R. Aguiar, J. Palau and M. Varela 86 (1995) 95
- $\text{Si}_{1-x}\text{Ge}_x$ thin films deposited by the pulsed excimer laser ablation technique, F. Antoni, E. Fogarassy, C. Fuchs, B. Prévot and J.P. Stoquert 86 (1995) 175
- Laser-induced forward transfer of ultra-fine diamond particles for selective deposition of diamond films, S.M. Pimenov, G.A. Shafeev, A.A. Smolin, V.I. Konov and B.K. Vodolaga 86 (1995) 208
- Tunable UV-flash krypton lamp array useful for large area deposition and in situ UV annealing of Si-based dielectrics, J. Flicstein, Y. Vitel, O. Dulac, C. Debauche, Y.I. Nissim and C. Licoppe 86 (1995) 286
- Thermodynamics and kinetics of solidification of Si-As solutions, R. Reitano 86 (1995) 323
- Morphology of $\text{Si}_{1-x}\text{Ge}_x$ thin crystalline films obtained by pulsed-excimer-laser annealing of heavily Ge-implanted Si, E.L. Mathé, A. Naudon, F. Repplinger and E. Fogarassy 86 (1995) 338
- Formation of poly- $\text{Si}_{1-x}\text{Ge}_x$ using excimer-laser processing, A. Slaoui, C. Deng, S. Talwar, K.J. Kramer, T.W. Sigmon, J.P. Stoquert and B. Prevot 86 (1995) 346
- Surface morphology and structure modification of silicon layers induced by nanosecond laser radiation, A.V. Demchuk and V.A. Labunov 86 (1995) 353
- Theoretical and experimental studies of a-Si:H recrystallization by XeCl excimer laser irradiation, R. Černý, V. Vydra, P. Píkrýl, I. Ulrych, J. Kočka, K.M.A. El-Kader, Z. Chvoj and V. Cháb 86 (1995) 359
- Laser-induced formation of porous silicon, V. Baranauskas, G.P. Thim and A. Peled 86 (1995) 398
- Laser-assisted etching-like damage of Si, A.V. Simakin and G.A. Shafeev 86 (1995) 422
- Interrupted cycle chemical beam epitaxy of gallium phosphide on silicon with or without photon assistance, J.T. Kelliher, A.E. Miller, N. Dietz, S. Habermehl, Y.L. Chen, Z. Lu, G. Lucovsky and K.J. Bachmann 86 (1995) 453
- Laser processing of tungsten from WF_6 and SiH_4 , M. Meunier, P. Desjardins, M. Tabbal, N. Elyaagoubi, R. Izquierdo and A. Yelon 86 (1995) 475
- Kinetics of laser thermal decomposition of trimethylamine alane, D. Tonneau, J.E. Bourée and Y. Pauleau 86 (1995) 488
- Laser induced deposition of nanocrystalline Si with preferred crystallographic orientation, S. Tamir and S. Berger 86 (1995) 514
- VUV laser (157 nm) chemical vapor deposition of high quality amorphous hydrogenated silicon: gas phase chemistry and modelling, H. Karstens, J. Knobloch, A. Winkler, A. Pusel, M. Barth and P. Hess 86 (1995) 521
- Excimer laser-assisted etching of silicon in chlorine: adsorption and desorption, A.V. Kuzmichov 86 (1995) 559
- Excimer-laser-induced etching of silicon in chlorine atmosphere at a wavelength of 248 nm, W. Jiang, H. Baumgärtner and I. Eisele 86 (1995) 564
- Three-dimensional nanostructures by direct laser etching of Si, M. Müllenborn, H. Dirac and J.W. Petersen 86 (1995) 568

- P-doped polycrystalline silicon films obtained at low temperature by hot-wire chemical vapor deposition, J. Puigdollers, J. Cifre, M.C. Polo, J.M. Asensi, J. Bertomeu, J. Andreu and A. Lloret 86 (1995) 600
- Microstructure and field emission of diamond particles on silicon tips, E.I. Givargizov, V.V. Zhirmov, A.N. Stepanova, E.V. Rakova, A.N. Kiselev and P.S. Plekhanov 87/88 (1995) 24
- Atom probe field ion microscope studies of palladium silicide on silicon, R.A. King, R.A.D. Mackenzie, G.D.W. Smith and N.A. Cade 87/88 (1995) 279
- Scanning tunneling microscopy study of the (3×1) reconstruction induced by Li adsorption on the Si(111) surface, R.Z. Bakhtizin, C. Park, T. Hashizume and T. Sakurai 87/88 (1995) 347
- Thermal desorption spectroscopy study of chemically etched porous silicon, N. Hadj Zoubir and M. Vergnat 89 (1995) 35
- X-ray photoelectron spectroscopic study of room-temperature evolution of oxide-covered hydrogenated amorphous silicon/aluminium interface, C. Anandan 89 (1995) 57
- A graphical analysis of transient response curves at an early stage in SIMS depth profiling using a $^{133}\text{Cs}^+$ beam, H. Tomizuka and A. Ayame 89 (1995) 281
- Cadmium selenide-amorphous hydrogenated silicon heterostructures, S. Wu and D. Haneman 89 (1995) 289
- Chemistry at silicon crystalline surfaces, G.F. Cerofolini and L. Meda 89 (1995) 351
- Enhanced silicon oxidation in O_2 and $\text{O}_2:\text{F}_2$, G.F. Cerofolini, G. La Bruna and L. Meda 89 (1995) 361
- Medium energy electron diffraction and X-ray photoelectron diffraction study of pseudomorphic Fe silicides grown on Si(111). Evidence of Fe vacancy formation, S. Hong, C. Pirri, P. Wetzell, D. Bolmont and G. Gewinner 90 (1995) 65
- Hydrogen adsorption induced phase transitions on Si(100)-c(8×8): temperature dependence studied by LEED, X. Hu and Z. Lin 90 (1995) 111
- Silicon surface cleaning using XeF_2 gas treatment, V.S. Aliev, M.R. Baklanov and V.I. Bukhtiyarov 90 (1995) 191
- In situ DC-plasma cleaning of silicon surfaces, U. Kafader, H. Sirringhaus and H. von Känel 90 (1995) 297
- Charge transfer processes in a- WO_3/Si heterostructure during electro- and photochromism, E.A. Tutov and A.A. Baev 90 (1995) 303
- XPS investigation of electron beam effects on a trimethylsilane dosed Si(100) surface, P.W. Wang, S. Bader, L.P. Zhang, M. Ascherl and J.H. Craig, Jr. 90 (1995) 413
- Range profiles of 6-10 MeV ^{15}N ions implanted in silicon, T. Ahlgren, K. Väkeväinen, J. Räisänen, E. Rauhala and J. Keinonen 90 (1995) 419
- SIMS investigation of the Si(111) oxidation promoted by potassium overlayers, B. Lamontagne, F. Semond, A. Adnot and D. Roy 90 (1995) 447
- AFM and XPS characterization of the Si(111) surface after thermal treatment, B. Lamontagne, D. Guay, D. Roy, R. Sporken and R. Caudano 90 (1995) 481
- ### Silicon carbide
- Auger studies of chemical bonds and oxygen minimization in the interfaces between AlN and SiC thin films deposited by LPCVD, B. Aspar, R. Berjoan, C. Labatut and B. Armas 81 (1994) 55
- Surface chemical states on 3C-SiC/Si epilayers, A.T.S. Wee, Z.C. Feng, H.H. Hng, K.L. Tan, C.C. Tin, R. Hu and R. Coston 81 (1994) 377
- A combined use of SIMS and RBS techniques for the investigation of SiC and SiCN films, F. Caccavale, G. Brusatin and I. Kleps 81 (1994) 443
- Mechanisms of SiC growth by alternate supply of SiH_2Cl_2 and C_2H_2 , H. Nagasawa and Y. Yamaguchi 82/83 (1994) 405
- Adsorption and co-adsorption of boron and oxygen on ordered α -SiC surfaces, V.M. Bermudez 84 (1995) 45
- The (0001)-surface of 6H-SiC: morphology, composition and structure, U. Starke, Ch. Bram, P.-R. Steiner, W. Hartner, L. Hammer, K. Heinz and K. Müller 89 (1995) 175
- Characterization of ex-situ hydrogenated amorphous SiC thin films by X-ray photoelectron spectroscopy, S. Kennou, S. Ladas, E.C. Paloura and J.A. Kalomiros 90 (1995) 283
- ### Silicon nitride
- A combined use of SIMS and RBS techniques for the investigation of SiC and SiCN films, F. Caccavale, G. Brusatin and I. Kleps 81 (1994) 443
- Excimer laser reactive ablation deposition of silicon nitride films, E. D'Anna, G.

Leggieri, A. Luches, M. Martino, A. Perrone, G. Majni, P. Mengucci, R. Alexandrescu, I.N. Mihailescu and J. Zemek

86 (1995) 170

Silicon oxide

An AES study of intrinsic and ion-induced structure in the SiO₂-Si system, B. Lang, B. Sefsaf and G. Allan

81 (1994) 17

FT-IR investigation of methane adsorption on silica, J. Wu, S. Li, G. Li, C. Li and Q. Xin

81 (1994) 37

SIMS study of rapid thermal nitridation of silicon dioxide thick films in ammonia ambient, E. Bréelle, S. Rigo, J.A. Kilner and J.-J. Ganem

81 (1994) 127

Ultrathin SiO₂ films on Si formed by N₂O-plasma oxidation technique, A. Masuda, Y. Yonezawa, A. Morimoto, M. Kumeda and T. Shimizu

81 (1994) 277

Combined use of XPS, IR and EDAX techniques for the characterization of ZrO₂-SiO₂ powders prepared by a sol-gel process, J.A. Navío, M. Macías, G. Colón, P.J. Sánchez-Soto, V. Augugliaro and L. Palmisano

81 (1994) 325

Atomic layer controlled deposition of SiO₂ and Al₂O₃ using ABAB... binary reaction sequence chemistry, S.M. George, O. Sneh, A.C. Dillon, M.L. Wise, A.W. Ott, L.A. Okada and J.D. Way

82/83 (1994) 460

An X-ray scattering study of SiO_x/Si/Ge(001), S.D. Kosowsky, C.-H. Hsu, P.S. Pershan, J. Bevk and B.S. Freer

84 (1995) 179

Measurement of oxide thickness using a variable-energy positron beam, T.C. Leung, P.J. Simpson, A. Atkinson, I.V. Mitchell and P.J. Schultz

85 (1995) 292

SiO₂ film deposition by XeCl laser ablation of fused silica, P. Baeri, R. Reitano and N. Marino

86 (1995) 128

Improvement of silicon oxide film properties by ultraviolet excimer lamp annealing, E.G. Parada, P. González, J. Serra, B. León, M. Pérez-Amor, J. Flicstein and R.A.B. Devine

86 (1995) 294

Effect of UV annealing of radiation damage in SiO₂ films, I.P. Lisovskii, V.G. Litovchenko and V.B. Lozinskii

86 (1995) 299

Enhanced adherence of electroless metal deposit on SiO₂ via control of the chemical environment of the Pd seeding layer, G.A. Shafeev, L. Bellard, J.-M. Themlin, W. Marine and A. Cros

86 (1995) 387

Plasma-enhanced reactively evaporated deposition of SiO₂ films, A.A. Shklyayev and A.S. Medvedev

89 (1995) 49

A graphical analysis of transient response curves at an early stage in SIMS depth profiling using a ¹³³Cs⁺ beam, H. Tomizuka and A. Ayame

89 (1995) 281

IRAS and TDS study on the photolytic decarbonylation of iron pentacarbonyl adsorbed on a SiO₂ film with a buried metal layer, S. Sato, S. Minoura, T. Urisu and Y. Takasu

90 (1995) 29

Silver

Surface segregation study of Ib-VIII single-crystal alloys, F. Reniers, M.P. Delplancke, A. Asskali, M. Jardinier-Offergeld and F. Bouillon

81 (1994) 151

Scanning tunneling microscope observations of Si(111)3 × 1-Ag and 6 × 1-Ag structures, H. Ohnishi, Y. Yamamoto, I. Katayama, Y. Ohba and K. Oura

82/83 (1994) 444

Solution growth and characterization of silver sulfide films, I. Grozdanov

84 (1995) 325

Surface alloy formation in Pd/Ag, Cu/Au and Ni/Au bimetallic overlayers, A.K. Santra and C.N.R. Rao

84 (1995) 347

Secondary electron emission from Ag(100) stimulated by positron and electron impact, A.P. Knights and P.G. Coleman

85 (1995) 43

Adsorption of fullerenes on Cu(111) and Ag(111) surfaces, T. Sakurai, X.D. Wang, T. Hashizume, V. Yurov, H. Shinohara and H.W. Pickering

87/88 (1995) 405

Characterization of thin Ag films deposited onto InP(001)-p(2 × 4) surface at room temperature by means of LEED, RHEED, AES and RBS-channeling techniques, M. Hanebuchi, T. Katoh and K. Morita

89 (1995) 113

The effect of anodic polarization on a Ag electrode deposited on YSZ solid electrolyte, J.K. Hong, I.-H. Oh, S.-A. Hong and W.Y. Lee

89 (1995) 229

Interaction of oxygen and silver on the V(100) surface, T. Valla, P. Pervan and M. Milun

89 (1995) 375

Diffusion of Ag on Cu(110) and Cu(111) studied by spatially resolved UV-photoemission, U. Kürpick, G. Meister and A. Goldmann

89 (1995) 383

Interfacial reaction of Ag with the InP (100)4 × 2 surface - a photoemission study, H. Engelhard, F. Stietz, S. Sloboshanin, V. Persch, Th. Allinger, J.A. Schaefer and A. Goldmann

90 (1995) 89

- Angle resolved XPS study of inhomogeneous specimens of polycrystalline silver covered with uniform graphite overlayers, M. Sreemany and T.B. Ghosh
Surface studies of Cu/Cr/Ag impregnated microporous carbons, R.H. Bradley

90 (1995) 241

90 (1995) 271

Sputter deposition

- Origin of residual stress in a textured Au thin film on a LiF substrate, N. Durand, K.F. Badawi, A. Declémy and Ph. Goudeau
Oxidation of TiN thin films in an ion-beam-assisted deposition process, H. Kubota, M. Nagata, R. Miyagawa and M.A. Nicolet
AES and XPS study of thin RF-sputtered Ta₂O₅ layers, E. Atanassova, T. Dimitrova and J. Koprinarova
Study on the mechanical and chemical properties of (Ti,Al)N films prepared by DC magnetron sputtering, S. Jiang, D. Peng, X. Zhao, L. Xie and Q. Li
Comparison of the structure of laser deposited and sputtered metallic alloys, H.-U. Krebs, O. Bremert, M. Störmer and Y. Luo
In-situ spectroscopic ellipsometry to control the growth of Ti nitride and carbide thin films, S. Logothetidis, I. Alexandrou and J. Stoemenos

81 (1994) 119

82/83 (1994) 565

84 (1995) 193

84 (1995) 373

86 (1995) 90

86 (1995) 185

Sputtering

- Composition of sputtered material from Cu-Ni alloy during Xe⁺ ion sputtering at elevated temperatures, S. Sekine, H. Shimizu and S. Ichimura
Fabrication of microtips on planar specimens, D.J. Larson, C.-M. Teng, P.P. Camus and T.F. Kelly
Preferential sputtering of argon ion bombarded Ni₃Al and TaSi₂, S. Hofmann and M.G. Stepanova

84 (1995) 401

87/88 (1995) 446

90 (1995) 227

Steel

- Depth profiles of defects in Ar-ion-irradiated steels determined by a least-squares fit of *S* parameters from variable-energy positron annihilation, T. Aruga, S. Takamura, K. Nakata and Y. Ito
Microstructure, chemical composition and properties of the surface layer of M2

85 (1995) 229

steel after laser melting under different conditions, J. Kusiński

86 (1995) 317

The partitioning of substitutional solute elements during the tempering of martensite in Cr and Mo containing steels, R.C. Thomson and M.K. Miller

87/88 (1995) 185

Atom-probe study of phosphorus segregation to the carbide/matrix interface in an aged 9% chromium steel, L. Lundin and B. Richarz

87/88 (1995) 194

Microstructure of heat resistant chromium steel weld metals, H.-O. Andrén, G. Cai and L.-E. Svensson

87/88 (1995) 200

Atom probe field ion microscopy of type 308 CRE stainless steel welds, S.S. Babu, S.A. David, J.M. Vitek and M.K. Miller

87/88 (1995) 207

Comparison of low temperature decomposition in Fe-Cr and duplex stainless steels, M.K. Miller, J.M. Hyde, A. Cerezo and G.D.W. Smith

87/88 (1995) 323

Fabrication of microtips on planar specimens, D.J. Larson, C.-M. Teng, P.P. Camus and T.F. Kelly

87/88 (1995) 446

Determination of the spatial distribution of trace elements in stainless steel by imaging microprobe secondary ion mass spectrometry, G.N. Salaita

90 (1995) 465

Strontium

Atomic force microscopic study of directional SrSO₄(001) surface and its etching property, A. Seo and H. Shindo

82/83 (1994) 475

Morphology of epitaxial SrF₂ films on atomically modified InP(100), S. Heun, M. Sugiyama, S. Maeyama, Y. Watanabe and M. Oshima

82/83 (1994) 507

Structural study of SrTiO₃(100) surfaces by low energy ion scattering, Y. Tanaka, H. Morishita, M. Watamori, K. Oura and I. Katayama

82/83 (1994) 528

Recovery and recrystallization of SrTiO₃(100) surface characterized by ion channeling, F. Wang, M. Badaye, K. Ogawa and T. Morishita

90 (1995) 123

Sulphides

XPS study of clean metal sulfide surfaces, K. Laajalehto, I. Kartio and P. Nowak

81 (1994) 11

Growth of In₂S₃ thin films by atomic layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä

82/83 (1994) 122

The effect of growth parameters on the deposition of CaS thin films by atomic

- layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen 82/83 (1994) 553
- Comment on 'Scanning tunnelling microscopy studies of galena: the mechanism of oxidation in air' by B.S. Kim, R.A. Hayes, C.A. Prestidge, J. Ralston and R.St.C. Smart, A.N. Buckley and R. Woods 84 (1995) 223
- Solution growth and characterization of silver sulfide films, I. Grozdanov 84 (1995) 325
- Blast-wave studies of excimer laser ablation of ZnS, P.E. Dyer, P.H. Key, D. Sands, H.V. Snelling and F.X. Wagner 86 (1995) 18
- Laser-induced photodeposition from ZnS colloid solutions, A. Peled, B. Dragnea, R. Alexandrescu and A. Andrei 86 (1995) 538
- ### Sulphur
- Sulfur segregation in titanium and selected titanium alloys, R.A. Outlaw, W.S. Lee, S.J. Hoekje and S.N. Sankaran 81 (1994) 143
- A study of CaO-SO₂ interaction, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea 81 (1994) 409
- Atomic force microscopic study of directional SrSO₄(001) surface and its etching property, A. Seo and H. Shindo 82/83 (1994) 475
- Photo-assisted growth and characterization of Zn_xCd_{1-x}S by MOVPE, H. Dumont, Sz. Fujita and Sg. Fujita 86 (1995) 442
- ### Sulphur dioxide
- A study of CaO-SO₂ interaction in the presence of O₂, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea 81 (1994) 417
- A new parameter to characterize limestones as SO₂ sorbents, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea 89 (1995) 197
- ### Superconductors
- Pulsed laser deposition and nanometer scale characterization of YBa₂Cu₃O_{7-δ} thin films by scanning probe methods, R. Sum, H.P. Lang and H.-J. Güntherodt 86 (1995) 140
- ### Superconductivity
- Layer controlled growth of oxide superconductors, M. Kawai, Z.-Y. Liu, T. Hanada, M. Katayama, M. Aono and C.F. McConville 82/83 (1994) 487
- Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi 82/83 (1994) 494
- Fabrication of CuO₂-plane-based high-temperature superconducting thin films by atomic layer controlled molecular beam epitaxy, I. Yoshida, H. Furukawa, T. Hirose and M. Nakao 82/83 (1994) 501
- Aqueous degradation of Bi-2212 single crystals: an AFM study of surface alteration, S.A. Holt, R. Zhao and S. Myhra 84 (1995) 125
- The laser ablation threshold of YBa₂Cu₃O_{6+x} as revealed by using projection optics, B. Dam, J. Rector, M.F. Chang, S. Kars, D.G. de Groot and R. Griessen 86 (1995) 13
- Why are high-T_c superconductors, HTSC, deposited by 248 nm lasers at 400 MW/cm²?, R.W. Dreyfus 86 (1995) 29
- Plasma properties and stoichiometry of laser-deposited BiSrCaCuO thin films, J. Gonzalo, C.N. Afonso, F. Vega, D. Martínez García and J. Perrière 86 (1995) 40
- Laser ablation of BiSrCaCuO superconducting thin film: analysis of intermediate species in real time, U. Gambardella, A. Giardini, V. Marotta, A. Morone, S. Orlando and M. Snels 86 (1995) 45
- Characterisation of ionic species generated during ablation of Bi₂Sr₂Ca₂Cu₃O₁₀ by frequency-doubled Nd:YAG laser irradiation, G.C. Tyrrell, T.H. York and I.W. Boyd 86 (1995) 50
- Laser wavelength dependence of YBa₂Cu₃O_y laser ablation plumes, J. Palau, M. Sowinska, M. Varela, P. Summ, J. Esteve, P. Serra, J.L. Morenza and J.A. Miehé 86 (1995) 59
- SEM observations of YBCO on as-received and heat-treated MgO substrates, S. King, L. Coccia and I.W. Boyd 86 (1995) 134
- Macro-particle ejection by laser ablation of high-temperature superconductors, E.N. Sobol, M.S. Kitai, S.M. Gol'berg and A.N. Zherikhin 90 (1995) 235
- ### Superlattices
- Pulsed-jet epitaxy: application to device processes, Y. Sakuma, M. Ozeki, N. Ohtsuka, Y. Matsumiya, H. Shigematsu, O. Ueda, S. Muto, K. Nakajima and N. Yokoyama 82/83 (1994) 46
- Growth temperature dependence of optical properties of gas source MBE grown GaP/AIP short period superlattices, J.H.

- Kim, H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda
Fabrication of CuO₂-plane-based high-temperature superconducting thin films by atomic layer controlled molecular beam epitaxy, I. Yoshida, H. Furukawa, T. Hirose and M. Nakao
82/83 (1994) 76
82/83 (1994) 501
- Surface composition*
- Surface stoichiometry and the role of adsorbates during GaAs atomic layer epitaxy, J.R. Creighton
82/83 (1994) 171
- Surface diffusion*
- Modelling of barium transport in dispenser cathodes, A. Sil and D.S. Venkateswarlu
Surface diffusion and adatom stoichiometry in GaAs MBE studied by microprobe-RHEED/SEM MBE, T. Nishinaga and X.Q. Shen
81 (1994) 469
82/83 (1994) 141
- Surface plasmons*
- Positron surface-state trapping induced by surface plasmon excitation under grazing scattering conditions, M. Kato and A. Ishii
Oligonucleotide hybridization observed by surface plasmon optical techniques, D. Piscevic, R. Lawall, M. Veith, M. Liley, Y. Okahata and W. Knoll
85 (1995) 69
90 (1995) 425
- Surface segregation*
- Surface segregation study of Ib-VIII single-crystal alloys, F. Reniers, M.P. Delplancke, A. Asskali, M. Jardinier-Offergeld and F. Bouillon
Surface segregation and core-level shift of a Pd-Rh alloy studied by XPS, J.A. Leiro, M.H. Heinonen and I.G. Batirev
81 (1994) 151
90 (1995) 515
- Surface structure*
- Thermal etching of α -Zr single-crystal surfaces, H. Zou, G.M. Hood, R.J. Schultz and J.A. Roy
90 (1995) 59
- Tantalum*
- AES and XPS study of thin RF-sputtered Ta₂O₅ layers, E. Atanassova, T. Dimitrova and J. Koprinarova
84 (1995) 193
- Pulsed-laser deposition and characterization of TaC films, R. Teghil, L. D'Alessio, G. De Maria and D. Ferro
86 (1995) 190
- Tantalum oxide film formation by excimer laser ablation, Y. Nishimura, H. Ujita and M. Tsuji
89 (1995) 393
- A photoelectron study of the oxidation of Ta(110) and thin aluminum layers on Ta(110), M.W. Ruckman, S.-L. Qiu and M. Strongin
89 (1995) 401
- Tellurium*
- Study of PbTe(Ga) evaporation using a nanosecond pulsed laser, V.A. Mikhailov, F.N. Putlin and D.N. Trubnikov
86 (1995) 64
- Comparison of epitaxial films of Zn_{1-x}Mn_xTe on (111) and (100) GaAs produced by pulsed laser deposition, H.J. Masterson and J.G. Lunney
86 (1995) 154
- Pulsed laser deposition of NbTe_x thin films, F. Grangeon, H. Sassoli, Y. Mathey, M. Autric, D. Pailharey and W. Marine
86 (1995) 160
- Photo-luminescence of pulsed excimer laser annealed Sb-implanted CdTe, F.X. Wagner, K. Dhese, P.H. Key, D. Sands, S.R. Jackson, R. Kirbitson and J.E. Nicholls
86 (1995) 364
- Thermal desorption*
- A temperature-programmed desorption/X-ray photoelectron spectroscopy study of ditertiarybutylarsine on GaAs(100), M.S. Jackson, J.M. Heitzinger, J.W. Nail, R.D. Culp and J.G. Ekerdt
81 (1994) 195
- Adsorption of CO on Mg-promoted Co-(poly), J. Vaari, T. Vaara, J. Lahtinen and P. Hautajärvi
81 (1994) 289
- A study of CaO-SO₂ interaction in the presence of O₂, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea
81 (1994) 417
- A study of CaO-SO₂ interaction in the presence of O₂, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea
81 (1994) 417
- Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs, I. Sue-mune
82/83 (1994) 149
- Activation of the Ga-CH₃ bond using atomic hydrogen - a possible route to III-V semiconductor films with low carbon levels, J.T. Yates, Jr., A. Hübner,

- S.R. Lucas, W.D. Partlow, J. Schaefer and W.J. Choyke 82/83 (1994) 180
- CO adsorption on clean and atomic-layer-Cu-covered ZnO(10 $\bar{1}$ 0) surfaces, Q. Ge and P.J. Møller 82/83 (1994) 305
- Self-limiting adsorption of thermally cracked SiCl₂H₂ on Si surfaces, C. Sasaoka and A. Usui 82/83 (1994) 348
- Adaptive temperature program ALE of Si_{1-x}Ge_x/Si heterostructures from Si₂H₆/Ge₂H₆, S. Asami, N.M. Russell, A. Mahajan, P.A. Steiner IV, D.J. Bonser, J. Fretwell, S. Bannerjee, A. Tasch, J.M. White and J.G. Ekerdt 82/83 (1994) 359
- Isothermal H₂ desorption kinetics from Si(100)2 × 1: dependence on disilane and atomic hydrogen precursors, L.A. Okada, M.L. Wise and S.M. George 82/83 (1994) 410
- Adsorption and desorption of H₂O on potassium precovered Si(100)2 × 1 surface, S. Hongo, S. Taniguchi, K. Ojima, T. Urano and T. Kanaji 82/83 (1994) 437
- Temperature-programmed-desorption study of the process of atomic deuterium adsorption onto Si(100)2 × 1, M. Suemitsu, H. Nakazawa and N. Miyamoto 82/83 (1994) 449
- Observation of the interface of Ba/Si(100) by MDS and TDS, S. Hongo, K. Ojima, S. Taniguchi, T. Urano and T. Kanaji 82/83 (1994) 537
- Quantitative analysis of the thermal degassing of a beryllium powder, L. Buisson, P. Bracconi and X. Claudon 84 (1995) 211
- Coadsorption of water and selected aromatic molecules to model the adhesion of epoxy resins on hydrated surfaces of zinc oxide and iron oxide, M. Nakazawa and G.A. Somorjai 84 (1995) 309
- UV photo-annealing of thin sol-gel films, R.E. Van de Leest 86 (1995) 278
- Excimer laser-assisted etching of silicon in chlorine: adsorption and desorption, A.V. Kuzmichov 86 (1995) 559
- The distribution of activation energy for hydrogen desorption over silica-supported nickel catalysts determined from temperature-programmed desorption spectra, M. Arai, Y. Nishiyama, T. Masuda and K. Hashimoto 89 (1995) 11
- Thermal desorption spectroscopy study of chemically etched porous silicon, N. Hadj Zoubir and M. Vergnat 89 (1995) 35
- Reactions of CO and NO on Mg promoted cobalt, T. Vaara, J. Lahtinen and P. Hautojärvi 89 (1995) 103
- Temperature-programmed desorption and decomposition of NH₃ over molybdenum nitride films, H.J. Lee, J.-G. Choi, C.W. Colling, M.S. Mudholkar and L.T. Thompson 89 (1995) 121
- Oxygen exchange between adsorbed NO and MgO surfaces, Y. Yanagisawa 89 (1995) 251
- Synergistic alloying behaviour of Pd₅₀Cu₅₀ single crystals upon adsorption and co-adsorption of CO and NO, Y. Debauge, M. Abon, J.C. Bertolini, J. Massardier and A. Rochefort 90 (1995) 15
- IRAS and TDS study on the photolytic decarbonylation of iron pentacarbonyl adsorbed on a SiO₂ film with a buried metal layer, S. Sato, S. Minoura, T. Urisu and Y. Takasu 90 (1995) 29
- Superefficient diffusion of cesium atoms into rhenium covered by a 2D graphite film, A.Ya. Tontegode and F.K. Yusifov 90 (1995) 185
- Atomic hydrogen adsorption on sintered thin copper films, R. Duś, E. Nowicka, W. Lisowski and Z. Wolfram 90 (1995) 277
- In situ DC-plasma cleaning of silicon surfaces, U. Kafader, H. Sirringhaus and H. von Känel 90 (1995) 297
- ### Thin films
- Auger studies of chemical bonds and oxygen minimization in the interfaces between AlN and SiC thin films deposited by LPCVD, B. Aspar, R. Berjoan, C. Labatut and B. Armas 81 (1994) 55
- Coordination compounds as precursors for laser deposition of nickel-based conducting films, M. Devillers, O. Dupuis, A. Janosi and J.P. Soumillion 81 (1994) 83
- Origin of residual stress in a textured Au thin film on a LiF substrate, N. Durand, K.F. Badawi, A. Declémy and Ph. Goudeau 81 (1994) 119
- A Raman microprobe study of the electrochromic and photochromic thin films of molybdenum trioxide and tungsten trioxide, B.H. Loo, J.N. Yao, H.D. Coble, K. Hashimoto and A. Fujishima 81 (1994) 175
- Interface study on laser-induced material transfer from polymer and quartz surfaces, S. Lätsch, H. Hiraoka, W. Nieveen and J. Bargon 81 (1994) 183
- Ultrathin SiO₂ films on Si formed by N₂O-plasma oxidation technique, A. Masuda, Y. Yonezawa, A. Morimoto, M. Kumeda and T. Shimizu 81 (1994) 277
- Surface chemical states on 3C-SiC/Si epilayers, A.T.S. Wee, Z.C. Feng, H.H. Hng, K.L. Tan, C.C. Tin, R. Hu and R. Coston 81 (1994) 377

- Raman study of strained SiGe layers, S. Gu, R. Zhang, P. Han, R. Wang, P. Zhong and Y. Zheng 81 (1994) 431
- A combined use of SIMS and RBS techniques for the investigation of SiC and SiCN films, F. Caccavale, G. Brusatin and I. Kleps 81 (1994) 443
- Recent advances in atomic layer epitaxy devices, S.M. Bedair and N.A. El-Masry 82/83 (1994) 7
- Atomic layer epitaxy growth of doped zinc oxide thin films from organometals, V. Lujala, J. Skarp, M. Tammenmaa and T. Suntola 82/83 (1994) 34
- Atomic layer epitaxy in the growth of complex thin film structures for electroluminescent applications, L. Niinistö and M. Leskelä 82/83 (1994) 454
- In situ ellipsometric diagnostics for controlled growth of metal oxides with surface chemical reactions, H. Kumagai and K. Toyoda 82/83 (1994) 481
- Layer controlled growth of oxide superconductors, M. Kawai, Z.-Y. Liu, T. Hanada, M. Katayama, M. Aono and C.F. McConville 82/83 (1994) 487
- Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi 82/83 (1994) 494
- Oxidation of TiN thin films in an ion-beam-assisted deposition process, H. Kubota, M. Nagata, R. Miyagawa and M.A. Nicolet 82/83 (1994) 565
- Pretreatment of silicon substrates for CVD diamond deposition studied by atomic force microscopy, G. Friedbacher, E. Bouveresse, G. Fuchs, M. Grasserbauer, D. Schwarzbach, R. Haubner and B. Lux 84 (1995) 133
- AES and XPS study of thin RF-sputtered Ta₂O₅ layers, E. Atanassova, T. Dimitrova and J. Koprinarova 84 (1995) 193
- Solution growth and characterization of silver sulfide films, I. Grozdanov 84 (1995) 325
- Carrier transport in heavily doped polycrystalline silicon layers after annealing by a scanning laser beam, A.K. Fedotov, M.I. Tarasik and A.M. Yanchenko 84 (1995) 379
- Using the Lambert-Beer law for thickness evaluation of photoconductor coatings for recording holograms, A. Larena, G. Pinto and F. Millán 84 (1995) 407
- Energy loss measurements for 20 keV positrons in Al thin films, G.R. Mas-soumi, W.N. Lennard, P.J. Schultz, T.A. Porcelli and P.J. Simpson 85 (1995) 39
- Annealing studies of Au/GaAs and Al/GaAs interfaces using a variable energy positron beam, C.C. Ling, T.C. Lee, S. Fung, C.D. Beling, H. Weng, J. Xu, S. Sun and R. Han 85 (1995) 305
- Aluminium nitride layers investigated by slow positrons, A.S. Saleh, P.C. Rice-Evans and S.J. Bull 85 (1995) 325
- The laser ablation threshold of YBa₂Cu₃O_{6+x} as revealed by using projection optics, B. Dam, J. Rector, M.F. Chang, S. Kars, D.G. de Groot and R. Griessen 86 (1995) 13
- Blast-wave studies of excimer laser ablation of ZnS, P.E. Dyer, P.H. Key, D. Sands, H.V. Snelling and F.X. Wagner 86 (1995) 18
- Why are high-T_c superconductors, HTSC, deposited by 248 nm lasers at 400 MW/cm²?, R.W. Dreyfus 86 (1995) 29
- Plasma properties and stoichiometry of laser-deposited BiSrCaCuO thin films, J. Gonzalo, C.N. Afonso, F. Vega, D. Martínez García and J. Perrière 86 (1995) 40
- Laser ablation of BiSrCaCuO superconducting thin film: analysis of intermediate species in real time, U. Gambardella, A. Giardini, V. Marotta, A. Morone, S. Orlando and M. Snels 86 (1995) 45
- Characterisation of ionic species generated during ablation of Bi₂Sr₂Ca₂Cu₃O₁₀ by frequency-doubled Nd:YAG laser irradiation, G.C. Tyrrell, T.H. York and I.W. Boyd 86 (1995) 50
- Laser wavelength dependence of YBa₂Cu₃O_y laser ablation plumes, J. Palau, M. Sowinska, M. Varela, P. Summ, J. Esteve, P. Serra, J.L. Morenza and J.A. Miehe 86 (1995) 59
- Composition and gas dynamics of laser ablated AlN plumes, T.M. Di Palma, S. Orlando, A. Giardini-Guidoni, A.J. Paul, J.W. Hastie and A. Mele 86 (1995) 68
- Pulsed laser deposition of metal and metal multilayer films, J.G. Lunney 86 (1995) 79
- Comparison of the structure of laser deposited and sputtered metallic alloys, H.-U. Krebs, O. Bremert, M. Störmer and Y. Luo 86 (1995) 90
- Erbium oxide thin films on Si(100) obtained by laser ablation and electron beam evaporation, X. Queralt, C. Ferrater, F. Sánchez, R. Aguiar, J. Palau and M. Varela 86 (1995) 95
- Effects of laser wavelength and fluence on the growth of ZnO thin films by pulsed laser deposition, V. Craciun, S. Amirhaghi, D. Craciun, J. Elders, J.G.E. Gardeniers and I.W. Boyd 86 (1995) 99
- Influence of ion bombardment on the refractive index of laser pulse deposited oxide

- films, G. Reisse, S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz 86 (1995) 107
- Influence of LN_2 substrate cooling on optical properties of laser-pulse-deposited oxide films, G. Reisse, S. Weissmantel, B. Keiper, B. Steiger, H. Johansen, T. Martini and R. Scholz 86 (1995) 114
- Excimer laser sputtering deposition of TiO_2 optical coating for solar cells, H.-A. Durand, J.-H. Brimaud, O. Hellman, H. Shibata, S. Sakuragi, Y. Makita, D. Gesbert and P. Meyrueis 86 (1995) 122
- SiO_2 film deposition by XeCl laser ablation of fused silica, P. Baeri, R. Reitano and N. Marino 86 (1995) 128
- SEM observations of YBCO on as-received and heat-treated MgO substrates, S. King, L. Coccia and I.W. Boyd 86 (1995) 134
- Pulsed laser deposition and nanometer scale characterization of $\text{YBa}_2\text{Cu}_3\text{O}_{7-\delta}$ thin films by scanning probe methods, R. Sum, H.P. Lang and H.-J. Güntherodt 86 (1995) 140
- Structural properties of LiNbO_3 thin films grown by the pulsed laser deposition technique, P. Aubert, G. Garry, R. Bisaro and J. Garcia Lopez 86 (1995) 144
- Pulsed laser deposition of epitaxial layers of ZnSe, J.L. Deiss, A. Chergui, L. Koutti, J.L. Loison, M. Robino and J.B. Grun 86 (1995) 149
- Comparison of epitaxial films of $\text{Zn}_{1-x}\text{Mn}_x\text{Te}$ on (111) and (100) GaAs produced by pulsed laser deposition, H.J. Masterson and J.G. Lunney 86 (1995) 154
- Pulsed laser deposition of NbTe_x thin films, F. Grangeon, H. Sassoli, Y. Mathey, M. Autric, D. Pailharey and W. Marine 86 (1995) 160
- Structure and chemical composition of BN thin films grown by pulsed-laser deposition (PLD), T. Klotzbücher, W. Pflögging, M. Mertin, D.A. Wesner and E.W. Kreutz 86 (1995) 165
- $\text{Si}_{1-x}\text{Ge}_x$ thin films deposited by the pulsed excimer laser ablation technique, F. Antoni, E. Fogarassy, C. Fuchs, B. Prévot and J.P. Stoquert 86 (1995) 175
- Effect of laser power density and deposition temperature on electrical and optical properties of pulsed laser ablated diamond-like carbon films, J. Levoska and S. Leppävuori 86 (1995) 180
- In-situ spectroscopic ellipsometry to control the growth of Ti nitride and carbide thin films, S. Logothetidis, I. Alexandrou and J. Stoemenos 86 (1995) 185
- Pulsed-laser deposition and characterization of TaC films, R. Teghil, L. D'Alessio, G. De Maria and D. Ferro 86 (1995) 190
- Metal pattern deposition by laser-induced forward transfer, Z. Kántor, Z. Tóth and T. Szörényi 86 (1995) 196
- New approach of a laser-induced forward transfer for deposition of patterned thin metal films, H. Esrom, J.-Y. Zhang, U. Kogelschatz and A.J. Pedraza 86 (1995) 202
- Laser-induced forward transfer of ultra-fine diamond particles for selective deposition of diamond films, S.M. Pimenov, G.A. Shafeev, A.A. Smolin, V.I. Konov and B.K. Vodolaga 86 (1995) 208
- Atypical characteristics of KrF excimer laser ablation of indium-tin oxide films, T. Szörényi, Z. Kántor and L.D. Laude 86 (1995) 219
- Excimer laser ablation patterning of dielectric layers, J. Ihlemann and B. Wolff-Rottke 86 (1995) 228
- UV photo-annealing of thin sol-gel films, R.E. Van de Leest 86 (1995) 278
- Improvement of silicon oxide film properties by ultraviolet excimer lamp annealing, E.G. Parada, P. González, J. Serra, B. León, M. Pérez-Amor, J. Flicstein and R.A.B. Devine 86 (1995) 294
- Diffusion and reactions in thin films, A.L. Greer 86 (1995) 329
- Morphology of $\text{Si}_{1-x}\text{Ge}_x$ thin crystalline films obtained by pulsed-excimer-laser annealing of heavily Ge-implanted Si, E.L. Mathé, A. Naudon, F. Repplinger and E. Fogarassy 86 (1995) 338
- Formation of poly- $\text{Si}_{1-x}\text{Ge}_x$ using excimer-laser processing, A. Slaoui, C. Deng, S. Talwar, K.J. Kramer, T.W. Sigmon, J.P. Stoquert and B. Prevot 86 (1995) 346
- Enhanced adherence of electroless metal deposit on SiO_2 via control of the chemical environment of the Pd seeding layer, G.A. Shafeev, L. Bellard, J.-M. Themlin, W. Marine and A. Cros 86 (1995) 387
- Laser-assisted selective metallisation of diamonds by electroless Ni and Cu plating, G.A. Shafeev, S.M. Pimenov and E.N. Loubnin 86 (1995) 392
- Laser-induced surface modification and metallization of polymers, H. Frerichs, J. Stricker, D.A. Wesner and E.W. Kreutz 86 (1995) 405
- Thin films of polymer blends: surface treatment and theoretical modeling, P. Viville, O. Thoelen, S. Beauvois, R.

- Lazzaroni, G. Lambin, J.L. Brédas, K. Kolev and L. Laude 86 (1995) 411
- Electrochemical and photoelectrochemical modification and characterisation of thin passive films, O. Blum and U. König 86 (1995) 417
- UV light irradiation effects on nucleation during chemical vapor deposition of Al films, M. Hanabusa and A. Komatsu 86 (1995) 428
- Photoassisted growth of II-VI semiconductor films, Sz. Fujita and Sg. Fujita 86 (1995) 431
- GaAs growth by photon-assisted metalorganic molecular beam epitaxy using ethyl derivatives of gallium and arsenic, F. Maury, K. Bouabid, N. Fazouan, A.M. Gué and D. Estève 86 (1995) 447
- Laser processing of tungsten from WF_6 and SiH_4 , M. Meunier, P. Desjardins, M. Tabbal, N. Elyaagoubi, R. Izquierdo and A. Yelon 86 (1995) 475
- Deposition of gold on polyimide from solutions, S. Pflüger, M. Wehner, F. Jansen, Th. Kruck and F. Lupp 86 (1995) 504
- Excimer laser-induced deposition of copper from $Cu(hfac)(TMVS)$, R. Izquierdo, J. Bertomeu, M. Suys, E. Sacher and M. Meunier 86 (1995) 509
- Laser induced deposition of nanocrystalline Si with preferred crystallographic orientation, S. Tamir and S. Berger 86 (1995) 514
- Laser chemical etching of Cu_2O , G. Stenberg, M. Boman, M. Ottosson and J.-O. Carlsson 86 (1995) 543
- In-situ laser reflectometry of the epitaxial growth of thin semiconductor films, T. Farrell and J.V. Armstrong 86 (1995) 582
- Laser diagnostics of C_{60} and C_{70} films by broadband surface acoustic wave spectroscopy, A.A. Kolomenskii, M. Szabadi and P. Hess 86 (1995) 591
- 16 MB DRAM trench depth characterization using dome scatterometry, Z.R. Hatab, S.L. Prins, S.S.H. Naqvi and J.R. McNeil 86 (1995) 597
- P-doped polycrystalline silicon films obtained at low temperature by hot-wire chemical vapor deposition, J. Puigdollers, J. Cifre, M.C. Polo, J.M. Asensi, J. Bertomeu, J. Andreu and A. Lloret 86 (1995) 600
- Atom probe and field emission electron spectroscopy studies of semiconductor films on metals, M. Ashino, M. Tomitori and O. Nishikawa 87/88 (1995) 12
- Electron field emission (FE) from quantum size systems, L.G. Il'chenko, Yu.V. Kryuchenko and V.G. Litovchenko 87/88 (1995) 53
- Comparison of NFIM and FIM of polymer layers with tetracyanoethylene and benzene as image gases, A. Theiss, F. Okuyama and F.W. Röllgen 87/88 (1995) 146
- APFIM study of the compositional inhomogeneity of sputtered Co-Cr magnetic thin film, A. Pundt and C. Michaelson 87/88 (1995) 264
- Plasma-enhanced reactively evaporated deposition of SiO_2 films, A.A. Shklyayev and A.S. Medvedev 89 (1995) 49
- Characterization of thin Ag films deposited onto $InP(001)-p(2 \times 4)$ surface at room temperature by means of LEED, RHEED, AES and RBS-channeling techniques, M. Hanebuchi, T. Katoh and K. Morita 89 (1995) 113
- Temperature-programmed desorption and decomposition of NH_3 over molybdenum nitride films, H.J. Lee, J.-G. Choi, C.W. Colling, M.S. Mudholkar and L.T. Thompson 89 (1995) 121
- Thermal effects on structural characterization of evaporated CdTe films during and after deposition, A. Ashour, M.R. Ebeid, N. El-Kadry, M.F. Ahmed and A.A. Ramadan 89 (1995) 159
- Preparation of a model Ziegler-Natta catalyst. Surface science studies of magnesium chloride thin film deposited on gold and its interaction with titanium chloride, E. Magni and G.A. Somorjai 89 (1995) 187
- Quantitative correction of backscattering in Auger electron spectroscopy of thin films, G. Lévêque and J. Bonnet 89 (1995) 211
- Dependence of electromigration rate on applied electric potential, B.H. Jo and R.W. Vook 89 (1995) 237
- XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. I. Hydrogen treatments on a 10 Å thick film, P.C. Wong, Y.S. Li, M.Y. Zhou and K.A.R. Mitchell 89 (1995) 255
- XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. II. Effects of heating a 26 Å thick film after treatment with a hydrogen plasma, Y.S. Li, P.C. Wong and K.A.R. Mitchell 89 (1995) 263
- Cadmium selenide-amorphous hydrogenated silicon heterostructures, S. Wu and D. Haneman 89 (1995) 289
- Interfacial reaction of NiO with $Al_2O_3(11\bar{2}0)$ and polycrystalline $\alpha-Al_2O_3$, P.H. Bolt, S.F. Lobner, J.W. Geus and F.H.P.M. Habraken 89 (1995) 339

- Interaction of oxygen and silver on the V(100) surface, T. Valla, P. Pervan and M. Milun 89 (1995) 375
- Tantalum oxide film formation by excimer laser ablation, Y. Nishimura, H. Ujita and M. Tsuji 89 (1995) 393
- Characterization of nickel films deposited by cold remote nitrogen plasma on acrylonitrile-butadiene-styrene copolymer, A. Brocherieux, O. Dessaux, P. Goudmand, L. Gengembre, J. Grimblot, M. Brunel and R. Lazzaroni 90 (1995) 47
- Ferroelectric BaTiO₃ films with a high-magnitude dielectric constant grown on p-Si by low-pressure metalorganic chemical vapor deposition, T.W. Kim, Y.S. Yoon, S.S. Yom and C.O. Kim 90 (1995) 75
- Multiple losses in off-specular electron energy loss spectra of thin NaCl films individually resolved in energy and momentum, V. Zielasek, A. Büssenschütt and M. Henzler 90 (1995) 117
- Conversion film formation on titanium anodes in acetonitrile at high voltages, F. Schlottig, J. Schreckenbach, D. Dietrich, A. Hofmann and G. Marx 90 (1995) 129
- Pulse plasma beam deposition of cubic boron nitride films on GCr15 steel bearing substrate at room temperature, P. Yan and S.-Z. Yang 90 (1995) 149
- An ellipsometric procedure for the characterization of very thin surface films on absorbing substrates, T. Easwarakhanthan, S. Ravelet and P. Renard 90 (1995) 251
- Atomic hydrogen adsorption on sintered thin copper films, R. Duś, E. Nowicka, W. Lisowski and Z. Wolfram 90 (1995) 277
- Characterization of ex-situ hydrogenated amorphous SiC thin films by X-ray photoelectron spectroscopy, S. Kennou, S. Ladas, E.C. Paloura and J.A. Kalomiros 90 (1995) 283
- Scanned laser spot photocurrent response studies of surface modifications of CdSe thin film electrodes, X.R. Xiao, Y. Lin, Y. Yang, X.G. Chen and J.K. You 90 (1995) 321
- The influence of the substrate material on the growth of V₂O₅ flash-evaporated films, C. Julien, J.P. Guesdon, A. Gorenstein, A. Khelifa and I. Ivanov 90 (1995) 389
- Rapid thermal nitridation of thin chromium films, S.W. Russell, J. Li, T.L. Alford, P.R. Oakey and S.C. Shatas 90 (1995) 455
- Characterization of RuO₂ thin films by Raman spectroscopy, S.Y. Mar, C.S. Chen, Y.S. Huang and K.K. Tiong 90 (1995) 497
- Characterization of the plasma plume and of thin film epitaxially produced during laser ablation of SnSe, R. Teghil, A. Santagata, V. Marotta, S. Orlando, G. Pizzella, A. Giardini-Guidoni and A. Mele 90 (1995) 505
- Time of flight techniques*
- Pulsed trimethylgallium scattering from As-stabilized and Ga-stabilized surfaces, M. Sasaki and S. Yoshida 82/83 (1994) 269
- Surface characterization by time-of-flight SIMS of a catalyst for oxygen electroreduction: pyrolyzed cobalt phthalocyanine-on-carbon black, L.T. Weng, P. Bertrand, G. Lalande, D. Guay and J.P. Dodelet 84 (1995) 9
- A multitechnique analysis of the outermost layers of the Teflon PFA surface, K. Piyakis, E. Sacher, A. Domingue, J.-J. Pireaux, G. Leclerc, P. Bertrand and J.B. Lhoest 84 (1995) 227
- Composition of sputtered material from Cu-Ni alloy during Xe⁺ ion sputtering at elevated temperatures, S. Sekine, H. Shimizu and S. Ichimura 84 (1995) 401
- Total cross-section measurements for positrons and electrons colliding with molecules: CCl₄, A. Hamada and O. Sueoka 85 (1995) 64
- Generation of an intense pulsed positron beam for positron lifetime and TOF experiments, R. Suzuki, T. Mikado, M. Chiwaki, H. Ohgaki and T. Yamazaki 85 (1995) 87
- Time of flight mass spectrometry and covariance mapping technique investigation of charged specie evolution in Pb(Ti_{0.48}Zr_{0.52})O₃ laser ablation, S. Amoruso, V. Berardi, N. Spinelli, R. Velotta, M. Armenante, F. Fuso, M. Allegri and E. Arimondo 86 (1995) 35
- Study of PbTe(Ga) evaporation using a nanosecond pulsed laser, V.A. Mikhailov, F.N. Putilin and D.N. Trubnikov 86 (1995) 64
- Surface reaction control in digital etching of GaAs by using a tunable UV laser system: reaction control mechanism in layer-by-layer etching, M. Ishii, T. Meguro, T. Sugano, K. Gamo and Y. Aoyagi 86 (1995) 554
- The performance of the IMR three-dimensional atom probe, K. Hono, R. Okano, T. Saeda and T. Sakurai 87/88 (1995) 453
- A quantitative time-of-flight secondary ion mass spectrometry study of ion formation mechanisms using acid-base alternating Langmuir-Blodgett films, J.-X. Li, J.A. Gardella, Jr. and P.J. McKeown 90 (1995) 205

Tin

- Nucleation and growth of θ' precipitation in Sn-modified Al-Cu alloys: APFIM/TEM observations, S.P. Ringer, K. Hono and T. Sakurai 87/88 (1995) 223
- SIMS microprofiles of Pb-5%Sn solder joints in electronic devices after accelerated life tests, A. Scandurra, A. Porto and O. Puglisi 89 (1995) 1
- Erratum to "Nucleation and growth of θ' precipitation in Sn-modified Al-Cu alloys: APFIM/TEM observations" [Appl. Surf. Sci. 87/88 (1995) 223], S.P. Ringer, K. Hono and T. Sakurai 90 (1995) 107
- Characterization of the plasma plume and of thin film epitaxially produced during laser ablation of SnSe, R. Teghil, A. Santagata, V. Marotta, S. Orlando, G. Pizzella, A. Giardini-Guidoni and A. Mele 90 (1995) 505

Tin oxide

- Are modulations of the Schottky surface barrier the only explanation for the gas-sensing effects in sintered SnO_2 ?, R. Ionescu, C. Moise and A. Vancu 84 (1995) 291
- Atypical characteristics of KrF excimer laser ablation of indium-tin oxide films, T. Szörényi, Z. Kántor and L.D. Laude 86 (1995) 219

Titanium

- Sulfur segregation in titanium and selected titanium alloys, R.A. Outlaw, W.S. Lee, S.J. Hoekje and S.N. Sankaran 81 (1994) 143
- Structural study of $\text{SrTiO}_3(100)$ surfaces by low energy ion scattering, Y. Tanaka, H. Morishita, M. Watamori, K. Oura and I. Katayama 82/83 (1994) 528
- Surface characterisation of plasma-nitrided titanium: an XPS study, I. Bertóti, M. Mohai, J.L. Sullivan and S.O. Saied 84 (1995) 357
- Study on the mechanical and chemical properties of (Ti,Al)N films prepared by DC magnetron sputtering, S. Jiang, D. Peng, X. Zhao, L. Xie and Q. Li 84 (1995) 373
- Time of flight mass spectrometry and covariance mapping technique investigation of charged specie evolution in $\text{Pb}(\text{Ti}_{0.48}\text{Zr}_{0.52})\text{O}_3$ laser ablation, S. Amoroso, V. Berardi, N. Spinelli, R. Velotta, M. Armenante, F. Fusco, M. Al-legrini and E. Arimondo 86 (1995) 35

- Laser ablation of refractory material, cluster formation and deposition, H. Yu, M.G. Huber and F.W. Froben 86 (1995) 74
- Electrochemical and photoelectrochemical modification and characterisation of thin passive films, O. Blum and U. König 86 (1995) 417
- APFIM investigations on ordered γ -TiAl using single-layer detection method, J. Wesemann, G. Frommeyer and M. Kreuss 87/88 (1995) 179
- A study of the composition distribution at the Ti/ Al_2O_3 interface using the MCs^+ -SIMS technique, X. Chen and Y. Wang 89 (1995) 169
- Preparation of a model Ziegler-Natta catalyst. Surface science studies of magnesium chloride thin film deposited on gold and its interaction with titanium chloride, E. Magni and G.A. Somorjai 89 (1995) 187
- Ferroelectric BaTiO_3 films with a high-magnitude dielectric constant grown on p-Si by low-pressure metalorganic chemical vapor deposition, T.W. Kim, Y.S. Yoon, S.S. Yom and C.O. Kim 90 (1995) 75
- Recovery and recrystallization of $\text{SrTiO}_3(100)$ surface characterized by ion channeling, F. Wang, M. Badaye, K. Ogawa and T. Morishita 90 (1995) 123
- Conversion film formation on titanium anodes in acetonitrile at high voltages, F. Schlottig, J. Schreckenbach, D. Dietrich, A. Hofmann and G. Marx 90 (1995) 129

Titanium carbide

- In-situ spectroscopic ellipsometry to control the growth of Ti nitride and carbide thin films, S. Logothetidis, I. Alexandrou and J. Stoemenos 86 (1995) 185

Titanium dioxide

- A photoemission study of electron states in Sb-ion implanted $\text{TiO}_2(110)$, A.E. Taverner, A. Gulino, R.G. Egdell and T.J. Tate 90 (1995) 383

Titanium nitride

- Effects of atomic hydrogen on Cu(II)bis-hexafluoroacetylacetonate interactions with a TiN surface, G. Nuesca, J. Prasad and J.A. Kelber 81 (1994) 237
- Oxidation of TiN thin films in an ion-beam-assisted deposition process, H.

Kubota, M. Nagata, R. Miyagawa and M.A. Nicolet

82/83 (1994) 565

Positron beam spectroscopy for the assessment of the structure and defect density of titanium nitride, P.C. Rice-Evans, A.S. Saleh and S.J. Bull

85 (1995) 320

In-situ spectroscopic ellipsometry to control the growth of Ti nitride and carbide thin films, S. Logothetidis, I. Alexandrou and J. Stoemenos

86 (1995) 185

Conversion film formation on titanium anodes in acetonitrile at high voltages, F. Schlottig, J. Schreckenbach, D. Dietrich, A. Hofmann and G. Marx

90 (1995) 129

Titanium oxide

Excimer laser sputtering deposition of TiO₂ optical coating for solar cells, H.-A. Durand, J.-H. Brimaud, O. Hellman, H. Shibata, S. Sakuragi, Y. Makita, D. Gesbert and P. Meyrueis

86 (1995) 122

Formation of Ti³⁺ ions at the surface of laser-irradiated rutile, T. Le Mercier, J.-M. Mariot, P. Parent, M.-F. Fontaine, C.F. Hague and M. Quarton

86 (1995) 382

Deposition by laser ablation and characterization of titanium dioxide films on polyethylene-terephthalate, N. Lobstein, E. Millon, A. Hachimi, J.F. Muller, M. Alnot and J.J. Ehrhardt

89 (1995) 307

The chemical interaction between plasma-excited nitrogen and the surface of titanium dioxide, S. Kameoka, T. Kuriyama, M. Kuroda, S. Ito and K. Kunitomi

89 (1995) 411

Surface segregation of Sb in doped TiO₂ rutile, A. Gulino, G.G. Condorelli, I. Fragalà and R.G. Egdell

90 (1995) 289

XPS oxygen line broadening in lead zirconium titanate and related materials, A. Zomorrodian, A. Mesarwi, N.J. Wu and A. Ignatiev

90 (1995) 343

Transition metals

A simple approach to the calculation of surface defect energies in transition metals, M.C. Desjonquères, D. Spanjaard, B. Piveteau and S. Papadia

87/88 (1995) 337

Photoemission studies on Pt foil implanted by carbon atoms accelerated in a Van de Graaff generator: nature of the interaction between Pt and carbon, R. Sundararajan, G. Pető, E. Koltay and L. Guzzi

90 (1995) 165

Tribology

Multi-spectral scanning Auger microscopy of tribological surfaces, I.R. Barkshire, M. Prutton and G.C. Smith

84 (1995) 331

Tungsten

A Raman microprobe study of the electrochromic and photochromic thin films of molybdenum trioxide and tungsten trioxide, B.H. Loo, J.N. Yao, H.D. Coble, K. Hashimoto and A. Fujishima

81 (1994) 175

Surface structure dependence of O₂-W adsorption system, M. Sato

82/83 (1994) 532

Laser processing of tungsten from WF₆ and SiH₄, M. Meunier, P. Desjardins, M. Tabbal, N. Elyaagoubi, R. Izquierdo and A. Yelon

86 (1995) 475

Laser-induced etching and deposition of tungsten in WF₆-H₂ atmosphere, K. Piglmayer, Z. Tóth and Z. Kantor

86 (1995) 484

Adsorption studies of iron on tungsten by probe-hole field emission microscopy, A.D. Adsool, R. Pande, R.B. Sharma, M.A. More and D.S. Joag

87/88 (1995) 37

Probe hole field electron/field ion microscopy and energy spectroscopy of ultrasharp [111]-oriented tungsten tips, J. Unger, Yu.A. Vlasov and N. Ernst

87/88 (1995) 45

A FEM study of liquid lithium on a <011>-oriented tungsten tip, K. Hata, M. Kumamura, T. Yasuda, Y. Saito and A. Ohshita

87/88 (1995) 117

M-S (M = Mo, W) cluster compound films on copper surfaces, X.R. Ye, H.W. Hou, X.Q. Xin and C.F. Hammer

89 (1995) 151

Charge transfer processes in a-WO₃/Si heterostructure during electro- and photochromism, E.A. Tutov and A.A. Baev

90 (1995) 303

Tunneling

Electron tunneling in double-barrier diode, Liu Yunpeng and Luo Enze

87/88 (1995) 75

Vanadium

Interaction of oxygen and silver on the V(100) surface, T. Valla, P. Pervan and M. Milun

89 (1995) 375

Vanadium oxide

The influence of the substrate material on the growth of V₂O₅ flash-evaporated

films, C. Julien, J.P. Guesdon, A. Gorenstein, A. Khelfa and I. Ivanov

90 (1995) 389

Water

Electron-beam-induced oxidation of CdS, V.B. Mityukhlyev

81 (1994) 137

The hydroxylation of Cu(111) and Zn(0001) surfaces, A.F. Carley, P.R. Davies, M.W. Roberts, N. Shukla, Y. Song and K.K. Thomas

81 (1994) 265

Room-temperature water adsorption on the Si(100) surface examined by UPS, XPS, and static SIMS, R.K. Schulze and J.F. Evans

81 (1994) 449

Adsorption and desorption of H₂O on potassium precovered Si(100)2 × 1 surface, S. Hongo, S. Taniguchi, K. Ojima, T. Urano and T. Kanaji

82/83 (1994) 437

Nucleation and island growth during water adsorption at sub-monolayer coverages, R.V. Kasza, K. Griffiths, V.P. Zhdanov and P.R. Norton

84 (1994) 97

Quantitative analysis of the thermal degassing of a beryllium powder, L. Buisson, P. Bracconi and X. Claudon

84 (1995) 211

Coadsorption of water and selected aromatic molecules to model the adhesion of epoxy resins on hydrated surfaces of zinc oxide and iron oxide, M. Nakazawa and G.A. Somorjai

84 (1995) 309

Field-induced redistribution and diffusion of water on a Pt field emitter, R. Bryl, T. Wysocki and R. Błaszczyszyn

87/88 (1995) 69

Field-induced oxygen layer formation from H₂O and its titration by hydrogen on a Pt-emitter, V. Gorodetskii, N. Ernst, W. Drachsel and J.H. Block

87/88 (1995) 151

Surface reactions on palladium hydride in vacuum, air and water studied in situ with mass spectrometry, L. Gråsjö, G. Hultquist, K.L. Tan and M. Seo

89 (1995) 21

Work function

Work function and epitaxial positron emission from copper, N. Overton, A.P. Knights, A. Goodyear and P.G. Coleman

85 (1995) 54

Method for the measurement of positron affinities and positron work functions suitable for both positive and negative work function materials, A.H. Weiss, S. Yang, H.Q. Zhou, E. Jung, A.R. Koy-men, S. Naidu, G. Brauer and M.J. Puska

85 (1995) 82

Adsorption studies of iron on tungsten by probe-hole field emission microscopy, A.D. Adsool, R. Pande, R.B. Sharma, M.A. More and D.S. Joag

87/88 (1995) 37

Xenon

Silicon surface cleaning using XeF₂ gas treatment, V.S. Aliev, M.R. Baklanov and V.I. Bukhtiyarov

90 (1995) 191

X-ray diffraction

Origin of residual stress in a textured Au thin film on a LiF substrate, N. Durand, K.F. Badawi, A. Declémy and Ph. Goudeau

81 (1994) 119

Diamond nucleation and growth at the early stages on Si(100) monitored by electron spectroscopies, F. Le Normand, A. Ababou, N. Brault, B. Carrière, L. Fayette, B. Marcus, M. Mermoux, M. Romeo and C. Speisser

81 (1994) 309

A study of CaO-SO₂ interaction in the presence of O₂, M.J. Muñoz-Guillena, A. Linares-Solano and C. Salinas-Martínez de Lecea

81 (1994) 417

Growth temperature dependence of optical properties of gas source MBE grown GaP/AlP short period superlattices, J.H. Kim, H. Asahi, K. Asami, K. Iwata, S.G. Kim and S. Gonda

82/83 (1994) 76

Selective epitaxial growth of GaInP by LP-MOCVD using ethyldimethylindium, trimethylindium, trimethylgallium and triethylgallium as group III sources, S.-H. Chan, S.M. Sze, C.-Y. Chang and W.-I. Lee

82/83 (1994) 85

Microscopic analysis of interface structure in InGaAs/InP MQW using Pendellösung oscillation around a satellite peak in high-resolution X-ray diffraction, M. Takemi, T. Kimura, K. Mori, K. Goto, Y. Mihashi and S. Takamiya

82/83 (1994) 115

Growth of In₂S₃ thin films by atomic layer epitaxy, T. Asikainen, M. Ritala and M. Leskelä

82/83 (1994) 122

Role of a metalorganic As source in atomic layer epitaxy of GaAs and AlAs, I. Sue-mune

82/83 (1994) 149

Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi

82/83 (1994) 494

Fabrication of CuO₂-plane-based high-temperature superconducting thin films by

- atomic layer controlled molecular beam epitaxy, I. Yoshida, H. Furukawa, T. Hirose and M. Nakao 82/83 (1994) 501
- The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen 82/83 (1994) 553
- Surface analysis of commercial lead/acid battery grids, R. De Marco and J. Liesegang 84 (1995) 237
- Solution growth and characterization of silver sulfide films, I. Grodzanov 84 (1995) 325
- Study on the mechanical and chemical properties of (Ti,Al)N films prepared by DC magnetron sputtering, S. Jiang, D. Peng, X. Zhao, L. Xie and Q. Li 84 (1995) 373
- The laser ablation threshold of $\text{YBa}_2\text{Cu}_3\text{O}_{6+x}$ as revealed by using projection optics, B. Dam, J. Rector, M.F. Chang, S. Kars, D.G. de Groot and R. Griessen 86 (1995) 13
- Laser ablation of BiSrCaCuO superconducting thin film: analysis of intermediate species in real time, U. Gambardella, A. Giardini, V. Marotta, A. Morone, S. Orlando and M. Snels 86 (1995) 45
- Comparison of the structure of laser deposited and sputtered metallic alloys, H.-U. Krebs, O. Bremert, M. Störmer and Y. Luo 86 (1995) 90
- Erbium oxide thin films on Si(100) obtained by laser ablation and electron beam evaporation, X. Queralt, C. Ferrater, F. Sánchez, R. Aguiar, J. Palau and M. Varela 86 (1995) 95
- Effects of laser wavelength and fluence on the growth of ZnO thin films by pulsed laser deposition, V. Craciun, S. Amirhaghi, D. Craciun, J. Elders, J.G.E. Gardeniers and I.W. Boyd 86 (1995) 99
- Structural properties of LiNbO_3 thin films grown by the pulsed laser deposition technique, P. Aubert, G. Garry, R. Bisaro and J. Garcia Lopez 86 (1995) 144
- Pulsed laser deposition of epitaxial layers of ZnSe, J.L. Deiss, A. Chergui, L. Koutti, J.L. Loison, M. Robino and J.B. Grun 86 (1995) 149
- Comparison of epitaxial films of $\text{Zn}_{1-x}\text{Mn}_x\text{Te}$ on (111) and (100) GaAs produced by pulsed laser deposition, H.J. Masterson and J.G. Lunney 86 (1995) 154
- Pulsed laser deposition of NbTe_x thin films, F. Grangeon, H. Sassoli, Y. Mathey, M. Autric, D. Pailharey and W. Marine 86 (1995) 160
- Excimer laser reactive ablation deposition of silicon nitride films, E. D'Anna, G. Leggieri, A. Luches, M. Martino, A. Perrone, G. Majni, P. Mengucci, R. Alexandrescu, I.N. Mihailescu and J. Zemek 86 (1995) 170
- Pulsed-laser deposition and characterization of TaC films, R. Teghil, L. D'Alessio, G. De Maria and D. Ferro 86 (1995) 190
- Morphology of $\text{Si}_{1-x}\text{Ge}_x$ thin crystalline films obtained by pulsed-excimer-laser annealing of heavily Ge-implanted Si, E.L. Mathé, A. Naudon, F. Repplinger and E. Fogarassy 86 (1995) 338
- Surface properties of excimer-laser-irradiated sintered alumina, L.D. Laude, K. Kolev, M. Brunel and P. Deleter 86 (1995) 368
- Photoassisted metalorganic vapor-phase epitaxy of ZnSe on GaAs, J.E. Bourée, R. Helbing, W. Kuhn and O. Gorochov 86 (1995) 437
- P-doped polycrystalline silicon films obtained at low temperature by hot-wire chemical vapor deposition, J. Puigdollers, J. Cifre, M.C. Polo, J.M. Asensi, J. Bertomeu, J. Andreu and A. Lloret 86 (1995) 600
- Thermal effects on structural characterization of evaporated CdTe films during and after deposition, A. Ashour, M.R. Ebeid, N. El-Kadry, M.F. Ahmed and A.A. Ramadan 89 (1995) 159
- Activation treatments and surface study of amorphous $\text{Fe}_{90}\text{Zr}_{10}$ and $\text{Fe}_{87.8}\text{Zr}_{10}\text{Co}_{2-\text{Al}_{0.2}}$ catalysts, X.K. Wang, N.F. Shen, Z.S. Yang and H.C. Gu 89 (1995) 297
- Deposition by laser ablation and characterization of titanium dioxide films on polyethylene-terephthalate, N. Lobstein, E. Millon, A. Hachimi, J.F. Muller, M. Alnot and J.J. Ehrhardt 89 (1995) 307
- Interfacial reaction of NiO with $\text{Al}_2\text{O}_3(11\bar{2}0)$ and polycrystalline $\alpha\text{-Al}_2\text{O}_3$, P.H. Bolt, S.F. Lobner, J.W. Geus and F.H.P.M. Habraken 89 (1995) 339
- Ferroelectric BaTiO_3 films with a high-magnitude dielectric constant grown on p-Si by low-pressure metalorganic chemical vapor deposition, T.W. Kim, Y.S. Yoon, S.S. Yom and C.O. Kim 90 (1995) 75
- Synthesis of molybdenum nitride $\gamma\text{-Mo}_2\text{N}$ by multipulse laser irradiation of molybdenum in nitrogen, J.D. Wu, C.Z. Wu, Z.M. Song, L.H. Wu and F.M. Li 90 (1995) 81
- Surface studies of oil-seal degradation, G.C. Smith, D. Park, K.J. Titchener, R.E. Davies and R.H. West 90 (1995) 357
- Lateral composition modulation in InGaAsP deposited by gas source molecular beam epitaxy on (100)- and (h11)-oriented InP substrates, R.R. LaPierre, B.J. Robinson and D.A. Thompson 90 (1995) 437
- Characterization of the plasma plume and of thin film epitaxially produced during

- laser ablation of SnSe, R. Teghil, A. Santagata, V. Marotta, S. Orlando, G. Pizzella, A. Giardini-Guidoni and A. Mele 90 (1995) 505
- X-ray fluorescence*
- Grafting onto the surface of plasma-modified fillers, G. Ji, J. Fang, S. Cai and G. Xue 81 (1994) 63
- The effect of growth parameters on the deposition of CaS thin films by atomic layer epitaxy, J. Rautanen, M. Leskelä, L. Niinistö, E. Nykänen, P. Soininen and M. Utriainen 82/83 (1994) 553
- X-ray scattering*
- Surface fractal dimension of sintered porous solid niobium, L.I. Skatkov, V.V. Konotop, P.G. Cheremskoy, V.P. Gomofov and B.I. Bayrachny 81 (1994) 427
- An X-ray scattering study of SiO_x/Si/Ge(001), S.D. Kosowsky, C.-H. Hsu, P.S. Pershan, J. Bevk and B.S. Freer 84 (1995) 179
- X-ray spectroscopy*
- Grafting onto the surface of plasma-modified fillers, G. Ji, J. Fang, S. Cai and G. Xue 81 (1994) 63
- Combined use of XPS, IR and EDAX techniques for the characterization of ZrO₂-SiO₂ powders prepared by a sol-gel process, J.A. Navío, M. Macías, G. Colón, P.J. Sánchez-Soto, V. Augugliaro and L. Palmisano 81 (1994) 325
- NbCl₅ as a precursor in atomic layer epitaxy, K.-E. Elers, M. Ritala, M. Leskelä and E. Rauhala 82/83 (1994) 468
- Preparation of ultra-flat YBCO thin films by MOCVD layer-by-layer deposition, M. Matsubara and I. Hirabayashi 82/83 (1994) 494
- Laser deposition of metallic alloys and multilayers, H.-U. Krebs, S. Fähler and O. Bremert 86 (1995) 86
- Formation of Ti³⁺ ions at the surface of laser-irradiated rutile, T. Le Mercier, J.-M. Mariot, P. Parent, M.-F. Fontaine, C.F. Hague and M. Querton 86 (1995) 382
- Photoassisted metalorganic vapor-phase epitaxy of ZnSe on GaAs, J.E. Bourée, R. Helbing, W. Kuhn and O. Gorochov 86 (1995) 437
- The effect of process parameters on the O/Mo ratio in laser deposition of molybdenum oxides from aqueous solutions, K. Bali, Zs. Geretovszky, A.L. Tóth and T. Szörényi 86 (1995) 500
- X-ray standing wave*
- LiBr on Si(111): an X-ray standing wave measurement, Th. Gog, G.C. Follis and S.M. Durbin 81 (1994) 485
- Yttrium*
- Excimer laser ablation of Nd:YAG and Nd:glass, S.R. Jackson, W.J. Metheringham and P.E. Dyer 86 (1995) 223
- Ultraviolet inverse photoemission study of the oxidation of YFe₂, P. Vavassori, L. Callegaro and E. Puppini 89 (1995) 93
- The effect of anodic polarization on a Ag electrode deposited on YSZ solid electrolyte, J.K. Hong, I.-H. Oh, S.-A. Hong and W.Y. Lee 89 (1995) 229
- Zeolites*
- In-situ FTIR investigation of coke formation on USY zeolite, C. Li, Y.-W. Chen, S.-J. Yang and R.-B. Yen 81 (1994) 465
- Theoretical estimation of ordered metal species in zeolite pores, H. Himei, E. Maruya, M. Kubo, R. Vetrivel and A. Miyamoto 82/83 (1994) 543
- An XPS study of the optimum loading of barium on high-silica MFI zeolite, M.H. Mohamed, M.M. Abdillahi, N.M. Abbas and A.B. Siddiqui 90 (1995) 409
- Zinc*
- XPS study of clean metal sulfide surfaces, K. Laajalehto, I. Kartio and P. Nowak 81 (1994) 11
- The hydroxylation of Cu(111) and Zn(0001) surfaces, A.F. Carley, P.R. Davies, M.W. Roberts, N. Shukla, Y. Song and K.K. Thomas 81 (1994) 265
- Atomic layer epitaxy of ZnSe using reflectance difference spectroscopy, H. Akinaga and K. Tanaka 82/83 (1994) 298
- Surface reaction mechanism in MOMBE-ALE of ZnSe and CdSe as determined by a new in-situ optical probing method, A. Yoshikawa, M. Kobayashi and S. Tokita 82/83 (1994) 316
- Coadsorption of water and selected aromatic molecules to model the adhesion of epoxy resins on hydrated surfaces of

- zinc oxide and iron oxide, M. Nakazawa and G.A. Somorjai 84 (1995) 309
- Blast-wave studies of excimer laser ablation of ZnS, P.E. Dyer, P.H. Key, D. Sands, H.V. Snelling and F.X. Wagner 86 (1995) 18
- Pulsed laser deposition of epitaxial layers of ZnSe, J.L. Deiss, A. Chergui, L. Koutti, J.L. Loison, M. Robino and J.B. Grun 86 (1995) 149
- Comparison of epitaxial films of $\text{Zn}_{1-x}\text{Mn}_x\text{Te}$ on (111) and (100) GaAs produced by pulsed laser deposition, H.J. Masterson and J.G. Lunney 86 (1995) 154
- Photoassisted metalorganic vapor-phase epitaxy of ZnSe on GaAs, J.E. Bourée, R. Helbing, W. Kuhn and O. Gorochov 86 (1995) 437
- Photo-assisted growth and characterization of $\text{Zn}_x\text{Cd}_{1-x}\text{S}$ by MOVPE, H. Dumont, Sz. Fujita and Sg. Fujita 86 (1995) 442
- Laser-induced photodeposition from ZnS colloid solutions, A. Peled, B. Dragnea, R. Alexandrescu and A. Andrei 86 (1995) 538

Zinc oxide

- Waveguide CARS spectroscopy of physisorbed methanol on a partially hydroxylated zinc oxide surface, W.M.K.P. Wijekoon, E.W. Koenig, W.M. Hetherington III and W.R. Salzman 81 (1994) 347
- Atomic layer epitaxy growth of doped zinc oxide thin films from organometals, V. Lujala, J. Skarp, M. Tammenmaa and T. Suntola 82/83 (1994) 34
- CO adsorption on clean and atomic-layer-Cu-covered $\text{ZnO}(10\bar{1}0)$ surfaces, Q. Ge and P.J. Møller 82/83 (1994) 305
- Influence of atomic Cu-layer epitaxy on CO_2 and CO photoinduced desorption from $\text{ZnO}(0001)$, P.J. Møller, S.A. Komolov and E.F. Lazneva 82/83 (1994) 569
- Effects of laser wavelength and fluence on the growth of ZnO thin films by pulsed laser deposition, V. Craciun, S.

- Amirhaghi, D. Craciun, J. Elders, J.G.E. Gardeniers and I.W. Boyd 86 (1995) 99

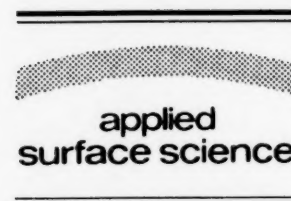
Zirconium

- Combined use of XPS, IR and EDAX techniques for the characterization of $\text{ZrO}_2\text{-SiO}_2$ powders prepared by a sol-gel process, J.A. Navío, M. Macías, G. Colón, P.J. Sánchez-Soto, V. Augugliaro and L. Palmisano 81 (1994) 325
- Time of flight mass spectrometry and covariance mapping technique investigation of charged specie evolution in $\text{Pb}(\text{Ti}_{0.48}\text{Zr}_{0.52})\text{O}_3$ laser ablation, S. Amoroso, V. Berardi, N. Spinelli, R. Velotta, M. Armenante, F. Fusco, M. Allegrini and E. Arimondo 86 (1995) 35
- The effect of anodic polarization on a Ag electrode deposited on YSZ solid electrolyte, J.K. Hong, I.-H. Oh, S.-A. Hong and W.Y. Lee 89 (1995) 229
- XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. I. Hydrogen treatments on a 10 Å thick film, P.C. Wong, Y.S. Li, M.Y. Zhou and K.A.R. Mitchell 89 (1995) 255
- XPS investigations of the interactions of hydrogen with thin films of zirconium oxide. II. Effects of heating a 26 Å thick film after treatment with a hydrogen plasma, Y.S. Li, P.C. Wong and K.A.R. Mitchell 89 (1995) 263
- Activation treatments and surface study of amorphous $\text{Fe}_{90}\text{Zr}_{10}$ and $\text{Fe}_{87.8}\text{Zr}_{10}\text{Co}_{2}\text{-Al}_{0.2}$ catalysts, X.K. Wang, N.F. Shen, Z.S. Yang and H.C. Gu 89 (1995) 297
- Thermal etching of $\alpha\text{-Zr}$ single-crystal surfaces, H. Zou, G.M. Hood, R.J. Schultz and J.A. Roy 90 (1995) 59
- XPS oxygen line broadening in lead zirconium titanate and related materials, A. Zomorrodian, A. Mesarwi, N.J. Wu and A. Ignatiev 90 (1995) 343



ELSEVIER

Applied Surface Science MI 81-90 (1995) 116-118



List of terms used in the subject index

Ablation
Alkali halides
Alkali metals
Alloys
Aluminium
Aluminium oxide
Ammonia
Annealing
Antimony
Argon
Arsenic
Atomic force microscopy
Atomic probe analysis
Auger electron spectroscopy

Barium
Beryllium
Biological materials
Bismuth
Borides
Boron
Boron nitride

Cadmium
Cadmium selenide
Cadmium sulphide
Cadmium telluride
Calcium
Carbides
Carbon
Carbon dioxide
Carbon monoxide
Catalysis
Ceramics
Chemical vapour deposition
Chromium
Clusters
Cobalt

Computer simulations
Copper

Depth profiling
Deuterium
Diamond
Dielectric constant
Diffusion
Doping effects

Elastic recoil detection
Electrical properties
Electromigration
Electron bombardment
Electron diffraction
Electron emission
Electron energy loss spectroscopy
Electron microscopy
Electron spin resonance
Ellipsometry
Epitaxy
Erbium
Etching
Evaporation

Field desorption
Field effect
Field electron microscopy
Field emission
Field emission microscopy
Field evaporation
Field ion microscopy

Gallium
Gallium arsenide
Gallium phosphide
Germanium
Glass

- Gold
Graphite

Hafnium
Halides
Halogenides
Halogens
Helium
Hydrides
Hydrocarbons
Hydrogen

Indium
Indium antimonide
Indium arsenide
Indium phosphide
Infrared spectroscopy
Interfaces
Ion bombardment
Ion implantation
Ion scattering
Iron

Krypton

Langmuir-Blodgett structures
Lanthanides
Laser processing
Lead
Low energy electron diffraction
Luminescence

Magnesium
Magnesium oxide
Magnetic properties
Manganese
Mass spectroscopy
Mercury telluride
Metals
Methane
Methanol
Mica
Molecular dynamics
Molybdenum
Monte Carlo simulations
Mössbauer spectroscopy
Multilayers

Nickel
Niobium

Niobium oxide
Nitric oxide
Nitrides
Nitrogen
Noble gases
Nuclear magnetic resonance
Nuclear reaction analysis
Nucleation

Optical properties
Organic substances
Organometallic vapour deposition
Oxidation
Oxides
Oxygen

Palladium
Phase transitions
Phosphorus
Photochemistry
Photoelectron spectroscopy
Photoemission
Photon emission
Plasma processing
Platinum
Polymers
Positron beams
Positron diffraction
Positron microscopy
Positron scattering
Positron spectroscopy

Quantum effects
Quartz

Radiation damage
Raman scattering
Rhenium
Rhodium
Ruthenium

Scanning tunneling microscopy
Schottky barrier
Secondary ion mass spectrometry
Selenium
Semiconductors
Silane
Silicides
Silicon

Silicon carbide
Silicon nitride
Silicon oxide
Silver
Sputter deposition
Sputtering
Steel
Strontium
Sulphides
Sulphur
Sulphur dioxide
Superconductors
Superconductivity
Superlattices
Surface composition
Surface diffusion
Surface plasmons
Surface segregation
Surface structure

Tantalum
Tellurium
Thermal desorption
Thin films
Time of flight techniques
Tin
Tin oxide
Titanium

Titanium carbide
Titanium dioxide
Titanium nitride
Titanium oxide
Transition metals
Tribology
Tungsten
Tunneling

Vanadium
Vanadium oxide

Water
Work function

Xenon
X-ray diffraction
X-ray fluorescence
X-ray scattering
X-ray spectroscopy
X-ray standing wave

Yttrium

Zeolites
Zinc
Zinc oxide
Zirconium

INSTRUCTIONS FOR AUTHORS

Submission: Contributions must be written in English and should have an abstract. They should be submitted to one of the Editors in triplicate with one set of *original drawings* (no larger than ca. 20×30 cm) of the figures and two sets of duplicate copies. Micrographs should *always* be submitted in triplicate. The Publisher prefers to have an ELECTRONIC FILE of the final text on a 3 1/2" or 5 1/4" diskette. Both double density and high density diskettes are acceptable. There is little restriction on the word processor used. The name and version of the word-processing program, type of computer and format of the files should be clearly indicated. It is the responsibility of the author to ensure that the version on disk exactly matches the paper copies. For editorial addresses, see inside front cover.

Rapid publication: Short papers, for which rapid publication is appropriate, may be submitted as a "Letter to the Editor". The manuscripts should not exceed 1000 words in length, contain a modest number of illustrations and a short abstract.

Copyright transfer: The submission of a paper will be taken to imply that the author has satisfied himself that no copyright will thereby be infringed. Upon acceptance of an article by this journal the author(s) will be asked to transfer copyright of the article to the Publisher. This transfer will ensure the widest possible dissemination of information.

Preparation of manuscripts

- (1) *Manuscripts* should be typed throughout with double line spacing and wide margins on numbered pages.
- (2) *Title page(s)* should contain, in addition to the article title, author(s)' names and affiliations, the text of related footnotes and the text of the abstract. Indicate which author will act as contact author and *provide E-mail No., FAX No. and telephone No.*, if available.
- (3) *Tables* should be typed on separate sheets at the end of the manuscript. In addition to its serial number, each table should have a sufficiently detailed heading or caption to explain the data displayed in it.
- (4) *Figures* should be numbered and their captions listed together at the end of the manuscript.
- (5) *References* in the text to other publications should be numbered consecutively within square brackets, for example: "Hoekje and Hoflund [1] have shown ..." and listed together at the end of the text, for example:

[1] S.J. Hoekje and G.B. Hoflund, *Appl. Surf. Sci.* 47 (1991) 43.

[2] A. Roth, *Vacuum Technology*, 3rd ed. (North-Holland, Amsterdam, 1990).

[3] V. Celli, in: *Dynamical Properties of Solids*, Vol. 6, Eds. G.K. Horton and A.A. Maradudin (North-Holland, Amsterdam, 1990) p. 337.

References to unpublished or not readily accessible reports should be avoided. In the case of multiple authorship all authors should be listed in the references provided they number less than ten. Only in the case of more than ten authors is the first author et al. acceptable.

- (6) *Formulae* in the manuscript should be typed with particular consideration given to characters that may be misinterpreted, e.g.

l (cap.), l (el), 1 (one), ' (prime)

o (lower case), O (cap.), 0 (zero), ° (deg)

× (times), x (lower case), X (cap.)

c, C; k, K, κ (kappa); p, P, ρ (rho)

u, v (lower case), ν (nu), V (cap.)

Σ (sigma), Σ (sum), Π (pi), Π (product); etc.

If necessary, unusual symbols should be explained in pencil in the margin.

- (7) *Vectors* should be indicated by a wavy underlining, and will be printed in bold-face italics.

Preparation of figures

The publisher requires a set of good quality drawings and photographs to produce the printed line figures and half-tone plates in the journal. Photographic copies ("glossy prints") of drawings are also acceptable for the line figures if they have been sharply focused and evenly exposed. **As a rule, Xerox copies cannot be accepted.** Original drawings and photographs will be returned after publication of the paper.

- (1) *Line figures:* The drawings or glossy prints supplied for the line figures should be 1.5–3 times larger than the printed size of the figures and should contain all the required, carefully applied lettering.

Figures are preferably reduced to a single column width (7.6 cm) unless their complexity, large width-to-height ratio, or need to display special detail makes a larger format necessary (max. printed width ~ 20 cm). Inappropriately sized lettering on a figure may prevent its reduction to the size optimum for its information content. The lettering used on a drawing should be chosen so that after reduction, the height of numbers and (capital) letters falls within the range 1.2–2.4 mm. Care should be exercised in choosing the pen width of machine-plotted graphs. Frequently lines in these figures are too fine compared to the area of the figure.

Shaded areas in line figures should be shown by means of cross-hatching (or a matrix of dots) rather than a continuous grey "wash". Cross-hatching, after reduction, of density less than ~ 25 lines/cm is satisfactory.

- (2) *Half-tone plates:* The photographs supplied for reproduction should be unmounted unless they form part of a composite figure and they should have a somewhat greater contrast than is desired in the printed figure. It is important that the photographs supplied are not already screened (overprinted with the point-matrix used by printers) or moiré patterns will form when they are screened for a second time. When necessary, the top side of a photograph should be marked on the back. A reduction factor should be recommended for a photo when it is not obvious what detail in the photo is of interest.
- (3) *Colour plates:* Illustrations can be printed in colour when they are judged by the Editor to be essential to the presentation. The Publisher and the Author will each bear part of the extra costs involved. Further information concerning colour illustrations and the costs to the author can be obtained from the Publisher.

IMPORTANT: When page proofs of the accepted manuscript are made and sent out to authors, this is in order to check that no undetected errors have arisen in the typesetting (or file conversion) process. At the proof stage only printer's errors may be corrected. No changes in, or additions to, the edited manuscript will be accepted.

Offprints: 50 offprints of the article will be supplied free of charge. Additional offprints may be ordered from the publisher. An order form will be sent to contributors together with the proofs. There is **no** page charge.

applied surface science

Abstracted/indexed in: Aluminium Industry Abstracts; Chemical Abstracts; Current Contents: Physical, Chemical and Earth Sciences; EI
Compendex Plus; Engineering Index; INSPEC; Metals Abstracts

MASTER INDEX Volumes 81-90

Author index	1
Subject index	33
List of terms used in the subject index	116



0169-4332(1996)81/90*;1-B